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-: HAND WRITTEN NOTES:-

OF

ELECTRONICS & COMMUNICATION

ENGINEERING

-: SUBJECT:-

ELECTRONIC DEVICES & CIRCUITS

1





THERMAL VOLTAGE $\rightarrow (V_T) \rightarrow$

" Volt equivalent of temp."

$$\Rightarrow \boxed{V_T = \frac{kT}{q} \text{ volts}}$$

T = Temp. in Kelvin

q = charge $\rightarrow 1.6 \times 10^{-19} C$.

$$\left\{ \begin{array}{l} k = \text{Boltzmann constt.} \rightarrow 1.381 \times 10^{-23} J/\text{°K} \\ k = 8.62 \times 10^{-5} \text{ ev/°K} \end{array} \right.$$

$$\Rightarrow \boxed{V_T = \frac{T}{11600} \text{ volt}}$$

$$\Rightarrow \boxed{V_T \propto T}$$

$$\therefore T = 0K, V_T = 0$$

$$\Rightarrow T = 300K, V_T = 26 \text{ mV}$$

$$\left[\because V_T = \frac{300}{11600} = 26 \text{ mV} \right]$$

* For a large variation in temperature there will be small variation in thermal voltage.

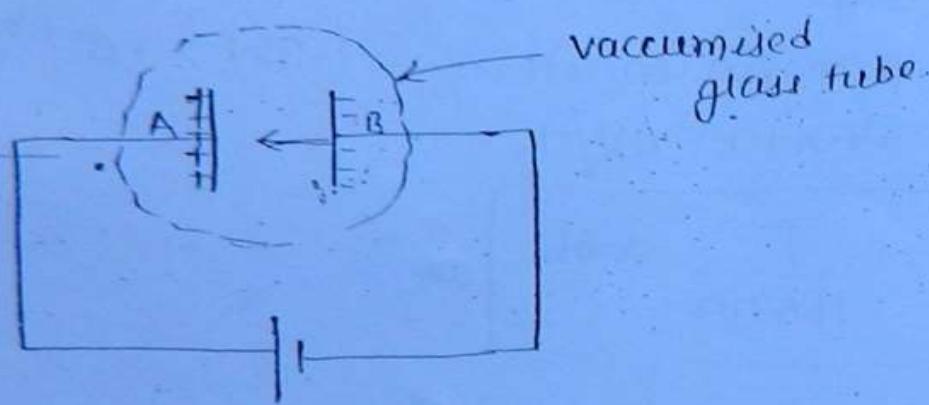
Temp. in $^{\circ}\text{C}$ = Temp. in Kelvin - 273

$T=0K \Rightarrow -273^{\circ}\text{C}$ (Absolute Temp)

$T=300K \Rightarrow 27^{\circ}\text{C}$ (Room temp)

$$\boxed{\text{Temp. in Kelvin} = {}^{\circ}\text{C} + 273}$$

- Electron volt (eV)
- It is the practical unit for energy in electronics
- 1 eV is defined as the energy gain by electron in moving do a potential difference of 1 volt



$$1 \text{ eV} = 1.6 \times 10^{-19} \text{ C} \times 1 \text{ volt}$$

$$1 \text{ eV} = 1.6 \times 10^{-19} \text{ C-volt/Joule}$$

$$\Rightarrow 1 \text{ eV} = 1.6 \times 10^{-19} \text{ J}$$

$$\text{K.E.} = \frac{1}{2}mv^2, \quad \text{P.E.} = qV$$

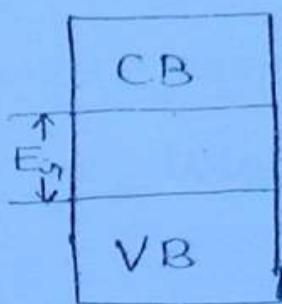
∴ eV indicates the kinetic energy gain by electron
or potential energy lost by electron

$$\text{K.E. gain} = \text{P.E. lost}$$

$$\frac{1}{2}mv^2 = qV \Rightarrow v = \sqrt{\frac{2qV}{m}} \Rightarrow \boxed{v = \sqrt{\frac{2qV}{m}} \text{ metre/sec.}}$$

$$m = 9.1 \times 10^{-31} \text{ kg}$$

Energy Gap $\rightarrow E_G$ or E_g \Rightarrow



Also called Band gap
or
Forbidden energy band.

	<u>Gie</u>	<u>Si</u>
E_{G10} =	0.785 eV	1.81 eV
E_{G300} =	0.72 eV	1.1 eV

$$\Rightarrow \boxed{E_G \propto \frac{1}{\text{Temperature}}}$$

\Rightarrow In semiconductors and insulators, energy gap decreases with the temperature increases.

$$\Rightarrow \boxed{E_{G(T)} = (E_{G0} - \beta_0 T) \text{ eV}}$$

$\beta_0 \rightarrow$ material constant $\rightarrow \text{eV}/^\circ\text{K}$

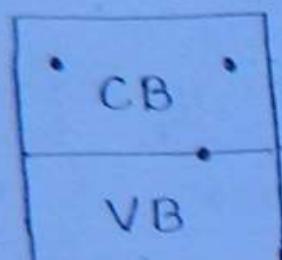
For Si

$$\Rightarrow \boxed{E_{G(\text{Si})} = (1.81 - 3.6 \times 10^{-4} T) \text{ eV}}$$

For Gie

$$\Rightarrow \boxed{E_{G(\text{Gie})} = (0.785 - 2.2 \times 10^{-4} T) \text{ eV}}$$

(i) Energy band diagram for metal or conductor :-
⇒ for metal $E_F = 0$ at $T = 0K$

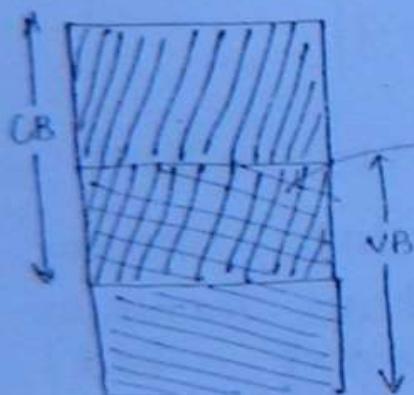


e^- (free e^- available)

at $T = 0K$

In metal free e^- concn is available at 0 K.

[At $T = 300K$]



overlapping of VB & CB

⇒ [overlap of Temperature]

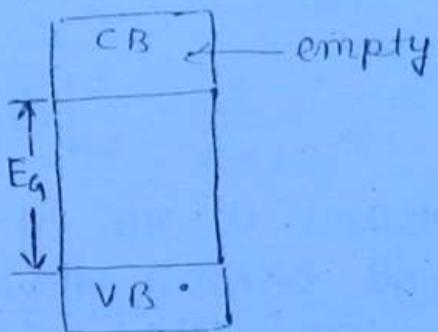
density or concn of e^- (n) = $10^{28}/m^3$ in metal

- ⇒ metals possesses metallic bonding.
- ⇒ Due to overlapping of VB & CB, metals will exhibit positive temperature coefficient of resistance (PTC).
- ⇒ free e^- concn in the metal is almost independent of temperature.

\Rightarrow In metal electron concentration : $n = 10^{29}/m^3$
which is highly concentrated electron.

(ii) Energy band diagram for Insulators :-

$E_g \rightarrow$ large $\geq 5\text{ eV}$.



\Rightarrow All insulators are bad conductors of current
i.e. they do not allow any flow of current through them

\Rightarrow Ionic bonding occurs in insulators.

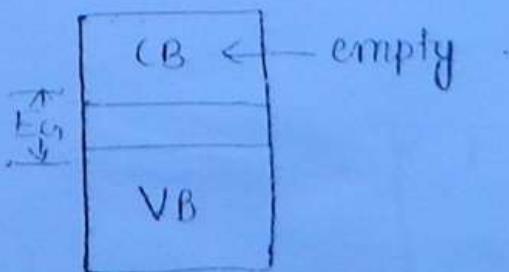
e.g. Air, diamond, Mica, Ceramic, glass, paper,
wood, SiO_2 ; rubber, Bakelite, PVC, cloth
Porcelain.

(iii) Energy band diagram for semiconductor :-

$E_g \rightarrow$ small \rightarrow around 1 eV

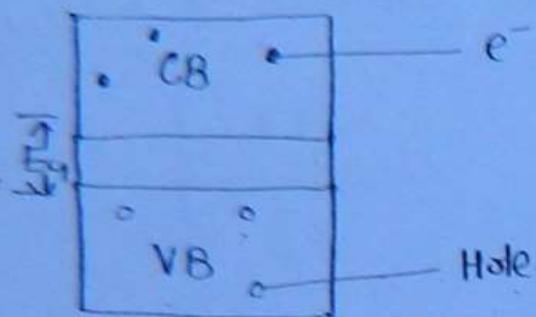
$\hookrightarrow 0.7\text{ eV to } 1.3\text{ eV}$

[at $T=0\text{ K}$]



→ All semiconductors are insulator at 0K.

At $T = 300\text{ K}$



→ When temperature increases a no. of covalent bond will be broken and electron and holes are created and therefore a conductivity in semiconductor.
eg Silicem and Germanium.

Semiconductor are the elements whose conductivity lies between the conductivity of a insulator and the conductivity of a conductor of a conductor.

Electric field Intensity (E or \mathcal{E})

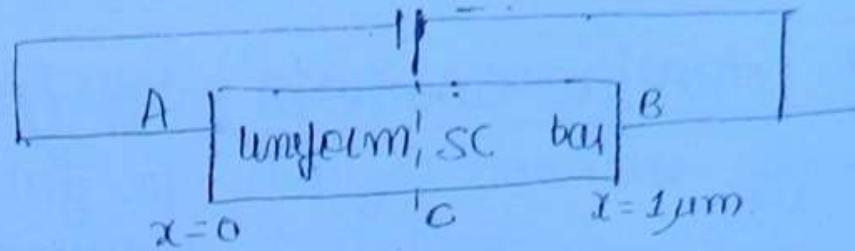
or field Intensity

or field gradient

or field

$$\Rightarrow \boxed{\mathcal{E} = - \frac{dv}{dx} \text{ V/m}}$$

$$\Rightarrow \boxed{|\mathcal{E}| = \frac{\text{Voltage existing}}{\text{Spacing or distance}}}$$



$|E|$ at point B

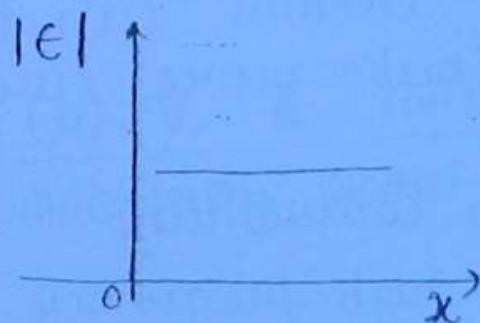
$$|E| = \frac{|V_B|}{\lambda \epsilon_{at B}}$$

$$|E|_{at B} = \frac{1}{1 \times 10^{-6}} = \underline{10^6 V/m}$$

$|E|$ at the centre of bar

$$|E|_{at C} = \frac{0.5 V}{0.5 \mu m} = \underline{10^6 V/m}$$

→ On a uniform semiconductor bar field intensity will remain a constant throughout the semiconductor bar except at $x=0$ (not defined).



Mobility of charge carriers $\Rightarrow (\mu)$

Mobility is defined as

$$\boxed{\mu = \frac{\text{Drift Velocity}}{\text{Field Intensity}} = \frac{V}{E}} = \frac{m}{s} \times \frac{m}{V} = m^2/V\text{-sec}$$

\Rightarrow Mobility indicates how fast the charge carriers will be moving from one place to another place.

$$\text{electron mobility } (\mu_n) = \begin{cases} 61e & \text{Ge} \\ & \text{Si} \end{cases} 3800 \text{ cm}^2/\text{V-sec}$$

$$\text{Hole mobility } (\mu_p) = \begin{cases} 61e & \text{Ge} \\ & \text{Si} \end{cases} 1800 \text{ cm}^2/\text{V-sec}$$

$$\boxed{\frac{\mu_n}{\mu_p} = 2.1 : 1, \quad \frac{\mu_n}{\mu_p} = 2.6 : 1}$$

\Rightarrow Electron mobility is always greater than hole mobility and therefore electron can travel faster and also contributes more current than a hole.

$\begin{cases} \text{Ge} \\ \text{Si} \end{cases} \rightarrow$ Higher conductivity
 \rightarrow used for high frequency becoz of high product gain bandwidth [more suitable than Si]

\rightarrow Switching time are very small and therefore Si is more suitable for switching applications

- ⇒ Si: High power handling.
- ⇒ mobility of charge carriers decreases with the temperature.
- ⇒ As temperature is increasing the atom in the material will be vibrating and due to this thermal vibration it causes the mobility of charge carriers decreases.

$$\boxed{\mu \propto T^{-m}}$$

where m is material constant.

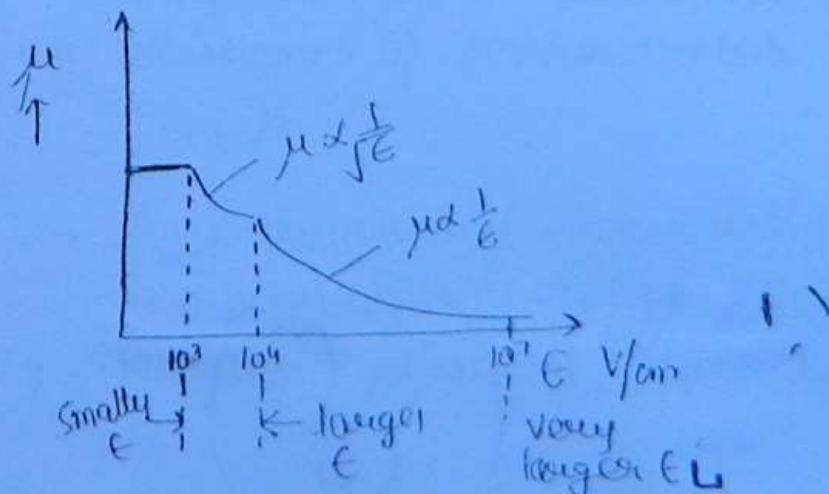
For Ge → 1.66 for e^-	}
2.33 for hole	

only for IES.

Si → 0.5 for e^-	}
2.7 for hole	

- ⇒ Mobility decreases with the temperature or a non-linear variation.

⇒ Mobility (μ) Vs E curve of graph → {Only for IES
(experimentally plotted graph)}



$$\Rightarrow \text{Drift velocity } v = ue$$

\Rightarrow For smaller field intensity is applying (10^3) or $< 10^3$

- (i) mobility of charge carrier will remain constant.
- (ii) drift velocity will be linearly increasing with field intensity.

\Rightarrow For larger field intensity is applying ($> 10^7$) \Rightarrow

- (i) mobility of charge carriers decreases
- (ii) drift velocity will remain almost a constant
drift velocity will enters into saturation.

\Rightarrow In a semiconductor the field intensity is gradually increasing \Rightarrow The drift velocity \Rightarrow

- (i) linearly increases
- (ii) sublinearly increases
- (iii) enters into saturation for larger field applied

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Current :-

Current is defined as rate of change of charge.

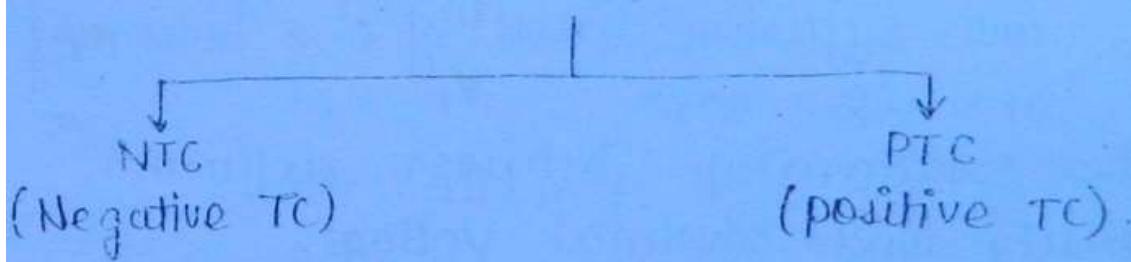
$$\Rightarrow i = \frac{dq}{dt} \text{ Amphere}$$

⇒ In the semiconductor current is carried by both electrons and holes.

Drift current :-

It is the flow of current to the material or device under the influence of electric field intensity.

Temperature coefficient (TC) :-



NTC :- Any parameter decreasing with the temperature is called NTC.

e.g. Resistance of semiconductor or insulator.
 E_G , μ .

PTC :- Any parameter increasing with the temperature is called PTC.

e.g. Resistance of metal, V_T , I_0 (leakage current).

L

Einstein's Equation.

In a SC

$$\Rightarrow \boxed{\frac{D_n}{\mu_n} = \frac{D_p}{\mu_p} = V_T}$$

$$\Rightarrow \boxed{\frac{D_n}{\mu_n} = \frac{D_p}{\mu_p} = \frac{T}{11600}}$$

* $\Rightarrow \boxed{\frac{\mu_n}{D_n} = \frac{\mu_p}{D_p} = \frac{1}{V_T} = \frac{11600}{T}}$

[$\because D_n$ and D_p are diffusion constt of e- & hole resp.]

\Rightarrow It gives the relationship between diffusion constt, mobility and thermal voltage.

*
$$\left. \begin{array}{l} \frac{D}{\mu} \propto \text{Temp.} \\ \frac{\mu}{D} \propto \frac{1}{\text{Temp}} \end{array} \right\}$$

* The unit of mobility to diffusion constt is $V^{-1} A$

* The unit of D/μ is [Volts] \checkmark

Diffusion constant of charge carriers (D) :-

$$e^- \text{ diffusion const. } D_n = \mu_n V_T$$

$$\text{Hole } " \quad D_p = \mu_p V_T$$

Unit for diffusion constant

$$\frac{\text{cm}^2}{\text{V}\cdot\text{sec}} = \begin{cases} \text{m}^2/\text{sec} \\ \text{or} \\ (\text{cm}^2/\text{sec}) \end{cases}$$

⇒ It is a material constant and is responsible for the property called diffusion in the semiconductor.

⇒ Diffusion const. decreases with the temperature.

For Ge at 300K

$$D_n = \mu_n V_T = 3800 \times 2.6 \times 10^{-1}$$

$$D_n = 99 \text{ cm}^2/\text{s.}$$

$$D_p = 47 \text{ cm}^2/\text{s}$$

For Si at 300K.

$$D_n = 34 \text{ cm}^2/\text{s}$$

$$D_p = 13 \text{ cm}^2/\text{s}$$

→ Diffusion constant cannot be negative and also it cannot be fraction.

Mass Action Law.

$$\Rightarrow \boxed{n_p = n_i^2} \Rightarrow \text{[other than IES exam]}$$

In a semiconductor (intrinsic or extrinsic) under thermal equilibrium. The product of electrons and holes in the semiconductor will be always a constant and is equal to the square of intrinsic concentration. (n_i^2).

\Rightarrow The law is mainly used for extrinsic semiconductor to calculate the minority carrier concentration.

N-type SC

Majority carriers are $e^- \Rightarrow n_n$

Minority carrier are holes $\Rightarrow P_h$

$$\Rightarrow \boxed{P_n = \frac{n_i^2}{n_n}}$$

P-type semiconductor

Majority carriers are holes $\Rightarrow P_p$

Minority carriers are $e^- \Rightarrow n_p$

$$\Rightarrow \boxed{n_p = \frac{n_i^2}{P_p}}$$

→ In a semiconductor :-

$$\Rightarrow n_n p_n = n_i^2$$

$$\Rightarrow n_p p_p = n_i^2$$

$$\Rightarrow \boxed{n_p = n_n p_n = n_i^2}$$

$$n_p = n_p p_p = n_i^2$$

$$\Rightarrow \boxed{\text{Minority carrier conc} = \frac{n_i^2}{\text{majority carrier conc}}}$$

$$\Rightarrow \boxed{\text{Majority carrier conc} \propto \text{Doping conc}}$$

$$\Rightarrow \boxed{\text{Minority carrier conc} \propto \frac{1}{\text{Doping conc}}}$$

INTRINSIC CONC (n_i) :-

$$\boxed{n = p = n_i}$$

Intrinsic conc (n_i) → It is conc available in pure semiconductor at a given temp.

n_i indicates electron or hole conc for per unit volume for at a given temp.

$$\Rightarrow \boxed{n_i^3 = A_0 T^3 e^{-E_{\text{gap}}/kT}}$$

Replacing E_{gap} by E_g .

$$\Rightarrow \boxed{n_i^3 = A_0 T^3 e^{-E_g/kT}}$$

$\therefore A_0 \rightarrow \text{material constant}$

$$\Rightarrow \left\{ \begin{array}{l} n_i^3 \propto T^3 \\ n_i^3 \propto e^{-E_g/kT} \end{array} \right. \begin{array}{l} \xrightarrow{\quad} \text{dominating more} \\ \xrightarrow{\quad} E_g \text{ dominating less} \end{array}$$

\Rightarrow Intrinsic conc' depends on \therefore

① Temperature.

② Energy gap.

$$\text{Intrinsic conc' } n_i \propto \boxed{T^{3/2}}$$

$$\text{Intrinsic conc' } n_i^3 \propto \boxed{T^3}$$

\Rightarrow Beacuz of smaller E_g , Ge is having larger value of n_i^3 than compare to Si.

$$\left\{ \begin{array}{l} \text{For Ge } n_i \rightarrow n_i = 2.5 \times 10^{13} \text{ atoms/cm}^3 \\ \text{For Si } n_i \rightarrow n_i = 1.5 \times 10^{10} \text{ atoms/cm}^3 \end{array} \right.$$

Resistivity (ρ) \Rightarrow or Specific resistance of the material.

unit of $\rho \rightarrow \Omega \cdot m$ or $\Omega \cdot cm$ or S .

For metals \Rightarrow

PTC of Resistance

$R \uparrow$ with $T \uparrow$

$$[\because \rho = \frac{Rl}{A}]$$

* \Rightarrow $\boxed{\rho \uparrow \text{ with } T \uparrow}$

For SC. \Rightarrow

NTC of Resistance

$R \downarrow$ with $T \uparrow$

$\rho \downarrow$ with $T \uparrow$

* \Rightarrow $\left\{ \begin{array}{l} R \downarrow \text{ with } T \uparrow \\ \rho \downarrow \text{ with } T \uparrow \end{array} \right\}$

Conductivity (σ) :-

σ is the reciprocal of reciprocal resistivity.

$$\text{unit of } \sigma \rightarrow \boxed{\frac{1}{\Omega \cdot \text{m}}} \text{ or } \boxed{\Omega^{-1}/\text{m}} = \boxed{\text{S/m}}$$

or $\boxed{\text{S/m}}$

- Conductivity denotes current carrying capacity of material or device.
- $\boxed{\text{Conductivity} = \text{Carrier conc} \times \text{charge} \times \text{mobility}}$

- Conductivity depends on :-

 - carrier conc
 - mobility of charge carriers
 - charge

For metal

↓
unipolar

$$\Rightarrow \boxed{\sigma = nq\mu_n} \text{ S/m}$$

$$\Rightarrow \boxed{\sigma \downarrow \text{ with } T \uparrow}$$

- In metals as temp. is increasing, mobility of charge carrier decreases and therefore conductivity of metal decreases.

\Rightarrow In metal-free e^- conc' is. Independent of temperature.

For SC.

\downarrow
Bipolar

$$\Rightarrow \boxed{\sigma = nq\mu_n + p q \mu_p} \text{ S/cm.}$$

$$\Rightarrow \boxed{\sigma \uparrow \text{ with Temp } \uparrow}$$

\Rightarrow When temperature is increasing, mobility of charge carrier decreases it will slightly reduce the conductivity. But at the same time becoz of thermal energy a large no. of covalent bond will be broken and e^- and holes are created and this will increase the conductivity by a larger value and the net result in the semiconductor conductivity increases with the temperature.

\Rightarrow In a semiconductor conductivity mainly depends on cavrier concentration.

Current density (J):

J is the current passing per unit area.

$$\boxed{J = \frac{I}{\text{Area}}} \Rightarrow \text{Amp/m}^2$$

$$\boxed{J = \sigma \epsilon \text{ Amp/cm}^2}$$

Current density in metal:

$$\Rightarrow \boxed{J = nq u_n \epsilon_0}$$

For semiconductor:

$$\Rightarrow \boxed{J = [nq u_n + p q u_p] \epsilon_0 \text{ Amp/cm}^2}$$

Electrical properties of Ge and Si

Properties

	Ge	Si
1) Atomic No.	32	14
2) Total No. of atom or density	4.421×10^{22}	5×10^{22}
3) Intrinsic concn (n_i) at 300K (atoms/cm ³)	2.5×10^{13}	1.5×10^{10}
4) Intrinsic resistivity (ρ_i) (n-cm)	45	2,30,000
5) Likeage current (I_o)	μA	$n\text{A}$
6) Maximum operating temp	75°C	175°C
7) Power handling capability	Low	High

⇒ Silicon is more fancy when compare to germanium and this is due to :-

- (1) Smaller leakage current.
- (2) High temperature application.
- (3) High power handling.
- (4) Abundance on surface of earth.
(This is primary reason why Si is more fancy by semiconductor device manufacturer)
- (5) Low cost.
- (6) Suitable to modify into SiO_2 .

↓
This is the main reason why Si is very much fancy by IC manufacturer.

Disadvantages of Si

⇒ Main disadvantages is conductivity is less.

⇒ Why carbon is not considered as semiconductor material?

IV group → C, Si, Ge.

⇒ C belongs to fourth group of periodic table but $E_g > 1.5 \text{ eV}$

⇒ The properties of C are highly unstable, unpredictable and unpredictable properties.

⇒ C sometimes will behaves as conductor e.g. Graphene sometimes it behaves as insulator e.g. Diamond

⇒ Due to this reason C never consider as a SC element.

MAXIMUM Operating Temperature

For Ge,

-60°C to +75°C

⇒ Max operating temp. = 75°C.

For Si,

-60°C to 175°C

⇒ max operating temp. = 175°C.

Normal working Temperature

⇒ [100K to 400K]

Gallium Arsenide (GaAs)

3rd group ← → 5th group

$$\left. \begin{array}{l} \text{Direct band gap SC} \\ \Rightarrow E_G = 1.47 \text{ eV} \end{array} \right\} \quad \left. \begin{array}{l} \mu_n = 5600 \text{ to } 85 \text{ cm}^2/\text{Vs} \\ \mu_p = 400 \text{ cm}^2/\text{Vs} \end{array} \right\}$$

- ⇒ GaAs is artificially made with Ga from 3rd group & Asenic from 5th group
- ⇒ Highly expensive material
- ⇒ Best e.g. of Direct Band gap SC
- ⇒ During the recombination energy will be dissipated in the form of light

- ⇒ The Best microwave material.
- ⇒ GaAs exhibits negative differential mobility.
due to this property it is more suitable for microwave application
- ⇒ GaAs is low noise material. ($\frac{1}{f}$ noise) ↓
- ⇒ GaAs is used in the fabrication LED's, tunnel diode, varactor diode, p-n diode, impact diode, Gunn diode, microwave IC.
- ⇒ InP (Indium Phosphate) is used in place of GaAs
Nowadays



leakage current (I_o) :-

$$\text{Ge} \quad \text{Si}$$
$$I_o = \mu\text{A} \quad \text{nA}$$

I_o of Ge > I_o of Si

{ For $1^\circ\text{C} \uparrow$ by approx. 7% }
* { I_o doubles for every 10°C }

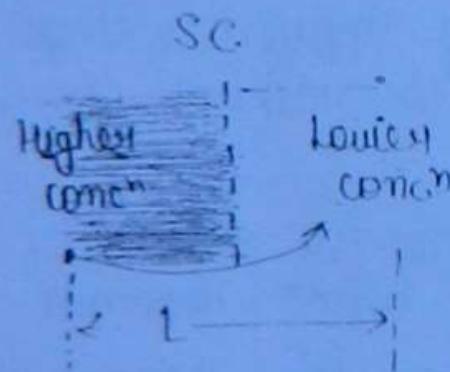
- ⇒ Also called minority carrier current or reverse saturation current or Thermally generated current.
- ⇒ For the better performance of the material or device, leakage current must be smaller. So that the temperature effect on the material will be less.
- ⇒ Si is having better thermal stability than Ge.
- ⇒ I_o is independent of applied voltage. i.e. this current is saturated in respect to the applied voltage.
- ⇒ I_o depends on the no. of minority carriers and minority carrier conc' depends on temp.
- ⇒ I_o is highly sensitive to temperature.

$$I_o(T_2) = I_o(T_1) \left[2^{\frac{T_2 - T_1}{10}} \right] \text{Amp}$$

where $T_2 > T_1$

Diffusion and Diffusion Current

- ⇒ Diffusion is a natural phenomena
- ⇒ The migration of charge carriers of higher concⁿ to lower concⁿ or from higher density to lower density is called Diffusion.
- ⇒ Diffusion current flows only in semiconductors
- ⇒ In a semiconductor diffusion is mainly due to concentration gradient
- ⇒ In a semiconductor diffusion is due to unequal distribution of charge carriers.
- ⇒ Diffusion is also associated with random motion of charge carriers due to thermal vibrations.



$$\text{gradient} \rightarrow \frac{d}{dx}$$

$$\frac{dn}{dx} \rightarrow e^- \text{ conc}^n \text{ gradient}$$

$$\frac{dp}{dx} \rightarrow \text{hole conc}^n \text{ gradient}$$

$$\checkmark \left\{ \text{Length of Diffusion } L = \sqrt{D \cdot \tau} \text{ (m)} \right.$$

$D \rightarrow$ Diffusion const. of charge carriers.

$\tau \rightarrow$ carrier lifetime

↳ Average lifetime of e^- or hole.

$$\Rightarrow \left\{ \text{Length of Diffusion prefers to average length.} \right.$$

$$\therefore D = \mu V_T$$

$$\Rightarrow \boxed{L = \sqrt{\mu V_T \cdot \tau}}$$

\Rightarrow Length of diffusion depends on

- (1) Diffusion const. of charge carriers.
- (2) Temperature
- (3) Carrier lifetime
- (4) Mobility of charge carriers.

$$\boxed{e^- \text{ diffusion current density } J_{n(\text{diff})}}$$

$$\star \boxed{J_{n(\text{diff})} = + q D_n \frac{dn}{dx} \text{ A/cm}^2}$$

for gate
exam
problem

$$\boxed{\text{Hole diffusion current density } J_{p(\text{diff})}}$$

$$\star \boxed{J_{p(\text{diff})} = - q D_p \frac{dp}{dx} \text{ A/cm}^2}$$

\Rightarrow In the above equation q is charge and its value is taken in magnitude ($1.6 \times 10^{-19} C$).

$$\Rightarrow e^- \text{ diffusion current } (J_{n(\text{diff})}) = J_{n(\text{diff})} \times A$$

$$\Rightarrow \text{hole diffusion current } (J_{p(\text{diff})}) = J_{p(\text{diff})} \times A$$

\therefore if A is not given take $A=1$ while solving problem.

Total Current Density in a semiconductor

\Rightarrow The total current density (J)

$$\Rightarrow J = J_n + J_p \text{ A/cm}^2$$

$$\text{where } J_n = J_{n(\text{diff})} + J_{n(\text{diff})}$$

$$\Rightarrow J_n = nq\mu_n e + qD_n \frac{dn}{dx}$$

$$\text{where } J_p = J_{p(\text{diff})} + J_{p(\text{diff})}$$

$$J_p = nq\mu_p e + (-q)D_p \frac{dp}{dx}$$

$$\Rightarrow J_p = p\mu_p e - qD_p \frac{dp}{dx}$$

Ques If the drift velocity of holes under a field gradient of 100 V/m is 5 m/sec what is mobility?

Ans $\mu = \frac{V}{E} = \frac{5}{100} = 0.05 \text{ m}^2/\text{V-sec}$

Ques The carrier mobility in a semiconductor is $0.4 \text{ m}^2/\text{V-sec}$. If diffusion const. at 300K will be _____.

Soln $D = \mu V_T$
= $0.4 \times 0.6 \times 10^{-3}$
= $0.0104 \text{ m}^2/\text{s}$

Ques The minority carrier lifetime and diffusion const. in a semiconductor material are $100\mu\text{s}$ and $100 \text{ cm}^2/\text{s}$ resp. Diffusion length of charge carriers _____.

Soln $L = \sqrt{D \cdot \tau}$
 $L = \sqrt{100 \times 10^{-6} \times 100}$
[$L = 10^{-4} \text{ cm}$]

Ques A sample of n-type SC has e- density of $6.25 \times 10^{18}/\text{cm}^3$ at 300 K. If intrinsic conc. of charge carriers in sample is $8.5 \times 10^{13}/\text{cm}^3$ find hole conc.

Soln $P_n = \frac{n_i^2}{N_m} = \frac{(8.5 \times 10^{13})^2}{6.25 \times 10^{18}} = 10^8/\text{cm}^3$

Ques A flat Al strip with a resistivity of $3.44 \times 10^{-8} \Omega\text{-m}$ and length 5mm and a cross sectional area $2 \times 10^{-4} \text{ mm}^2$ find the voltage drop across the strip when a current of 0.50mA is passing through it.

Soln

$$V = IR$$

$$R = \frac{\rho L}{A} = \frac{3.44 \times 10^{-8} \times 10^3 \times 5}{2 \times 10^{-4}}$$

$$R = \frac{1.72}{8.44 \times 10^{-7} \times 5} = 0.86 \Omega$$

$$V = IR$$

$$V = 0.50 \times 0.86$$

~~crossed out~~

$$\boxed{V = 43 \text{ mV}}$$



Ques

- A Si wafer is 0.5mm thick a potential of 100mV is applied across thickness
- what is the e- drift velocity if the mobility is $0.2 \text{ m}^2/\text{v}\cdot\text{sec}$.
- How much time is reqd. for an e- to move across this thickness.

Soln

$$\mu = \frac{V}{E} \Rightarrow \mu = \frac{V}{V/l} = 0.2 = \frac{V}{200 \times 10^{-3}} = \frac{1}{0.8 \times 10^4}$$

$$V = 200 \times 0.2 = 40 \text{ m/s}$$

$$\text{Time taken by } e^- = \frac{0.5 \times 10^{-3}}{40 \times 10^{-3}} = \boxed{12.5 \text{ usec}} \text{ ms}$$

Ques A small conc' of minority carrier is injected into a homogeneous SC resistor crystal at one point and having an electric field of 10 v/cm is applied across the sys. crystal so that minority carrier in that crystal will be moving at distance of 1 cm in 20μs. calculate mobility in $\text{cm}^2/\text{V}\cdot\text{sec}$.

$$E = 10 \text{ V/cm}$$

$$dx = 1 \text{ cm}$$

$$\mu = \frac{v}{E}$$

$$\Rightarrow E = \frac{V}{L} \Rightarrow 10 = \frac{V}{1} = \boxed{V = 10 \text{ V}}$$

$$\text{Drift velocity} = \frac{\text{distance}}{\text{Time}}$$

$$= \frac{1 \text{ cm}}{20 \times 10^{-6} \text{ sec}} = 50,000 \text{ cm/sec}$$

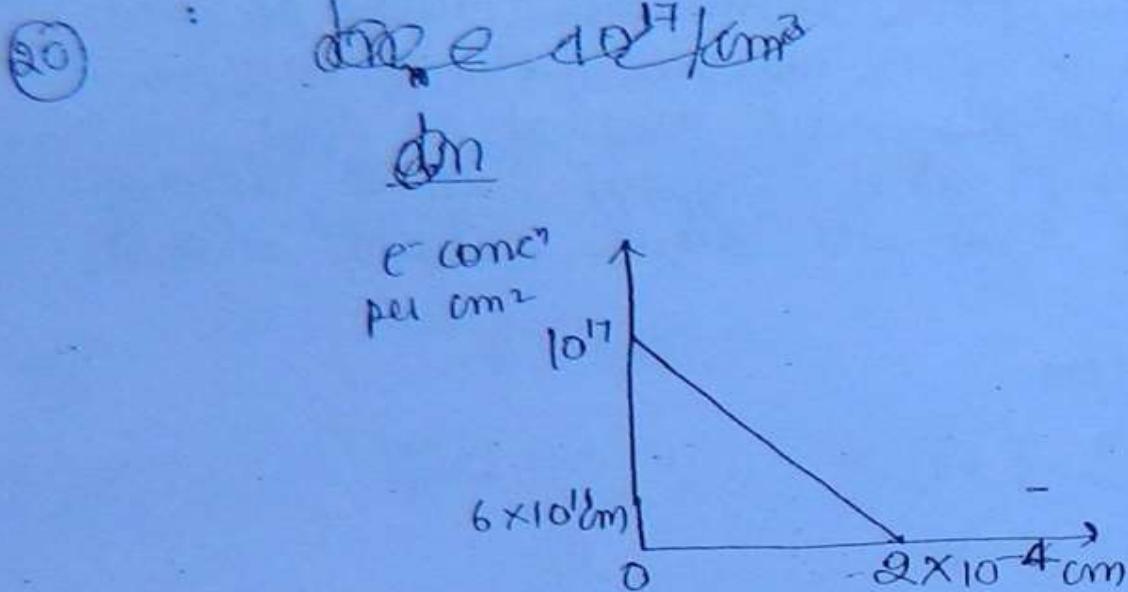
$$\mu = \frac{v}{E} = \frac{50,000}{10} = 5000 \text{ cm}^2/\text{sec.}$$

Ques If the leakage currents are $5 \mu\text{A}$ at 10°C find its value at the temperature is 85°C .

$$\begin{aligned} I_{0(T_2)} &= I_{0(T_1)} \left[2^{\frac{T_2 - T_1}{10}} \right] \\ &= 5 \mu\text{A} \left[2^{\frac{85 - 10}{10}} \right]. \end{aligned}$$

$$= 14.14 \mu\text{A}$$

workbook problem



$$e^- \text{ current density} = J_n(\text{diff}) + J_n(\text{drift})$$

since $E = 0$ (given)

$$\therefore J_n(\text{diff}) = 0$$

$$J_n = J_n(\text{diff.})$$

$$= + q D_n \frac{dn}{dx}$$

$$= 1.6 \times 10^{-19} \times 35 \left[\frac{6 \times 10^{16} - 10^{17}}{2 \times 10^{-4} - 0} \right]$$

~~A B~~ $J = -1120 \text{ A/cm}^2$

INTRINSIC SEMICONDUCTOR.

or Pure SC.

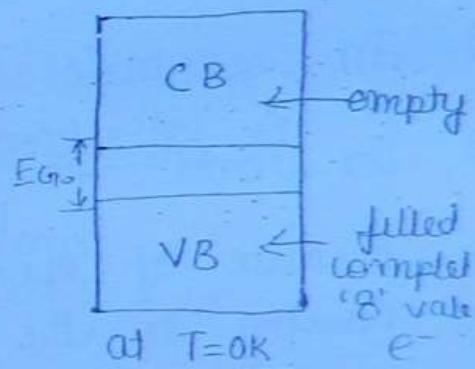
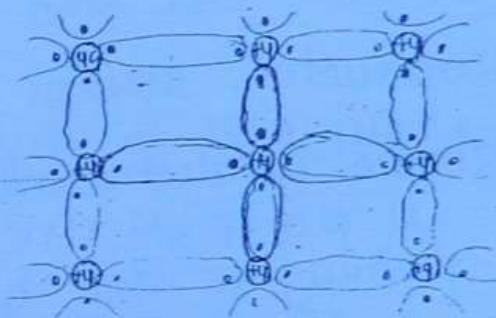
or Non-degenerated SC.

⇒ The maximum valency e^- in the atom is 8.

⇒ Semiconductor exhibit the property of covalent bonding.

Crystalline Structure.

at $T=0K$

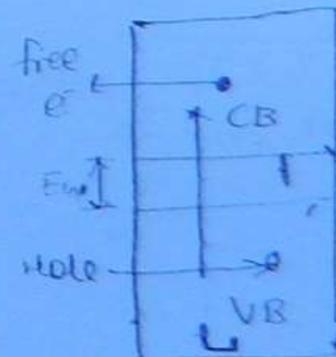
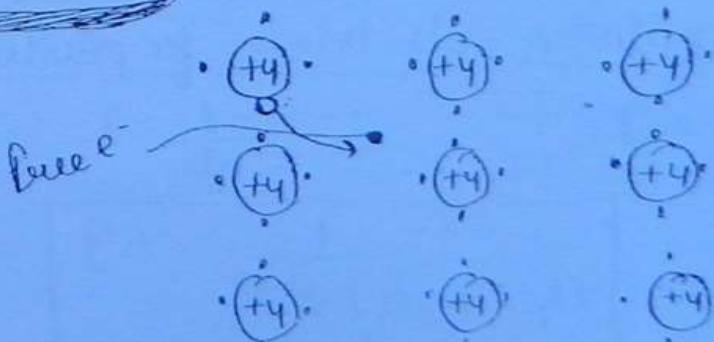


⇒ The sharing of e^- with the neighbouring atom is called covalent Bonding.

⇒ In one covalent bonding there will be two e^- at 0K, All valency e^- are in perfect covalent bonding and therefore the valency band is completely filled.

⇒ Intrinsic semiconductor at 0K will behave as perfect insulator.

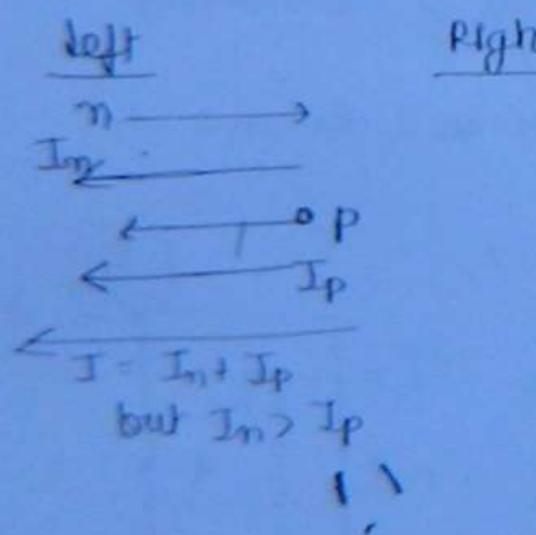
At $T=300K$



$$\Rightarrow [n = p]$$

- When a covalent bond is broken it will create one e⁻ and one hole (e⁻ will be jumping from VB to CB and becomes a free e⁻ and hole will remain in VB)
- Hole is defined as deficiency of e⁻ in the broken covalent bond.
- Hole is a carrier of current with a +ve charge of $+1.6 \times 10^{-19}$ C.
- In intrinsic semiconductor always $n=p$
- The condⁿ for intrinsic semiconductor $[n=p=n_i]$
- Because of opposite polarity e⁻ and hole will be moving in the opposite direction.
- Current direction is opposite to the flow of e⁻
- Current direction is in direction hole flow.

In a SC



e^- and hole will be always moving in the opposite direction but they contribute the current in the ~~the~~ same direction.

The free e^- will be moving in the conduction band and will contribute some current but at the same time hole will be moving in VB but in the opposite direction and will contribute some current and the total current I is the sum of e^- current and hole current.

The conductivity of intrinsic semiconductor is

$$\sigma_i = nq\mu_n + p q \mu_p \text{ A/cm}$$

$$\text{but } n = p = n_i$$

$$\Rightarrow \boxed{\sigma_i = n_i q [\mu_n + \mu_p]} \text{ A/cm}$$

$$\sigma_i \propto n_i$$

$$\text{but } n_i \propto T^{3/2}$$

$$\sigma_i \propto T^{3/2} \text{ (approx.)}$$

$$\boxed{\sigma_i \uparrow \quad T \uparrow} \text{ As a Non-Linear variation.}$$

The resistivity of intrinsic semiconductor

$$\rho = \frac{1}{\sigma_i}$$

$$\Rightarrow \boxed{\rho = \frac{1}{n_i q (\mu_n + \mu_p)}}$$

(i) Disadvantages of Intrinsic sc. :-

⇒ Conductivity is very small.

(ii) Generation of e⁻ hole pair :-

⇒ When temperature is increasing covalent bonds will be broken creating e⁻ and holes. and this process is called generation of e⁻ hole pair.

(iii) Recombination :-

⇒ The free e⁻ pairing with hole is called Recombination.

⇒ During the recombination the free e⁻ and the hole will disappear and a covalent bond is created.

⇒ During the recombination the free e⁻ will be falling from conduction band to valence band to recombine with the hole and the energy is dissipated in the form of heat and light.

(iv) Carrier lifetime (τ):-

⇒ It is the interval of time from breaking of covalent bond until its recombination.

⇒ Carrier lifetime is average lifetime.

⇒ τ is μ sec to n sec measured.

\Rightarrow hole is a valency e⁻ but taken with a positive charge.

Ques Calculate intrinsic conductivity and intrinsic resistivity of Ge at room temp. assume $n_i = 2.5 \times 10^{13}$ atom/cm³. $\mu_n = 3800$ cm²/V-sec
 $\mu_p = 1800$.

$$\sigma_i = n_i q (\mu_p + \mu_n)$$

$$\sigma_i = 2.5 \times 10^{13} \times 1.6 \times 10^{-19} (3800 + 1800)$$

$$\therefore \sigma_i^o = 2.5 \times 10^{-6} \times 5600 \times 1.6$$

$$\sigma_i^o = 2.5 \times 56 \times 10^{-4} \times 1.6$$

$$\sigma_i^o = 140.0 \times 10^{-4} \times 1.6$$

$$\sigma_i^o = 140 \times 10^{-4} = 1.4 \times 10^{-2} \times 1.6$$

$$\Rightarrow \sigma_i^o = 0.0224 \text{ } \Omega^{-1}/\text{cm}$$

$$\Rightarrow \rho_i = \frac{1}{0.0224} = 44.6 \text{ } \Omega \text{-cm}$$

Ques Calculate conductivity & resistivity of pure Si at room temp. assume $n_i = 1.5 \times 10^{10}/\text{cm}^3$
 $\mu_n = 1300$ & $\mu_p = 500$

$$\sigma_p = 1.5 \times 10^{10} \times 1.6 \times 10^{-19} (1300)$$

$$\sigma_i = 1.5 \times 1.6 \times 10 \times 10^{-7}$$

$$\sigma_i = 2.40 \times 10 \times 10^{-7} = 4.32 \times 10^{-6} \text{ } \Omega^{-1}\text{cm}^{-1}$$

$$\rho_i = \frac{1}{\sigma_i} = \boxed{231,481 \text{ } \Omega \text{-cm}}$$

Conductivity variation in the semiconductor with temp.

⇒ In intrinsic semiconductor conductivity will increase with temperature

For 1°C , In Ge $\sigma \uparrow$ by 6% }
" " Si $\sigma \uparrow$ by 8% }

When compared to Ge Si is more sensitive to temperature but Si is widely used for high temperature applications and this is due to smaller value of leakage current in the Si.

X ————— X
END OF DAY

82

Doping

Bivalent (Acceptor) Impurities \rightarrow B Al Ga In
Pentavalent (Donor) Impurities \rightarrow P As Sb Bi
 ∇ more affinity toward Si.

- \Rightarrow It is the process of adding impurities to the pure semiconductor.
- \Rightarrow Doping increases carrier concn therefore increases the conductivity

$$1:10^6 \text{ or } 1 \text{ in } 10^6 \text{ or } \frac{1}{10^6}$$

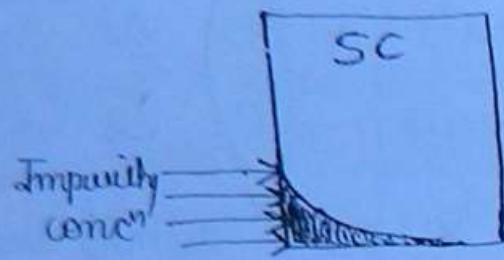
Standard Doping concn :-

- (1) Moderate Doping $\Rightarrow 1: (10^6 \text{ to } 10^8) \rightarrow p^- n^-$
- (2) Lightly Doped $\Rightarrow 1: 10^{11} \rightarrow p^- n^-$
- (3) Heavily (Highly) Doped $\Rightarrow 1: 10^3 \rightarrow p^+ n^+$

- \Rightarrow The minimum doping required to convert intrinsic semiconductor into extrinsic semiconductor is $1: 10^8$.

{ with $1: 10^8$ Doping in Ge $\sigma \uparrow$ by 12 times
with $1: 10^7$ Doping in Ge $\sigma \uparrow$ by 120 times }

Doping Profile:



In Intrinsic semiconductor there will be always unequal distribution of charge carriers and therefore it has only the diffusion current.

- ⇒ The impurity is added to the semiconductor is called doping profile.
- ⇒ The Doping profile can be Homogeneous or Non-homogeneous.
- ⇒ The Doping profile will be maximum on the surface where the profile is introduced and gradually decreases into the depth of the semiconductor.
- ⇒ The doping profile must introduce the built-in electric field (internal electric field). So the semiconductor will now exhibit the drift current.

Extrinsic Semiconductor

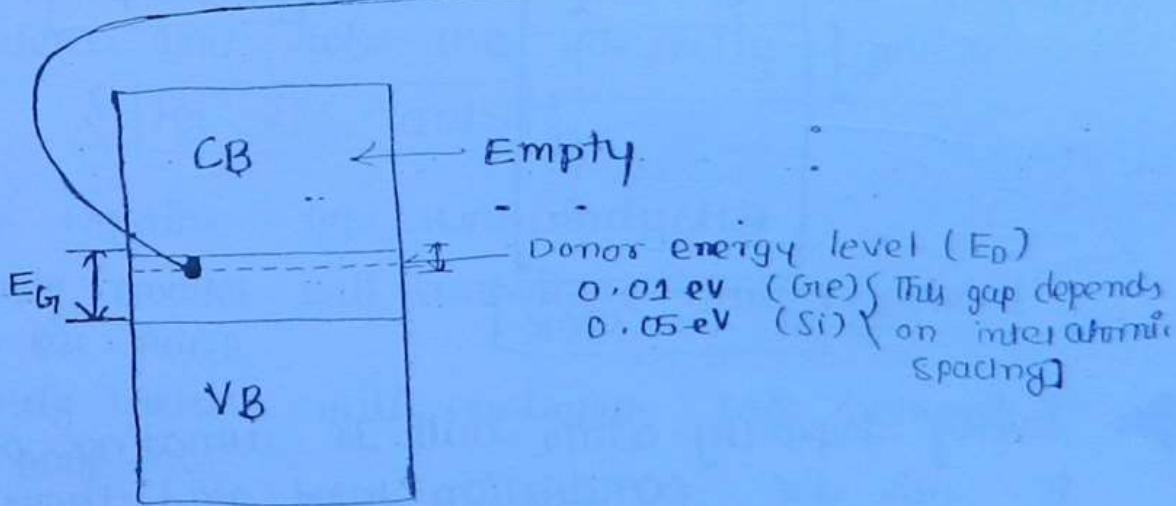
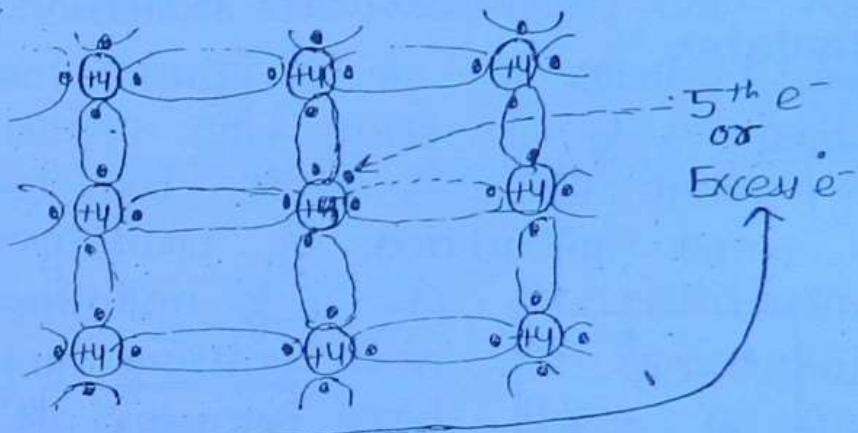
- or Doped Semiconductor
 - or Impurity Semiconductor
 - or Artificial Semiconductor
- (a) Degenerate SC
 (b) Compensated SC.

N-type Semiconductor (DONOR)

⇒ The impurity is pentavalent (5^{th} group).

crystalline structure

at $T=0\text{K}$

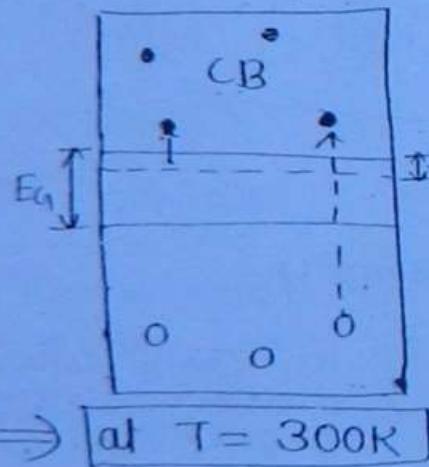


⇒ Donor energy level is a discrete energy level created thus below the conduction band.

⇒ Donor energy level (E_D) denotes the energy level of all the pentavalent atoms added to the pure semiconductor.

- At $T=0K$ the fifth e⁻ of all the impurity atom will be existing in the donor energy level.
- The additional energy required to detect the fifth e⁻ from its orbit is equal to 0.01 eV for Ge & 0.05 eV for Si.
- At $0K$ entire semiconductor behaves as perfect insulator.

At $T=300K$



$m \gg p$

- Every impurity atom will be donating one e⁻ into the conduction band and therefore N-type is also called Donor.
- Donor level ionisation means the 5th e⁻ moving from donor energy level into conduction band.
- Donor level ionisation increases with temperature. As temp. it increases from 0K to 300K more 5th e⁻ will be moving from donor energy level into conduction band.

- Donor level ionisation is completed at 300K :
 (i.e. 5th e⁻ of all the impurity atom have shifted into the conduction band)
- Above 300K, there is no donor level ionisation.
- ⇒ As temperature is increasing from 0K to 300K the 5th e⁻ of the impurity atom will be moving from donor energy level into conduction band (due to donor level ionisation) and because of thermal energy a no. of covalent bonds will be broken and equal no. of e⁻ and holes are created and these e⁻ will move from valency band to conduction band so that the concentration of e⁻ in the conduction band is far greater than the concentration of holes in the valency band. Hence e⁻ are majority carriers and holes are minority carrier.

{ For IES only }

- ⇒ N- Negative-type semiconductor.
- ⇒ Majority carrier will contribute more current and less noise
- ⇒ Minority carrier will contribute less current & more noise.
- ⇒ Minority carrier noise is thermal noise and it increases with the temperature.
- ⇒ In N-type SC current is predominating dominated by the flow of e⁻
- ⇒ The condⁿ for N-type SC is
- $$n > n_i$$
- $$p < n_i$$

→ In N-type semiconductor as e⁻ conc' increasing above n_i, the hole conc' will be falling below n_i and thus is due to a large no. of recombination.

→ According to law of electrical Neutrality

$$\Rightarrow [N_D + P = N_A + n]$$

In N-type SC.

$$N_A = 0$$

$$[n = N_D + P] \quad \left\{ \text{mainly used for TES} \right\}$$

$$\Rightarrow [n \approx N_D]$$

$$\Rightarrow [n \approx N_D] \quad \left\{ \text{for other exams} \right\}$$

↓
Donor concentration.

If denotes the no. of pentavalent atoms added to the pure semiconductor.

$$\Rightarrow [N_D = \text{Total No. of atom/cm}^3 \times \text{Impurity ratio}]$$

\Rightarrow The conductivity of N-type sc is \Rightarrow

$$\sigma_n = nq\mu_n + pq\mu_p \text{ esu/cm}$$

$$\Rightarrow \boxed{\sigma_n \approx N_D q \mu_n \text{ esu/cm}}$$

\Rightarrow In N-type semiconductor the free e^- conc
is approximately equal to donor conc ($n \approx N_D$)

\Rightarrow Minority carrier conductivity is almost negligible

Considering Si crystal.

When pure,

$$n = p = n_i = 1.5 \times 10^{10} \text{ cm}^{-3}$$

\Rightarrow By adding donor impurity 1×10^6

$$N_D = 5 \times 10^{22} \times \frac{1}{10^6} = 5 \times 10^{16} \text{ atom/cm}^3$$

\Rightarrow Total Impurity atoms $= 5 \times 10^{16} \text{ atom/cm}^3$

\Rightarrow No. of 5^{th} e^- $= 5 \times 10^{16} \text{ atom/cm}^3$

\Rightarrow Due to donor level ionisation $= 5 \times 10^{16} \text{ atom/cm}^3$
emitting donor energy level into conduction band

\Rightarrow Due to temp let 10^6 covalent bond are broken

Then generated $e^- \Rightarrow 10^6/\text{cm}^3$
 \dots holes $\Rightarrow 10^6/\text{cm}^3$

e^- moving from VB into CB = $10^6/\text{cm}^3$

$$\begin{aligned}\text{Total no. of } e^- \text{ in CB} &= 5 \times 10^{16} + 10^6 \\ &= 5 \times 10^{16}/\text{cm}^3\end{aligned}$$

Total no. of holes in VB \Rightarrow

$$p = 10^6/\text{cm}^3$$

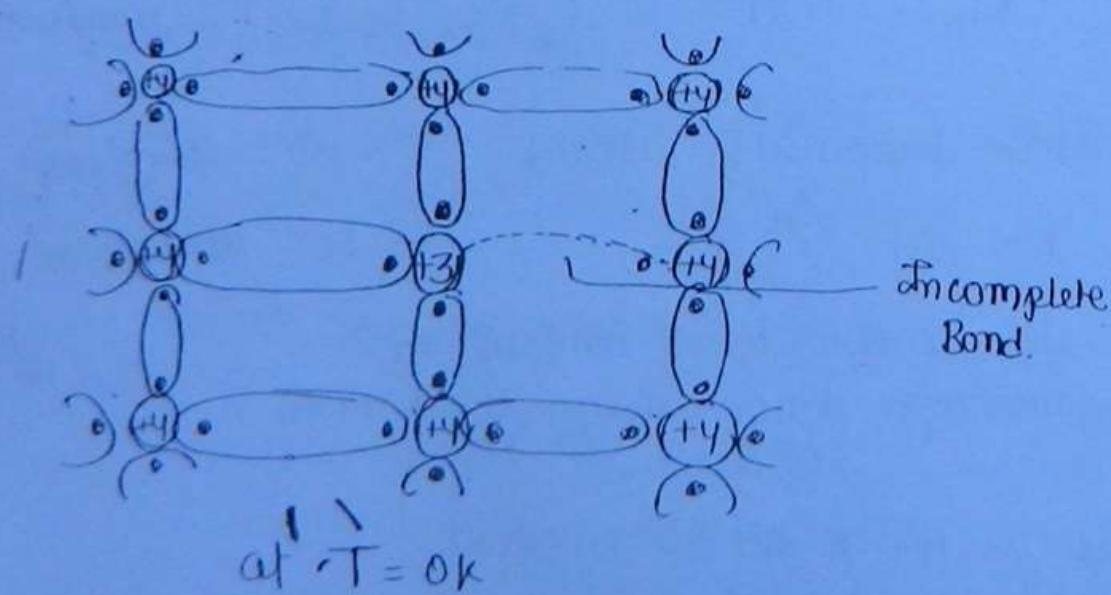
$$\Rightarrow n \gg p$$

P-type Semiconductor.

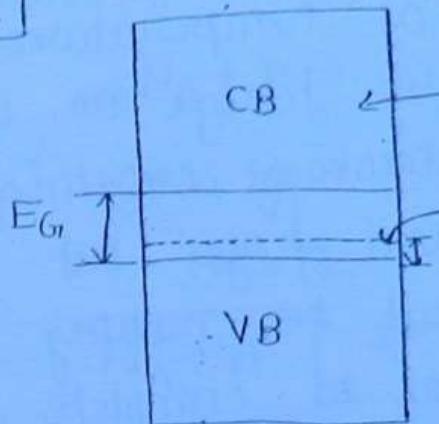
or

Acceptor-type sc.

\Rightarrow Impurity is Tetravalent.



At $T=0K$

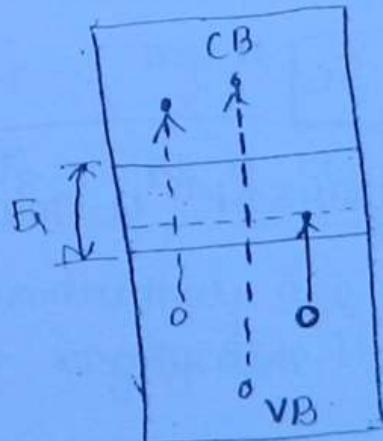


Empty

Acceptor energy level (E_A)
0.01 eV Ge } This gap depends
0.05 eV Si } on interatomic spacing }

- ⇒ Acceptor energy level is created a discrete energy level created just above the valency band.
- ⇒ Acceptor energy level denotes the energy level of all the trivalent atoms added to the pure semiconductor.
- ⇒ P-type semiconductor at $(0K)$ behaves as a insulator.

At $T=300K$



$$p \gg n$$

- ⇒ $p \gg n$
- ⇒ In p-type sc every impurity atom will be receiving one e^- to completes the covalent bonding & hence name acceptor.

In p-type semiconductor as temperature is increased to 300K then a large no. of covalent bond will be broken creating equal no. of electrons and holes but majority of these e^- will be moving into the acceptor energy level to complete its bonding and very few e^- will be moving from VB to CB. Hence hole concⁿ in the VB is a far greater than e^- concⁿ in the CB. Therefore holes are majority carriers and e^- are minority carriers.

{ for conventional }

$$\Rightarrow P \gg n$$

$$\Rightarrow \boxed{\text{positive - p-type SC}}$$

\Rightarrow In p-type SC the current is mainly dominated by holes.

\Rightarrow The condⁿ for p-type is \Rightarrow

$$\left. \begin{cases} P > n_i \\ n < n_i \end{cases} \right\}$$

According to law of electrical neutrality \Rightarrow

$$N_D + P = N_A + n$$

In P-type

$$N_D = 0$$

$$\Rightarrow \boxed{P = N_A + n} \quad \text{if } \boxed{P > N_A} \quad (\text{for IES})$$

$$\boxed{P \approx N_A} \quad (\text{For other exams})$$

Acceptor impn & it denotes the no. of trivalent atoms added to pure sc.

$$\Rightarrow \boxed{N_A = \text{Total No. of Atom/cm}^3 \times \text{Impurity ratio}}$$

The conductivity of p-type SC \rightarrow

$$\sigma_p = nq\mu_n + pq\mu_p \quad \text{S/cm}$$

*
$$\boxed{\sigma_p = N_A q / \mu_p}$$

\Rightarrow The conductivity due to minority carrier is almost negligible.

Ques. A pure sc (Ge) is doped with donor impurities to extent of $1:10^7$ calculate

- Donor conc' (N_D)
- e^- & hole conc'
- conductivity & resistivity of doped sc.
- How many times the σ is increased due to doping.

Let total no of atoms = $4.481 \times 10^{22}/\text{cm}^3$

$$n_i = 8.5 \times 10^{13} \text{ atoms}/\text{cm}^3$$

$$\mu_n = 3800 \text{ cm}^2/\text{V-sec}$$

$$\mu_p = 1800 \text{ cm}^2/\text{V-sec}$$

Ans Because of donor impurity sc becomes n-type

(a) $N_D = \frac{\text{Total no of atoms}/\text{dm}^3 \times \text{Impurity ratio}}{10^7}$

$$N_D = 4.481 \times 10^{15} \text{ atoms}/\text{cm}^3$$

(b) In N-type e^- conc'

$$n \approx N_D$$

$$n = 4.481 \times 10^{15} \text{ atoms}/\text{cm}^3$$

$$n_p = n_p^2$$

$$P = \frac{n_i^2}{n} = \frac{8.5 \times 10^{13}}{4.481 \times 10^{15}} = 1.41 \times 10^{-11}/\text{cm}^3$$

(c) $\sigma_n = \mu_n N_D q_V = 3800 \times 4.481 \times 10^{15} \times 1.6 \times 10^{-19}$

$$\rho = \frac{1}{\sigma} = 2.68 \text{ } \Omega/\text{cm}$$

(d) $R = \frac{1}{\sigma} = 0.373 \text{ } \Omega \cdot \text{cm}$

Q) Before doping semiconductor is intrinsic

$$\sigma_i = n_i q (\mu_n + \mu_p)$$

$$\sigma_i = 8.5 \times 10^{13} \times 1.6 \times 10^{-19} [3800 + 1800]$$

$$\sigma_i = 0.0824 \text{ S/cm}$$

By adding doping conc' 1:10⁷ the conductivity increased 0.0824 S/cm to 8.682.

$$\frac{8.68}{0.0824} \rightarrow [100 \text{ Times}] \checkmark$$

Ques A pure sc (Si) is doped with acceptor impurity to extent of 4 impurity atoms per every million of atom find its conductivity. (Ans 16)

Total no. of atoms $5 \times 10^{22} / \text{cm}^3$

$$n_i = 1.5 \times 10^{10} \text{ atom/cm}^3$$

$$\mu_n = 1300 \text{ cm}^2/\text{V-sec}$$

$$\mu_p = 500 \text{ cm}^2/\text{V-sec}$$

$$N_A = 5 \times 10^{22} \times \frac{4}{10^6} = 2 \times 10^{13} \text{ atom/cm}^3$$

$$\sigma_p = N_A q / \mu_p$$

$$= 2 \times 10^{13} \times 1.6 \times 10^{-19} \times 500$$

$$[\sigma_p = 16.25 \text{ S/cm}] \checkmark$$

Date :
11-09-2021

Ques In a semiconductor at room temp. the intrinsic conc & intrinsic resistivity are $1.5 \times 10^{16} / \text{m}^3$ and $2 \times 10^3 \Omega \cdot \text{m}$ resp.

If it is converted into an extrinsic sc if a doping conc of $10^{20} / \text{m}^3$ for the extrinsic semiconductor.

(i) calculate minority carrier conc

(ii) electron mobility

(iii) Resistivity of doped SC

(iv) minority carrier conc when its temp is increased to a value where there intrinsic conc is doubled.

Assume the mobility of minority carriers is equal to the majority carrier mobility.

$$\text{Soln} \quad (\text{i}) \text{ minority carrier conc (p)} = \frac{n_p^2}{n}$$

$$p = (1.5 \times 10^{16})^2$$

$$p = \frac{2.25 \times 10^{32}}{10^{20}}$$

$$p = 2.25 \times 10^{12} / \text{m}^3$$

(ii)

~~Majority carrier mobility~~

$$\mu_n = \mu_p = \mu$$

$$\ell_i = \frac{1}{n_i q (\mu_n + \mu_p)} = \frac{1}{n_i q 2\mu}$$

$$\mu = \frac{1}{2 \times 10^3 \times 1.5 \times 10^{16} \times 2} = 0.1042$$

$$(\text{iii}) \quad \ell_{\text{doped}} = \frac{1}{\ell_{\text{doped}}} = \frac{1}{\text{Doping conc} \times q \times \mu} = \frac{1}{10^{20} \times 1.6 \times 10^{-19} \times 0.1042} = 0.5996 \Omega^{-1}$$

$$(\text{iv}) \quad \text{minority carrier conc} = \frac{(2 n_i)^2}{10^{20}} = 4 \times 10^{12} / \text{m}^3$$

Prob In a semiconductor at room temp the intrinsic conc & intrinsic resistivity are $1.5 \times 10^{16} / m^3$ and $2 \times 10^3 \Omega \cdot m$ resp.

if it is converted into an extrinsic sc if a doping conc of $10^{20} / m^3$ for the extrinsic semiconductor.

(i) calculate minority carrier conc

(ii) electron mobility

(iii) Resistivity of doped sc

(iv) minority carrier conc when its temp is increased to a value where there intrinsic conc is doubled.

Assume the mobility of minority carriers is equal to the majority carriers mobility.

Soln

$$(i) \text{ minority carrier conc } (P) = \frac{n_p^2}{n}$$

$$P = (1.5 \times 10^{16})^2$$

$$P = \frac{2.25 \times 10^{32}}{10^{20}}$$

$$\boxed{P = 2.25 \times 10^{12} / m^3}$$

Ans

(ii)

~~Minority carrier conc~~

$$\mu_n = \mu_p = \mu$$

$$\ell_i = \frac{1}{n_i q (\mu_n + \mu_p)} = \frac{1}{n_i q 2\mu}$$

$$\mu = \frac{1}{2 \times 10^3 \times 1.5 \times 10^{16} \times 2} = \boxed{0.1042}$$

$$(iii) \text{ Doped} = \frac{1}{\ell_{\text{doped}}} = \frac{1}{\text{Doping conc} \times q \times \mu} = \frac{1}{10^{20} \times 1.6 \times 10^{-19} \times 0.1042} = 0.5996 \Omega^{-1}$$

$$(iv) \text{ Minority carrier conc} = \frac{(2n_i)^2}{10^{20}} = 4 \times 10^{12} / m^3$$

Ques A Si SC is doped with donor impurities with resultant in doping profile as $[n = G_1x]$: $n \gg n_i$; the sample is placed isolated and built in E·F. as a function of x also calculate field at $x = 1\mu m$ at room temperature.

$$\Delta \rho \rho =$$

$$n = G_1x$$

$$n \gg n_i$$

SC is N-type

$$J_n = J_{n(\text{diff})} + J_{n(\text{drift})}$$

$$J_n = nq\mu_n E + qD_n \frac{dn}{dx}$$

Since Sample is isolated

$$J_n = 0$$

$$n = G_1x$$

$$\therefore \frac{dn}{dx} = G_1$$

$$0 = G_1x q\mu_n + qD_n G_1$$

$$q\mu_n \in = -D_n$$

$$E = -\frac{D_n}{\mu_n \cdot x}$$

$$\text{but } \frac{D_n}{\mu_n} = V_T$$

$$\boxed{E = -\frac{V_T}{x}} \quad \left| \quad \text{at } x = 1\mu m \right.$$

$$E = -\frac{V_T}{1 \times 10^{-6}}$$

$$E = -10^6 V_T \text{ in volt/m}$$

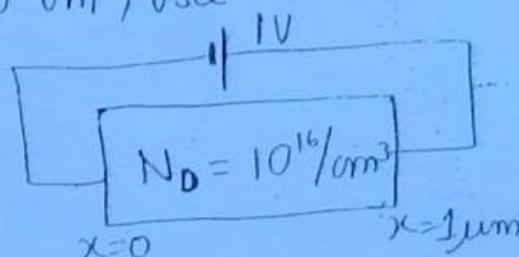
$$E = -10^6 \times 10^{-3} \times 26 \Rightarrow -26 \times 10^3$$

$$\boxed{E = -2.6 \times 10^4 \text{ volt/m}}$$

Prob The Si sample with unit cross sectional area given below is under thermal equilibrium the following information is given

$$T = 300K, q = 1.6 \times 10^{-19}, V_T = 26 mV$$

$$\mu_n = 1350 \text{ cm}^2/\text{V sec}$$



- (1) The magnitude of the E.F. at $x = 0.5\mu\text{m}$ is _____
- (2) The magnitude of e drift current density at $x = 0.5\mu\text{m}$ _____

~~Electric field $E = \frac{V}{d}$ at $x = 0.5\mu\text{m}$~~

$$E = \frac{0.5}{0.5 \times 10^{-6}} = 10 \text{ kV/m}$$

$J_{n(\text{drift})}$ at $x = 0.5\mu\text{m}$

$$= nq\mu_n E$$

$$= 10^{16} \times 1.6 \times 10^{19} \times 1350 \times 10 \times 10^3$$

$$J_{n(\text{drift})} = 2.16 \times 10^4 \text{ A/cm}^2$$

Minimum Value of conductivity in a SC.] Q 7TQ4

$$\Rightarrow \sigma = nq\mu_n + p q \mu_p \rightarrow ①$$

By mass action law.

$$p = \frac{n_i^2}{n} \quad \dots \quad ②$$

Substitute in eq ① & ②

$$\sigma = nq\mu_n + \frac{n_i^2}{n} \mu_p \cdot q \rightarrow ③$$

Differentiating eq wrt n ,

$$\frac{d\sigma}{dn} = q\mu_n + \left(-\frac{1}{n^2}\right) n_i^2 q \mu_p$$

$$\frac{d^2\sigma}{dn^2} = 0 + \left(\frac{2}{n^3}\right) n_i^2 q \mu_p$$

Since II^{nd} derivative is +ve, we get cond'n for minimum conductivity

=> The minimum conductivity can be obtain by

$$\frac{d\sigma}{dn} = 0$$

$$0 = q\mu_n + \left(-\frac{1}{n^2}\right) n_i^2 q \mu_p$$

$$\mu_n = \frac{n_i^2}{n^2} \mu_p \Rightarrow n^2 = n_i^2 \frac{\mu_p}{\mu_n}$$

$$\Rightarrow \boxed{n = n_i \sqrt{\frac{\mu_p}{\mu_n}}} \rightarrow \textcircled{A}$$

- ⇒ Eqn ① denotes the concⁿ of e⁻ in the sc and conductivity is minimum.
- ⇒ Eqn ① also denotes thermal equilibrium e⁻ if the sc is p-type.
- ⇒ Substituting eq ① in eq ②

$$p = \frac{n_i^2}{n}$$

$$p = \frac{n_i^2}{n_i \sqrt{\mu_n / \mu_p}}$$

$$\Rightarrow P = n_i \sqrt{\mu_n / \mu_p} \rightarrow ③$$

- ⇒ Eq ③ denotes the concⁿ of holes in sc when conductivity is minimum.

- ⇒ Eq ③ also denotes thermal equilibrium holes if semiconductor is N-type.

- Substituting ① & ③ in eq ① we get eqn for minimum conductivity.

$$I_{min} = n_i \sqrt{\mu_n / \mu_p} q \mu_n + n_i \sqrt{\mu_n / \mu_p} \cdot q \mu_p$$

$$I_{min} = n_i q \left[\sqrt{\mu_n \mu_p} + \sqrt{\mu_n \mu_p} \right]$$

$$\Rightarrow I_{min} = 2 q n_i \sqrt{\mu_n \mu_p}$$

Ques A semiconductor has following parameters

$$\mu_n = 7500 \text{ cm}^2/\text{V-sec}$$

$$\mu_p = 300 \text{ cm}^2/\text{V-sec}$$

$$n_i = 3.6 \times 10^{12} / \text{cm}^3$$

Find ① min T

② hole concn in SC when Tmin.

③ Thermal equilibrium e^-

$$T_{\min} = \frac{q n_i \sqrt{\mu_n \mu_p}}{k}$$

$$= \frac{2 \times 1.6 \times 10^{-19} \times 3.6 \times 10^{12}}{1.38 \times 10^{-23} \times 7500 \times 300} \sqrt{7500 \times 300}$$

$$= \frac{2 \times 1.6 \times 3.6 \times 10^{-5}}{1.38 \times 10^{-23} \times 75} \sqrt{75 \times 3}$$

$$= 3.2 \times 3.6 \times 10^{-5} \times \sqrt{225}$$

$$= (3.2 \times 3.6) \times (15) \times 10^{-5} = 48 \times 3.6 \times 10^{-5}$$

$$= 172.8 \times 10^{-5} = 1.72 \times 10^{-3} \text{ K}$$

~~1.72 × 10⁻³~~

$$P = n_i \sqrt{\frac{\mu_p}{\mu_n}} = 3.6 \times 10^{12} \sqrt{\frac{300}{7500}} = 3.6 \times 10^{12}$$

$$P = 18 \times 10^{12} = 1.8 \times 10^{13}$$

$$n > n_i \sqrt{\frac{\mu_p}{\mu_n}} = \frac{3.6 \times 10^{12}}{1.8} = 7.2 \times 10^{12}$$

1)

L

GERMANIUM - Si Crystal {Not for Gates IES}

- ⇒ When Ge is added to Si or Si is added to Ge we get Ge-Si crystal the type of bonding provided is covalent bonding.
- ⇒ At 0K they behave as insulator
- ⇒ At room temperature they behave as intrinsic semiconductor.
- ⇒ When SC is subjected to donor or acceptor impurities
- ⇒ In Intrinsic SC :-
 - (i) if $N_A = N_D$ is applied
⇒ SC remains Intrinsic
 - (ii) if $N_A > N_D$ is applied
⇒ SC turns P-type
 - (iii) if $N_A < N_D$ is applied
⇒ SC turns N-type.

Ques → A p-type SC having $N_A = 8 \times 10^{16}/\text{cm}^3$ is subjected to donor impurity or concn of $N_D = 8.5 \times 10^{16}/\text{cm}^3$ then SC is N-type. & e⁻ conc is $0.5 \times 10^{16}/\text{cm}^3$

Ques A / 85 gm of P-type Ge crystal exhibit a resistivity of 5 Ω-cm at room temp by uniform Sb doping if it is converted into N-type SC having 1 Ω-cm resistivity at 300K. if each atom of the initial acceptor impurity is exactly neutralized by 1 atom of Sb. find m_{Ag}, the amt of antimony required

$$\text{The density of Ge } 5.32 \text{ gm/cm}^3 / \text{No. of Sb atoms/gm} = 5 \times 10^{21} \\ d_m = 3800 \text{ kg/m}^3, N_A = 8.5 \times 10^{16}/\text{cm}^3, q = 1.6 \times 10^{-19} \text{ C}$$

Q3 Before doping the SC is P-type with resistivity of $5\Omega \cdot \text{cm}$ & therefore if N_A or density of hole conc.

$$N_A = \frac{1}{\rho_p \cdot q \cdot \mu_p}$$

$$N_A = \frac{1}{5 \times 1.6 \times 10^{-19} \times 1800}$$

p $\Rightarrow N_A = 6.944 \times 10^{14} / \text{cm}^3$

By adding Sb doping the P-type SC is converted into N-type SC with ρ of $1\Omega \cdot \text{cm}$ & N_D or e^- conc.

$$N_D = \frac{1}{\rho_n \cdot q \cdot \mu_n}$$

$$n = N_D = \frac{1}{1 \times 1.6 \times 10^{-19} \times 3800} = 16.45 \times 10^{14} / \text{cm}^3$$

Total no. of Sb atom reqd = $N_A + N_D$

$$= (6.944 + 16.45) \times 10^{14}$$

$$= 23.39 \times 10^{14} / \text{cm}^3$$

\Rightarrow Net No. of e^- in SC obtained neutralising the initial holes of P-type SC

\Rightarrow The no. of Sb reqd is above.

$$\text{Volume} = \frac{\text{lit}}{\text{density}}$$

85 gms crystal of Ge has a

$$\text{Vol} = 85 / 5.32 = 4.699 \text{ cm}^3$$

Total no. of Sb reqd

$$\hookrightarrow \text{lit} \quad 23.39 \times 10^{14} \times 4.699 \text{ atoms/cm}^3 = 109.928 \times 10^{14} \text{ atoms}$$

$$\Rightarrow 109.928 \times 10^{14} / 5 \times 10^{21} \Rightarrow 0.1995 \text{ microm}$$

CARRIER CONCⁿ: IN INTRINSIC SEMICONDUCTOR

- ⇒ Carrier concⁿ means the charge carrier responsible for the conductivity
- ⇒ In intrinsic SC carrier concⁿ means e⁻ concⁿ and hole concⁿ.

EFFECT OF TEMPERATURE ON CARRIER CONCⁿ IN INTRINSIC SC

In intrinsic SC

$$n = p = n_i$$

$$\text{but } n_i \propto T^{3/2}$$

∴ $n_i \uparrow$ with $T \uparrow$

$$\boxed{\therefore p \uparrow \text{ with } T \uparrow}$$

- ⇒ In intrinsic SC carrier concⁿ increases with temp.

EFFECT OF TEMPERATURE ON CONDUCTIVITY OF INTRINSIC SC.

In intrinsic SC

$$\sigma_i = n_i q [\mu_n + \mu_p]$$

$$\sigma_i \propto n_i$$

$$\text{but } n_i \propto T^{3/2}$$

$$\boxed{\therefore \sigma_i \uparrow \text{ with } T \uparrow}$$

- ⇒ In intrinsic SC conductivity increases with temp.

CARRIER CONCⁿ IN EXTRINSIC SC

In extrinsic SC carrier concⁿ means majority carrier concⁿ.

Effect of temp. doping in extrinsic SC

N-type SC :-

$$\sigma_N = N_D q \mu_n$$

$$\Rightarrow [\sigma_N \propto N_D]$$

P-type SC :-

$$\sigma_P = N_A q \mu_p$$

$$[\sigma_P \propto N_A]$$

\Rightarrow Conductivity increases with doping in extrinsic SC.

$1:10^8$	$\sigma \times 12$
$1:10^7$	$\sigma \times 120$
$1:10^6$	$\sigma \times 1200$
$1:10^5$	$\sigma \times 12K$

$1:10^4$	$\sigma \times 120K$
$1:10^3$	$\sigma \times 1200K$
—	—

\rightarrow A highly doped SC exhibits metallic properties i.e.

- (1) larger conductivity
- (2) Bipolar nature can be converted into unipolar
- (3) NTC converted into PTC of resistance.

Note A highly doped SC behaves as a conductor.

Effect of Doping on majority & minority carrier

N type

majority carriers are $e^- \rightarrow n$

$$n \approx N_D$$

minority carriers are holes $\rightarrow p$

$$P = \frac{n^2}{N} = \frac{n^2}{N_D}$$

P-type

Majority carriers are holes $\rightarrow P$
 $P \approx N_A$

Minority carriers are e^- 's $\rightarrow n$

$$n = \frac{n_i^2}{P} = \frac{n_i^2}{N_A}$$

\Rightarrow Doping increases majority carrier concn and reduces the minority carrier concn.

Effect of temp. on majority & minority carriers

Considering Si bar

when pure

$$n = p = n_i = 1.5 \times 10^{10}/\text{cm}^3$$

By adding donor concn $1: 10^6$

$$N_D = 5 \times 10^{22} \times \frac{1}{10^6}$$

$$N_D = 5 \times 10^{16}/\text{cm}^3$$

SC turns N-type

In "I-type SC at 300 K

$$n \approx N_D = 5 \times 10^{16}/\text{cm}^3$$

$$P = \frac{n^2}{N_D} = \frac{(1.5 \times 10^{10})^2}{5 \times 10^{16}} = 4500/\text{cm}^3$$

Let temp. \uparrow $\&$ 10^6 covalent bonds are broken

Thermally generated $e^- \Rightarrow 10^6/\text{cm}^3$

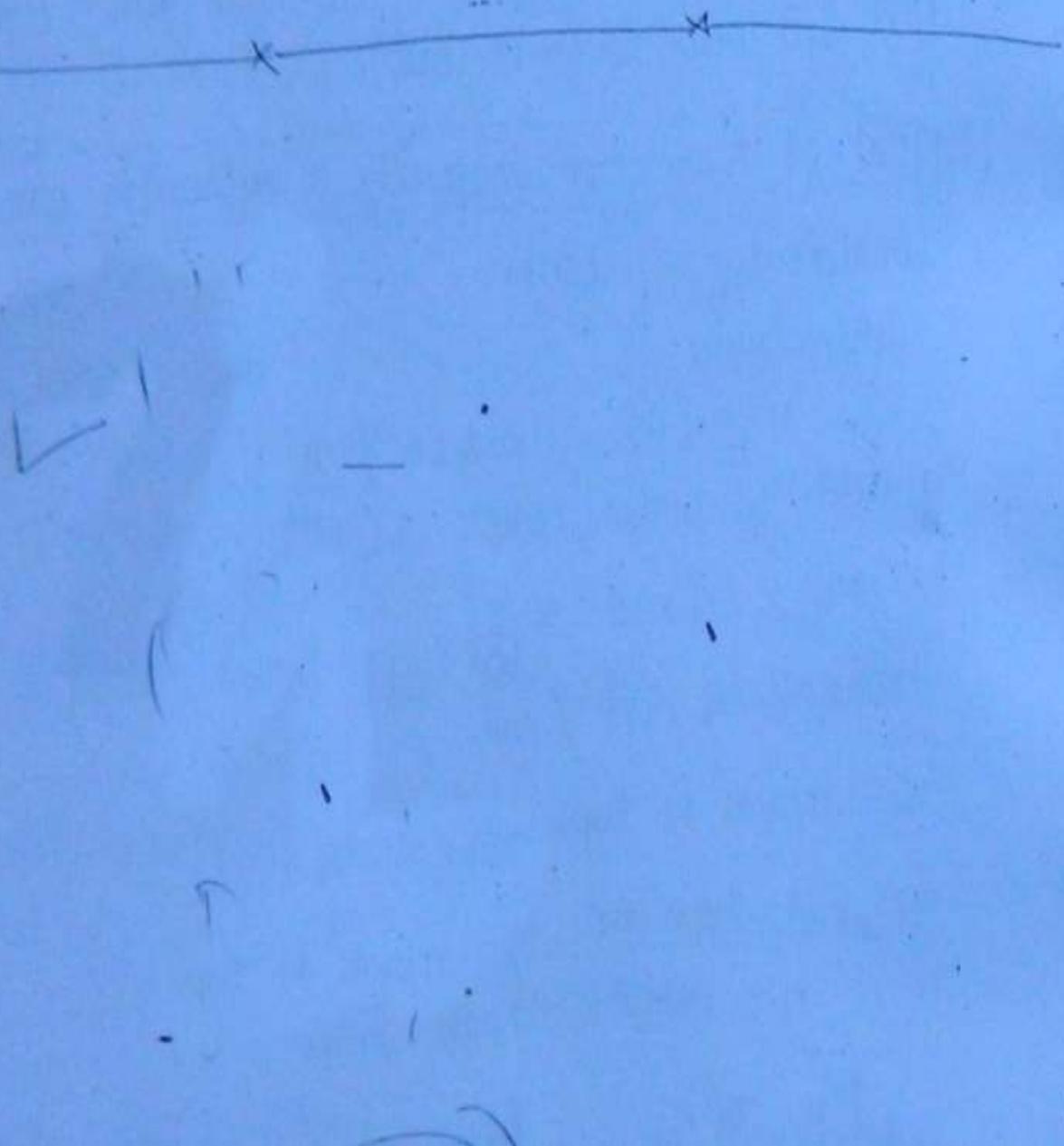
" holes $\Rightarrow 10^6/\text{cm}^3$

Total no. of e^- in CB $\Rightarrow 5 \times 10^{16}/\text{cm}^3 + 10^6/\text{cm}^3 \Rightarrow 5 \times 10^{16}/\text{cm}^3$

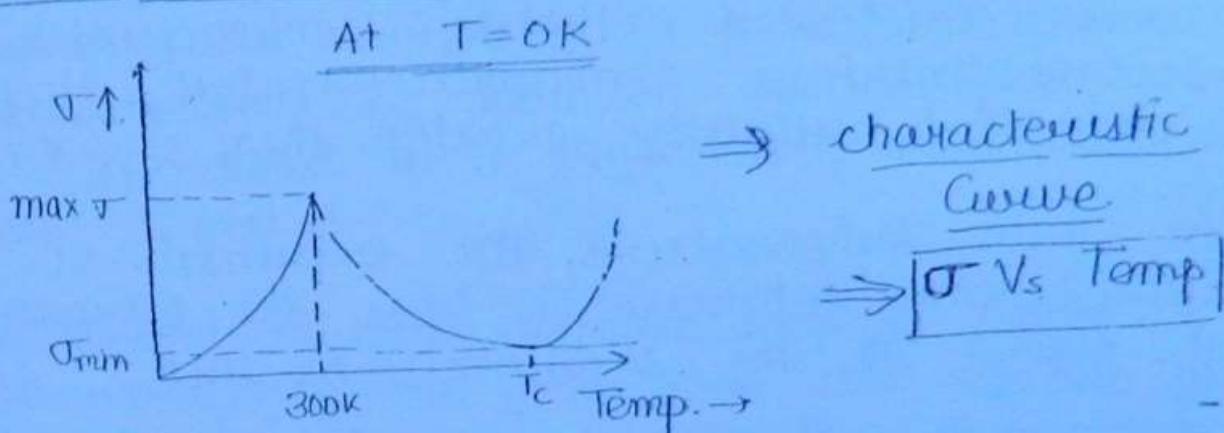
\rightarrow Increase in e^- concn (majority) is negligible

Total no. of holes in VB $p = 4500/\text{cm}^3 + 10^6 = 10^6/\text{cm}^3$
 \rightarrow Increase in minority concn (hole) is very high.

- ⇒ In a SC majority carrier conc' is almost independent of temperature
- ⇒ In a SC minority carrier conc' it will increase with temperature



⇒ Effect of temp. on the conductivity of extrinsic semiconductor.



T_c = Intrinsic Temp.

At $T=0K$ Carrier conc' are zero and therefore σ is zero. An extrinsic SC at 0K is a insulator.

At $0K < T < 300K$

As temperature is increasing because of thermal energy a no. of covalent bond will be broken and also majority and minority carriers are created and therefore the conductivity will be increases with temperature.

At $T=300K$

The conductivity of extrinsic semiconductor will become maximum.

When $300K < T < T_c$

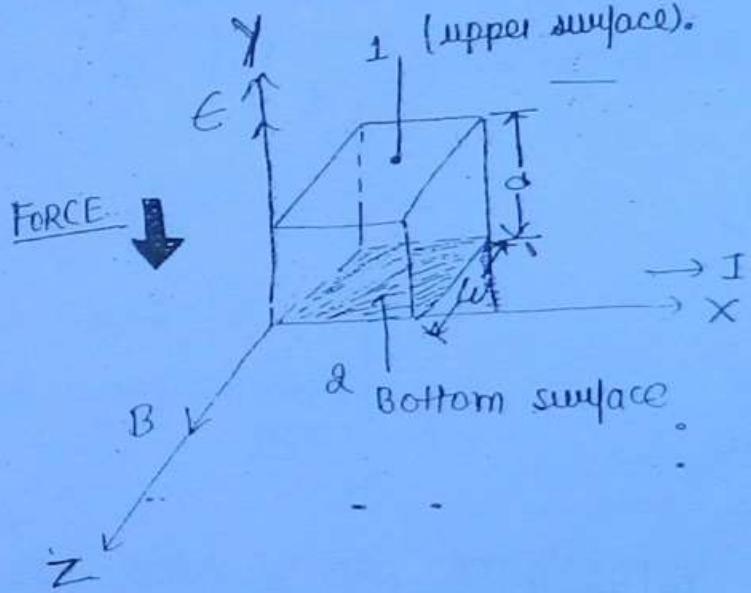
- As temp. is increases mobility of charge carriers decreases and therefore conductivity decreases
- As temp is increasing, minority carrier conc' will increasing with temp.
- As temp is increasing majority carrier conc' will remain almost a const.

$$F = T_c \quad \text{At } T = T_c \quad [\text{At } T = T_c]$$

- minority carrier "cone" approaches majority carrier "cone" and extrinsic semiconductor will become intrinsic semiconductor but the conductivity slightly greater than T_i .
- At some temperature the extrinsic SC will become intrinsic SC and the purpose of doping in the semiconductor lost.
- $\boxed{\text{At } T > T_c}$
- Above some temperature extrinsic SC is intrinsic & therefore the conductivity will be increasing with the temp.
- * At very high temp. extrinsic SC will become intrinsic semiconductor.
- * At low temp. extrinsic SC as temp. is increasing the conductivity increases with temp.
- * In extrinsic SC the conductivity decreases with temp. (Becoz temp. as temp. is increasing mobility of charge carrier decreases).

HALL Effect

- ⇒ Hall effect states that—" If a specimen (metal or semiconductors) carrying the current 'I' is placed in transverse magnetic field B . Then an electric field intensity 'E' is induced in a direction perpendicular to both I and B."
- ⇒ A current carrying metallic strip is placed in transverse magnetic field then an electric field intensity E is induced in a direction \perp to both I & B (upper surface).



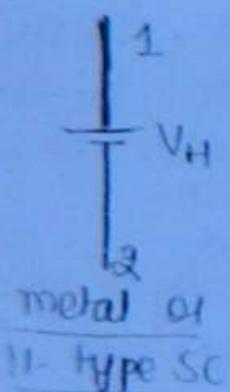
- ⇒ The specimen should be square or rectangular in shape
- ⇒ 'w' is width of the specimen
- ⇒ 'd' is height or thickness of the specimen and it is also the spacing between the bottom and upper surface
- ⇒ The current direction is taken on x-direction and magnetic field in z-direction and field intensity in y-direction
- ⇒ Direction of force is downward for e-holes because hole is valency e^- for taken with +ve charge

⇒ By using the hall experiment, we can determine

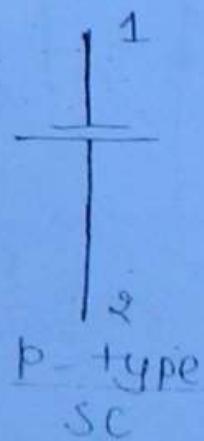
- (1) whether the given specimen is a metal or SC.
- (2) Concentration of charge carriers
- (3) Mobility of charge carriers.
- (4) Magnetic flux density
- (5) In designing of hall effect transducers
- (6) To measure the signal power in EM wave

⇒ The polarity and magnitude of the induced hall voltage will indicate whether the given specimen is metal or SC.

⇒



metal or
II-type SC



p-type
SC

⇒ Electric field intensity

$$|E| = \frac{|V_H|}{d} \text{ V/m}$$

⇒ Hall voltage V_H

$$\Rightarrow V_H = \epsilon d \text{ volt}$$

$$\Rightarrow V_H = \frac{BI}{PW} \text{ volt}$$

$$\left[\frac{1}{e} = R_H \right] \text{ Hall coefficient}$$

$\rho \rightarrow$ charged density.

$$\Rightarrow \boxed{V_H = \frac{IB}{w} R_H}$$

$$\Rightarrow \boxed{V_H \propto R_H}$$

\Rightarrow From the Hall experiment mobility of charge carrier

$$\boxed{\mu = \frac{8}{3\pi} \sigma R_H}$$

$$\boxed{\mu \approx \sigma R_H}$$

$\{\sigma \rightarrow \text{conductivity of specimen}\}$

\Rightarrow Applications :-

\rightarrow Hall effect multiplier

\rightarrow Magnet-o-field meter.

$\Rightarrow \boxed{\text{IES ONLY}}$

\Rightarrow Magneto-field meter is an instrument used for measurement of magnetic flux density.

\Rightarrow By using hall-experiment we can measure magnetic flux density $\rightarrow \boxed{H \propto B}$

\Rightarrow By using hall experiment we can measure magnetic field intensity.

\Rightarrow if the polarity of Induced hall voltage is +ve for the bottom surface, the given specimen is

P-type sc

- ⇒ Hall voltage is measured with respect to bottom surface of specimen.
 - ⇒ For metal Hall voltage is -ve
 - ⇒ For N-type SC Hall voltage is -ve
 - ⇒ For P-type SC Hall voltage is +ve
 - ⇒ For Intrinsic semiconductor Hall voltage is "zero". (PSU)
 - ⇒ In Hall experiment if one input signal is applied in the form of current and another input signal is applied in the form of magnetic field then induced Hall voltage is equal to the product of two input signals and Hence Hall experiment can be used in designing of Hall-effect multiplier.
 - ⇒ The charge density
- $$\Rightarrow \boxed{\rho = \text{charge} \times \text{carrier conc}^n} \quad C/m^3$$

$$\Rightarrow \text{Hall coefficient } R_H$$

$$\boxed{R_H = \frac{1}{\rho} = \frac{1}{\text{charge} \times \text{carrier conc}^n}} \quad m^3/C.$$

- ⇒ From the Hall experiment

$$\Rightarrow \mu \approx \sigma R_H$$

$$\Rightarrow \boxed{R_H \approx \frac{\mu}{\sigma}}$$

$$\boxed{V_{H0} \propto R_H}$$

$$R_H \propto V_H \propto \frac{1}{\sigma}$$

(For metals)

→ σ is large, V_H is small (μV)

(For SC)

→ σ is small, V_H is large (mV).

⇒ Hall voltage is small [metals]

⇒ Hall voltage is large in [SC.]

⇒ The mobility of charge carriers can be experimentally found by using Hall effect.

⇒ The mobility of charge carriers can be experimentally found by using Haynes - Shockley experiment *

⇒ By using Haynes - Shockley experiment we can measure

→ Mobility of charge carriers

→ Diffusion length of charge carriers ($D = \mu V_T$, $D \propto \mu$)

To

Prob A doped SC specimen has Hall coefficient $3.6 \times 10^{-4} m$ and resistivity $9 \times 10^3 \Omega \cdot m$ assuming single carrier conduction, the mobility & density of charge carriers in the specimen approximately are given by

AOM

$$R_H = 3.6 \times 10^{-4}, \quad \rho = 9 \times 10^3$$

$$\mu = \sigma R_H = \frac{1}{9 \times 10^3} \times 3.6 \times 10^{-4} = 0.4 \times 10^{-4} = 4 \times 10^{-5}$$

$$\mu = 4 \times 10^{-5} m^2/V \cdot sec \quad 0.04 \text{ m}^2/V \cdot sec$$

$$Q = e \rho \cdot 6 \times 10^{19} \times$$

$$R_H = \frac{1}{\text{carrier conc}}$$

$$\text{carrier conc} = \frac{1}{e R_H} = 1.73611 \times 10^{22}/m^3$$

For
TES

Assuming single carrier conc'

$$V = \text{carrier conc} \times q \times \mu$$

$$\text{carrier conc} = \frac{V}{q\mu}$$

$$= \frac{1}{\rho \times q \times \mu} = \frac{1}{9 \times 10^{-3} \times 1.6 \times 10^{-19} \times 0.04}$$

$$\text{carrier conc} = 1.73611 \times 10^{22} / \text{m}^3$$

Ques Find the magnetic field in a rectangular SC specimen 4mm wide and 2mm thick & having hall coefficient of $10^{-3} \text{ m}^3/\text{C}$ when a current 1mA is passed through the sample, a hall voltage of 2mV is obtained.

$$V_H = \frac{BI}{\rho w}$$

$$V_H = \frac{R_H B}{w}$$

$$2 \times 10^{-3} = \frac{10^{-3} \times B \times 10^{-3}}{4 \times 10^{-3}}$$

$$B = \frac{8 \times 10^{-3}}{10^{-3}} = 8 \text{ Wb/m}^2$$

18

1

Prob Find the magnetic field coefficient in a N-type Ge bar of width 3mm and height 2mm assume $B = 0.9 \text{ wb/m}^2$, $E = 5 \text{ V/cm}$ and current $I = 1.5 \text{ mA}$.

$$V_H = \frac{BR_H}{\omega}$$

$$V_H = Ed = 5 \times 10^2 \times 2 \times 10^{-3}$$

$$V_H = 10^3 \times 10^{-3} = 1 \text{ V}$$

$$I = \frac{0.9 \times R_H \times I}{3 \times 10^{-3}}$$

$$R_H = \frac{0.9 \times 10^{-3}}{0.9 \times 10^{-3}} = 1.0 \times 10^2 = 9.9 \times 10^2 \times 1.5 \times 10^{-3}$$

$$R_H = 2.2 \text{ m}^3/\text{C}$$

(ii) page

AEN (5)

$$\omega = 2 \text{ mm}, d = 0.2 \text{ mm}$$

$$I = 10 \text{ mA} \quad B = 0.1 \text{ wb/m}^2$$

$$V_H = -1.0 \text{ mV}, R_H = ? , n = ?$$

$$V_H = \frac{BIR_H}{\omega}$$

$$R_H = \frac{|V_H| \omega}{B \cdot I} = \frac{-1.0 \times 10^{-3} \times 2 \times 10^3}{0.1 \times 10 \times 10^{-3}}$$

$$R_H = 2 \times 10^{-3}$$

$$\eta = \frac{1}{qR_H} = \frac{1}{1.6 \times 10^{-19} \times 2 \times 10^{-3}}$$

$$n = 3.2 \times 10^{19} / \text{m}^3$$

Classification of

Classification of Semiconductor.

↓
Direct band gap sc
DBG - SC

1) During the recombination energy is dissipated in the form of light e.g. GaAs.

2) Other examples GaN, GaAsP, InAs, ZnS, CdS, CdSe, InP

During recombination most of the falling e^- will be directly falling from CB to VB and release the energy in the form of light and very few e^- will be colliding with crystal of atom & these crystals will absorbing energy in the absorbing energy from falling e^- and gets heated up & they will release the energy in the form of heat (99% light 1% heat).

During the recombination most of the falling e^- will be directly releasing the energy in the form of light & therefore called Direct band gap sc.

The energy of falling e^- changes with R.E & D.E changes

↓
Indirect band gap sc
IBG - SC

1) During the recombination energy is dissipated in the form of heat (Ge, Si)

2) Other examples AlP, PbS, AlAs, AlSb, (GaP) PbSe.

3) During recombination most of falling e^- will be colliding with crystal of the atom and these crystal will be absorbing the energy from falling e^- And they dissipate the energy in the form of heat. But very few falling e^- will be escaping the collision and they will directly fall into the valency band & energy is released in the form of light (99% heat & 1% light).

4) The falling e^- are indirectly responsible in releasing the energy to the crystal of atom in the form of heat & therefore called Indirect band gap - sc.

same as

- | | |
|--|---|
| (6) The direction of falling e ⁻ will remain the same but also the path of e ⁻ will remain the same. | (6) The "dwell" of falling e ⁻ will remain the same but also the path of e ⁻ slightly changes because of collision. |
| (7) The momentum of the falling e ⁻ changes for both SC. | |
| (8) Relatively carrier lifetime is less. | (8) Relatively carrier lifetime is large. |
-

⇒ * Si is never used in fabrication of LED & LASER because it is Indirect band gap SC.

* Si is not used for fabrication of following devices

- LED
- Tunnel diodes
- Varactor diode
- PIN Diode
- Gunn Diode
- IMPATT Diode
- LASER

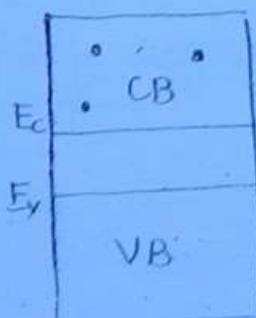
* GaAs is a e.g. for DBG_I-SC

- ✓ (1) DBG_I-SC
- (2) IBG_I-SC
 - (3) Wide-band gap - SC.
 - (4) Narrow band gap - SC.

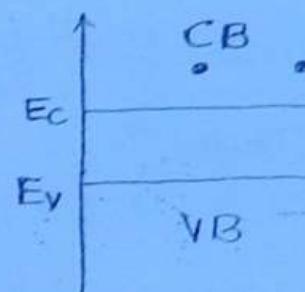
Ques Semiconductor LASER are fabricated with :-

- ① DBR-SC with larger time const. \rightarrow Au
- ② DBR-SC with smaller time const.
- ③ IBR-SC with smaller time const.
- ④ IBR-SC with larger time const.

Equation for conc' of e^- in the CB.



Approx. Energy
Band Diagram



Exact Energy
Band Diagram

- E_c minimum energy of the conduction band
- E_v maximum energy of the valency band
- Energy possessed by free e^- in the conduction band has energy in the range of E_c to $+\infty$.

→ The eqn for conc' of e^- in the conduction band

$$\Rightarrow n = N_c e^{-(E_c - E_f)/kT}$$

$E_f \rightarrow$ Fermi energy in eV.

$N_c \rightarrow$ material const. it is function of temp.

$$N_c = \alpha \left(\frac{2\pi k T m_n}{h^2} \right)^{3/2}$$

$$\therefore N_c = \alpha \left(\frac{2\pi k T m_n}{h^2} \right)^{3/2} T^{3/2} \propto$$

$m_n \rightarrow$ effective mass of e^-

\hookrightarrow the mass of e^- when e^- is revolving in the given material. (effective mass).

For Si.

$$\left(\frac{m_n}{m}\right) = 1.08$$

- Effective mass of e^- is always greater than rest mass of e^- .

$$m \rightarrow 9.1 \times 10^{-31} \text{ kg} \rightarrow \text{rest mass of } e^-$$

$$m_n = 1.08m$$

$$= 1.08 \times (9.1 \times 10^{-31}) \text{ kg}$$

$$\Rightarrow [m_n = 1.08 \times 9.1 \times 10^{-31}]$$

- N_v is approx. equal to the density of states in the CB.

Equation for concn of holes in VB. \Rightarrow

- The energy possessed by holes in VB is $-E_F + E_v$

- The eqn for concn of holes in VB is given by.

$$P = N_v e^{-[E_F - E_v]/kT}$$

- N_v is a material constt. and it is a funcⁿ of temp.

$$N_v = 2 \left(\frac{2\pi k T m_p}{h^2} \right)^{3/2} = 2 \left(\frac{2\pi k T m_p}{h^2} \right)^{3/2} T^{3/2}$$

$m_p \rightarrow$ effective mass of the hole.

Fol si

$$\left(\frac{m_p}{m}\right) = 0.56$$

$$m_p = 0.56 m$$

$m \rightarrow$ is the mass of hole

$$m \rightarrow 1.6 \times 10^{-27} \text{ kg.}$$

$$m_p = 0.56 \times 1.6 \times 10^{-27}$$

→ ② N_v is approximately equal to density of states in the valency band

[NOTE] → mass of the hole is equal to mass of proton

→ Effective mass of hole is always greater than effective mass of $e^- \Rightarrow m_p > m_n$

Derive an equation for intrinsic concn (n_i) →

$$n = N_c e^{-[E_c - E_F]/kT} \rightarrow ①$$

$$p = N_v e^{-[E_F - E_V]/kT} \rightarrow ②$$

Multiplying eq ① & ②

$$np = N_c N_v e^{-[E_c + E_V]/kT}$$

$$np = N_c N_v e^{-\left[\frac{E_c - E_V}{kT}\right]} \left[\begin{array}{l} \Rightarrow \text{but } E_c - E_V = E_g \\ \& np = n_i^2 \end{array} \right]$$

$$\Rightarrow n_i^2 = N_c N_v e^{-E_g/kT} \Rightarrow \left[n_i^2 = \frac{N_c N_v e^{-E_g/kT}}{N_c N_v e^{-E_g/kT}} \right]$$

$$\text{but } N_e N_{\nu} = \frac{2}{h^2} \left(\frac{2\pi k T m_n}{h^2} \right)^{3/2} \cdot \frac{2}{h^2} \left(\frac{2\pi k T m_p}{h^2} \right)^{3/2} T^3$$

$$\Rightarrow A_0 T^3$$

$$\Rightarrow \boxed{\therefore n_i^2 = A_0 T^3 e^{-E_F/kT}}$$

$$\text{when: } \Rightarrow \boxed{A_0 = 4 \left(\frac{2\pi \bar{k}}{h^2} \right)^3 (m_n m_p)^{3/2}}$$

[FERMI ENERGY] $\Rightarrow (E_F)$

→ Fermi energy is defined as the maximum energy possessed by the e^- at 0K

(or)

→ Fermi energy is also defined as the maximum kinetic energy by the e^- at 0K.

$$E_F = \max K.E.$$

$$= \frac{1}{2} m v_{\max}^2$$

Max. velocity of e^-
or
velocity of e^-

$$\boxed{v = \sqrt{\frac{2 E_F}{m}} \text{ m/s.}}$$

eqn for velocity of e^- in
terms of fermi energy.

→ Fermi energy is also define as the energy possessed by the fastest moving e⁻ at 0K.

[Fermi Dirac function. [f(E)]] :-

→ It is also called Fermi Dirac probability function.

→ The Fermi Dirac function for a metal or SC is given by

$$\Rightarrow f(E) = \frac{1}{1 + e^{(E - E_F)/kT}}$$

E → Energy possessed by e⁻ in eV.

→ Fermi Dirac func. is used to find the probability of e⁻ existing as a function of energy level.

→ At T=0K, we get two conditions.

(i) If E > E_F

$$f(E) = \frac{1}{1 + e^{+\infty}} = \frac{1}{1+0} = 0 \text{ } \textcircled{S} \text{ } 0\%$$

→ This indicates at T=0K, no e⁻ are available in the material with energies greater than E_F.

(ii) If E < E_F

$$f(E) = \frac{1}{1 + e^{-\infty}} = \frac{1}{1+0} = 1 \text{ } \textcircled{S} \text{ } 100\%$$

→ This indicates at T=0K, e⁻ are available with energies less than E_F.

At $T \neq 0K$

③ $T > 0K$

If $E = E_F$ \rightarrow

$$f(E) = \frac{1}{1 + e^{\frac{E-E_F}{kT}}} = \frac{1}{1+1} = \frac{1}{2} \text{ or } 0.5 \text{ or } 50\%$$

- ⇒ The above analysis indicates when $T > 0K$ e^- may or may not be available with energies $E = E_F$.
- ⇒ Fermi level is the energy level with 50% probability of being filled if no forbidden band exists.
- ⇒ In metal $f(E) = 1$ or 100%.
- ⇒ In SC, the probability of e^- existing is $f(E)$ then probability of hole existing is $1 - f(E)$.

Fermi level in intrinsic Semiconductor. \rightarrow

$$n = p \\ N_c e^{-[E_C - E_F]/kT} = N_V e^{-[E_F - E_V]/kT}$$

$$\frac{N_c}{N_V} = e^{-2E_F + E_V + E_C/kT}$$

$$\ln \left(\frac{N_c}{N_V} \right) = \frac{E_C + E_V - 2E_F}{kT}$$

∴ $E_F = \frac{E_C + E_V}{2} - \frac{kT}{2} \log \frac{N_c}{N_V}$

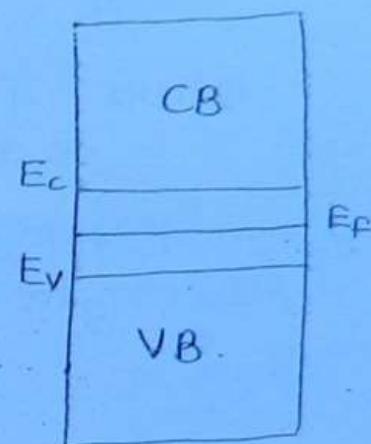
⇒ In intrinsic SC fermi level depends only on temperature.

case-I

$$\text{Let } \left\{ \begin{array}{l} m_n = m_p \\ N_c = N_v \end{array} \right\}$$

$$\therefore \frac{kT}{q} \log \frac{N_c}{N_v} = 0$$

$$\Rightarrow \boxed{E_f = \frac{E_c + E_v}{2}}$$



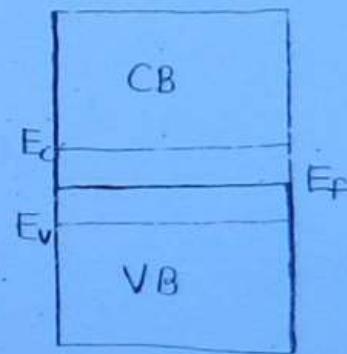
⇒ The fermi level will now exist at the centre of energy gap.

case-II

→

$$\text{Let } T = 0K$$

$$\Rightarrow \boxed{E_f = \frac{E_c + E_v}{2}}$$



At T=0K

⇒ At T=0K, an intrinsic SC fermi level is existing at the centre of the energy gap.

⇒ At T=0K, carrier conc' are zero and therefore conductivity is zero and intrinsic SC will behave as insulator.

NOTE → In Intrinsic SC fermi level will be existing exactly at the centre of energy gap under 3 cond'n:

- (1) $m_n = m_p$
- (2) $N_c = N_v$
- (3) $T = 0K$

Case III

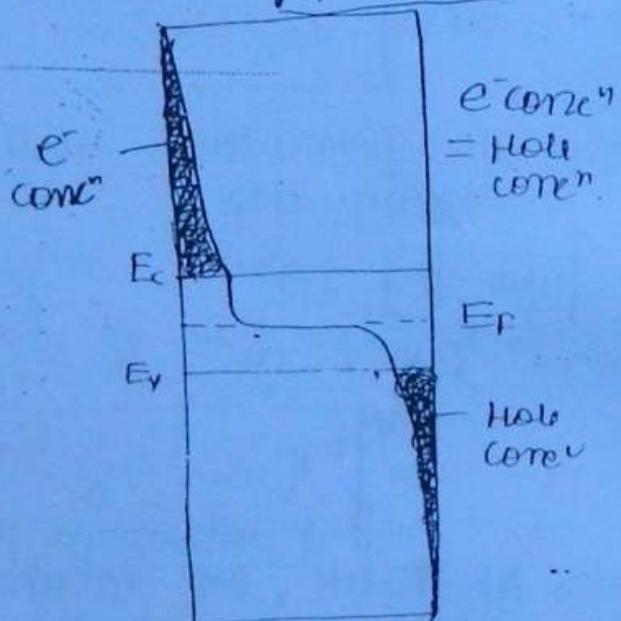
[At T = 300 K]

$$E_F = \frac{E_c + E_v}{2} - \frac{kT}{2} \log e \frac{N_c}{N_v}$$

where T = 300K

$$E_F = \frac{E_c + E_v}{2} \approx 150T \log e \frac{N_c}{N_v}$$

(At T=300K)

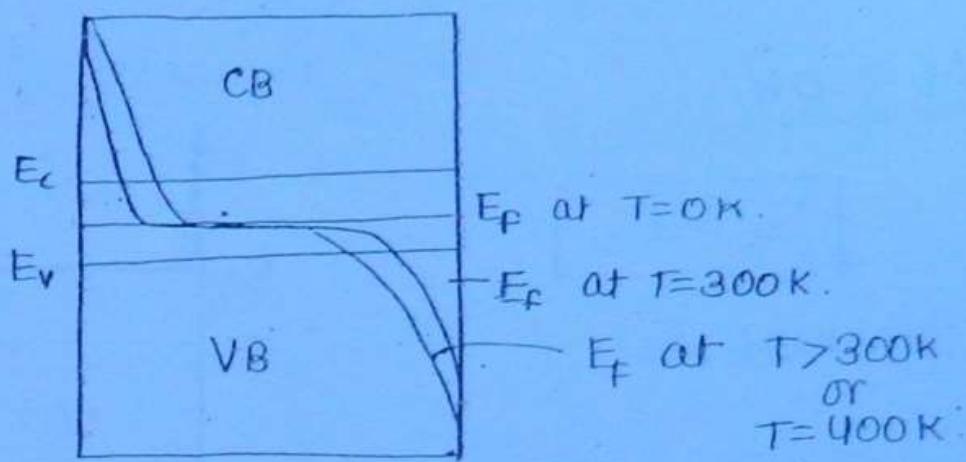


- ⇒ In Intrinsic semiconductor at room temp, Fermi level will be passing through the centre of energy gap
- ⇒ At room temp because of thermal energy, a no covalent bond will be broken and equal no. of e⁻ and holes are created and there will be a conductivity in the SC.

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case IV.

(Fermi level positions at different temp.) \Rightarrow



[Fermi level in N-type sc.] \Rightarrow

$$n \simeq N_D$$

$$N_c e^{-[E_C - E_F]/kT} \simeq N_D$$

$$\frac{N_c}{N_D} = e^{E_C - E_F/kT}$$

$$\log_e \frac{N_c}{N_D} = \frac{E_C - E_F}{kT}$$

/ E_C

$$E_F = kT \log_e \frac{N_c}{N_D}$$

* \approx

$$E_F = E_C - kT \log_e \frac{N_c}{N_D}$$

L

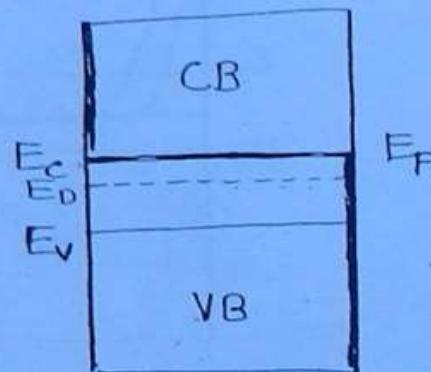
→ In N-type SC Fermi level depends on temp. and doping conc.

Case-I

At T=0K

$$E_F = E_c$$

⇒ E_F coincides E_c



⇒ At 0K carrier conc' are zero and therefore conductivity is zero and N-type SC will behave as insulator.

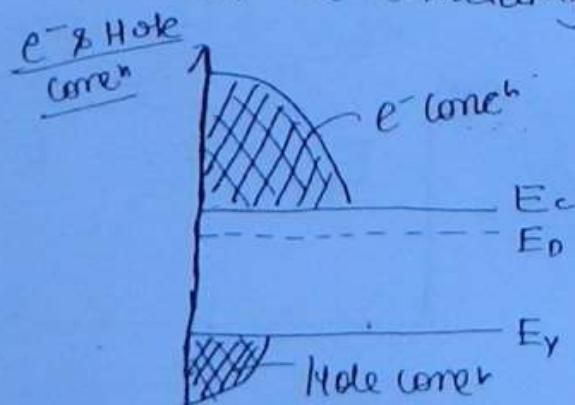
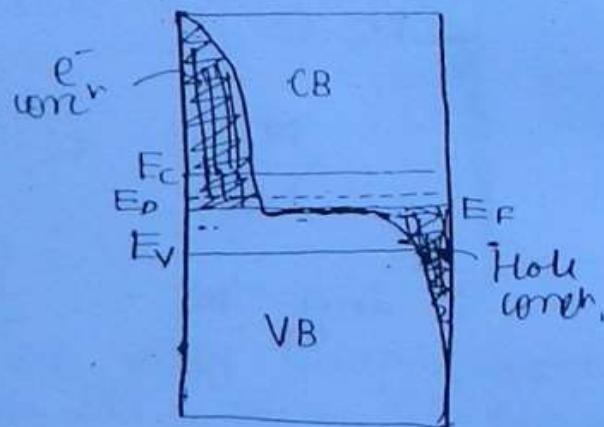
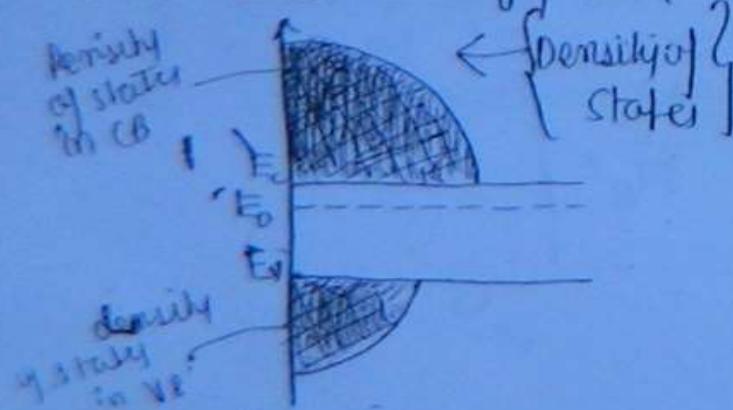
Case-II

At T=300K

$$E_F = E_c - kT \log_e \frac{N_c}{N_D}$$

⇒ In N-type SC at room temp Fermi level exists just below the donor energy level.

⇒ As temp. is increasing from OK to 300K at some intermediate temp. the Fermi level will be coinciding with donor energy level.



Case III Condition :

$$E_c - E_F = kT \log_e \frac{N_c}{N_D}$$

(i) Let $T \Rightarrow$ increases. \rightarrow

$N_c \uparrow$ & let $N_c > N_D$

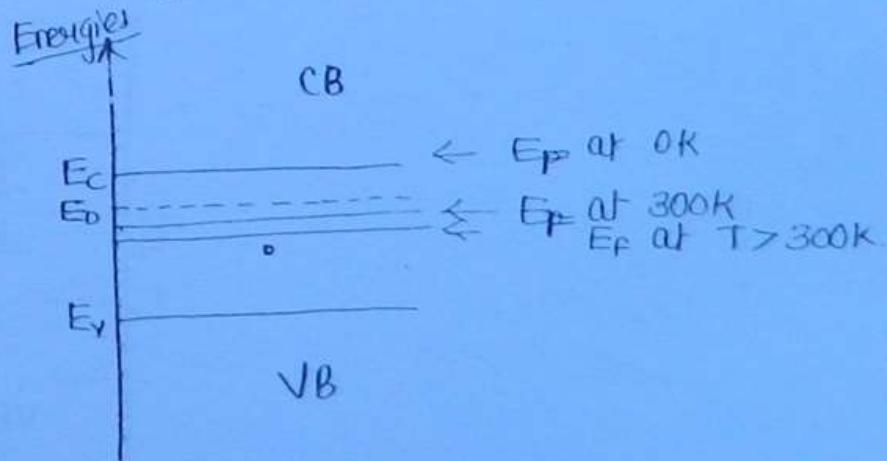
$$E_c - E_F > 0$$

$$\Rightarrow [E_c > E_F]$$

$\rightarrow T \uparrow$ in N-type SC Fermi level moves away from CB (or)

\rightarrow Fermi level moves towards the centre of energy gap.
Hence conductivity decreases with temperature.

\rightarrow The position of Fermi level for different temp in N-type SC is given below : \rightarrow



\rightarrow At some temperature, E_F will be existing at the centre of energy gap.

\Rightarrow

(iii) Let Doping $\uparrow \Rightarrow$

$$N_D \uparrow \text{ and } N_D > N_c$$

$$E_c - E_F < 0$$

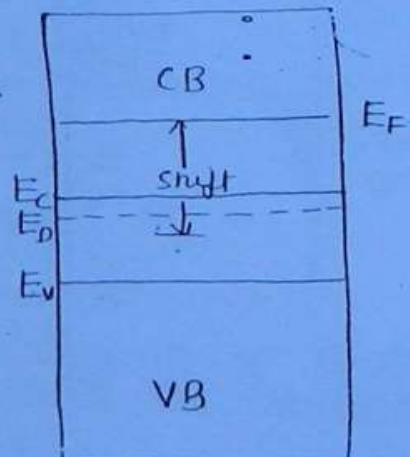
$$\Rightarrow [E_c < E_F]$$

\Rightarrow In N-type SC Doping $\uparrow (N_D)$ Fermi level moves into the conduction band or moving away from the centre of energy gap.

Hence σ will increases with doping \uparrow .

\Rightarrow In N-type SC as Doping increases, E_F takes upward shift.

\Rightarrow In a Highly Doped N-type SC or Highly degenerated N-type SC, the E_F exist in CB.



CURR IV

Shift in the position of Fermi level due to Doping.
(Or)

Shift in the position of E_F w.r.t E_F of Intrinsic sc.
(Or)

Shift in position of E_F w.r.t to centre of energy gap.

* \Rightarrow
$$\text{Shift} = kT \log_e \frac{N_D}{n_i} \text{ eV.}$$

$$\Rightarrow \text{Shift} = kT \log_e \frac{n}{n_i} \text{ eV}$$

Fermi-level in p-type Semiconductor

$$P \approx N_A$$

$$N_V e^{-(E_F - E_V)/kT} = N_A$$

$$\frac{N_V}{N_A} = e^{E_F - E_V/kT}$$

$$\frac{E_F - E_V}{kT} = \log_e \frac{N_V}{N_A}$$

★

$$E_F - E_V = kT \log_e \frac{N_V}{N_A}$$

★

$$E_F = E_V + kT \log_e \frac{N_V}{N_A}$$

→ In p-type SC Fermi-level depends on temp. and doping concn

Case I

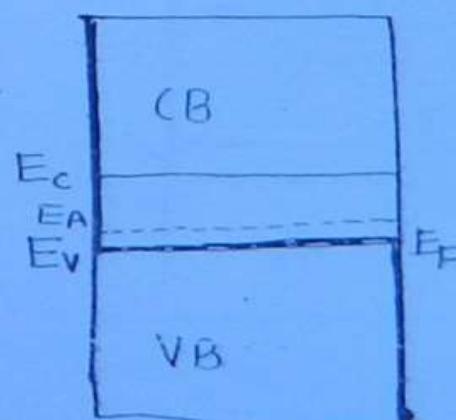
$$\xrightarrow{?}$$

$$\text{Let } T=0\text{K}$$

$$E_F = E_V$$

E_F coincides with E_V

At $T=0\text{K}$

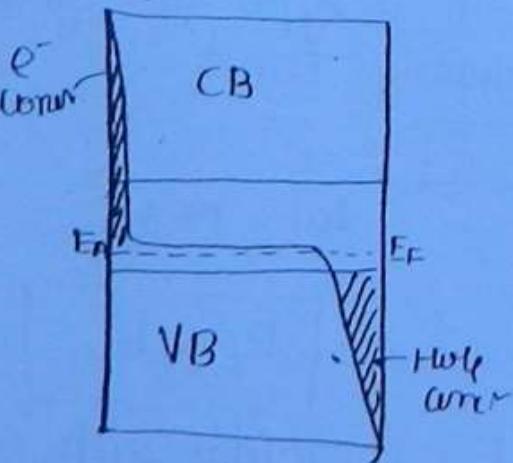
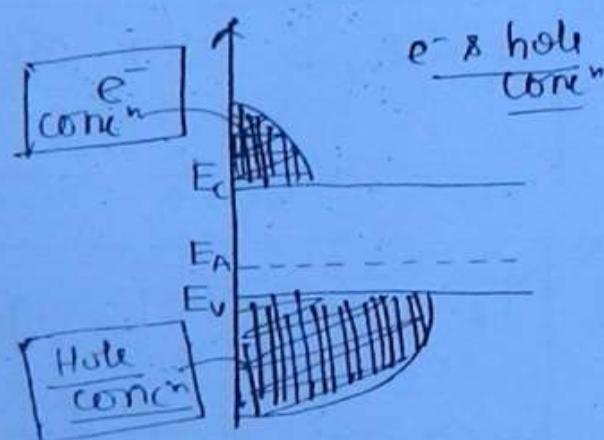
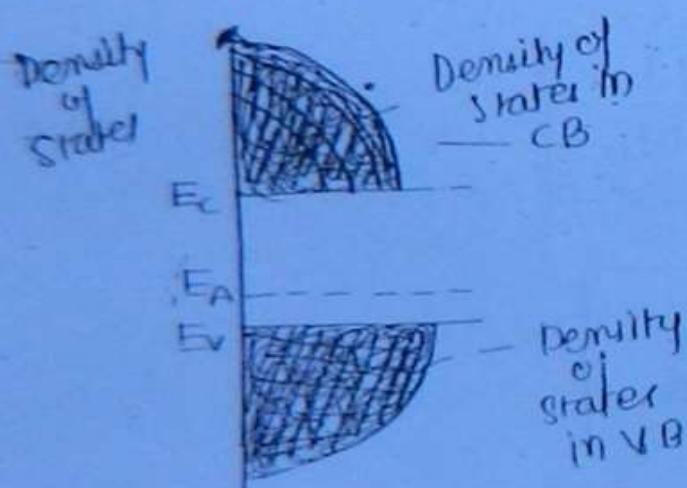
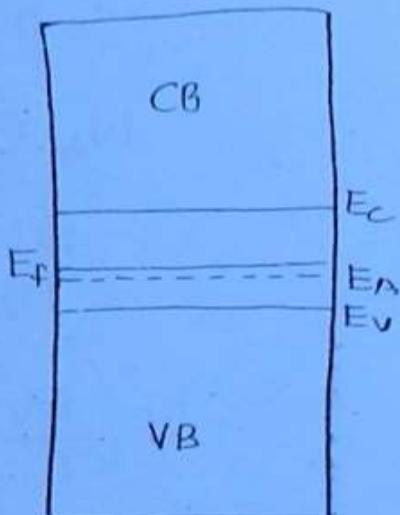


⇒ At 0K carrier concn are zero and therefore conductivity is zero and therefore p-type SC at 0K behaves as insulator

Calculation for $T = 300\text{ K}$

$$E_F = E_V + kT \log \frac{N_V}{N_A}$$

⇒ In p-type semiconductor at room temp. fermi-level is existing just above the acceptor energy level



case III

$$E_F - E_V = kT \log_e \frac{N_V}{N_A}$$

(i) Let Temp \uparrow

$N_V \uparrow$ and let $N_V > N_A$

$$E_F - E_V > 0$$

$$\Rightarrow [E_F > E_V]$$

\rightarrow In P-type SC Temp \uparrow E_F moves away from VB or E_F moves towards the centre of energy gap.

$$\Rightarrow [\therefore \sigma \downarrow \text{ with temp } \uparrow]$$

\rightarrow In P-type SC the position of Fermi level for different temperature is given below.

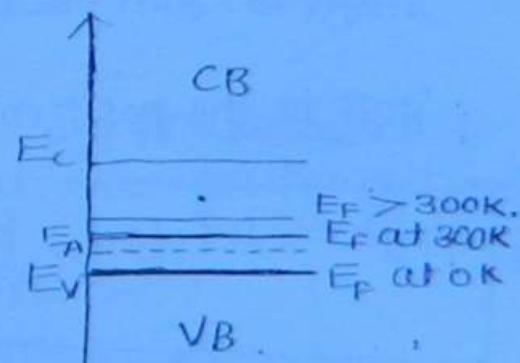
\rightarrow At some temperature, the Fermi level will be at the centre of the energy gap

(ii) Let Doping concn \uparrow .

N_A / \uparrow & let $N_A > N_V$

$$E_F - E_V < 0$$

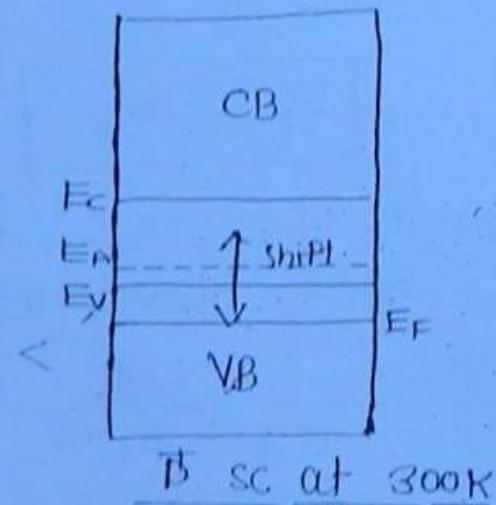
$$\Rightarrow [E_F < E_V]$$



\rightarrow In P-type SC as doping \uparrow E_F moves into the VB or E_F away from the centre of energy gap.

$$\Rightarrow [\therefore \sigma \uparrow \text{ with doping } \uparrow]$$

- In p-type SC as doping increases Fermi-level takes downward shift. (denoted with -ve sign)
- In a highly doped p-type SC or highly degenerated p-type SC, the Fermi level will cross in the VB.



Ques N Shift in the position of Fermi level due to Doping
 or
 Shift in the position of E_F w.r.t. E_F of intrinsic SC.
 or
 Shift in the position of E_F w.r.t. centre of energy gap.

$$\Rightarrow \boxed{\text{Shift} = kT \log_e \frac{N_A}{n_i}} \text{ eV}$$

$$\boxed{\text{Shift} = kT \log_e \frac{P}{n_i}} \text{ eV}$$

(v)

downward

Ques. In a N-type SC, the Fermi level lies 0.3 eV below the CB at 300K if the temp. is increased to 330K find the approximate new position of Fermi level.

Soln

N-type SC

$$E_c - E_F = kT \log_e \frac{N_c}{N_D}$$

$$E_c - E_F \propto T$$

$$E_c - E_F \propto \log \frac{N_c}{N_D}$$

Neglecting the variation of N_c with temp

$$E_c - E_F \propto T$$

$$0.3 \propto 300\text{K}$$

$$E_c - E_{F2} \propto 330$$

$$E_c - E_{F2} = \frac{330 \times 0.3}{300} = 0.33\text{ eV}$$

Ques. i) In N-type SC, the E_F lies 0.4 eV below CB the concn of N_D is doubled find New position of E_F . Assume $kT = 0.03\text{ eV}$.

$$\text{Eq. of } E_F \quad N_D = N_c e^{-(E_c - E_F)/kT}$$

$$N_D = N_c e^{-0.4/0.03} \rightarrow ①$$

$$\& N_D = N_c e^{-(E_c - E_{F2})/0.03} \rightarrow ②$$

$$\frac{1}{2} = \frac{e^{-0.4/0.03}}{e^{-(E_c - E_{F2})/0.03}}$$

$$\frac{1}{2} = e^{-0.4/0.03 + (E_c - E_{F2})/0.03} \Rightarrow -\frac{0.4}{0.03} + \frac{E_c - E_{F2}}{0.03} = \log\left(\frac{1}{2}\right)$$

$$\Rightarrow E_c - E_{F2} = 0.4 + 0.03 \log_e \frac{1}{2} \Rightarrow 0.37\text{ eV}$$

Q8 In P-type Si the Fermi level lies 0.4 eV above the VB if concn of acceptor atoms is tripled find new position of E_F . Assume $kT = 0.03 \text{ eV}$

$$N_A = N_V e^{(E_F - E_V)/kT}$$

$$(0.367 \text{ eV})$$

$$N_A =$$

but In a SC at room temp, the intrinsic carrier concn and intrinsic resistivity are $1.5 \times 10^{16}/\text{m}^3$ & $2 \times 10^{13} \Omega\text{-m}$ resp. If it is converted into an extrinsic semiconductor with doping concn of $10^{20}/\text{m}^3$ find the shift in the E_F due to doping.

$$n_i = 1.5 \times 10^{16}/\text{m}^3$$

$$\rho_i = 2 \times 10^{13} \Omega\text{-m}$$

$$\text{Doping concn} = 10^{20}/\text{m}^3$$

$$\text{Shift} = KT \log_e \frac{\text{Doping concn}}{n_i^0} \text{ eV}$$

$$= 8.68 \times 10^{-5} \times 300 \log_e \frac{10^{20}}{1.5 \times 10^{16}}$$

$$\Rightarrow \boxed{\text{Shift} = 0.287 \text{ eV}}$$

but Si is doped with B to a concn of $4 \times 10^{17}/\text{Atom}/\text{cm}^3$. Assume $n_i = 1.5 \times 10^{16}/\text{cm}^3$ & $T = 300\text{K}$ compare to undoped Si the doped, the Fermi level of doped Si is.

$$\begin{aligned} n_i &= 1.5 \times 10^{16}/\text{cm}^3 \\ N_A &= 4 \times 10^{17}/\text{cm}^3 \end{aligned} \quad \left. \begin{array}{l} \\ \end{array} \right\} \text{P-type}$$

$$\text{Shift} = 8.68 \times 10^{-5} \times 300 \log_e \frac{4 \times 10^{17}}{1.5 \times 10^{16}}$$

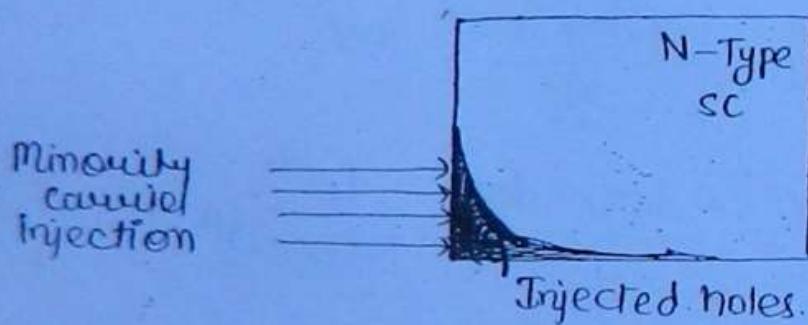
$$\text{Shift} = 0.44 \text{ eV}$$

In P-type SC E_F takes downward shift of 0.44eV

$$\boxed{\text{Shift} = -0.44 \text{ eV}} \quad \text{Ans}$$

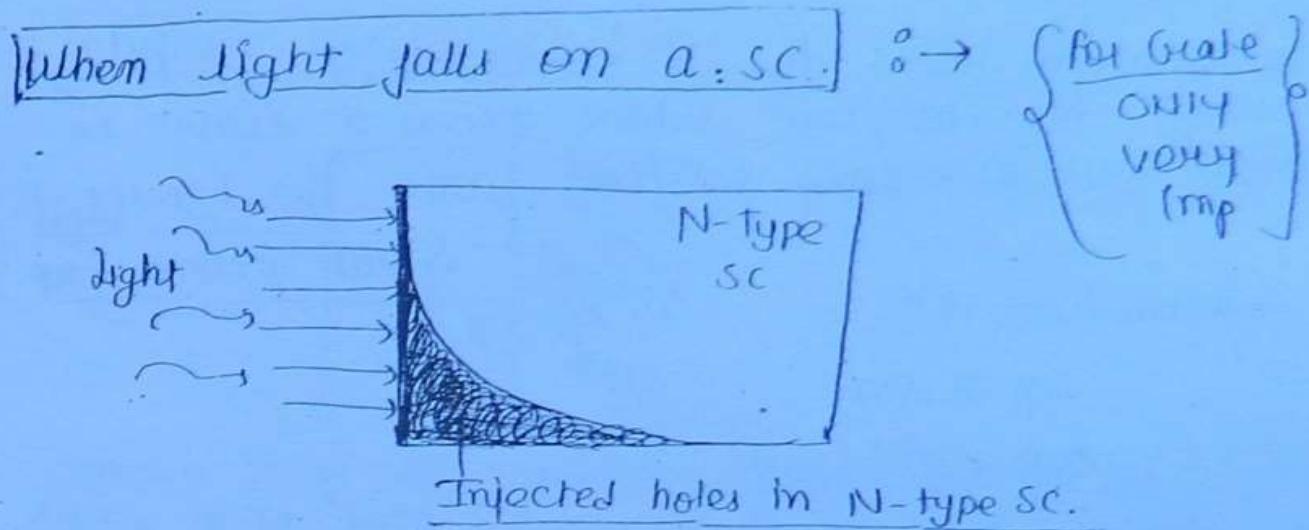
⇒ Low Level Injection

- It means the concⁿ of majority carrier concⁿ is far greater than minority carrier concⁿ.
- Under low level injection light is focused on semiconductor.
- Minority Carrier Injection into SC



- When minority carriers are injected into the semiconductor bar, the injected minority carrier concⁿ will be maximum at the surface where it is introduced into the semiconductor and the injected minority carrier concⁿ will be moving in the semiconductor from higher concⁿ to lower concⁿ i.e. due to the diffusion mechanism.
- When hole is introduced into the N-type SC bar the injected hole will be moving in the SC from higher concⁿ to lower concⁿ i.e. due to property called diffusion.

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- Light is focused on the sc under low level injection
- A light falls on SC, because of photon energy the surface of the SC gets heated up and due to this thermal energy a no. of covalent bond will be broken creating equal no of e^- and equal no. of holes
- Under steady state condⁿ excess e^- generated is equal excess holes generated i.e.

$$\Rightarrow \boxed{\Delta n \equiv \Delta p}$$

- The injected minority carrier concⁿ will be maximum on the surface of the sc where light is focussed and the injected minority carrier concⁿ will be moving in the SC from higher concⁿ to lower concⁿ i.e. due to the diffusion mechanism
- The generation rate or generation of e^- -hole pair is given by : \Rightarrow

$$\frac{dp}{dt} = \frac{\text{Excess holes generated}}{\text{minority carrier life time}}$$

$$\rightarrow \boxed{\frac{dp}{dt} = \frac{\Delta P}{\tau_p} e^- \text{ hole pairs/cm}^3/\text{sec}}$$

Prob. Generation rate due to irradiation in N-type SC having $N_D = 10^{17}/\text{cm}^3$ when excess e⁻ conc in steady state is $\Delta n = 10^{15}/\text{cm}^3$ and $\tau_p = 10 \mu\text{sec}$.

Ans

$$\text{Generation rate} = \Delta p / \tau_p$$

$$\Delta p \equiv \Delta n$$

$$\Delta p = 10^{15}/\text{cm}^3$$

{GATE exam imp.}

$$\text{Generation rate} = \frac{10^{15}}{10 \times 10^{-6}} = 10^{20} \text{ e-hole pair/cm}^2/\text{sec}$$

→ Considering N-type SC and light is focussed.

→ When light falls on a SC, minority carriers are generated.

→ When light is focussed on N-type SC, there will be two current component in the SC & they are
 ◊ hole diffusion current (because of photon energy)
 ◊ hole drift current (because of doping profile)

→ Under low level injection minority hole drift current is almost negligible.

→ Under low level injection current in the SC is dominated by diffusion.

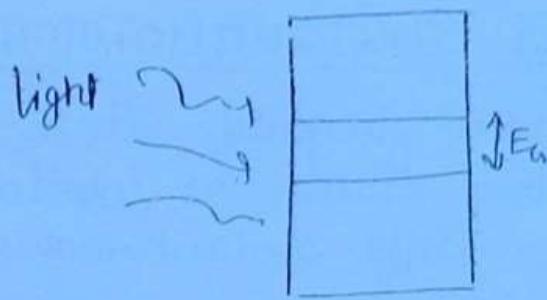
Wavelength of light

$$\rightarrow \boxed{\lambda = \frac{1.24}{E_G}} \text{ } \mu\text{m} \quad E_G \rightarrow \text{Energy gap of material in eV}$$

→ Wavelength of visible light is in range of [0.38 μm to 0.76 μm]

→ If wavelength > 0.76, it belongs to Infrared region.

Intrinsic Excitation :-



if photon energy $\geq E_g$

i.e.

$$h\nu \geq E_g$$

- Electron may be exciting from VB to CB
- When light falls on SC, an e^- may be exciting from VB to CB & this called Intrinsic excitation.
- The minimum photon energy required for Intrinsic excitation is equal to E_g .

Extrinsic Excitation

- When light falls on N-type SC, an e^- may be exciting from donor energy level into the conduction band & this is called extrinsic excitation.
- When light falls on P-type SC, an e^- may be exciting from valency band into acceptor energy level and this is called extrinsic excitation.
- The minimum photon energy required for extrinsic excitation { 0.01 eV for Ge } / { 0.05 eV for Si }

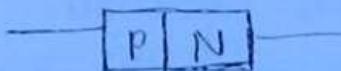
DIODE

PHOTO CONDUCTIVE Effect :-

- It is the property where the conductivity of a material or device increases with the light is called photoconductive effect.
- Photoconductive effect is sometimes called photoresistive effect.
- The property where the resistivity of material or device decreases with the light is called photoresistive effect.

SEMICONDUCTOR DIODE

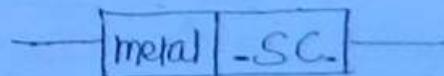
P-N junction diode



→ Rectification properties are existing.

→ Can be used as rectifier

Metal SC junction diode



→ No such properties

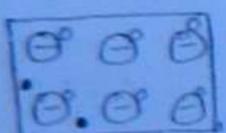
→ Cannot work as rectifier
e.g. ① Shottky Diode

② Point contact Dia

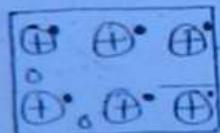
P-N Junction Diode

- A p-n junction will form only when a bonding force is created between the p-type and n-type semiconductors.
- Diodes are fabricated by using :-

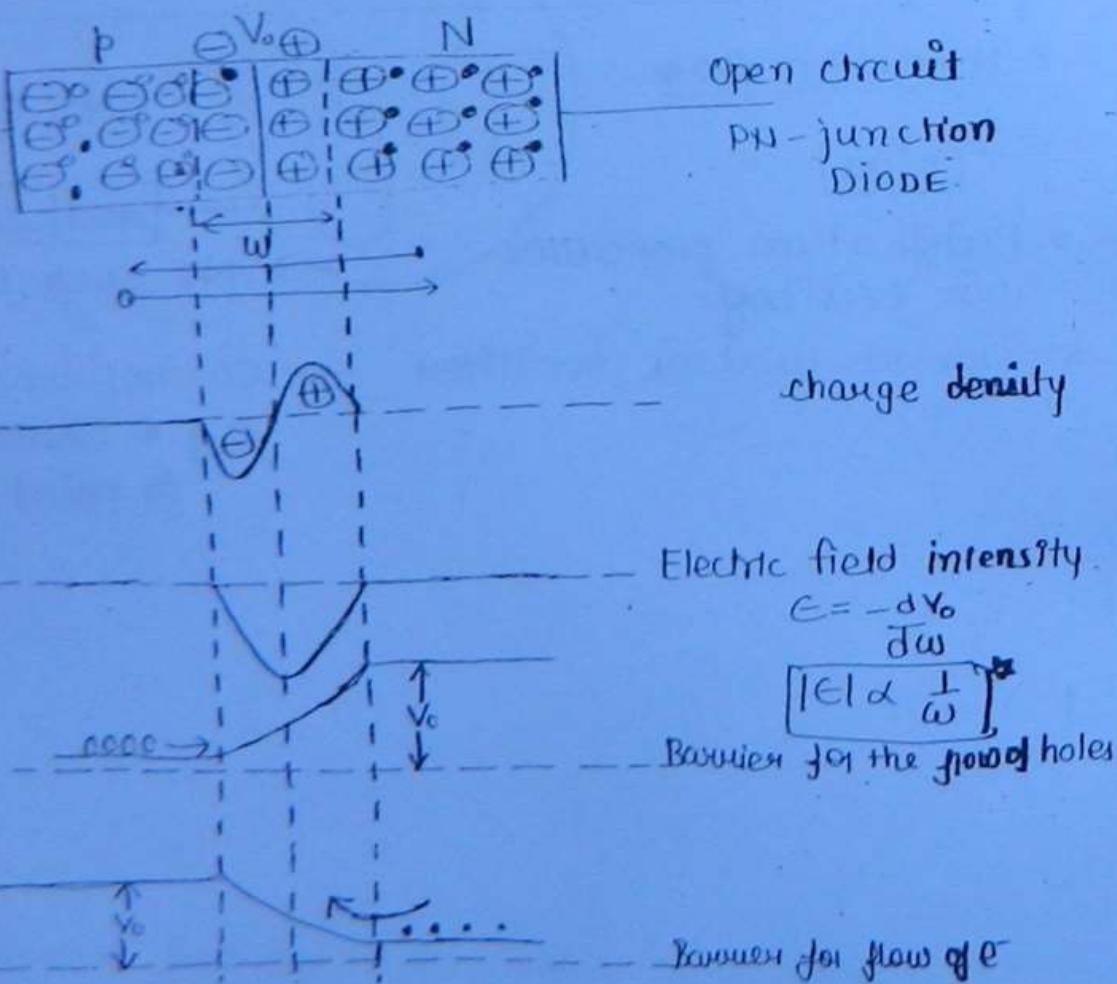
 - (1) Alloy - Junction Technique
 - (2) Cadmium - Junction Technique
 - (3) Epitaxial method.
 - (4) Diffusion method.



P-type



N-Type



- Depletion layer is also called space charge region or transition region.
 - Depletion layer is created due to diffusion of majority carriers across the junction.
 - Depletion layer width
- $$w \propto \frac{1}{\sqrt{\text{Doping}}}$$
- w is the range of $0.1 \mu\text{m}$ to $1 \mu\text{m}$.
 - Typical value of w is $0.5 \mu\text{m}$.
 - In the depletion layer mobile charge carriers are zero.
 - Depletion layer consist of ions and covalent bonds.
 - Depletion layer consist of immobile charged particles.
 - Depletion layer consist of negative and positive charges on the either side of the junction.
 - Depletion layer consist of negative ions (acceptor ions on the p-side) and positive ions (donor ions on the N-side).
 - Depletion layer will oppose the majority carriers in crossing the junction.
 - Depletion layer will not oppose minority carriers in crossing the junction.
 - Depletion layer will help minority carriers in crossing the function.
 - Depletion layer is extremely narrow where doping conc' is very high.

→ V_0 is called potential hill or contact potential or barrier potential or diffusion voltage or Built-in voltage (V_{bi}).

→ For Ge diode

$$V_0 = 0.1\text{ V to } 0.5\text{ V}$$

and Typical value 0.2 V

For Si Diode.

$$V_0 = 0.6\text{ V to } 0.9\text{ V}$$

Typical value 0.7 V

→ Contact potential of diode cannot be practically measured by using a voltmeter.

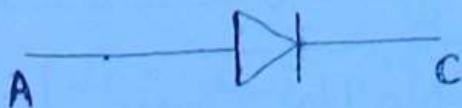
→ In any type of p-n junction, the field intensity is always maximum at the junction.

→ In a normal diode, field intensity is negative and it is maximum at the junction and it tapers on either side of junction and it is zero outside the depletion layer.

→ Majority carriers will be climbing up the barrier voltage and therefore there will be an opposition.

→ Minority carriers will be falling down the barrier voltage and therefore there will be no opposition for the minority carriers.

SYMBOL



- The arrow mark on diode symbol denotes the direction of forward current.
- Equation for width of Depletion layer in OS Dia

$$W = \sqrt{\frac{2\epsilon}{q} \left(\frac{1}{N_A} + \frac{1}{N_D} \right) V_0} \text{ metres}$$

ϵ = Permittivity in $F/m = \epsilon_0 \epsilon_r$.

ϵ_0 = Absolute permittivity of free space.

$$\epsilon_0 = 8.854 \times 10^{-12} F/m$$

ϵ_r = Relative permittivity of medium.

$$\begin{cases} \epsilon_r \text{ for Si} = 11.7 \\ \epsilon_r \text{ for Ge} = 16 \end{cases}$$

- The width of Depletion layer in OC diode depends on :-
- ① Doping concⁿ of P-N region.
- ② Contact potential of diode.
- ③ Relative permittivity of medium.

Assume $N_A = N_D$

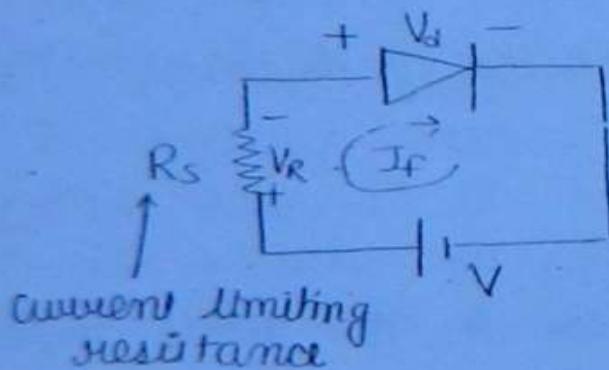
$$W = \sqrt{\frac{2\epsilon}{q} \left(\frac{2}{N_A \text{ or } N_D} \right)} \Rightarrow \boxed{W \propto \frac{1}{\sqrt{\text{Doping}}}}$$

Contact Potential in OC, P-N-junction.

$$V_0 = V_{bi} = V_T \log_e \frac{N_A N_D}{n_i^2} \text{ volts}$$

- Contact potential of diode depends on:-
 - Doping conc' of P & N region
 - Temperature.
- In OC p-N-junction, if doping conc' are increased can contact potential of diode slightly increases.

FORWARD BIASED



$$W \propto \frac{1}{\sqrt{F.B.}}$$

$$V = V_R + V_d$$

$$V = I_f R_s + I_f R_f$$

- When a P-N junction is FB, the width of depletion layer decreases and also the barrier height reduces.

NOTE :- In a FB P-N junction the effect of barrier is nullified i.e. the barrier voltage will not oppose the majority in crossing the junction.

→ Forward current is only due to majority carriers:

$$I_f = I_o [e^{\frac{V_d}{\eta V_T}} - 1] \text{ Amp}$$

$$\Rightarrow \boxed{I_f \approx I_o e^{\frac{V_d}{\eta V_T}}} \text{ Amp.}$$

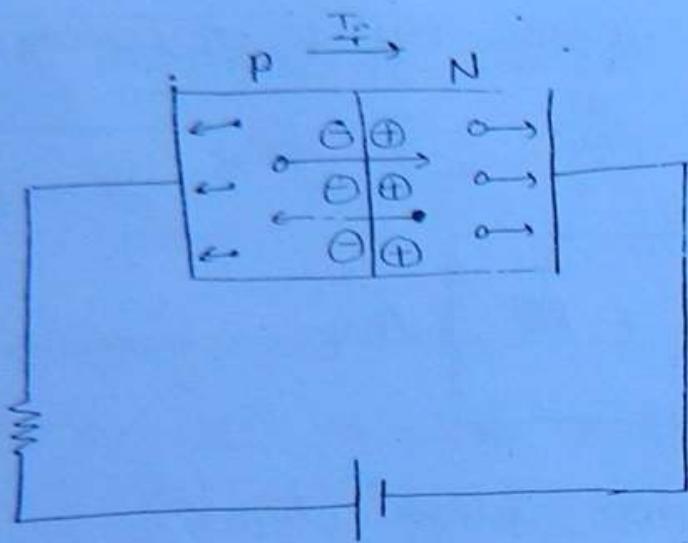
→ { V_T is thermal voltage (26 mV)
 V_d forward voltage across the diode
(below 0.5 V for Ge, 0.9 V for Si)
 η is called recombination factor or utility factor
 $\eta = 1$ for Ge or for larger current
or for Si or for smaller current }

→ In the given problem of Ge & Si is not specified then by default $\eta=1$.

I_o is reverse saturation current
or minority carrier current.

→ Forward current is only due to majority carriers but it is mathematically derive in terms of minority carrier current.

→ Forward current exponentially increases with forward voltage across the diode.



- Forward current flows from P to N.
- Forward current is large (mA)
- In forward biased diode the minority carriers will be moving away from the junction and they will not contribute any current.
- Forward current is a diffusion current.
- Forward current is only due to majority carriers and majority carriers are crossing the junction from higher to lower concn i.e. due to property called diffusion. Hence forward current is diffusion current.

Cut-in Voltage V_F

- Also called offset voltage or threshold voltage or knee voltage or break voltage.
- If it is defined as the minimum forward voltage above which the current flows in the diode.

For Ge Diode

$$V_F = 0.1 \text{ V to } 0.5 \text{ V (0.8 V)}$$

For Si Diode

$$\hookrightarrow V_F = 0.6 \text{ V to } 0.9 \text{ V (0.7 V)}$$

- Saturation voltage decreases with temperature.
- * { For 1°C $V_T \downarrow$ by 2.3 mV (latest) }
or
 2.5 mV (old).

Effect of temperature on Forward current.

- Forward current of diode is independent of temperature.
- Forward current is due to majority and minority carrier current is independent of temperature.

FORWARD Voltage Across the Diode, V_d .

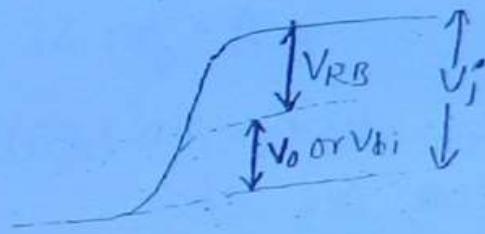
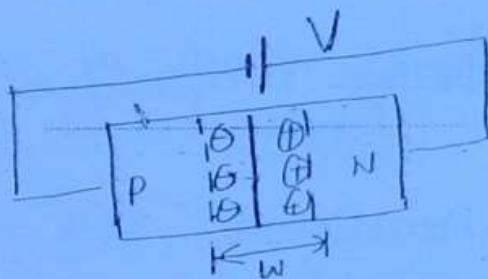
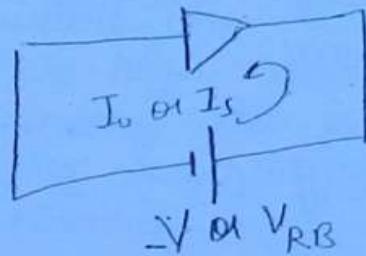
$$\Rightarrow V_d = \eta V_T \log_e \left(\frac{I_F}{I_c} \right)$$

- Between V_T & I_c , I_c is more sensitive to the temperature.
- Voltage drop (V_d) decreases with the temp.
- * { For 1°C $V_d \downarrow$ 2 mV (latest) }
or
 2.5 mV (old).
- A forward biased diode is subjected to a temperature variation of 10°C then the forward voltage of diode changes by 20 mV .

REVERSE BIAS

or
Blocking Bias
or
Back Bias.

→



Junction Voltage V_j = sum of V_{bi} & V_{RB}

$$V_j = V_{bi} + V_{RB}$$

Width of depletion layer $w \propto \sqrt{V_j}$

$$w \propto \sqrt{V_{bi} + V_{RB}}$$

if V_{bi} is neglected

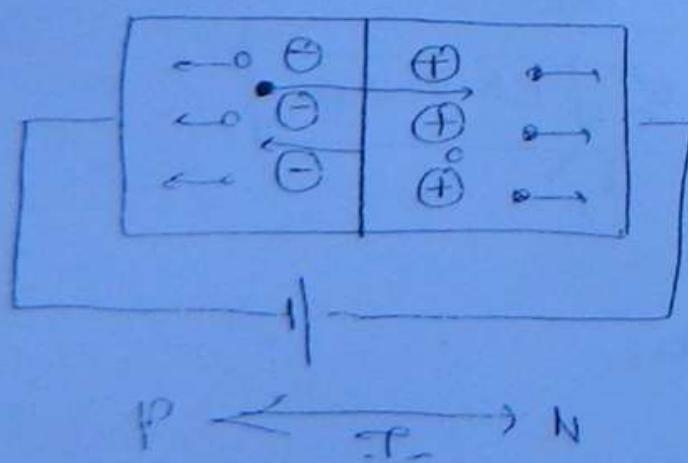
$$V_j \approx V_{RB}$$

$$\therefore w \propto \sqrt{RB \text{ voltage}}$$

^{when}
P-N junction is reverse biased the width of the depletion layer increases and also the barrier height increases.

- The reverse current I_o is called Thermally generated current or leakage current or reverse saturation current.
- $I_o = \mu A$ for Ge & I_o of Ge $>$ I_o of Si
 nA for Si
- Si diode is having better thermal stability than Ge diode.
- I_o flows from N to P.
- I_o is independent of applied voltage (the current is saturated with respect to applied voltage)
- For $1^\circ C$ I_o approx increases by 7%
- For $10^\circ C$ I_o will becomes doubles :-

$$I_o(T_2) = I_o(T_1) \left[2^{\frac{T_2 - T_1}{10}} \right]$$



In a RB PN junction, the majority carriers will be moving away from the junction and therefore they will not contribute any current.

- Reverse current is a drift current
- Reverse current is due to minority carriers and thus minority carriers are crossing the junction from low concn to high concn of the minority carriers will be crossing the junction due to electric field intensity and therefore a reverse current is a drift current.

Equation for width of Depletion layer in Reverse Biased Diode

In RB P-N Junction

$$W = \sqrt{\frac{2\epsilon}{q} \left(\frac{1}{N_A} + \frac{1}{N_D} \right) (V_D + V_{RB})}$$

$$W \propto \sqrt{V_{bi} + V_{RB}} \quad \text{or} \quad W \propto \sqrt{V_j}$$

- Majority carriers are blocked in crossing the junction and therefore it is called blocking bias

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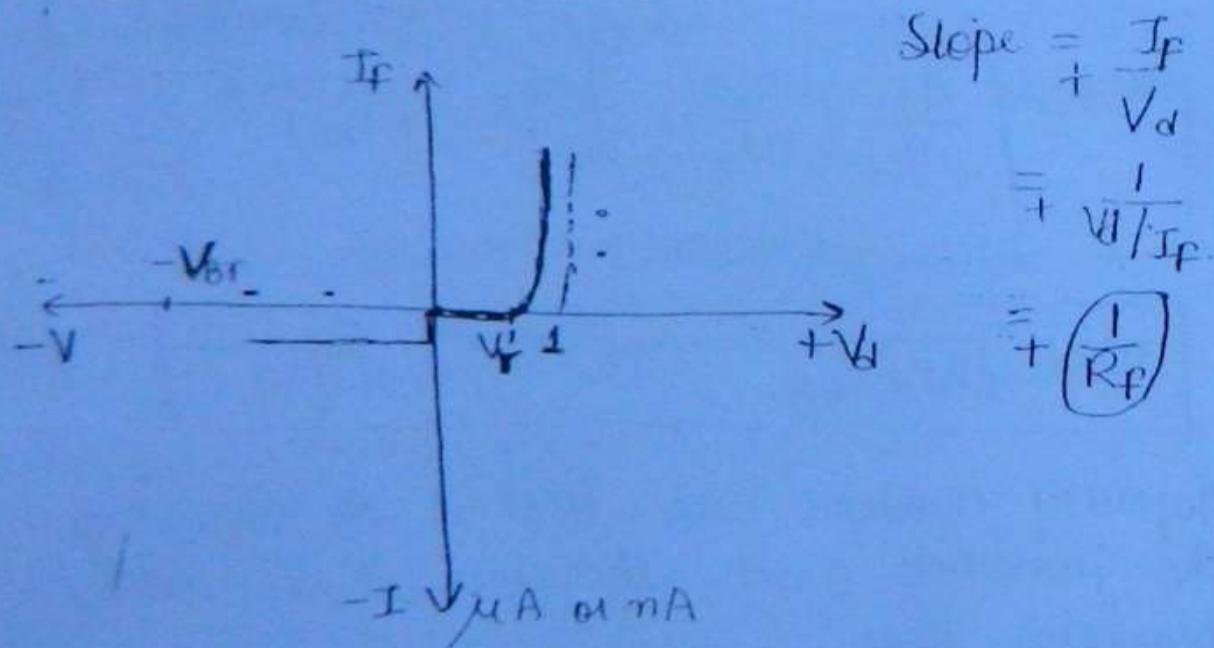
Equation for current I in a RB Diode :-

$$\Rightarrow I = I_o$$

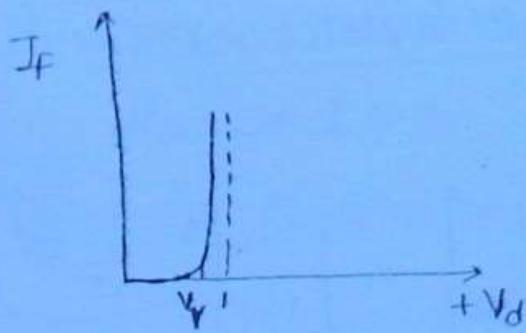
$$\Rightarrow I = -I_o \left[e^{-\frac{V}{nV_L}} - 1 \right]$$

V-I CHARACTERISTICS OF DIODE

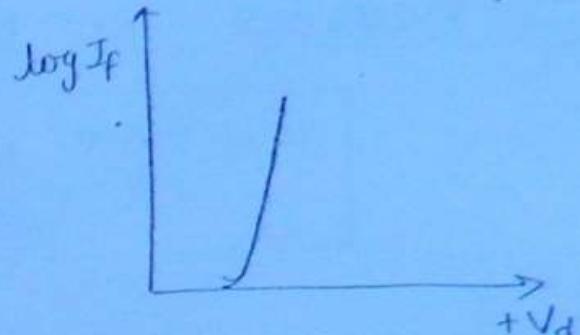
volt-Ampere characteristics of Diode.



→ When a normal diode is reverse biased the reverse voltage must be less than breakdown voltage of the diode otherwise the diode will be destroyed.



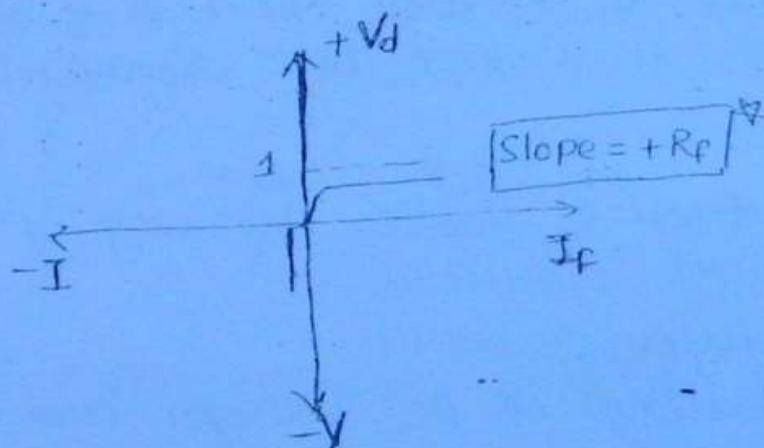
$\left\{ \begin{array}{l} I_F \text{ exponentially } \uparrow \\ \text{with } V_d \end{array} \right\}$



$\left\{ \begin{array}{l} \log I_F \text{ vs } V_d \text{ curve} \\ \text{represents a st. line} \end{array} \right\}$

→ For increasing curve slope is positive and vice versa

IV characteristics



Diode Resistance

Forward Resistance

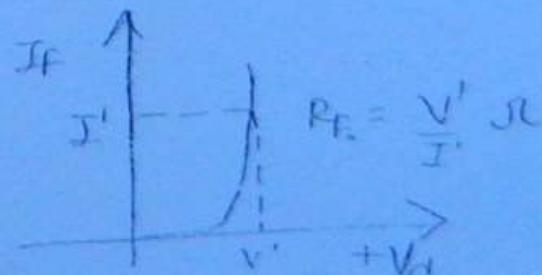
10 Ω to 100 Ω

DC Resistance

Static Resistance

R_F

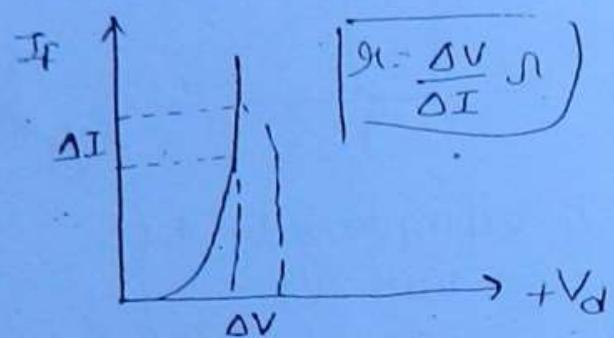
It is resistance of diode when '0' input signal is applied or resistance of diod under



$$R_F = \frac{V'}{I'}$$

→ AC Resistance or Dynamic Resistance

$$R_d = \frac{\Delta V}{\Delta I} R$$



→ R_d is the resistance of diode when signal is applied i.e. under A.C. Analysis

→ D.C. resistance is greater than A.C. resistance
(static resistance is greater than dynamic resistance)

→ Under DC analysis of diode, All signal voltages are short circuited.

→ Under AC analysis of diode

→ Biasing ~~V_d~~ voltages & DC voltages are AC.

→ The diode is replaced by its dynamic resistance.

REVERSE Resistance

$$R_R > 1 \text{ M}\Omega$$

Dynamic Resistance of Diode

$$\Rightarrow R_d = \frac{\eta V_T}{I_F}$$

At 300K, if $I_F = 26 \text{ mA}$

For Ge diode, $R_d = 1 \Omega$.

Si diode, $R_d = 2 \Omega$

when compared to germanium diode Si diode has larger dynamic resistance.

$$\Rightarrow R_d = \frac{\eta V_T}{I_F} = \frac{\eta kT}{q I_F}$$

Dynamic Conductance of diode (g) :-

$$\left[g = \frac{1}{R_d} \text{ or } S \text{ or } \text{A/V} \right]$$

$$1 \star \left[g = \frac{I_F}{\eta V_T} \right]$$

$$\left[g \propto I_F \right]$$

$$\Rightarrow \left[g = \frac{q I_F}{\eta k T} \right]$$

Breakdown Voltage [V_{BR} or Br] \Rightarrow

→ In any type of PN junction breakdown voltage.

★ ★ $\Rightarrow \boxed{V_{BR} \propto \frac{1}{Doping}}$

Equivalent Circuit of Diode \Rightarrow

1) When diode is FB \Rightarrow

$$\text{A} + \text{D} \text{--- K} = \frac{\text{R}_f}{\text{A}} \parallel \frac{V_r}{\text{K}} \quad V_r = \text{cutin voltage}$$

→ Supposing forward resistance of diode is zero or not given then

$$\text{A} + \frac{V_r}{\text{K}}$$

→ A FB Diode can be replaced by its cutin voltage

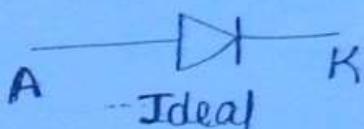
2) When diode is RB \Rightarrow

$$\text{A} - \text{D} \text{--- K} = \text{A} \parallel \frac{\text{R}_r}{\text{K}} + \text{very large resistance} (> 1 \text{ M}\Omega)$$

[IDEAL DIODE] \Rightarrow

Perfect Diode or Imaginary Diode :-

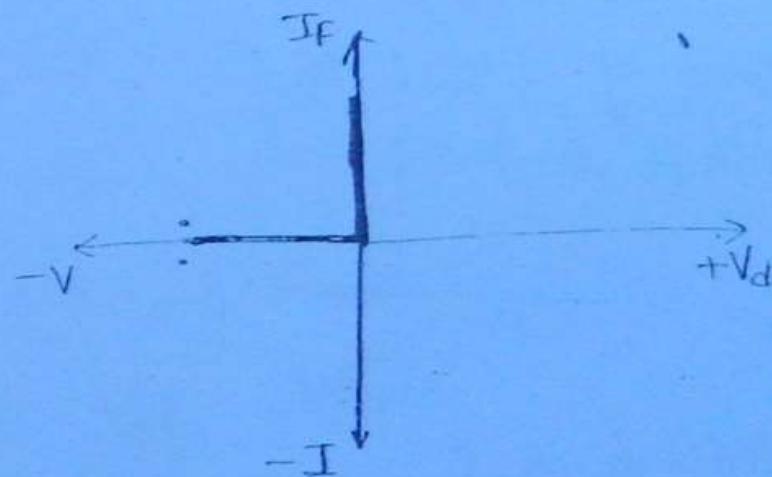
Symbol :-



Properties :-

$$\left\{ \begin{array}{l} R_f = 0 \\ R_r = \infty \\ V_r = 0 \end{array} \right\}$$

[VI characteristics]



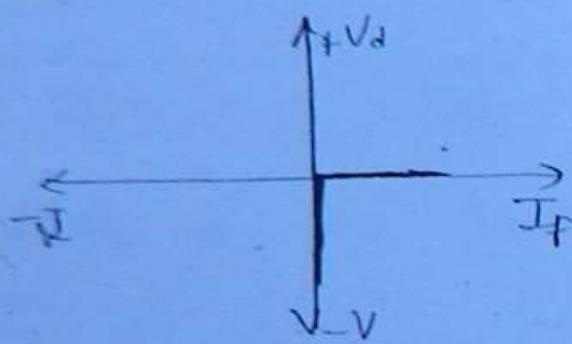
if Ideal diode is FB
It is SC
 $I \rightarrow \text{max.}$
 $V \rightarrow 0$

if I_D is RB
It is OC
 $I = 0$
 $V \rightarrow \text{max}$

→ When Ideal diode is FB, it is treated as SC
 $\therefore R_f = 0$

→ When ideal diode is RB it is treated as OC.
 $\therefore R_d = \infty$

IV characteristics

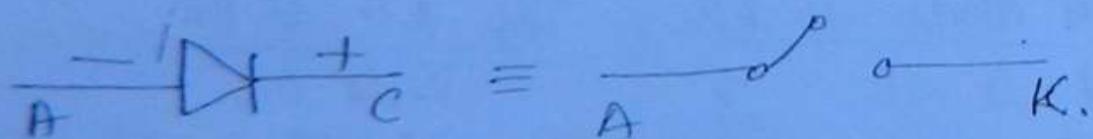


Equivalent circuit of Ideal diode

(i) when Ideal diode in FB :-



(ii) when ideal diode is RB :-



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B1b. Find the forward current of a Ge diode operating at room temperature with a forward voltage of 100 mV across it. The reverse saturation current = 20 μA

$$I_f = I_o e^{\frac{V_d}{\eta V_t}}$$

$$I_f = 20 \times 10^{-6} e^{\frac{100 \text{ mV}}{260}}$$

$$\boxed{I_f = 0.936 \text{ mA}}$$

B1b. A Si diode operating at room temp with forward voltage of 650 mV and having a leakage current 20 nA. find its dynamic resistance.

$$I_f = I_o e^{\frac{V_d}{\eta V_t}}$$

$$I_f = 20 \times 10^{-9} e^{\frac{650 \times 10^{-3}}{2 \times 26 \times 10^{-3}}}$$

$$I_f = 5.367 \text{ mA}$$

$$\Rightarrow R = \frac{\eta V_t}{I_f}$$

$$\Rightarrow R = \frac{2 \times 26}{5.367}$$

$$\Rightarrow \boxed{R = 9.688 \Omega}$$

Ques A diode has a leakage current of $10\mu\text{A}$ at certain temperature. Find its value when temp is increased by 25°C .

$$I_{02} = I_{01} \left[2^{\frac{T_2 - T_1}{10}} \right]$$

$$\text{Ques} \quad 10 \times 10^{-6} = \text{---}$$

$$= 10\mu\text{A} \left[2^{\frac{T_2 + 25 - T_1}{10}} \right]$$

$$\approx 10\mu\text{A} \left[2^{2.5} \right]$$

$$\Rightarrow \boxed{I_{02} = 56.56\mu\text{A}}$$

Ques A step graded pn diode having

$N_D = 500 N_A$. Acceptor impurities to extent of

2×10^8 is added at room temp. Find its contact potential. Assume $n_i^o = 2.5 \times 10^{13} \text{ atom/cm}^3$. Total no. of atoms = $4.421 \times 10^{24} \text{ cm}^{-3}$

$$V_o = V_T \log_e \frac{N_A N_D}{n_i^o}$$

$$N_A = 4.421 \times 10^{22} \times \frac{2}{10^8} = 8.842 \times 10^{14}$$

$$V_o = 26 \times 10^{-3} \log_e \frac{8.842 \times 10^{14} \times 500 \times 8.842 \times 10^{14}}{(2.5 \times 10^{13})^2}$$

$$V_o = 26 \times 10^{-3} \log_e \frac{3.90 \times 10^{32}}{6.25 \times 10^{26}}$$

$$V_o = 26 \times 10^{-3} \log_e 624000 \rightarrow \boxed{0.347 \text{ V}}$$

Prob A step graded Si diode having $N_D = 500 N_A$
the acceptor impurities $\& : 10^8$ are added at
room temperature find its contact potential

Assume $n_i = 1.5 \times 10^{10}$

Total no. of atoms = 5×10^{22} atom/cm³.

$$\boxed{V_0 = 739 \text{ mV}} \quad \cancel{\text{dc}}$$

Ques A Si Diode indicates forward current of 8mA and 10mA when diode voltages are 0.6V and 0.7V resp. Estimate the operating temperature of the diode junction.

Soln $I_F \approx I_0 e^{\frac{V_d}{nV_T}}$

but $V_T = T/11600$

$$\Rightarrow I_F = I_0 e^{\frac{11600 V_d}{nT}}$$

$$\frac{8mA}{10mA} = \frac{e^{\frac{11600(0.6)}{2T}}}{e^{\frac{11600(0.7)}{2T}}}$$

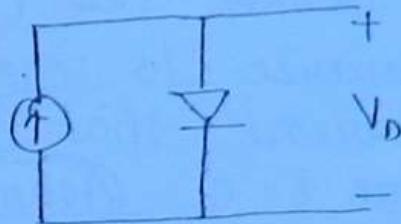
$$\frac{1}{5} \approx e^{\frac{11600(0.6)}{2T} - \frac{11600(0.7)}{2T}}$$

$$\frac{1}{5} \approx e^{-\frac{580}{T}}$$

$$T = -\frac{580}{\log(\frac{1}{5})}$$

$$\Rightarrow \boxed{T = +360K}$$

Ques In the circuit given below, Si diode is carrying a constt. current of 1mA.



When temperature of diode is 20°C , V_D is found to be forward voltage across diode is 700mV if temp increases to 40°C then V_D becomes equal to _____

Soln Temp. \uparrow from 20°C to 40°C

$$\Delta T = 20^\circ\text{C}$$

$$1^\circ\text{C}, V_D \downarrow 2\text{mV}$$

$$20^\circ\text{C} \quad \Delta V_D \downarrow \frac{2\text{mV}}{^\circ\text{C}} \times 20\text{mV}$$

$$\Delta V_D = 40\text{mV}$$

$$\begin{aligned} V_D &= 700\text{mV} - \Delta V_D \\ &= 700 - 40 = 660\text{mV.} \end{aligned}$$

Ques A FB SP Diode when carrying negligible current as a voltage drop of 0.64V when current is 1A it dissipates 1 watt. ON resistance of diode is 1R

Soln $I = 1\text{A}$

$$P = 1\text{W}$$

$$P = I^2 R$$

$$R_{\text{ON}} = 1\text{R} \text{ Ans.}$$

A PN junction in series with a 100Ω resistor is FB so that a current of 100mA flows if the voltage across this combination is 10V .
 i) Instantaneously reverse to 10V at time $t=0$. The reverse current that flows through diode at time $t=0$ is $\boxed{100\text{mA}}$.

Ans → At time $t=0$, the diode is still under forward biased and the current in the circuit is $\boxed{100\text{mA}}$.

Ques At 300K , for a diode current of 1mA , a certain Ge diode requires a FB of 0.1435V across it whereas Si diode requires FB of 0.718V across it. Under condn given above find ratio of $I_o(\text{Ge})/I_o(\text{Si})$.

$$\frac{I_o(\text{Ge})}{I_o(\text{Si})} = ?$$

$$I_F = I_o e^{\frac{q}{kT} V_T}$$

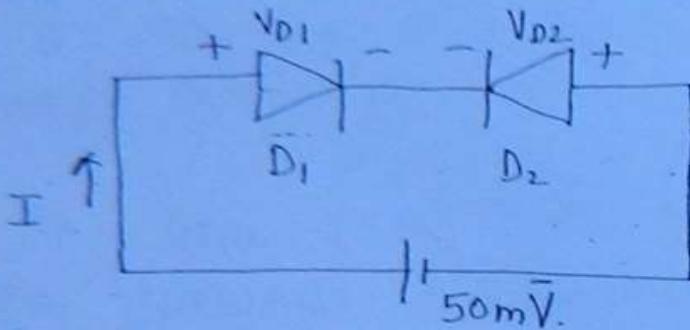
$$\text{for Ge} \quad 1 = I_o e^{\frac{0.1435}{26 \times 10^{-3}}}$$

$$\text{for Si} \quad 1 = I_o(\text{Si}) e^{\frac{-0.718}{26 \times 10^{-3} \times 2}}$$

$$\frac{I_o(\text{Ge})}{I_o(\text{Si})} = 3977$$

only for IES

Prob. The circuit given below consist of two identical diodes each value having a utility factor of unity. Assume thermal voltage 25mV



Find V_{D1} & V_{D2}.

Soln: In the given circuit D₁ is FB and non-conductive and D₂ is RB & non conducting.

→ The forward current of D₁ will be flowing as reverse current in D₂.

For D₁,

$$I = I_F = I_0 \left[e^{\frac{V_{D1}}{\eta V_T}} - 1 \right] \rightarrow ①$$

For D₂,

$$I = I_R = -I_0 \left[e^{\frac{-V_{D2}}{\eta V_T}} - 1 \right] \rightarrow ②$$

equating ① & ②

$$I_0 \left[e^{\frac{V_{D1}}{\eta V_T}} - 1 \right] = -I_0 \left[e^{\frac{-V_{D2}}{\eta V_T}} - 1 \right]$$

$$e^{\frac{V_{D1}}{\eta V_T}} - 1 = -e^{\frac{-V_{D2}}{\eta V_T}} + 1$$

$$e^{\frac{V_{D1}}{\eta V_T}} + e^{\frac{-V_{D2}}{\eta V_T}} = 2 \quad \left. \begin{array}{l} \Rightarrow e^{\frac{V_{D1}}{\eta V_T}} - e^{-\frac{(V_{D1}-V_{D2})}{\eta V_T}} = 2 \\ \Rightarrow e^{\frac{V_{D1}}{\eta V_T}} [1 + e^{-2}] = 2 \end{array} \right\}$$

$$\left. \begin{array}{l} \because V_{D1} + V_{D2} = 50 \Rightarrow V_{D2} = 50 - V_{D1} \\ \Rightarrow e^{\frac{V_{D1}}{\eta V_T}} [1 + e^{-2}] = 2 \end{array} \right\}$$

$$\Rightarrow V_{D1} = \eta V_T \log_e \frac{2}{1+e^{-2}} \Rightarrow \boxed{V_{D1} = 14.15 \text{mV}}$$

- In above circuit none of diode will be conducting but one diode is FB and non-conducting & other diode is RB and non-conducting
- This ckt. is used in power supply as overload protection ckt. or short ckt. protection ckt.

(1) (Conventional page no 18)

SOL

$$e^{\frac{V_{D1}}{\eta V_T}} + e^{-\frac{V_{D2}}{\eta V_T}} = 2$$

$$e^{\frac{V_{D1}}{\eta V_T}} + e^{-\frac{(5-V_{D1})}{\eta V_T}} = 2$$

$$e^{\frac{V_{D1}}{\eta V_T}} + e^{-\frac{(5-V_{D1})}{\eta V_T}} = 2$$

$$e^{\frac{V_{D1}}{\eta V_T}} + e^{-50} \cdot e^{\frac{V_{D1}}{\eta V_T}} = 2$$

$$e^{\frac{V_{D1}}{\eta V_T}} (1 + e^{-50}) = 2$$

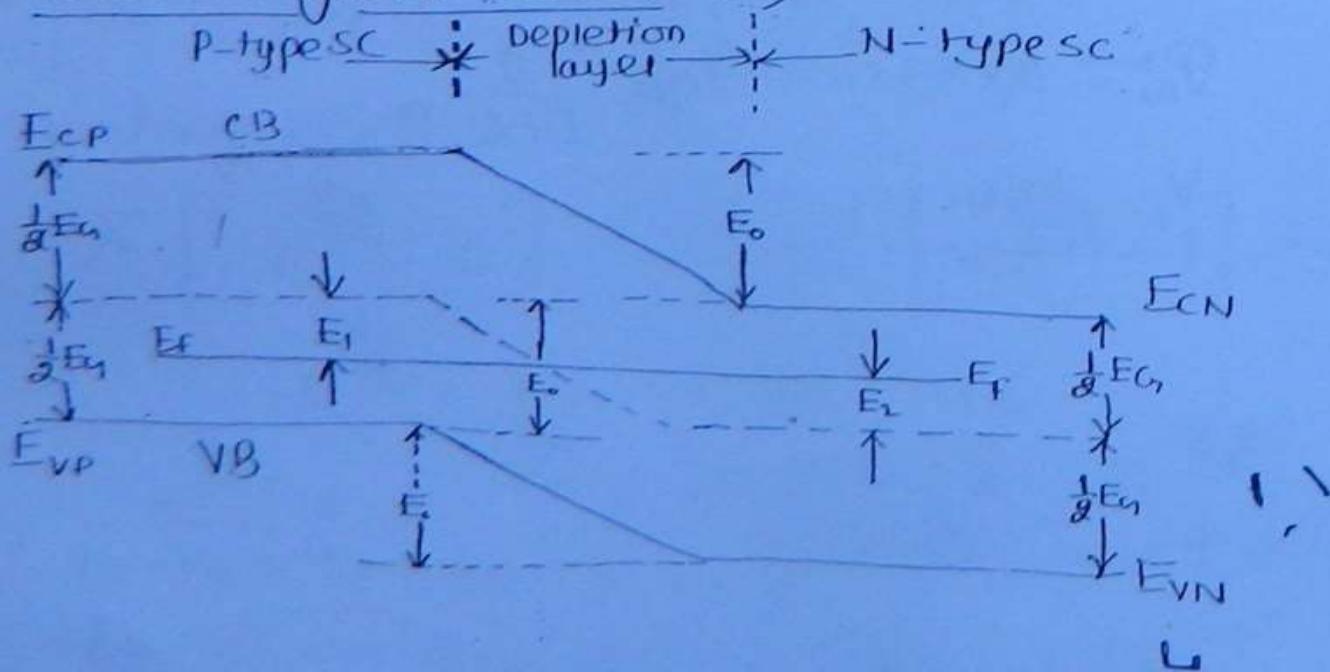
$$V_{D1} = \eta V_T \log_e \frac{2}{1 + e^{-50}}$$

$$V_{D1} = 2 \times 25 \times 10^{-3} \log_e \frac{2}{1 + e^{-50}}$$

$$V_{D1} = 34.325$$

Draw the energy band diagram of OC p-n junction diode and derive an equation for contact potential of diode.

- In p-type SC at room temperature, Fermi level will be existing just above the acceptor energy level.
- In N-type SC at room temperature the Fermi level will be existing just below the donor energy level.
- When P-N junction is created the energy band diagram of p and N-region will be adjusted so that the Fermi level will maintain a straight line force.
- The energy band diagram of OC PN junction diode is given below. \Rightarrow



In the above diagram E_o is the potential energy of the e^- at the junction expressed in eV.

In the diagram

$$\Rightarrow E_o = E_{CP} - E_{CN} = E_{VP} - E_{VN} = E_1 + E_2 \rightarrow ①$$

$$\Rightarrow E_F - E_{VP} = \frac{1}{2} E_G - E_1 \rightarrow ②$$

$$\Rightarrow E_{CN} - E_F = \frac{1}{2} E_G - E_2 \rightarrow ③$$

→ Adding eq ② & ③

$$\Rightarrow (E_F - E_{VP}) + (E_{CN} - E_F) = E_G - (E_1 + E_2)$$

from eq ① $E_1 + E_2 = E_o$

$$\Rightarrow (E_F - E_{VP}) + (E_{CN} - E_F) = E_G - E_o$$

$$\Rightarrow E_o = E_G - (E_F - E_{VP}) - (E_{CN} - E_F) \quad ④$$

From p-type SC

$$\Rightarrow E_F - E_{VP} = KT \log_e \frac{N_V}{N_A} \dots A$$

From N-type SC

$$\Rightarrow E_{CN} - E_F = KT \log_e \frac{N_C}{N_D} \dots B$$

From the derivation of n_i :

$$n_i^2 = N_c N_v e^{-E_a/KT}$$

$$\Rightarrow \left[E_a = KT \log_e \frac{N_c N_v}{n_i^2} \right] \dots \textcircled{C}$$

\Rightarrow Substituting \textcircled{A} , \textcircled{B} , & \textcircled{C} in eq (1)

$$E_0 = KT \log_e \frac{N_c N_v}{n_i^2} - KT \log_e \frac{N_v}{N_A} - KT \log_e \frac{N_c}{N_D}$$

$$E_0 = KT \log_e \left[\frac{N_c N_v}{n_i^2} \times \frac{N_A}{N_v} \times \frac{N_D}{N_c} \right]$$

* $\Rightarrow \boxed{E_0 = KT \log_e \frac{N_A N_D}{n_i^2}} \text{ eV.}$

It is the equation for the potential energy of e^- at the junction.

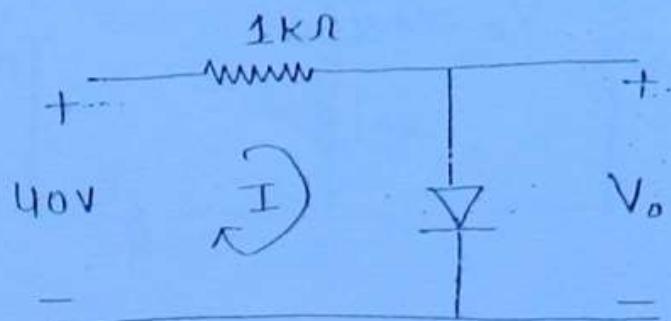
The contact potential of the diode is denoted by V_o & it is numerically equal to potential energy of e^- expressed in V.

$\Rightarrow \boxed{V_o = V_r \log_e \frac{N_A N_D}{n_i^2}}$ Volt.

Simple Diode Circuits :-

① Ideal Diodes :-

Find I and V_o

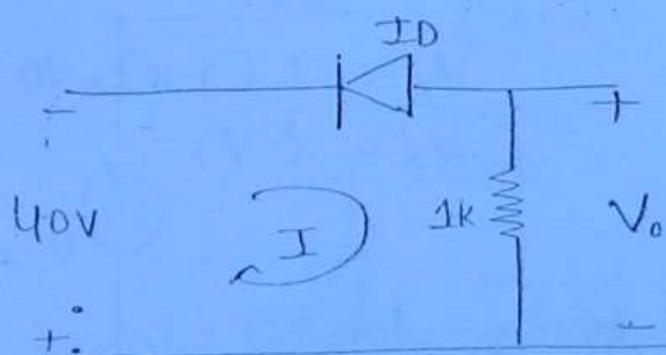


PD & FB & SC

$$V_o = 0$$

$$I = \frac{40}{1k} = 40\text{mA}$$

Find I & V_o



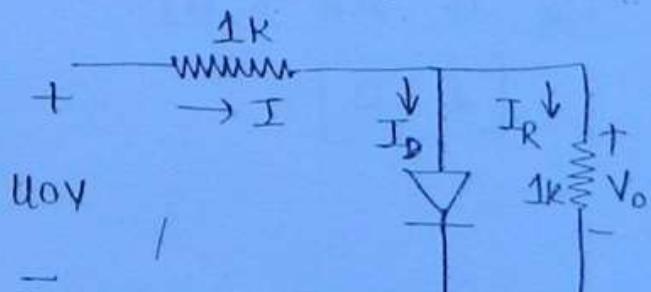
ID & FB & SC

$$V_o = -40\text{V}$$

$$I = \frac{V_o}{1k} = \frac{-40}{1k}$$

$$I = -40\text{mA}$$

Find V_o , I , I_R & I_D

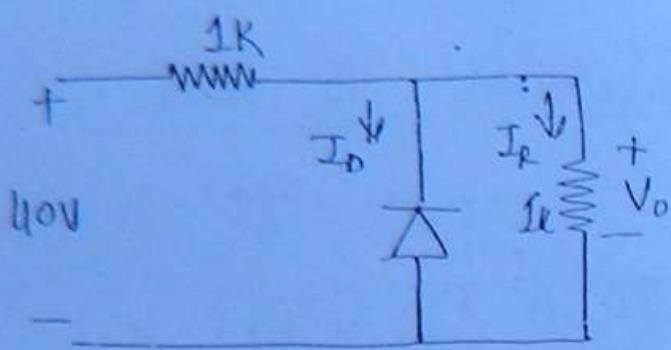


ID & FB & SC.

$$V_o = 0$$

$$I_R = 0$$

$$I = I_D = \frac{40}{1k} = 40\text{mA}$$



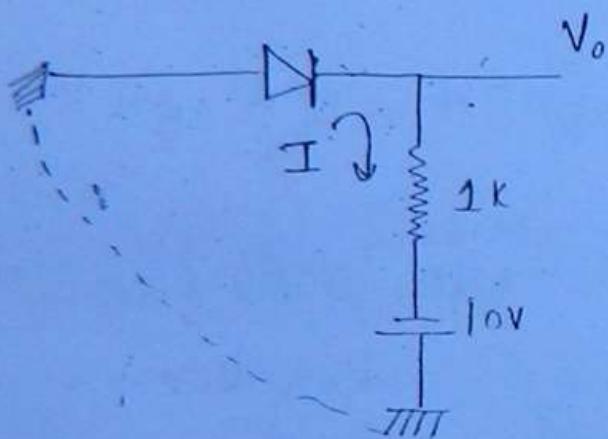
ID & RB & OC.

$$I_D = 0$$

$$I_R = I = \frac{40V}{1k} = 20mA$$

$$V_o = 20V$$

Find I & V_o



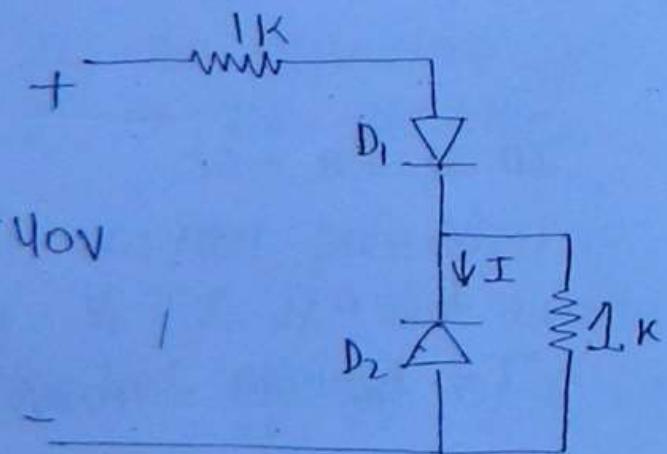
ID & FB & SC

$$I = \frac{10V}{1k} = 10mA$$

$$V_o = I(1k) - 10$$

$$\boxed{V_o = 0V}$$

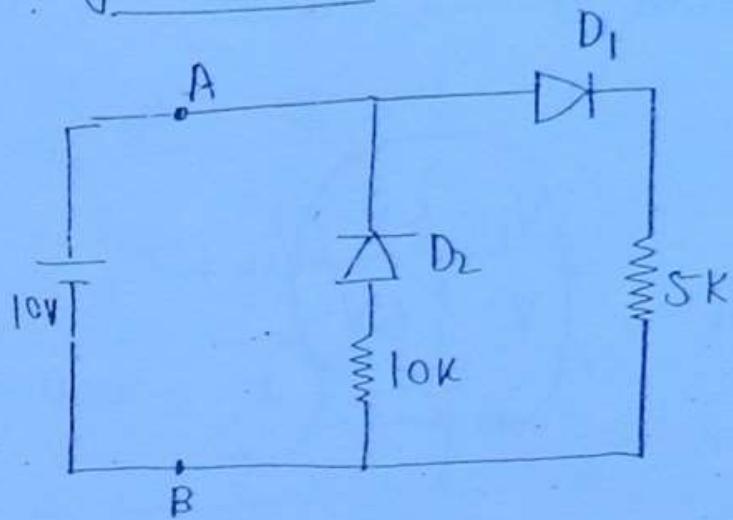
Assuming D₁ & D₂ are ideal diodes find I.



D₂ & RB & OC

$$\boxed{I = 0}$$

Find Z_{AB}



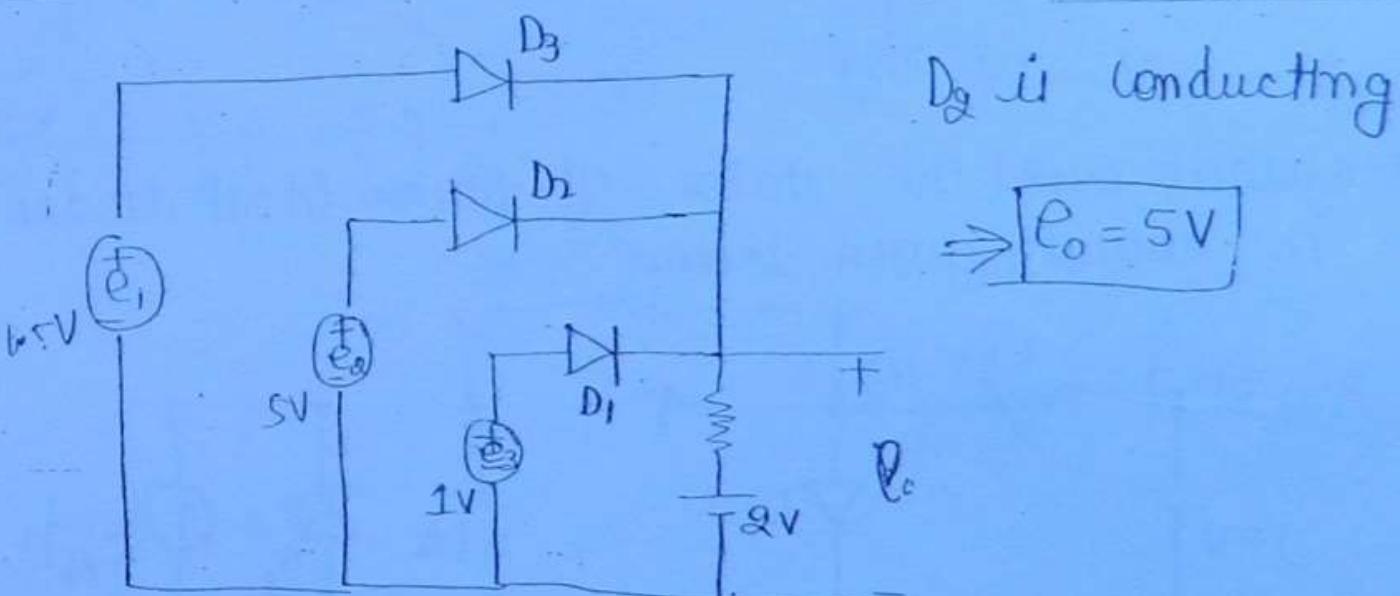
A is +ve w.r.t. B.

D₁ is FB & SC

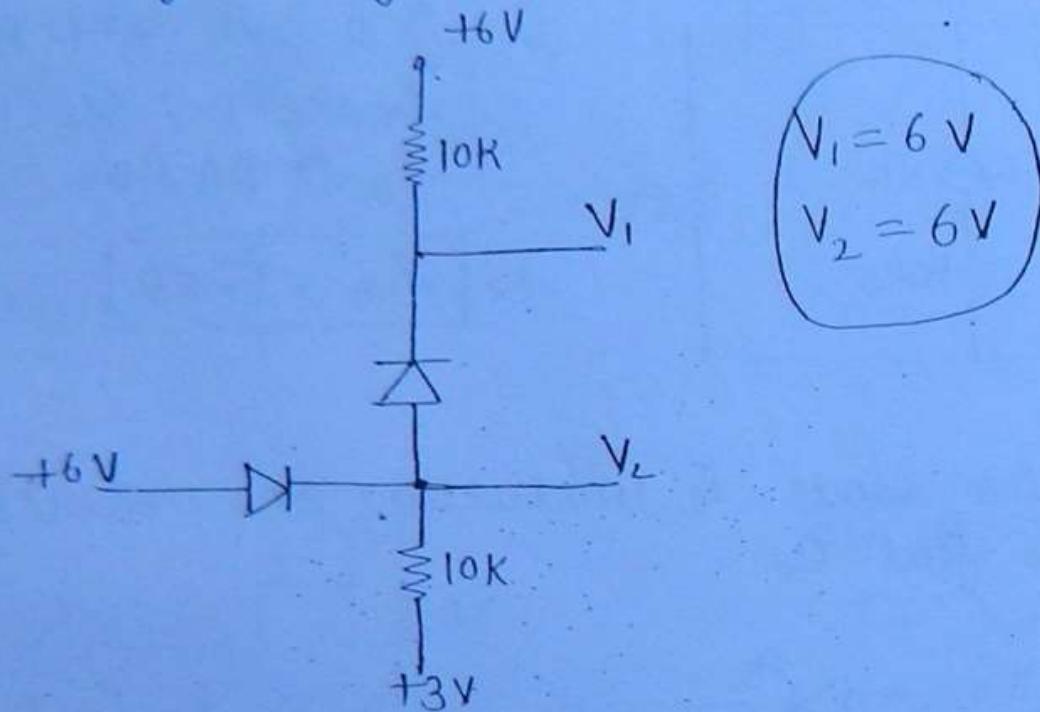
D₂ is RB & OC

$$\Rightarrow [Z_{AB} = 5 \text{ k}\Omega]$$

Ques: find which diode is conducting in circuit
and also find e_o .

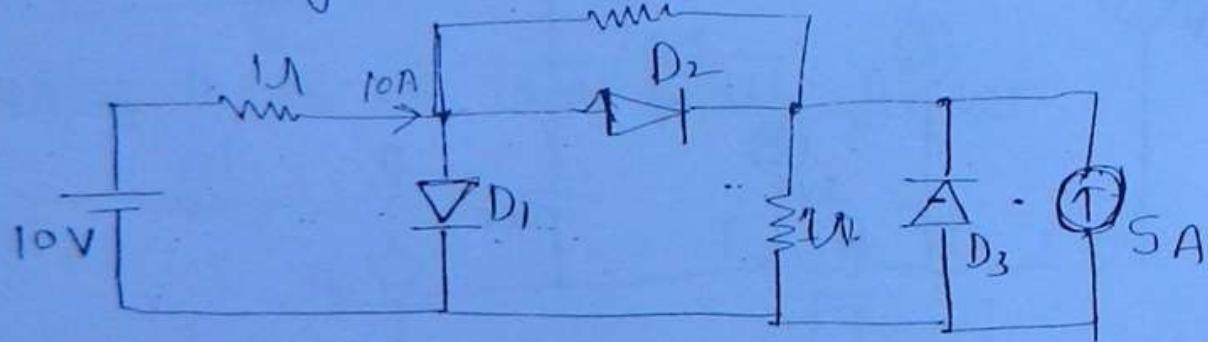


Ques The voltages at V_1 & V_2 for the circuit arrangement given below is



$$V_1 = 6 \text{ V}$$
$$V_2 = 6 \text{ V}$$

Ques What are the states of three ideal diodes in circuit given below. 1A



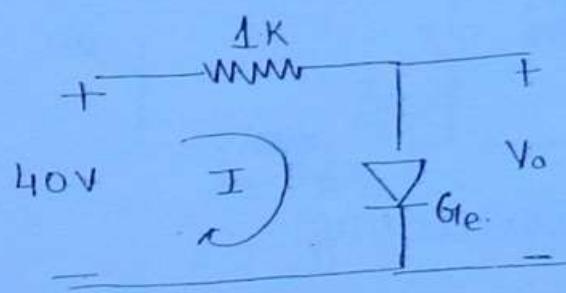
D_1 ON
FB

D_2 OFF
RB

D_3 OFF
RB. As.

(ii) Practical Diode Circuits \rightarrow

Find I & V_o



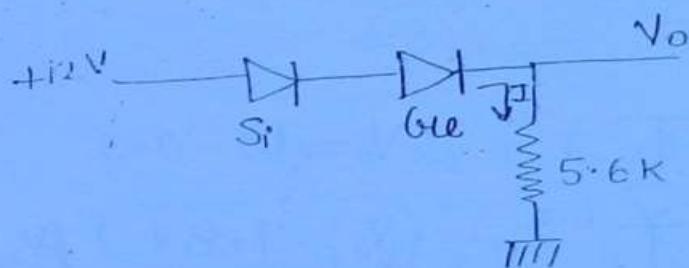
Ge D is FB & replaced by

$$V_o = V_{T_{Ge}} \\ = 0.8 \text{ V}$$

$$I = \frac{40 - V_{T_{Ge}}}{1k}$$

$$I = 39.8 \text{ mA}$$

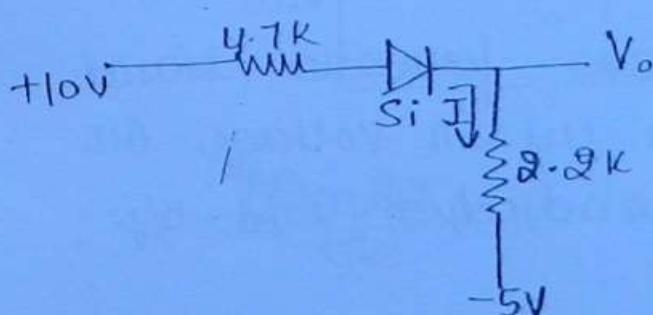
Find I & V_o



$$V_o = 12 - V_{T_{Si}} - V_{T_{Ge}} \\ = 12 - 0.7 - 0.8 \\ = 11.1 \text{ V}$$

$$I = \frac{V_o}{5.6k} = 1.98 \text{ mA}$$

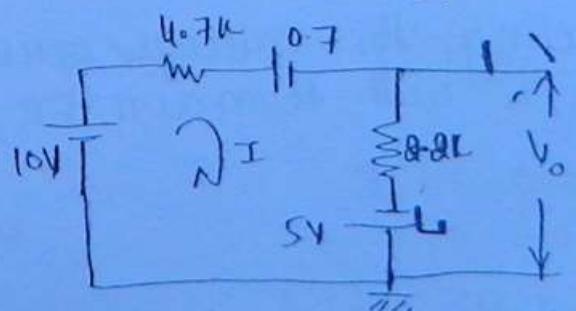
Find I & V_o



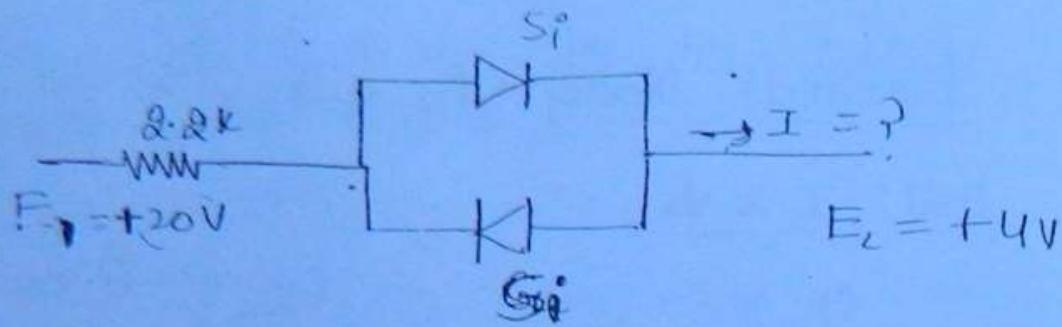
$$I = \frac{5 + 10 - 0.7}{6.9 \cancel{2.2}}$$

$$I = 2.07 \text{ mA}$$

$$V_o = I(2.2k) - 5 \\ = 4.55 - 5 \\ = -0.45 \text{ V}$$



Doubt



Ans

$$E_1 > E_2$$

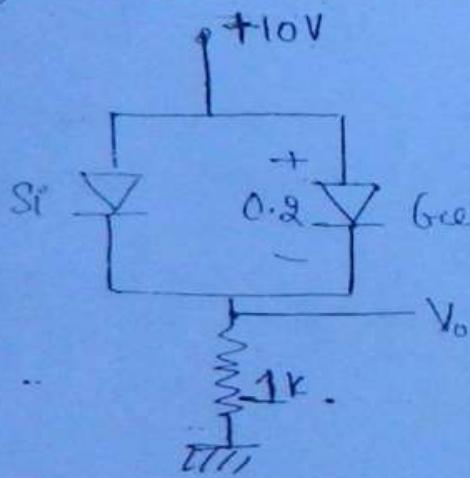
UD is FB & conducting

$$I = \frac{20 - 4 - 0.7}{2.2k} = (6.95 \text{ mA}) \cancel{\text{A}}$$

Doubt find V_o

$$\left\{ \begin{array}{l} V_{DSI} > V_{Dout} \\ 0.7 > 0.2 \end{array} \right\}$$

so Gee D conducting I^T



$$V_o = 10 - 0.2$$

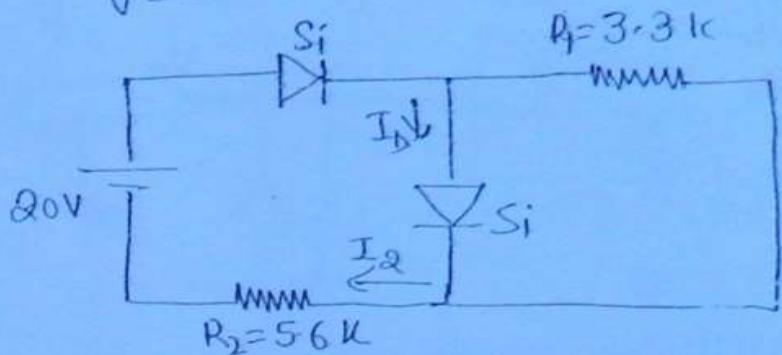
$$(V_o = 9.8V) \cancel{\text{A}}$$

→ Both Gee & Si Diode are forward biased
but because of smaller wr in Voltage on
diode will enter into conduction and o/p
Voltage is $(9.8V) \cancel{\text{A}}$.

→ When Gee diode is conducting, the voltage across
Si diode is 0.2V therefore it will remain FB &
non-conducting.

But

find I_D .



$$I_D = \frac{20 - 0.7 - 0.7}{5.6}$$

$$I_D = \frac{20 - 1.4}{5.6}$$

$$I_D = \frac{18.6}{5.6}$$

$$\boxed{I_D = 3.321 \text{ mA}}$$

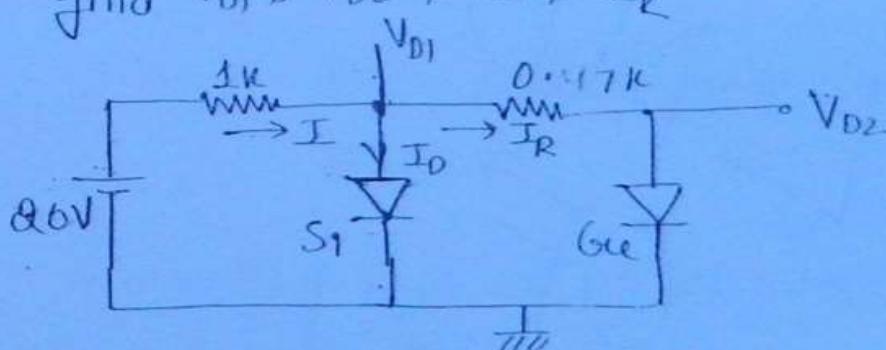
$$V_{P1} = V_{rS1} = 0.7 \text{ V.}$$

$$I_I = \frac{0.7 \text{ V}}{3.3 \text{ k}} = 0.212 \text{ mA}$$

$$I_D = I_D + I_I \Rightarrow \boxed{I_D = 3.109 \text{ mA}}$$

But

find V_{D1} , V_{D2} , I & I_R



~~$V_{D1} = 0.7 \text{ V}$~~

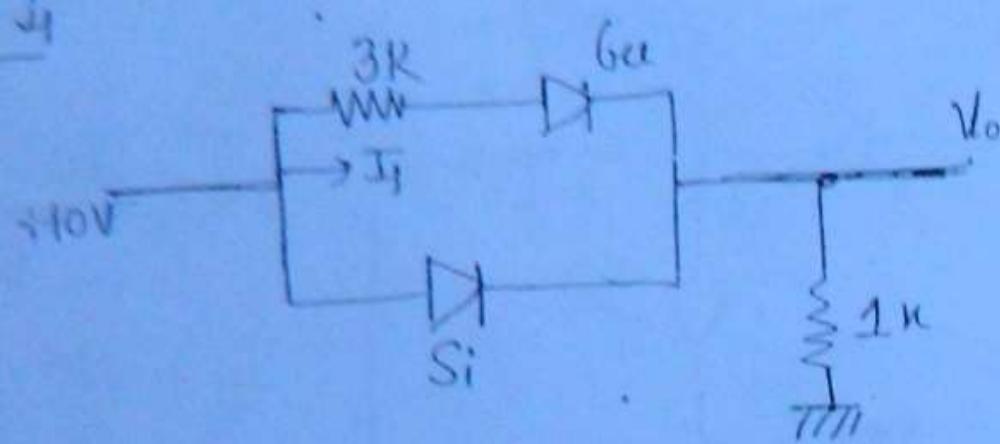
$$V_{D1} = V_{rS1} = 0.7 \text{ V.}$$

$$V_{D2} = V_{rSi} = 0.8 \text{ V.}$$

$$I = \frac{20 - 0.7}{10 \text{ k}} = \frac{19.3}{10 \text{ k}} = 19.3 \text{ mA}$$

$$I_R = \frac{0.7 - 0.2}{0.47} = \frac{0.5}{0.47} = 1.06 \text{ mA}$$

$$I_D = 19.3 - 1.06 = 18.24 \text{ mA}$$



Both Ga & Si diodes will be conducting

$$\begin{aligned} V_0 &= 10 - V_{fSi} \\ &= 10 - 0.7 \\ &= 9.3 \text{ V} \end{aligned}$$

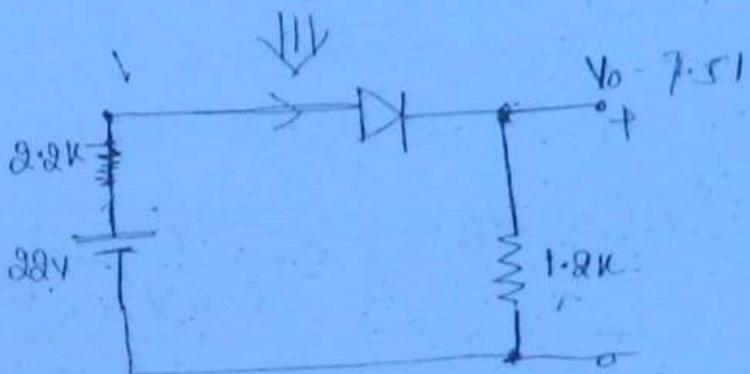
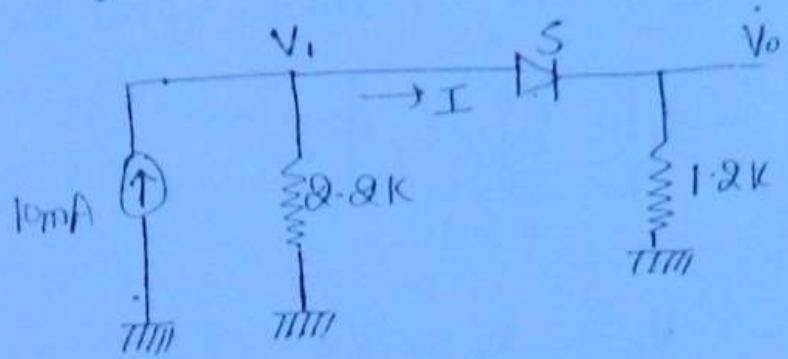
$$I_f = \frac{0.5 \text{ V}}{3 \text{ k}} = 0.1667 \text{ mA}$$

X

X

END
OF
DPY

Find I , V_1 , and V_o .



$$I = \frac{2.2 - 0.7}{2.2 + 1.2} = 0.626 \text{ mA}$$

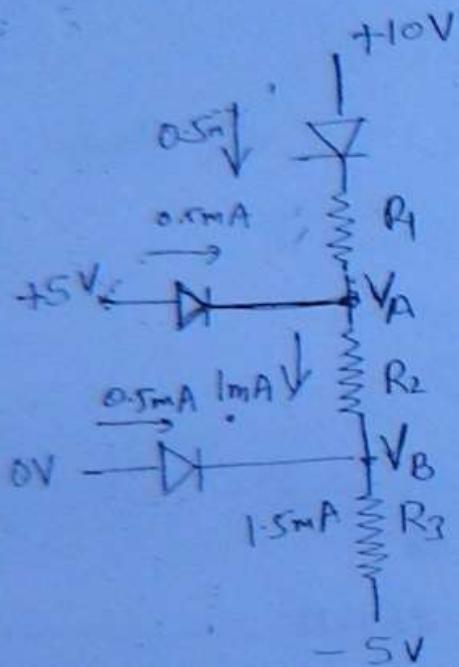
$$\begin{aligned} V_1 &= 2.2 - I(R) \\ &= 2.2 - 6.26 \text{ mA} (2.2 \text{ k}\Omega) \\ &= 8.21 \text{ V} \end{aligned}$$

$$V_o = V_1 - V_{\text{out}} = 8.21 - 0.7 = 7.51 \text{ V.}$$

or

$$\begin{aligned} V_o &= IR \\ &= 6.26 \text{ mA} (1.2 \text{ k}\Omega) \\ &= 7.51 \text{ V.} \end{aligned}$$

Ques The cutin voltage for each diode is 0.6 V and each diode current is 0.5 mA . Find the values of R_1 , R_2 & R_3 .



$$\begin{aligned}V_A &= 5 - V_F \\&= 5 - 0.6 \\&= 4.4\text{ V}\end{aligned}$$

$$\begin{aligned}V_B &= 0 - V_F \\&= -0.6\text{ V}\end{aligned}$$

$$R_1 = \frac{10 - V_F - V_A}{0.5}$$

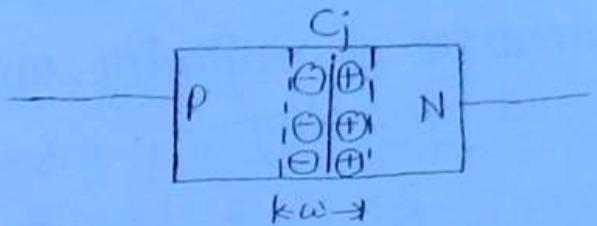
$$R_1 = \frac{10 - 0.6 - 4.4}{0.5}$$

$$[R_1 = 10\text{ k}\Omega]$$

$$R_2 = \frac{V_A - V_B}{1\text{ mA}} = \frac{4.4 - (-0.6)}{1\text{ mA}} = 5\text{ k}\Omega$$

$$R_3 = \frac{V_B + 5}{1.5} = -\frac{0.6 + 5}{1.5} = \frac{4.4}{1.5} = \underline{\underline{2.93\text{ k}\Omega}}$$

Junction Capacitance (C_j)



$$C_j = \frac{\epsilon_0 \epsilon_r A}{\omega}$$

- let $\epsilon_0 \epsilon_r = \epsilon$

$$\Rightarrow C_j = \frac{\epsilon A}{\omega}$$

The depletion layer in a p-n junction diode will be working as a parallel plate capacitor.

$$\Rightarrow C_j \propto A$$

$$\Rightarrow C_j \propto \frac{1}{\omega}$$

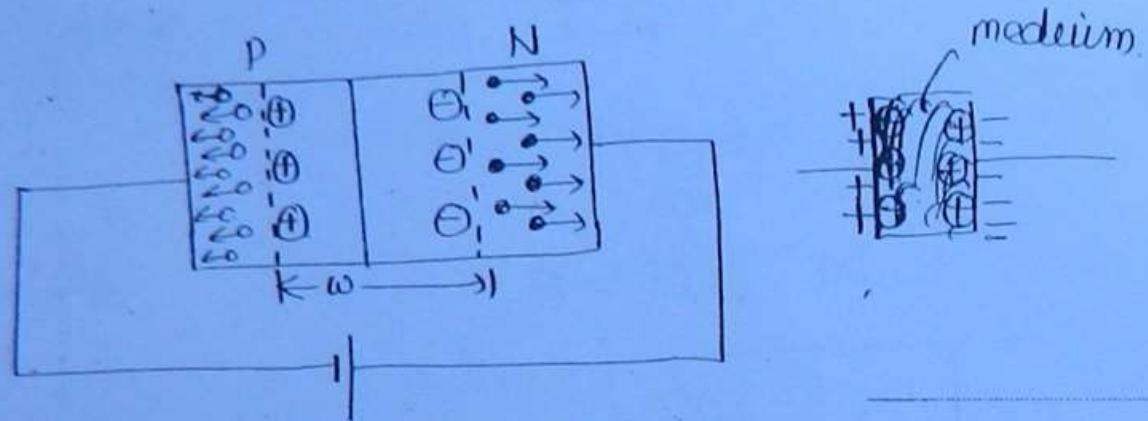
$$C_j \rightarrow \text{PF i.e. } 10^{-12} \text{ F}$$

⇒ When diode is unbiased or OC, both C_T and C_D will be appearing in the diode. and then biasing is provided one of the capacitance will be dominating.

⇒ $C_T \rightarrow$ Transition capacitance also called depletion layer capacitance or space charge capacitance

→ C_T is the junction capacitance dominated in a reverse biased diode.

→ C_T is due to the storage of majority carriers across the reverse biased junction.



$$C_T = C_j = \frac{eA}{w}$$

$$\begin{aligned} C_T &\propto A \\ C_T &\propto \frac{1}{w} \end{aligned}$$

$$\Rightarrow C_T \propto \sqrt{\text{Doping}} \quad \text{since } w \propto \frac{1}{\sqrt{\text{Doping}}}.$$

$$\Rightarrow C_T \propto \frac{1}{\sqrt{V_j}} \quad \text{since } w \propto \sqrt{V_j}$$

$$C_T \propto \frac{1}{\sqrt{V_{bi} + V_{RB}}} \quad \text{since } w \propto \sqrt{V_{bi} + V_{RB}}$$

Neglecting V_{bi}

$$\Rightarrow C_T \propto \frac{1}{\sqrt{RB \text{ voltage}}}$$

Typical Values

$C_T = 3 \text{ pF}$ for BJT \rightarrow Better performance.
 5 pf for Diode

- For better performance of diode or BJT, C_T value must be as small as possible.
- The property of C_T is used in designing of the varactor diode.
- In a reverse biased diode the transition capacitance C_T

$$C_T \propto V^{-\frac{1}{2}}$$

$$C_T \propto V^{-n}$$

Applied reverse voltage and n is a constant

i. given by

$$n = \frac{1}{2} \text{ for step graded diode.}$$

- Imp. \star : $n = \frac{1}{3}$ for linear graded diode.

$$n = \frac{1}{2.5} \text{ for diffused p-n junction diode}$$

n = grading coefficient and its value depends on concentration gradient.

→ C_T will appear in device both during the low frequency and high frequency operation.

C_D (Diffusion Capacitance)

- Also called storage capacitance.
- C_D is the junction capacitance dominating in forward biased diode.
- C_D is due to storage of minority carriers across forward biased diode,
- It is storing the minority carriers across the junction and therefore called storage capacitance.

$$C_D = C_J = \frac{\epsilon A}{\omega}$$

$$\Rightarrow \begin{cases} C_D \propto A \\ C_D \propto \frac{1}{w} \end{cases}$$

$$\rightarrow \begin{cases} C_D \propto \sqrt{\text{Doping}} \\ C_D \propto \sqrt{I_{FB}} \end{cases} \quad \begin{array}{l} \text{since } w \propto \frac{1}{\sqrt{\text{Doping}}} \\ \text{since } w \propto \frac{1}{\sqrt{I_{FB/\text{biased}}}} \end{array}$$

- High frequency operation of a diode or BJT is limited by presence of C_D .

$$\rightarrow C_D = \tau \cdot g \quad g = \frac{1}{R} \quad \left. \right\}$$

4

$$\left. \begin{array}{l} C_D = \frac{\tau}{R} \\ \Rightarrow C_D = \frac{\tau I_F}{\eta V_F} \end{array} \right\} \quad \left. \begin{array}{l} C_D \propto I_F \end{array} \right\}$$

Diffusion capacitance linearly increases with forward current.

$$\text{but } I_f \approx I_o e^{\frac{V_f}{\eta V_T}}$$

$$\Rightarrow C_D = \frac{\tau I_o e^{\frac{V_f}{\eta V_T}}}{\eta V_T}$$

Diffusion capacitance exponentially increases with forward voltage across the diode.

Cavalier lifetime (τ) \rightarrow

or mean lifetime of minority carriers.

or average lifetime ($\mu\text{ sec to n sec}$).

$$\Rightarrow \tau = \frac{C_D}{g} = C_D \cdot \tau = \frac{C_D \eta V_T \text{ sec}}{I_f}$$

Derive an equation for transition capacitance C_T
 C_T is the junction capacitance in a RB diode

$$C_T \Rightarrow C_J = \frac{\epsilon A}{w} \text{ fawad.}$$

$$w = \sqrt{\frac{\partial \epsilon}{q} \left(\frac{1}{N_A} + \frac{1}{N_D} \right) (V_0 + V_{RB})}$$

$$\Rightarrow C_J = \frac{\epsilon A}{\sqrt{\frac{\partial \epsilon}{q} \left(\frac{1}{N_A} + \frac{1}{N_D} \right) (V_0 + V_{RB})}}$$

Dividing numerator and denominator by ϵ

$$C_j = \frac{A}{\sqrt{\frac{q\epsilon}{2} \left(\frac{1}{N_A} + \frac{1}{N_D} \right) (V_o + V_{RB})}}$$

$$C_j = \frac{A}{\sqrt{\frac{q\epsilon}{2} \left(\frac{N_A + N_D}{N_A N_D} \right) V_o \left(1 + \frac{V_{RB}}{V_o} \right)}}$$

$$C_j = \frac{A \sqrt{\frac{q\epsilon}{2V_o} \left(\frac{N_A + N_D}{N_A N_D} \right)}}{\sqrt{1 + \frac{V_{RB}}{V_o}}}$$

if $V_{RB} = 0$

$C_j = C_{jo}$ = function capacitance of diode
when $V_{RB} = 0$.

$$\Rightarrow C_{jo} = A \sqrt{\frac{q\epsilon}{2V_o} \left(\frac{N_A N_D}{N_A + N_D} \right)} \quad \text{Farad}$$

C_{jo} can be expressed per cross sectional area

$$\Rightarrow C_{jo} = \sqrt{\frac{q\epsilon}{2V_o} \left(\frac{N_A N_D}{N_A + N_D} \right)} \quad \text{F/m}^2$$

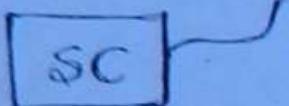
$$\Rightarrow \frac{C_j}{C_r} = \frac{C_{jo}}{\left(1 + \frac{V_{RB}}{V_o} \right)^{1/2}} \quad \text{Farad}$$

→ The transition capacitance : can be expressed
in generalised form :-

$$\cancel{\text{Imp}} \Rightarrow C_j = \left[C_{j0} \left(1 + \frac{V_{RB}}{V_0} \right)^m \right]$$

$m \Rightarrow$ grading coefficient.

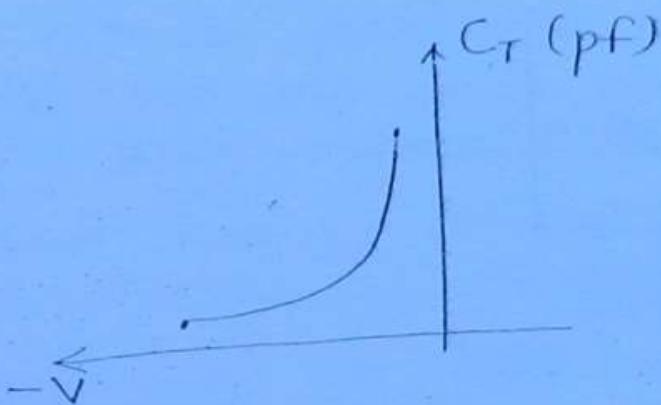
Point Contact Diode

- Earliest diode or first diode (100 years old)
- metal semiconductor junction diode.
- The least value of junction capacitance is obtained with point contact diode.
-  Tungsten wire in micron as a cat whisker

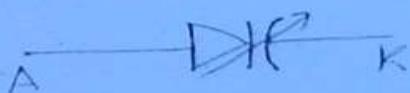
VARACTER DIODE →

- It is a linear graded diode.
- This is working on the principle of transition capacitance.
- Always operated under reverse biased
- $C_T \propto V^{-n}$, when $n = \frac{1}{3}$ for VD.
 $\Rightarrow C_T \propto \frac{1}{\sqrt[3]{RB \text{ voltage}}}$
- $\Rightarrow C_T \propto \frac{1}{\sqrt[3]{V_{bi} + V_{RB}}}$
- As VO is more RB, the $C_T \downarrow$
- Popularly used material GaAs.

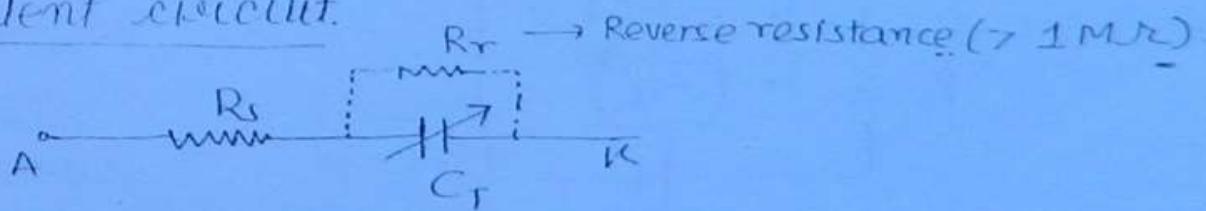
- Low Noise Device.
- By varying RB voltage we get a small variation in C_T (in pF).
- Characteristic curve of VD.



- Symbol



- Equivalent circuit



$R_s \rightarrow$ ohmic resistance or contact resistance or Bulk resistance. ($< 10\Omega$).

- Also called VARI-CAP (variable capacitance diode) or VOLTA-CAP (voltage dependent variable capacitance).

• epi-cap

- Varactor Diode used as Para-Amp.

- Applications :→ (1) For direct generation FM frequency by using varactor diode modulator circuit.
- (2) For self-balancing AC bridges.
- (3) For fine tuning of receiver.
- (4) For electronic tuning of receiver.
- (5) For tuning of LC resonant circuit.

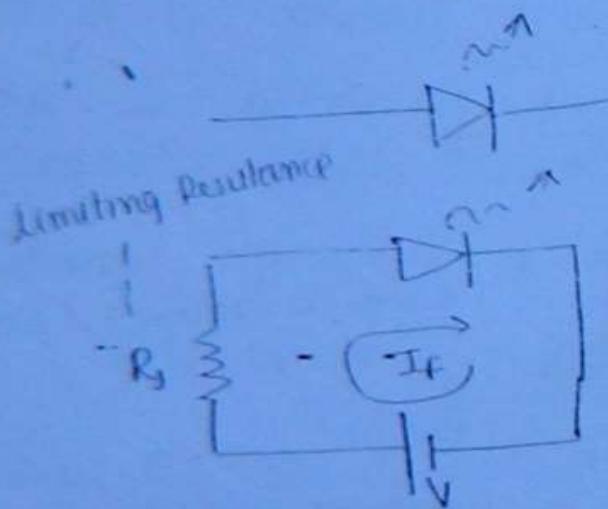
LED (Light Emitting Diode)

→ Based on principle electroluminescence.

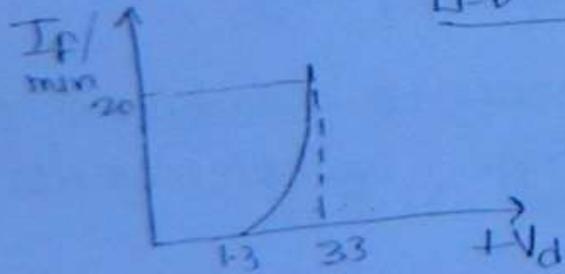
→ DBG-SG
GaAs $\left. \begin{array}{l} \text{InGa-SC} \\ \text{GaP.} \end{array} \right\}$ under special doping condⁿ

$$\boxed{\lambda = \frac{1.24}{E_g} \mu m}$$

$$\boxed{\lambda = \frac{C}{F}}$$



LED characteristics



- LED will emit the light when properly biased
- the best electroluminescent device is LED
- Generally fabricated with DBR-SC
- Popularly used material is GaAs
- LED can be fabricated with DBR-SC materials and also with some of the TBR-SC material under controlled doping.
- In LED light is emitted due to a large no. of recombination at the junction.
- LED can emit the light either in the visible spectrum or invisible spectrum of light.
- In the invisible spectrum LED emits IR light
- IR LED is used as remote control transmitter.
- In the visible spectrum of light LED can emit any one of the following colours such that

RED	YELLOW
GREEN	WHITE
ORANGE	AMBER.

- The colour of light given by LED depends on
 - (1) The wavelength of radiated light.
 - (2) The frequency of radiated light.
 - (3) The type of dopant
 - (4) The concn of dopant

→ LED fabricated with GaAs will emit IR light

→ LED materials are

GaAs → IR light

GaAs P → O

GaInP → Greenish Blue

- LED is always operated under forward biased
- with 20mA of forward current LED gives out the maximum intensity of light.
- If LED is heated up (temp. increasing) then its efficiency decreases.
- When Reverse biased LED will be working as a normal Diode and therefore it will not emit any light
- Power dissipation in mW.
- Response time in usec.
- Operating Life 1,00,000 + hrs.
- Cut-in voltage 1.3 to 1.5 v. depend on dopant.
- LED is faster than LCD. (because of smaller response time)
- When compared to LCD the disadvantage of LED is higher power dissipation applications.

Applications.

- As a Remote control transmitter
- In designing of opto-coupler.
- As a display device.

Ques A GaAs LED is operating at room temp. find its wavelength of radiation

Soln $\lambda = \frac{1.24}{E_G} \mu\text{m}$.

For GaAs, $E_{G,300} = 1.47 \text{ eV}$.

$$\lambda = \frac{1.24}{1.47} \mu\text{m} = 0.843 \mu\text{m}$$

- Since $\lambda > 0.76 \mu\text{m}$, GaAs LED will emit IR light

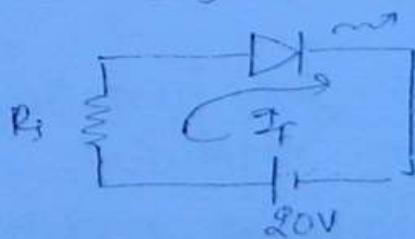
Ques A green colour LED emits light with a wavelength 5490 \AA unit find the energy gap of material in eV.

Soln $\lambda = \frac{1.24}{E_G}$

$$5490 \times 10^{-10} \times 10^6 \mu\text{m} = \frac{1.24}{E_G}$$

$$E_G = \frac{1.24}{5490 \times 10^{-4}} = 2.26 \text{ eV}$$

Ques find the value of limiting resistance required for the LED circuit given below.



Let $I_F = 90 \text{ mA}$, $V_d = 3.3 \text{ V}$

$$20 = I_F R_s + V_d$$

$$R_s = 8.352 \Omega$$

PHOTO-DIODE →

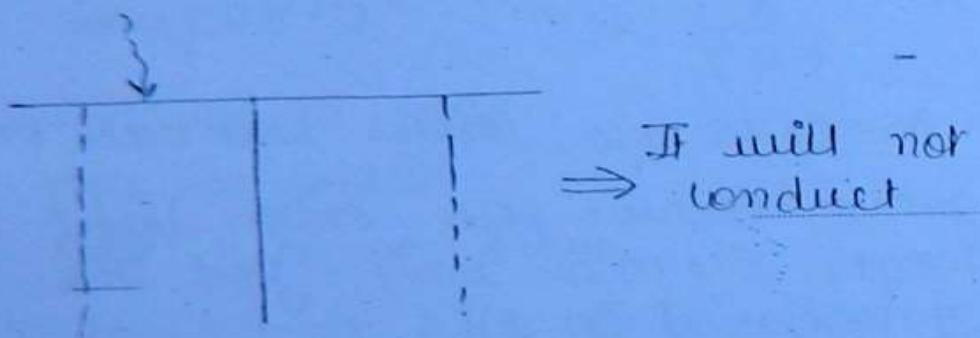
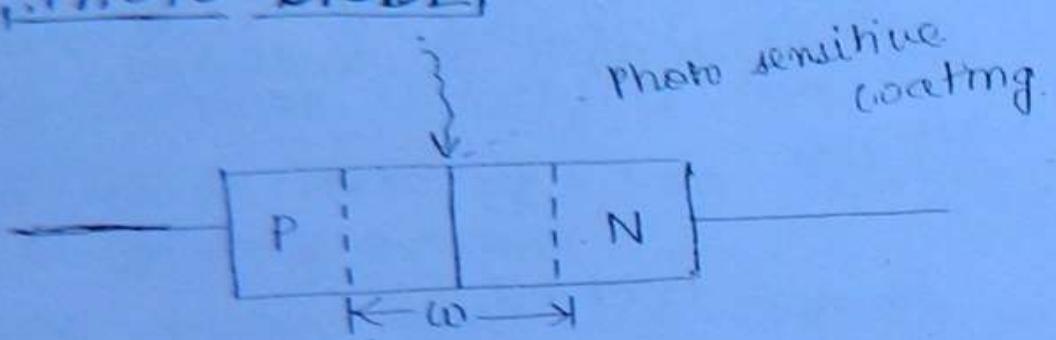
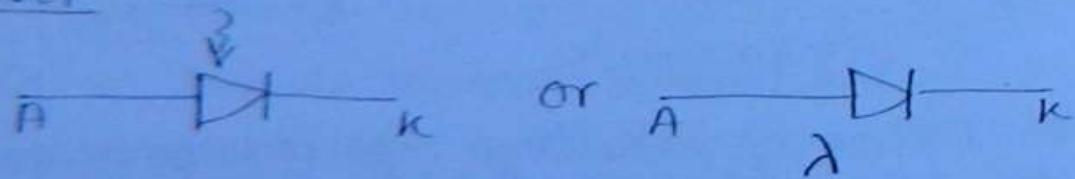


Photo-sensitive material → (CdS, Se, ZnS, PbS.)

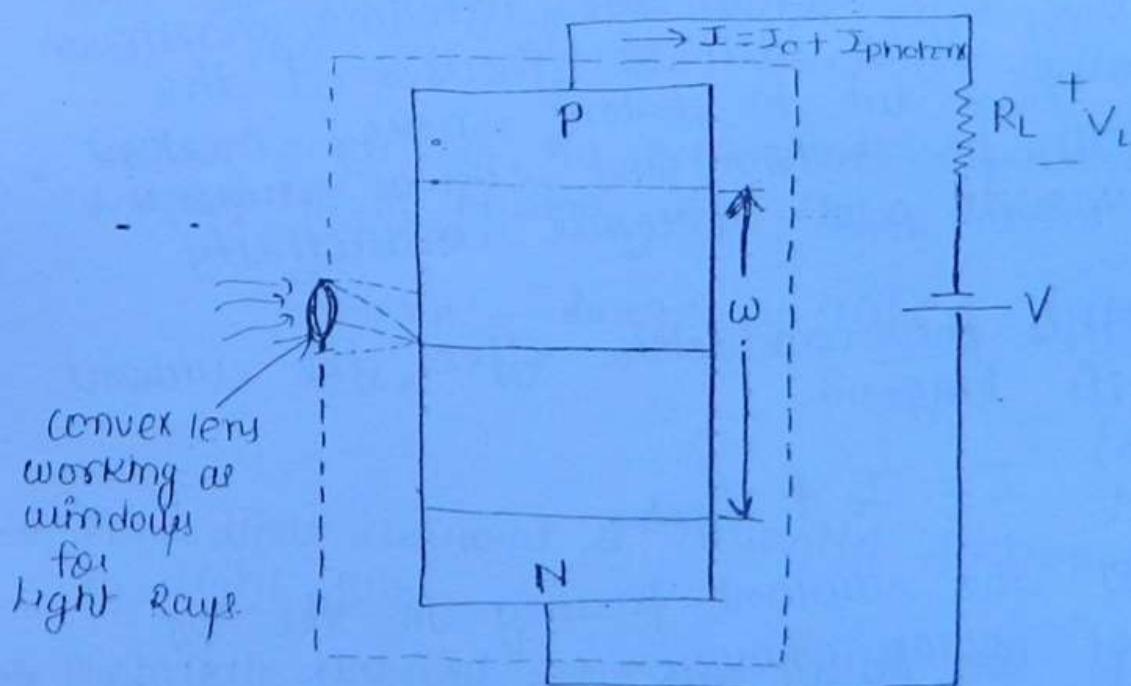
$$w \propto \frac{1}{\sqrt{\text{Depend.}}}$$

Symbol.



- Photo-sensitive Device.
- Basically a P-N junction for junction is coated with photo-sensitive material.
- In a photo-diode photo-sensitive coating is provided only at the junction
- In a PD if light falls slightly away from the junction then photo-diode will not respond to light.

- Principle → Photoconductive effect
- Photosensitive materials are CdS, Se, ZnS, PBS.
- PD has a larger depletion layer width and this is obtained by reducing the dopant concentration of P-N regions.
- PD has very high sensitivity and this is due to larger depletion layer width.
- GePD will be responding to visible light
- SiPD will be responding to Infrared Light
- SiPD are used as a remote control sensor
- PD is generally operated under RB.
- For special application PD can be operated in DC condⁿ or SC condⁿ



→ When PD is operated under complete darkness
i.e. no light is falling on the device.

PD will be working as a Normal diode
under RB.

$$\Rightarrow [I = I_0]$$

minority carrier current

or
Dark current. (I_{dark})

$$\Rightarrow \left\{ \begin{array}{l} I_{\text{dark}} = \mu A \text{ for Ge PD} \\ I_{\text{dark}} = m A \text{ for Si PD} \end{array} \right\}$$

At present photodiode is non-conducting
i.e. "OFF STATE".

→ When light is focus at the window, maximum intensity of light will be focused at the junction and due to photon energy covalent bonds will be broken and charge carriers are increases and therefore conductivity increases.

→ Due to this photoconductive effect the current in PD is large

$$\text{i.e., } I = I_c + I_{\text{photon}}$$

→ I_{photon} is the current passing in the PD because of photon energy.

→ PD current has two current component

(1) Thermally generated current (I_0)

(2) Photon current (I_{photon})

→ In a photodiode photocurrent is added to the existing thermally generated current.

$$I_{\text{photon}} > I_{\text{dark}}$$
$$\downarrow \text{mA} \quad \begin{array}{c} L_{\mu\text{A}} \\ n\text{A} \end{array} \quad \begin{array}{c} \text{Ge PD} \\ \text{Si PD} \end{array}$$

$$\Rightarrow [I \approx I_{\text{photon}}]$$

- Photodiode current flow from N to P
- PD current is a Reverse current
- PD current is a minority carrier current
- PD current is a diffusion current.
- When light falls on the semiconductor minority carriers are created and these minority carriers will be moving from high concn to lower concn thus due to the property called diffusion
- In a good PD the essential requirement is larger high photon to I_{dark} ratio

$$\frac{I_{\text{photon}}}{I_{\text{dark}}} = \text{large.} = 10^3 : 1 \quad 10^6 : 1$$
$$\text{Ge PD} \quad \text{Si PD}$$

(Better performance)

- Photodiode current is directly proportional to light flux.
- Photodiode current increases with no. of photon falling at the junction.
- The magnitude of reverse current in PD increases with intensity of light falling at the junction

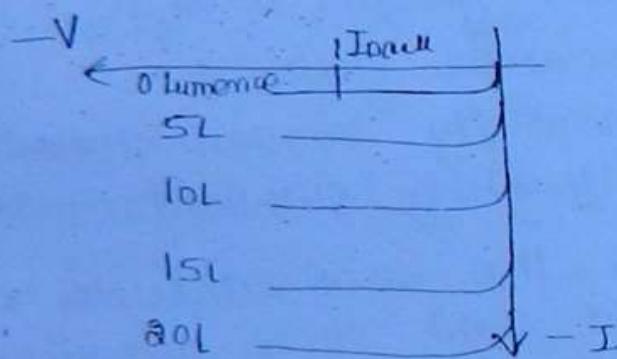
→ Equation for PD current

$$\Rightarrow I = I_s + I_e [1 - e^{-\frac{V}{nV_T}}]$$

↓
SC current of PD.

$$I \approx I_o [1 - e^{-\frac{V}{nV_T}}]$$

→ PD characteristics will be plotted in IVrd quadrant



L-lumen
unit for intensity
of light.

→ PD current increases exponentially with light flux.

→ PD is basically a light operated switch

→ photodiode is a minority carrier injector.

→ Applications

→ As a / Remote control sensor.

→ In designing of opto coupler.

→ As a light operated switch.

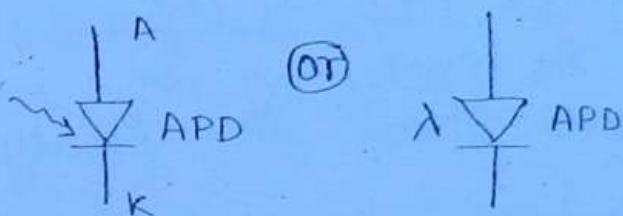
→ To read audio track recorded on motion picture film.

→ When PD is FB & light is applied at the junction.

→ It will work as normal FB diode, current is due to majority carriers. The effect of light on majority carriers is zero & therefore forward current will remain const. i.e. current independent of light.

→ And also the PD can not be used as light operated switch.

AVALANCHE PHOTODIODE → GATE ONLY



- Basically a photodiode along with avalanche effect always operated under RB.
- Fabricated only with Si. comparatively can hand it more signal power.
- Response time is very small (75ns).
- APD is faster than PD. because of smaller response time.
- Measure major applications as a receiver in fibre optic communication system

Types of JUNCTION →

Normal junction → P & N region are equally doped

Abrupt junction → P & N region are different doping level. e.g. P^+N or P^-N^+

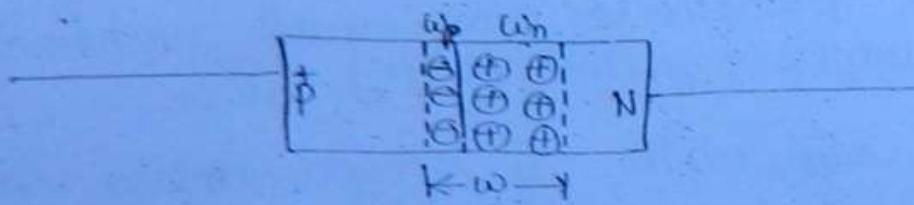
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Step Graded Diode :-

or

Abrupt p-n junction diode.

- It has abrupt junction (PN or PN diode)
- Faster than Normal diode (due to higher doping conc.)
- Depletion layer will be penetrating more into lightly doped region and lesser into highly doped region.



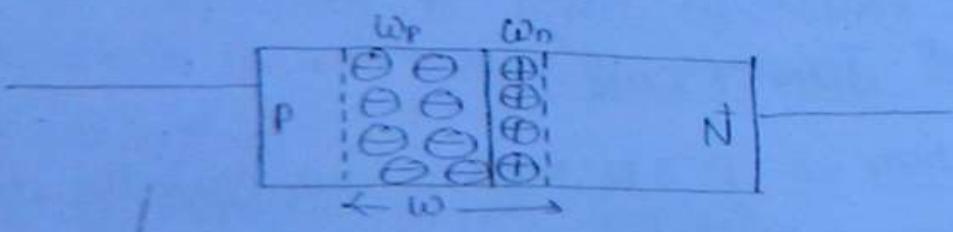
$$N_A > N_D$$

$$w_N > w_P$$

$$w = w_N + w_P$$

$$\Rightarrow w \approx w_N$$

or



$$N_D > N_A$$

$$w_p > w_n$$

$$w = w_N + w_P$$

$$\Rightarrow w \approx w_p$$

- In a step graded diode, most of depletion layer will be existing in the lightly doped region
- When step graded diode is RB.

(i) Considering PN diode

The width of depletion layer on the lightly doped region

$$w = w_n + w_p \\ \Rightarrow [w \approx w_n]$$

$$\Rightarrow w \approx \sqrt{\frac{2\epsilon}{q} \left(\frac{1}{N_A} + \frac{1}{N_D} \right) V_j}$$

$N_A \rightarrow$ Highly doped so $\frac{1}{N_A}$ is neglected

★ $w = \sqrt{\frac{2\epsilon \epsilon_0 \epsilon_r V_j}{q N_D}}$ metres.

The junction voltage V_j^o

★ $V_j^o = \frac{q N_D w^2}{2\epsilon}$ volts.

(ii) Considering $P\bar{N}$ diode.

$$[w \approx w_p]$$

$$w \approx \sqrt{\frac{2\epsilon}{q} \left(\frac{1}{N_A} + \frac{1}{N_D} \right) V_j} \quad \left\{ \frac{1}{N_D} \text{ is neglected} \right.$$

$$\Rightarrow w \approx \sqrt{\frac{2\epsilon V_j}{q N_A}}$$

$$\Rightarrow V_j^o = \frac{q N_A w^2}{2\epsilon}$$

→ In a step graded diode the width of the depletion layer on the p-region and N-region can be directly obtained from charge equality equation given below : →

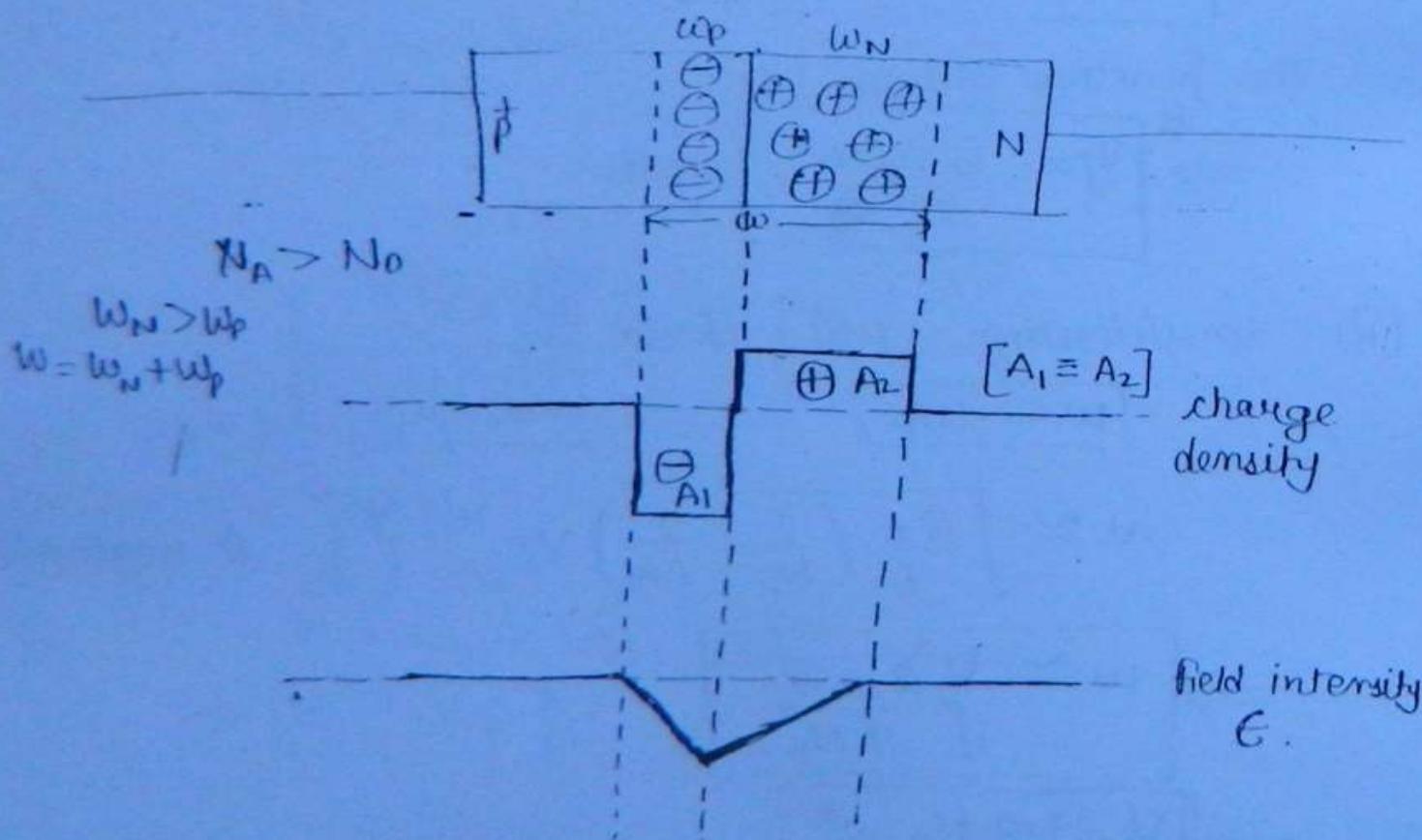
$$qA w_N N_D = qA w_P N_A$$

$$w_N N_D = w_P N_A$$

$$\Rightarrow \boxed{\frac{w_N}{w_D} = \frac{N_A}{N_D}}$$

→ The charge density curve and field intensity curve in a step graded diode is given below:

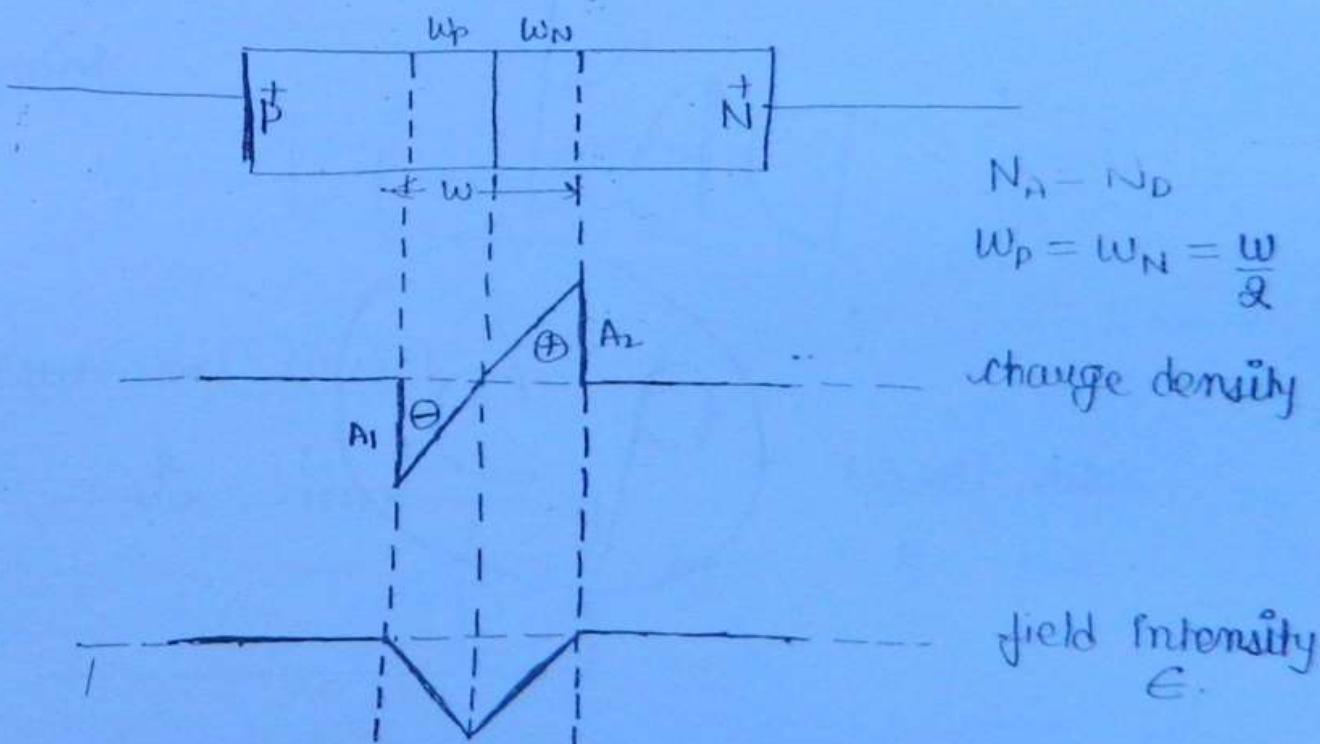
(1) Considering PN diode.



- In step graded diode field intensity is maximum at the junction
- In step graded diode field intensity is maximum at junction but it is not at the centre of depletion layer.

* Linear Graded Diode : → Conventional Ques

- If it is a P+N diode with highly doped N+ diode with normal junction.
- The charge density diagram and field intensity curve for linear graded diode is given below:-



- In a linear graded diode field intensity is maximum at junction (also max. at centre of depletion layer).

TUNNEL DIODE :-
OR
Esaki Diode.



$p^+ n^- \rightarrow$ Doped in $10^3 : 1$

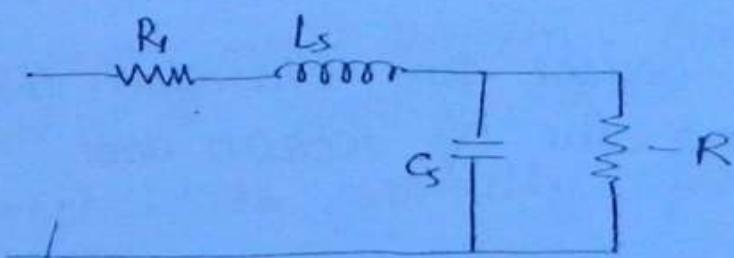
$$w \propto \frac{1}{\sqrt{\text{Doping}}}$$

Narrow Depletion $w = 100 \text{ \AA}$ to 200 \AA

Symbol



Equivalent circuit



Typical value
 $-R = -30 \Omega$

→ Also called Esaki Diode

→ p-n Diode with a normal junction

→ Doping conc' $1 : 10^3$

Narrow Doped Semiconductor Diode.

- Popularly used material is GaAs
- Low Noise Device.
- Narrow Depletion layer. (100 \AA to 200 \AA).
- Fastest switch.
- Switching time psec (10^{-12} sec).
- Negative Resistance Device.
- Tunnel Diode is more popular as a -ve resistance device for but not as a fast switch.
- Tunnel Diode exhibit the property of tunnelling effect.

→ ADVANTAGES :-

- Smaller in size, easier to fabricate, low cost, low noise device, high resistance to radiation, internal power consumption is negligible.

→ Disadvantages :-

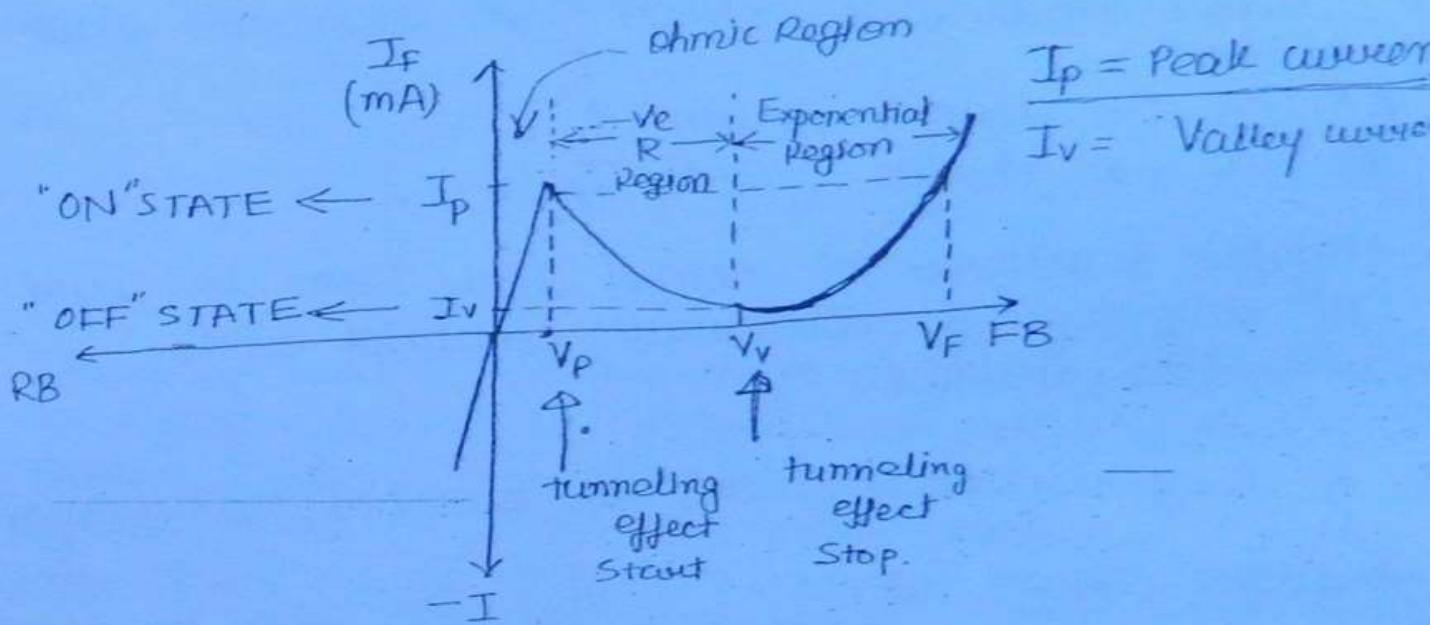
- It is a two terminal Device and therefore there is no isolation in between the O/p section and i/p section.
- Smaller voltage swing.

Definition of Tunnelling effect. →

In tunnel Diode the width of Depletion layer is very narrow and is almost equal to $1/50^{\text{th}}$ of wavelength's of visible light and therefore the charge carriers will be penetrating to the Depletion layer almost at the speed of light and thus quantum behaviour

of the charge carriers is called tunnelling effect.

VI characteristics of tunnel Diode :-



- A RB tunnel Diode is a resistor.
- When Tunnel Diode is RB the current is linearly increasing with the voltage and the device now working as a linear device i.e. a resistor.
- In exponential Region tunnel diode will be working as normal Diode.
- Tunnel Diode generally operated in -ve resistance region.
- The operating point or Q-point of tunnel Diode is located at the centre of -ve resistance region.
- In tunnel Diode -ve resistance mean as forward voltage increases the forward current decreases.
- The -ve resistance of tunnel diode is due to tunnelling effect.

→ Tunnel Diode will exhibit -ve resistance property when device changes its states from ON to OFF.

→ In tunnel diode twin voltage is zero.

→ Tunnel diode will exhibit -ve resistance property when :-

① FB :→ changes from V_p to V_B

② FC → changes from I_p to I_v .

→ Negative resistance of tunnel diode can be used in designing of microwave oscillator and relaxation oscillator.

→ For a good tunnel diode, the essential requirement is :-

→ Larger I_p/I_v ratio

$$\frac{I_p}{I_v} = 15 \text{ (GaAs)}, 7.5 \text{ (Ge)}, 2.5 \text{ (Si)}$$

→ Tunnel diode can be fabricated with GaAs or with Ge material and never with the Si material.

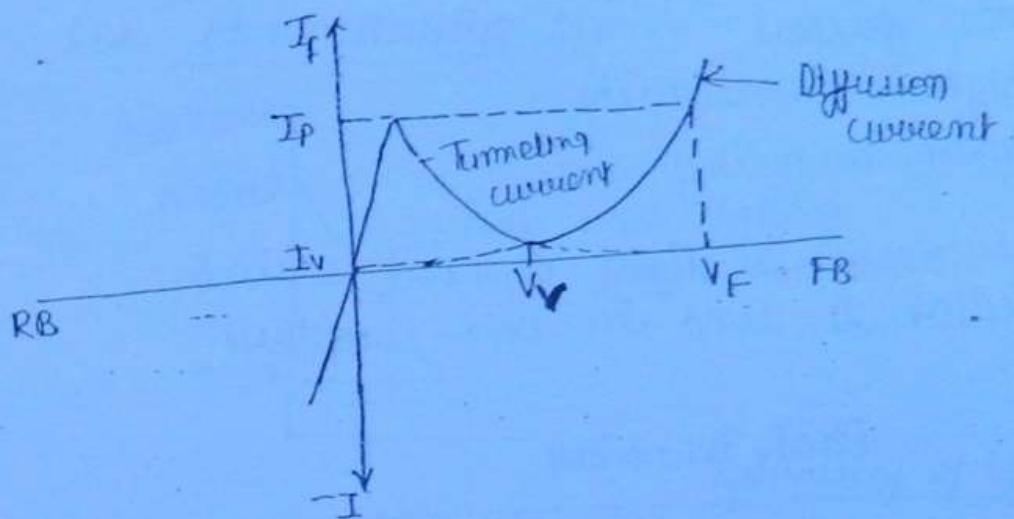
→ High quality tunnel diode are made with GaAs.

→ Commercial tunnel diode are made with Ge.

→ Tunnel diode exhibits multi-feature property or triple valued property. (i.e. any value of forward current between I_v & I_p can be obtained with three different sets of forward voltage and this property is used in designing of pulse circuit and industrial application)

→ Tunnel Diode is also used as PARA-Amp. (i.e. as a parametric amp and is microwave power amp used with satellite communication).

→ Parametric characteristics :-

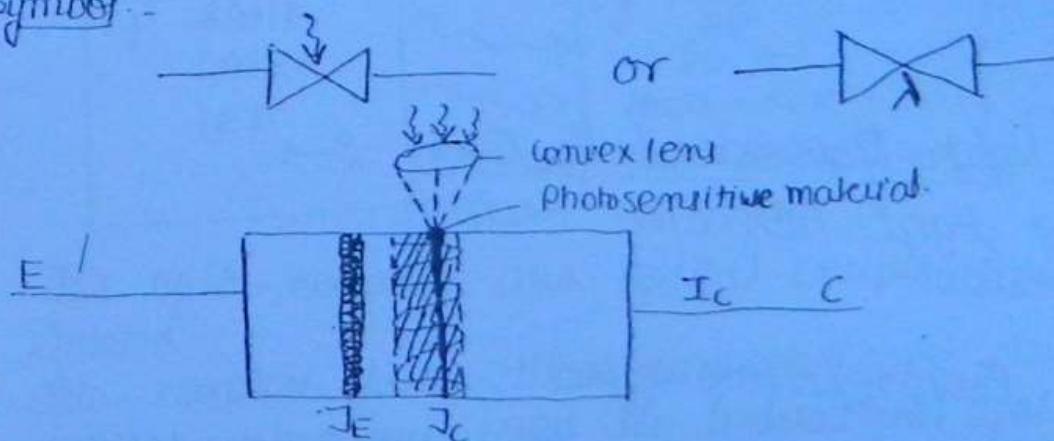


- Tunnelling current is maximum at peak point
- Tunnelling current is minimum at valley voltage.
- Beyond valley voltage tunnelling current reduces to zero
- Diffusion current is small at valley point.
- Above valley voltage diffusion current exponentially increases with the forward voltage.
- Diffusion current is large at peak point.

PHOTOTRANSISTOR :- → Photo-Duo-Diode.

→ Principle → photoconductive effect. *

→ Symbol :-



→ Collector junction i.e. J_C is made photosensitive.

* (NOT IMP)

Thyristors

- Power switching Device.
- Can hand it large amount of power with negligible internal power consumption.
- Fabricated only with Si.
- Ge Thyristor are not practical.
- Bistable Device.
- Basically a latch i.e. a device having ON state and OFF state which are highly stable.
- Basically a multilayer semiconductor device.
- can be unidirectional or bidirectional.
- Can be voltage operated or current operated or suitable for both.
- When thyristor changes states from OFF to ON due to applied voltage, it is called voltage operation.
- When a thyristor changes its states from OFF to ON becoz of applied current it is called current operation.
- Thyristor are faster than BJT.
- Thyristor family members are

SCR
SCS
SUS
SBS
TRIAC

DIAC

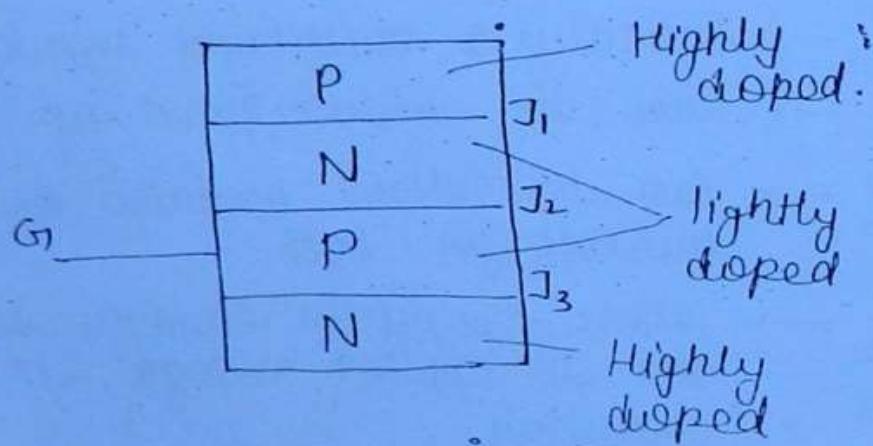
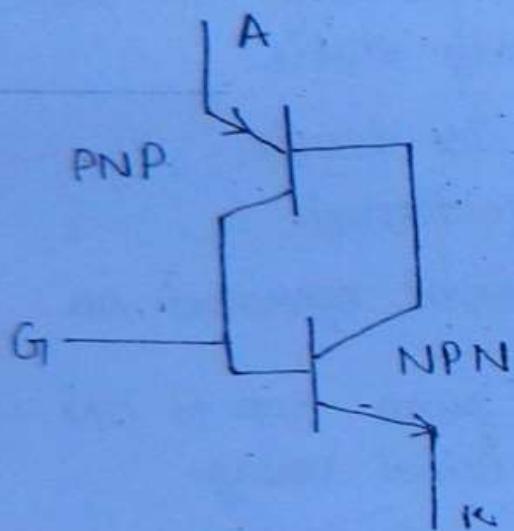
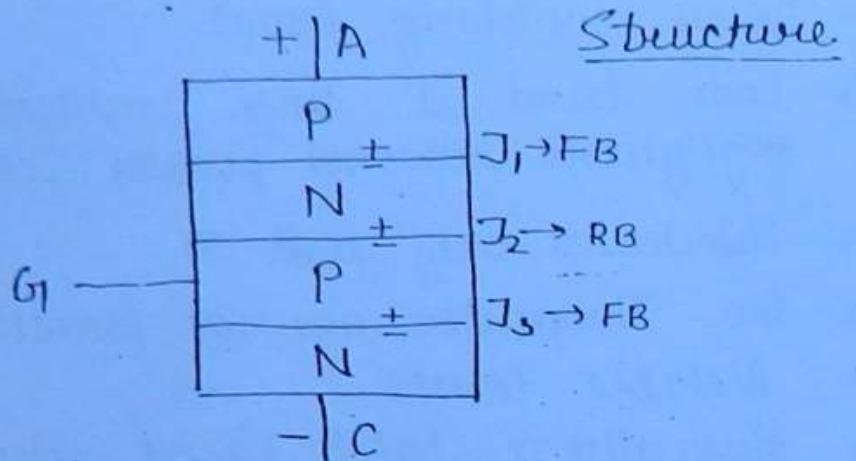
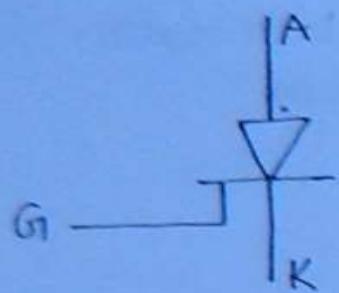
PNPN or shottkey D

UJT

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SCR (Silicon Controlled Rectifier) :-

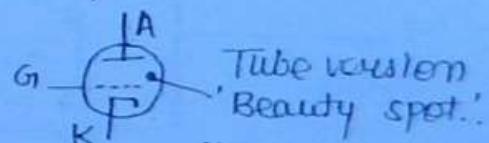
Symbol.



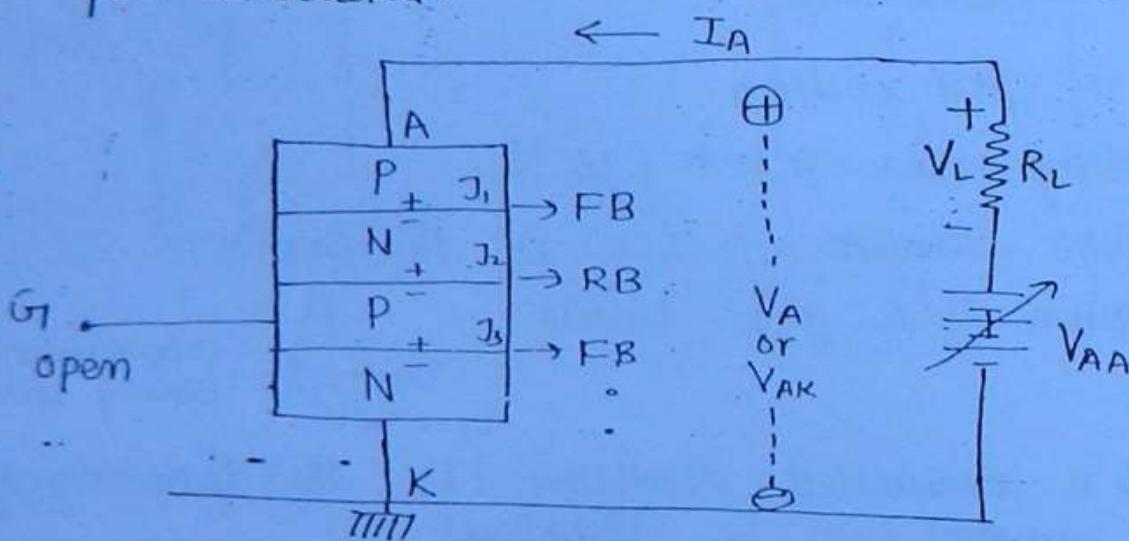
equivalent ckt.

- A three terminal device having anode, cathode and ~~controlled~~ gate.
- Four layer solid state device. (SC device) with three junction.
- In SCR gate is made with p-type SC.
- Unidirectional device (i.e. SCR will be conducting only when anode is +ve with respect to cathode).

- If anode is given -ve with respect to cathode then SCR will not conduct.
- The equivalent circuit of SCR is represented by a transistor latch.
- In the transistor latch when one transistor is ON the other transistor is OFF.
- The equivalent circuit of SCR is represented by one PNP transistor and one NPN transistor connected such that the collector of first transistor is given to base of second transistor and collector of second transistor is given to base of first transistor.
- SCR is fast switch.
- switching time nsec (10^{-9}).
- The tube version of SCR is Thyriation
- Thyriation is a gas triode
- SCR is a controlled Rectifier. (i.e. the duration of anode current can be controlled).
- SCR can be used in poly-phase rectifiers.
- SCR can be fabricated with
 - ① Planar technology.
 - ② MESA Technology.
- SCR is generally specified in terms of breakover voltage, (V_{BO}) \rightarrow 50V to 1800V.



- SCR is always operated under FB.
- When SCR is FB with a voltage less than V_{BO} then junction J_1 & J_3 are forward biased and J_2 is RB. Hence internal resistance of SCR is greater than $1\text{ m}\Omega$ and it is in OFF state i.e. Non-conducting.
- OFF state is also called forward Blocking state.
- Voltage Operation of SCR →
- Under voltage operation of SCR the gate is kept open circuited.



$$V_L = -I_A R_L$$

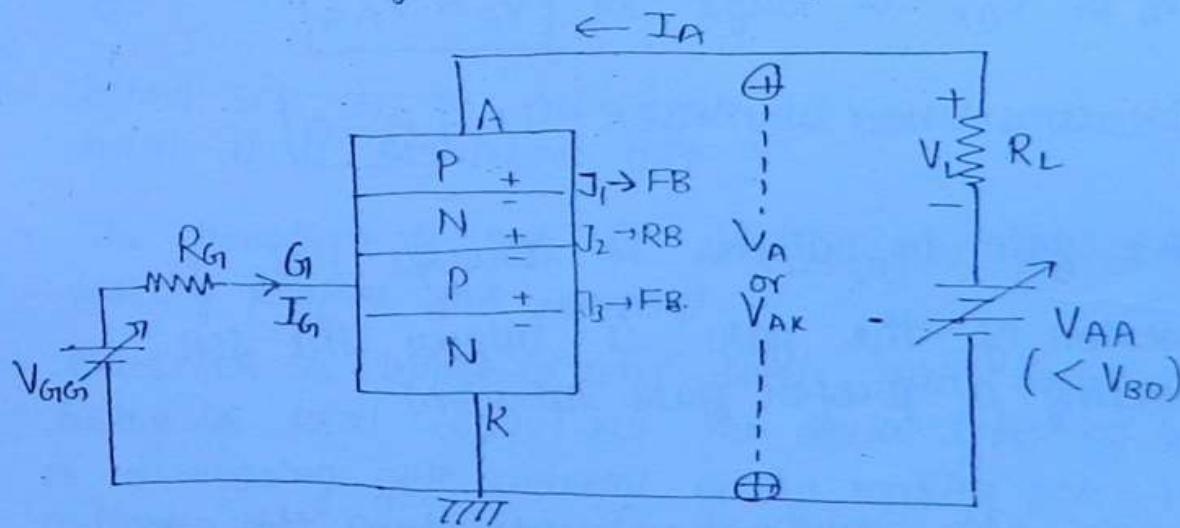
Let $V_{AA} < V_{BO}$, the junction J_1 & J_3 are FB & J_2 is RB, and the internal resistance of SCR will be greater than $1\text{ m}\Omega$ hence anode current is zero & SCR is not conducting i.e. it is in the OFF state.

When V_{AA} gradually increases junction J_2 moves more reverse biased

- When anode supplied voltage $V_{AA} = V_{BO}$ the RB junction J_2 will enter into breakdown and a large anode current is flow & SCR is in the ON state.
- SCR can be switched OFF by decreasing V_{AA} so that the anode voltage just falls below V_H (holding voltage) and SCR is switched off.
- The main disadvantage of voltage operation is we require anode supplied voltage equal to V_{BO} to operate the device.

Current Operation of SCR. :-

- Also called gate operation of SCR.



$$I_{G1} = \frac{V_{G1G1} - V_r}{R_{G1}}$$

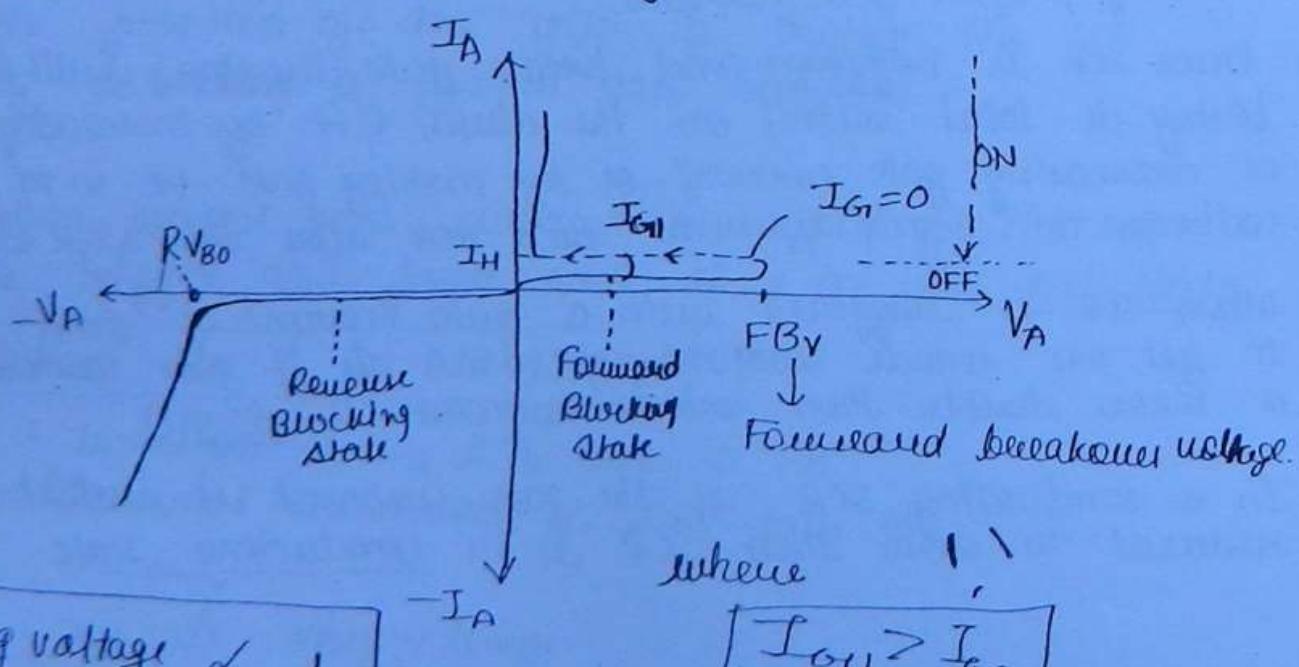
$$I_{G1} = \frac{V_{G1G1} - 0.7}{R_{G1}}$$

- The SCR can be switched OFF by using any one of following three technique :-
- (1) By disconnecting the power supply.
 - (2) By making anode negative w.r.t. to cathode.
 - (3) By reducing anode supply voltage so that the anode current falls below holding current (I_H). then SCR is OFF state.

(Low current knock out Technique).

- if $I_A > I_H$, SCR is in ON state.
- If $I_A < I_H$, SCR is in OFF state.
- When SCR is switched OFF, the gate terminal will be regaining its control on the device.

VI characteristics of SCR.



Forward voltage of SCR

$$\frac{1}{I_{G1}}$$

where

$$I_{G1} > I_{GO}$$

- By applying larger gate currents we can fire the SCR with smaller anode supply voltages.
- The main advantages of current operation is we can fire the SCR with smaller anode supply voltage than its breakdown voltage
- Technical data :-

 - (1) SCR can handle power upto 50 MW
 - (2) Breakover voltages are in range of 50 V - 1800 V
 - (3) Switching time n sec
 - (4) Max power dissipation 1 W
 - (5) SCR can handle current upto 2000 A

Holding Current (I_H) :-

If it is the minimum anode current required to keep the SCR in the ON state.

Holding current is very sensitive to temperature.

I_H decreases with increase in temperature.

LATCHING CURRENT (I_{latch}) :-

It is the minimum gate current required to trigger to SCR so SCR goes to the ON state.

Latching current typical value is 1mA.

In SCR Holding current < Latching current.

Turn-on-time (t_{on}) :-

It is the time required to switch on the SCR.

t_{on} increases with temperature.

t_{on} increases with anode current.

turn-off time (t_{off}) :-

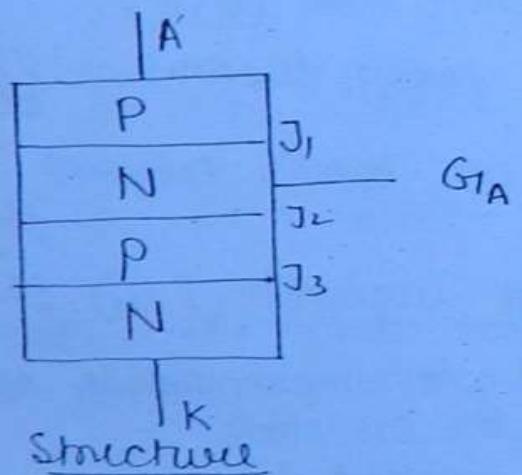
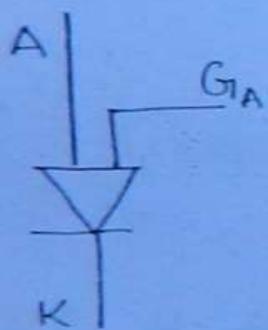
t_{off} is the time required to switch off SCR.

turn-off time increases with temperature.

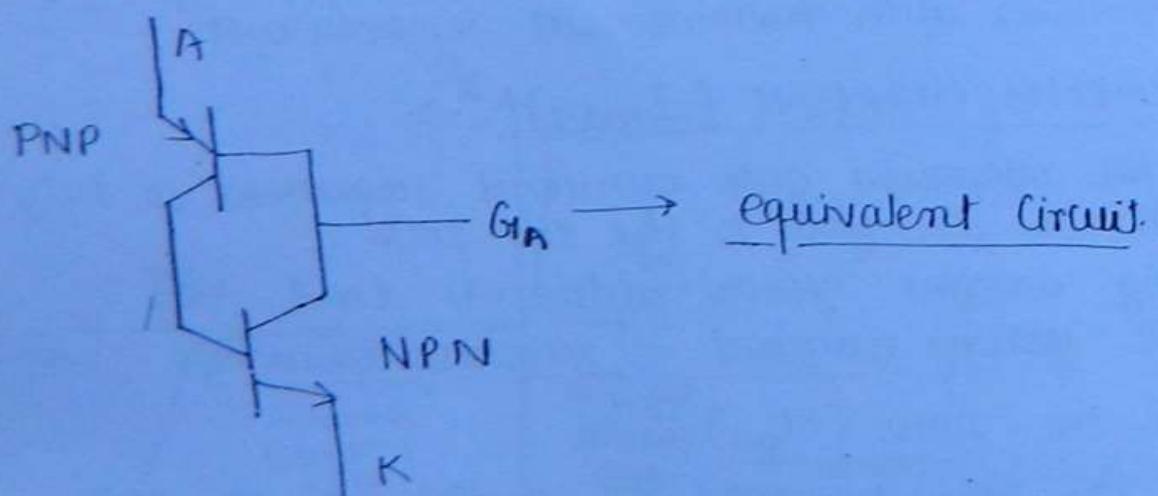
t_{off} increases with anode current.

→ SCR can be used to speed control of DC motor.

SUS (Silicon Unilateral switch) :-

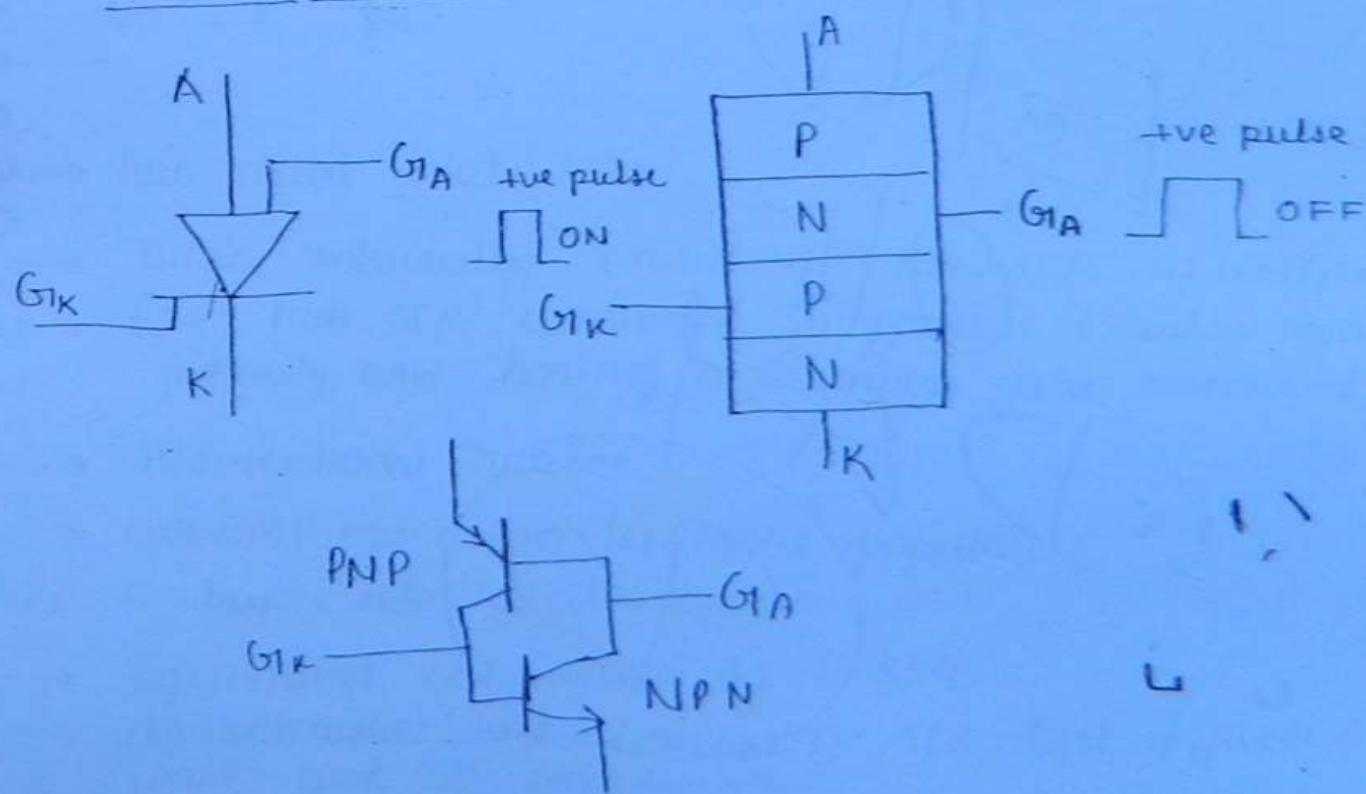


Symbol.



- 3-terminal device having anode, cathode and anode gate
 - four layer device with 3-junction
 - Unidirectional device.
 - Current operation is more popular.
 - Equivalent circuit is a transistor latch.
 - An SCR gate is p-type SC & therefore it is +ve triggered.
 - An SUS gate is N-type SC and therefore it is negative triggered.
 - Popularly known as complementary SCR (CSCR).
 - Characteristics are similar to SCR.
 - SUS can be used as
 - (1) As a relaxation oscillator.
 - (2) As a PUT (Programmable unijunction Transistor).
-

SCS (Silicon Controlled Switch) :-



- Four terminal device (Anode, cathode, cathode gate and anode gate) :
- Unidirectional device.
- Current operation is more popular.
- Four layer device with 3-junction.
- Equivalent circuit is given by transistor LATCH.
- Also known as "SCR with two gate"
 ①
 "low current SCR with & gate"
 ②
 "low current SCR with Additional gate"
- Characteristics & application are similar to SCR.
- SCS can be operated with either gate terminal and with either pulse.

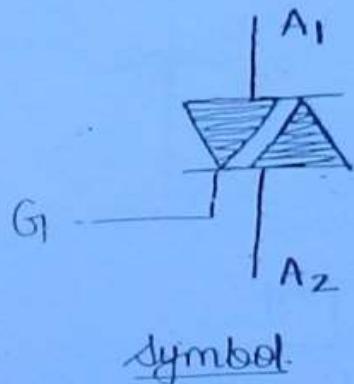
X X

END

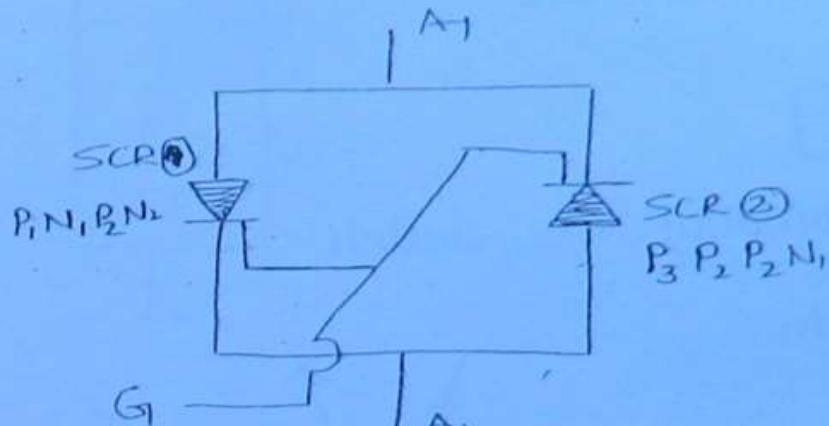
OF

TRIAC

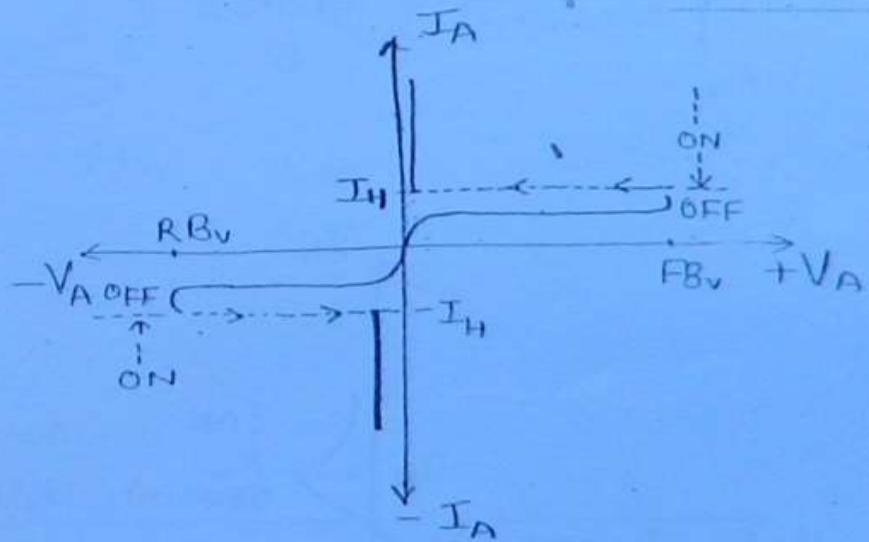
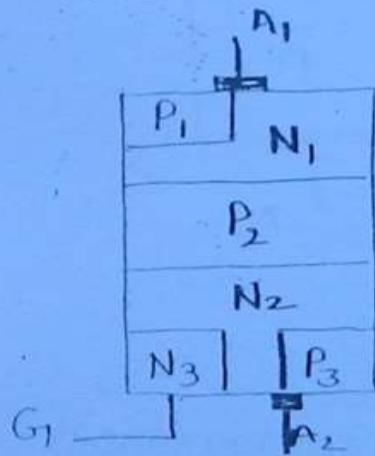
→ Three terminal AC switch.



Symbol



structure



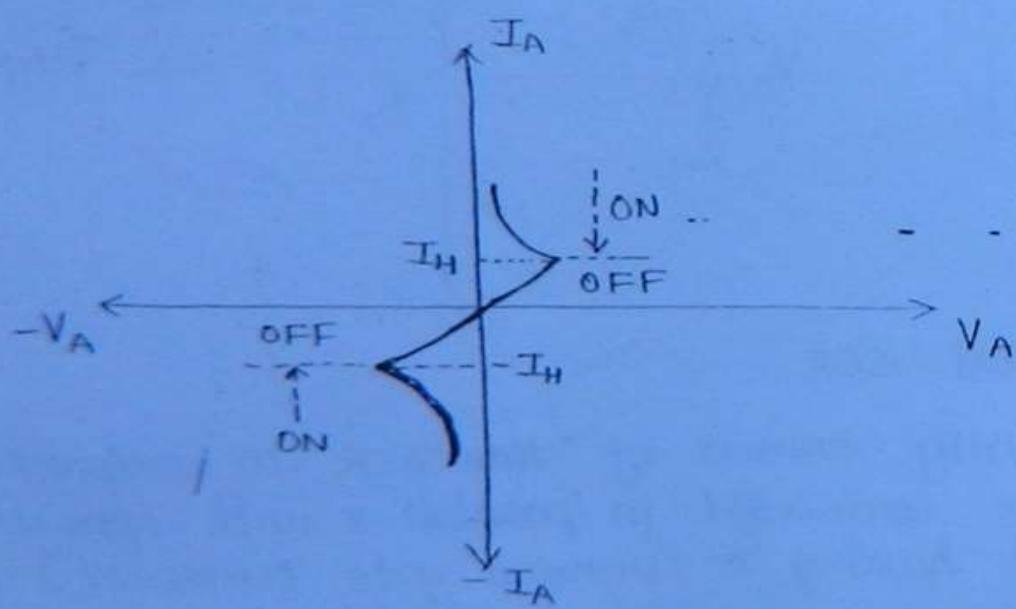
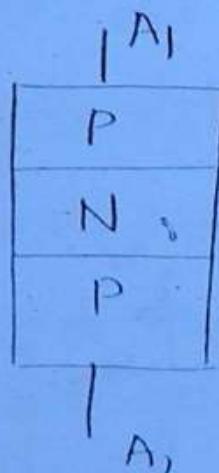
- Also called Dual SCR
- TRIAC internally consist of two SCR in antiparallel (i.e. two SCR connected in parallel & with opposite polarity and having a common gate terminal)
- Bidirectional Device
- Current operation is more popular
- 5 layer solid state device.
- Equivalent circuit consist of 2 SCR.
- characteristics are similar to SCR but reflected in first and III quadrant.

used for speed controller AC motor

- Triac can also be used for designing of inverter circuit.

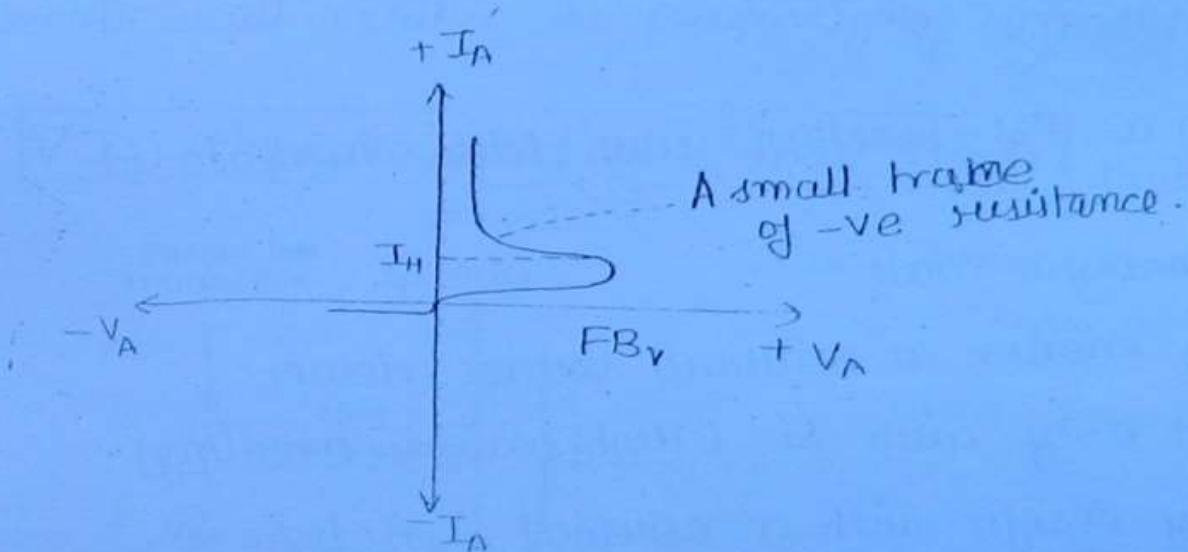
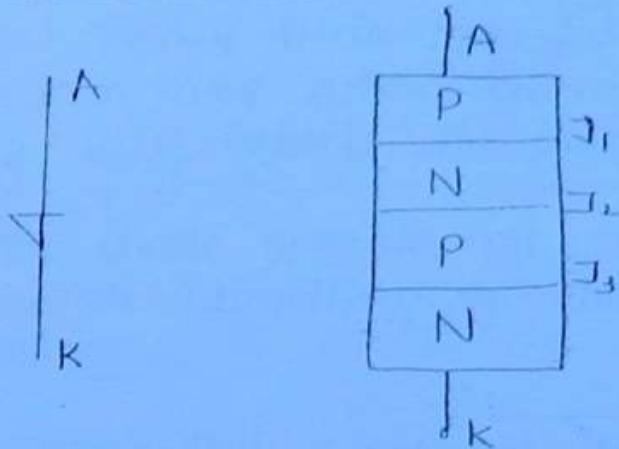
DIAC

- Two terminal AC switch.



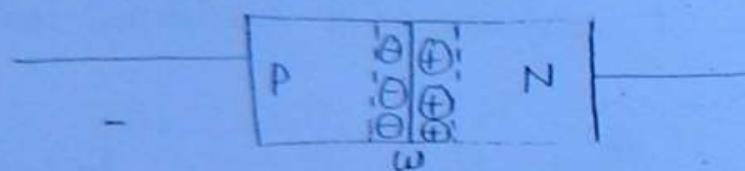
- Bidirectional device.
→ Only voltage operated device.
→ Three layer solid state device.
→ Widely used to trigger the SCR.

PNPN DIODE or Shockley Diode



- Unidirectional device
- Only voltage operated device
- Four layer solid state device with 3 junction
- Also called four layer diode
- Characteristics denotes a small trace of -ve resistance but it cannot be used for any practical application so shockley diode cannot be considered as a -ve resistance device.
- Major applications as a power diode

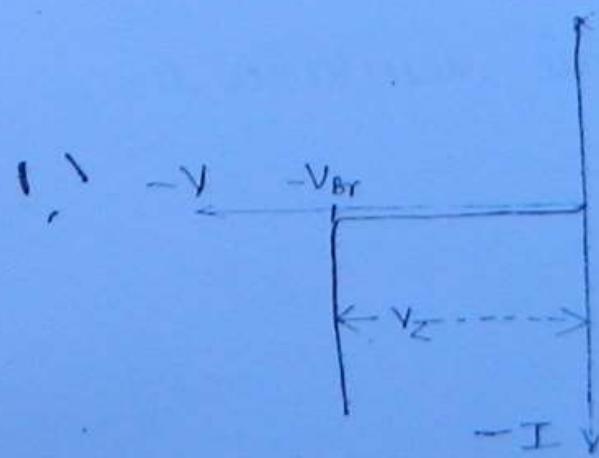
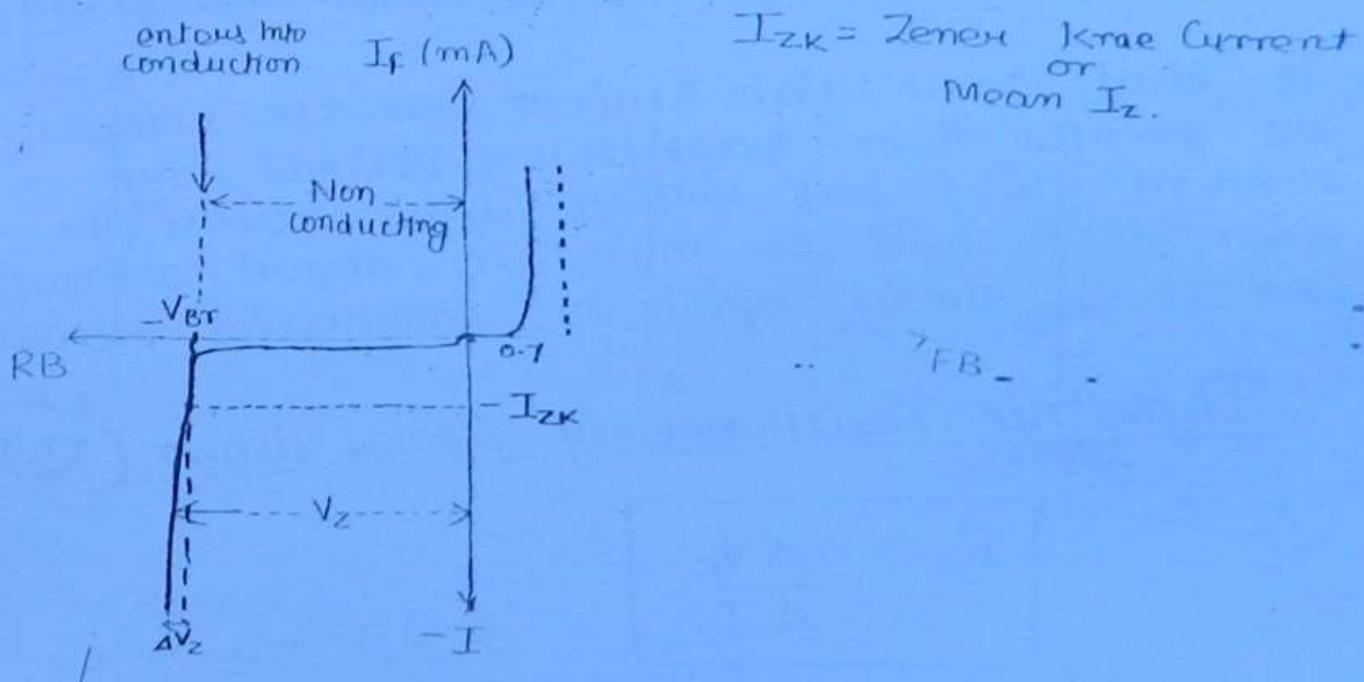
ZENER DIODE :



- Basically a PN junction with little increase in doping level ($1:10^5$)
- A Breakdown diode.
- Popularly known as constant voltage device.
- Fabricated only with Si (High power handling)
- Inversely design with a normal junction
- Major applications is as a voltage regulator circuit
- Can be used as reference voltage device.
- Always operated under reversed biased.
- Zener diode is specified in terms of breakdown voltage ($P_{Z\max}$)
- Zener diodes are available with breakdown voltage in the range 2.5V to 300V.
- When forward biased it will be working as a normal diode.

- Zener voltage is 0.7 V.
- Latest zener diode are fabricated with abrupt junction and when operated under reverse biased, they will exhibit the property of tunnelling effect.
- Zener diode operate on the principle of tunnelling effect or tunnelling of charge carriers across the junction
- A zener diode operated in voltage regulator circuit will exhibit the property of tunnelling effect.

VI Characteristics of Zener Diode



VI characteristics
of
ideal ZD

When zener diode is reverse biased with a voltage below the breakdown voltage. The current is practically zero and zener diode is non-conducting and at present it will be working as a normal diode.

When reverse voltage equal breakdown voltage the current suddenly increases to I_{ZK} . and this is due to breakdown phenomenon.

When reverse voltages are greater than breakdown voltage more and more current will be passing through the zener diode but the voltage across the zener diode will be maintain almost a constant and it is around the breakdown voltage.

In ideal zener diode when reverse voltages are greater than breakdown voltage large current flows but voltage drop across the zener diode will be maintain almost a const. and it is exactly equal to breakdown voltage.

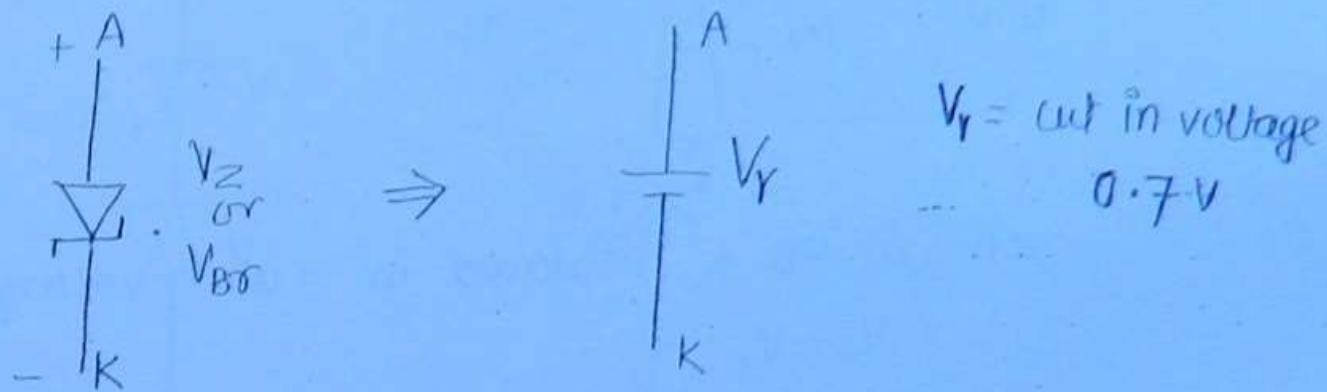
Dynamic Resistance of Zener diode (R_Z) :-

$$R_Z = \frac{\Delta V_Z}{\Delta I_Z}$$

For ideal zener diode dynamic resistance is zero.

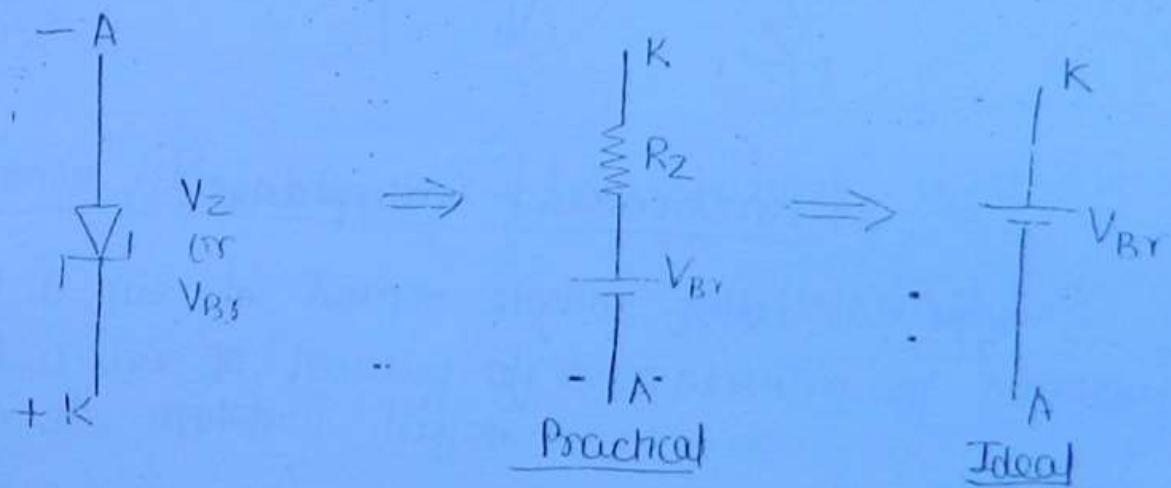
Equivalent circuit of Zener diode. \Rightarrow

(1) When zener diode is F.B. \Rightarrow

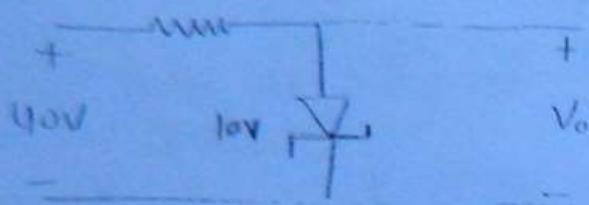


\rightarrow A forward biased zener diode is replaced by its cut-in voltage.

(2) When zener diode is R.B. \Rightarrow



Prob → Find output voltage V_o

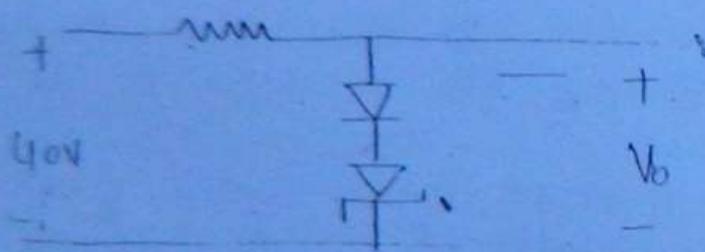


Sol ZD is in FB & replaced in cut-in voltage

$$V_o = V_V$$

$$V_o = 0.7V$$

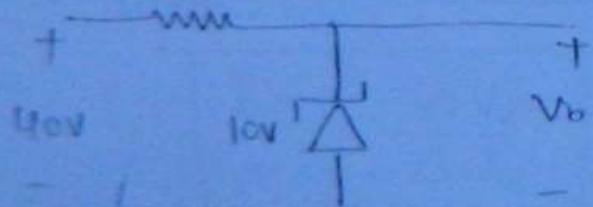
Prob



Si D is forward biased & replaced by

$$\boxed{V_o = 1.4V}$$

Prob

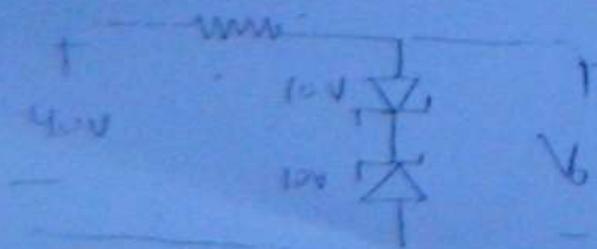


ZD is RB & conducting

$$V_o = V_{BR}$$

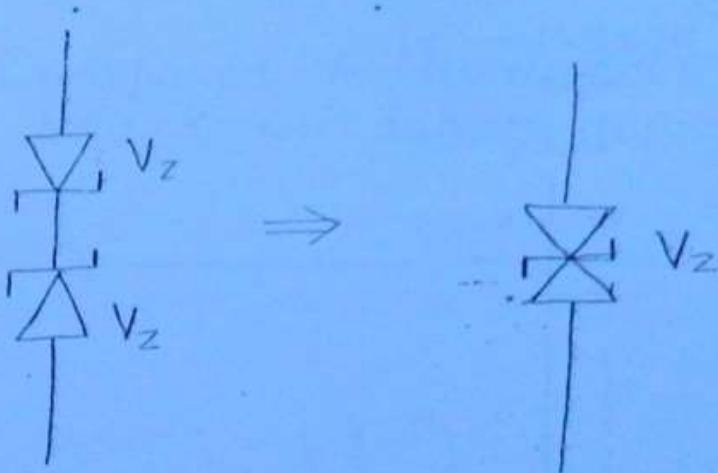
$$\boxed{V_o = 10V}$$

Sol

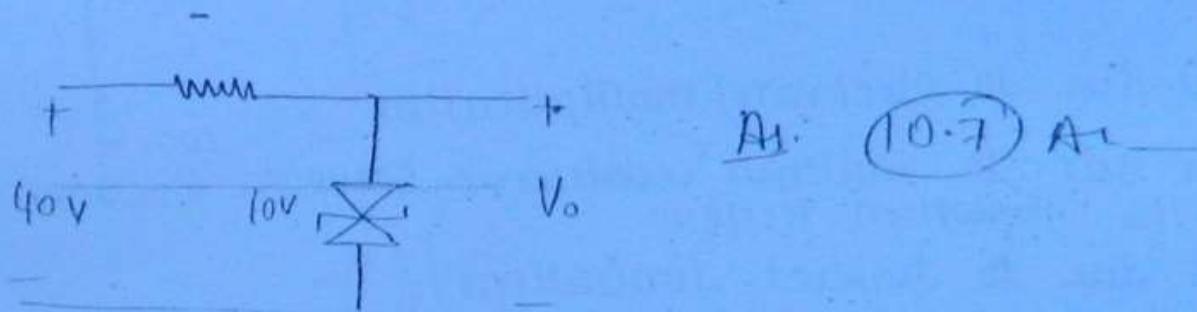


$$\begin{aligned}
 V_o &= V_V + V_{BR} \\
 &= 0.7 + 10 \\
 &= 10.7V
 \end{aligned}$$

→ When two identical Zener diode are connected back to back it can be replaced as given below.



Bias

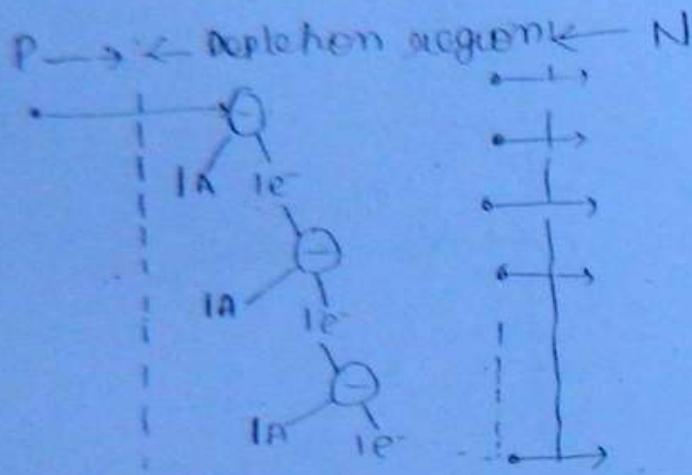


Zener Breakdown Phenomena →

- It is due to larger electric field intensity
- B. it is due to tearing off or rupturing of covalent bonds in the depletion layer
- Zener breakdown occurs for breakdown voltages below 6v
- Zener breakdown voltage decreases with the temperature (NTC)
- The temperature coefficient for zener breakdown voltage is negative

$$|E| = 2 \times 10^7 \text{ V/m}$$

Avalanche Breakdown Phenomena



- If is due to electron multiplication.
- If is due to multiple collisions between e^- and ions in the depletion layer.
- If is due to Impact ionization
- Avalanche breakdown occurs for breakdown voltages greater than 6V
- Avalanche breakdown voltage increases with temp (PTC)
- The temperature coefficient for avalanche breakdown voltage is +ve.

Ques → Impact ionization occurs in Zener diode

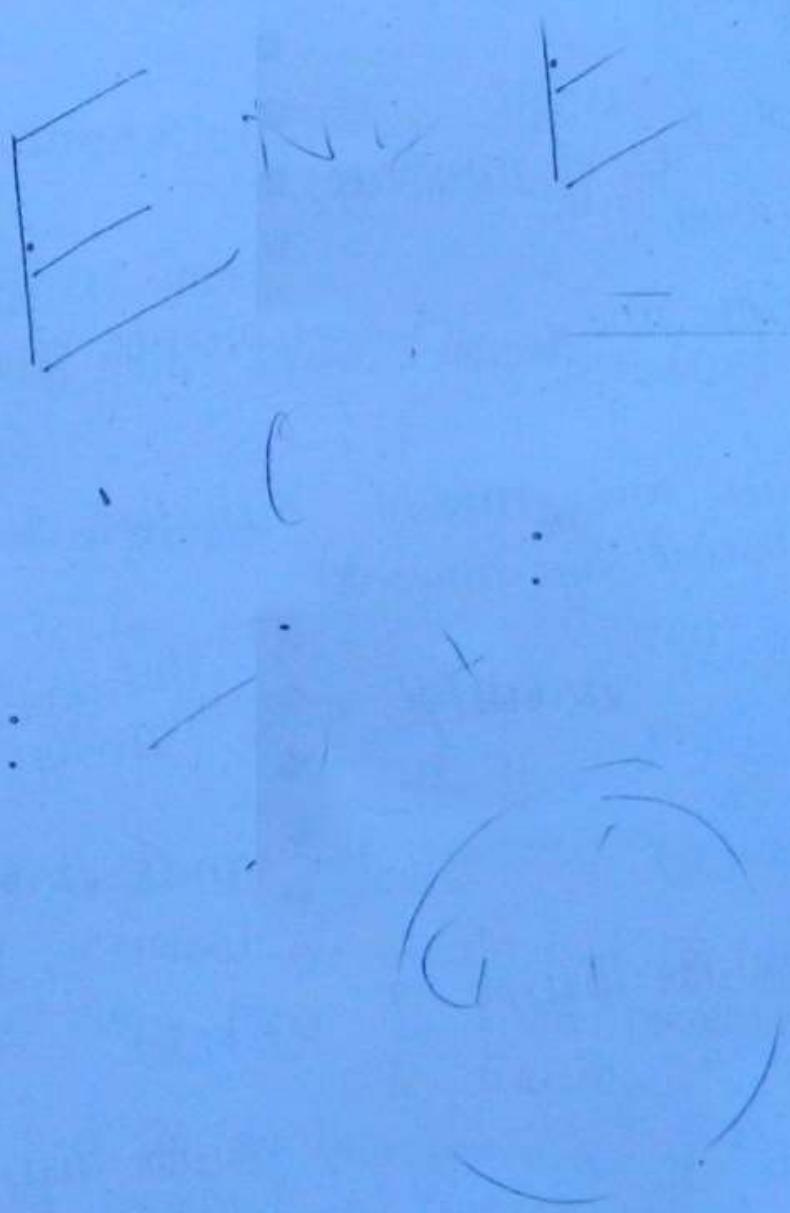
- Large flow of current through zener diode is due to flow of minority carriers.
- If the current passing through ZD is doubled then voltage drop across ZD is almost constant.
- In a highly doped Diode the breakdown is due to zener effect.

$$\downarrow V_{BR} \propto \frac{1}{\text{Doping}}$$

In a
a slightly doped diode, the breakdown is due
Avalanche effect

to

→ When compared to avalanche breakdown
Zener breakdown higher doping concentration.



FET (Field effect Transistor) :-

- Operation of FET :- Depends on electric field intensity produced in the channel.
- Voltage control device VCD
- Unipolar Device
- Majority carrier device
- No minority carrier
- less noisy device due to the absence of minority carriers.
- leakage currents are zero & therefore temp effect on the device is less
- Excellent thermal stability and this is due to the absence of minority carriers (leakage currents)
- FET is having better thermal stability than BJT
- High input resistance device ($> 1 \text{ M}\Omega$)
- Internal power consumption or power dissipation is less
- Fabricated only with Silicon.
- When compared to BJT FET is smaller in size and easier to fabricate.

- Offers a larger bandwidth and therefore reproduction of input signal is excellent.
- Gain bandwidth product is a constant.
- offset voltage is zero.
- FET is used as an excellent signal chopper and this is due to zero offset voltage.

Disadvantages of FET :-

- Offers smaller gain
- Low gain bandwidth product
- As compared to BJT FET is better device
- FET is an excellent amplifier at low frequency and high frequency.
- Source → It is source of majority carrier or it is terminal by which majority carrier will be entering into the device.
- Drain → In drains of majority carrier. It is the terminal by which majority carrier will be leaving the device.
- Gate → It is terminal which controls majority carriers moving from source to drain, or indirectly control the drain current.

channel → It is the space in between the two gates.

- BJT is asymmetrical device and therefore emitter and collector terminal cannot be practically interchange.
- FET is symmetrical device and therefore source and drain terminal can be interchange practically.

Classification of FET.

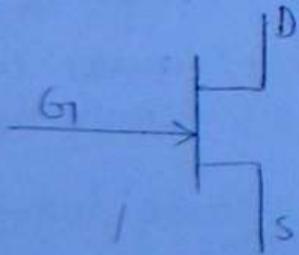
① JFET

(Junction field effect transistor).

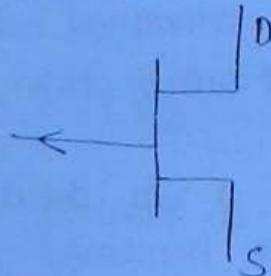
→ Three terminal Device (S, G & D)

→ $R \Rightarrow 10^4$ to $10^8 \Omega$.

→ (i) N-channel JFET. :-



(ii) p-channel JFET



② MOSFET (Metal oxide Semiconductor FET)
 or
IGFET (Insulated gate FET).
 or
MOST (Metal oxide semiconductor transistor)
 or
 (Metal oxide Silicon transistor)

- 4 terminal device [S, G, D and SUB (substrate)]
- $R_i = 10^{10}$ to $10^{15} \Omega$
- Highest input resistance device.

(i) Depletion MOSFET

→ There will be preexisting channel between source and drain region

→ Suitable to operate in depletion and enhancement mode

→ Also called DE-MOSFET



Depletion

n-channel

p-channel

n-channel

p-channel

(ii) Enhancement MOSFET

→ There is no preexisting channel; channel has to be created by applying proper gate to source voltage.

→ Suitable to operate only in the enhancement mode

→ E-only MOSFET

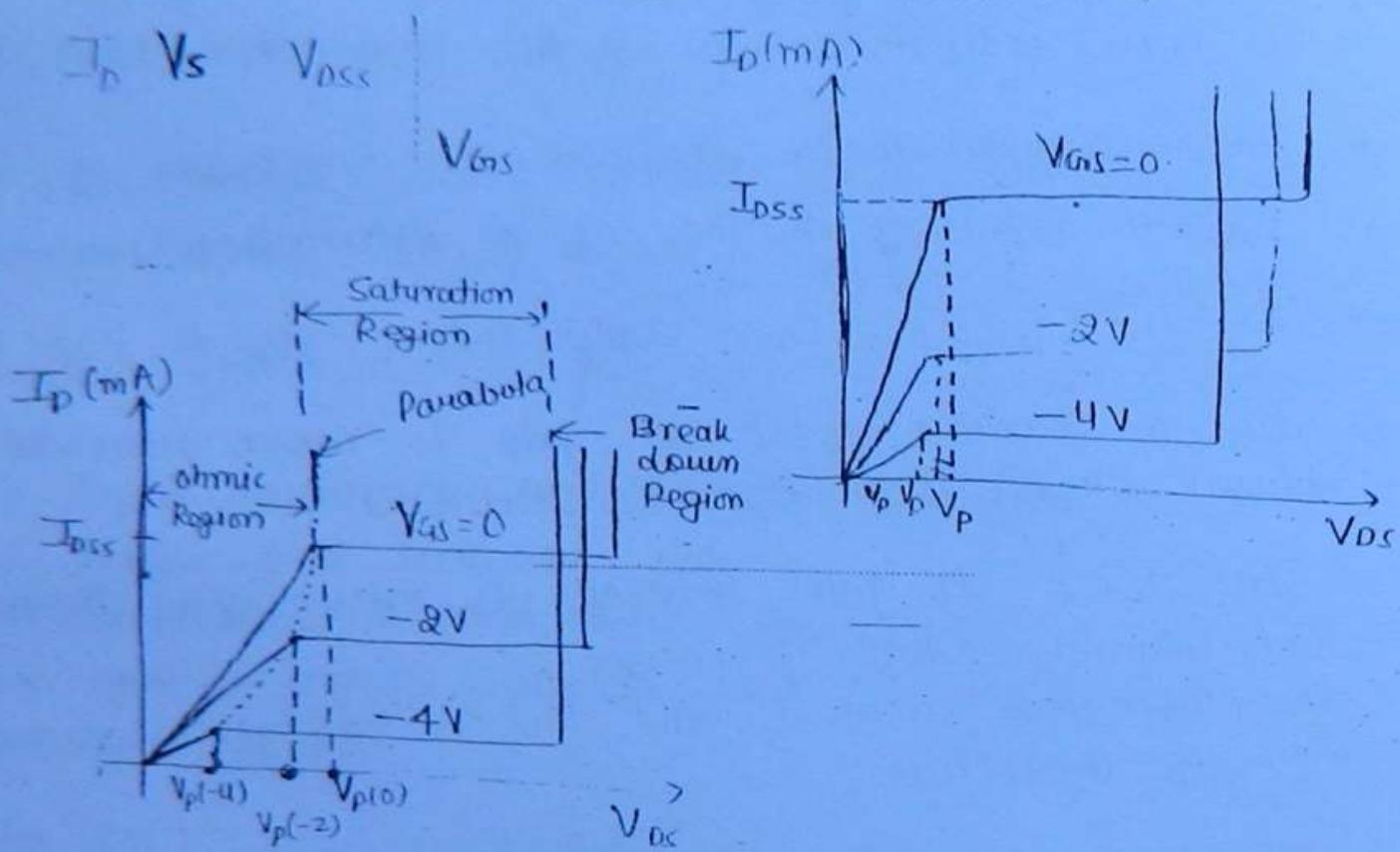


R_i of MOSFET $>$ R_i of FET

P_d of MOSFET $<$ P_d of FET

→ Step Q By keeping V_{GS} constant & by varying V_{DS}

Up characteristic or Drain characteristic



→ The drain characteristic of FET is called constant current characteristic (and it is similar to collector characteristic of common-base transistor)

→ FET can work as a constant current source

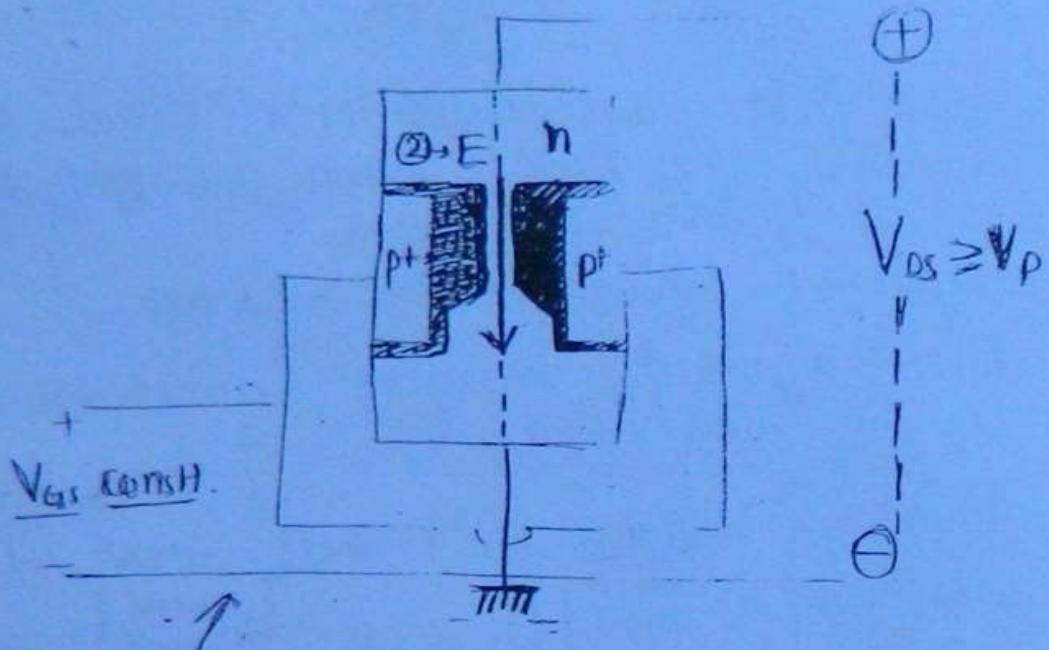
→ FET is voltage control current source (V_{GS})

→ Common base transistor is current control current source (CCCS)

→ Breakdown voltage is a function of V_{GS}

→ Breakdown voltage is maximum when V_{GS} is kept zero

- In FET breakdown is due to Avalanche effect.
- In ohmic region FET will work as a linear device i.e. as a resistor e.g. VVR (Voltage variable resistor) or VDR (Voltage dependent Resistor).
- In JFET channel behaves as a resistor.
- In the ohmic region by varying gate to source voltage, FET can work as a VVR.
- In the saturation region FET will work as:-
 - (1) As an amplifier
 - (2) As 'ON' switch
- Saturation region is also called current saturation region or pinch-off region.
- FET is generally operated in the saturation region.
- FET is generally operated with $V_{DS} > V_p$
- Pinch-off Voltage $\Rightarrow (V_p)$
- If I_D is the minimum value of I_D required where I_D enters into saturation.
- The maximum pinch off voltage is $V_p(0)$ or V_{D0} .
- Pinch off voltage is function of V_{GS} .
- In JFET when V_{GS} is applied, pinch off voltage decreases.
- The locus of $V_{D0}(0)$ corresponds to parabola.



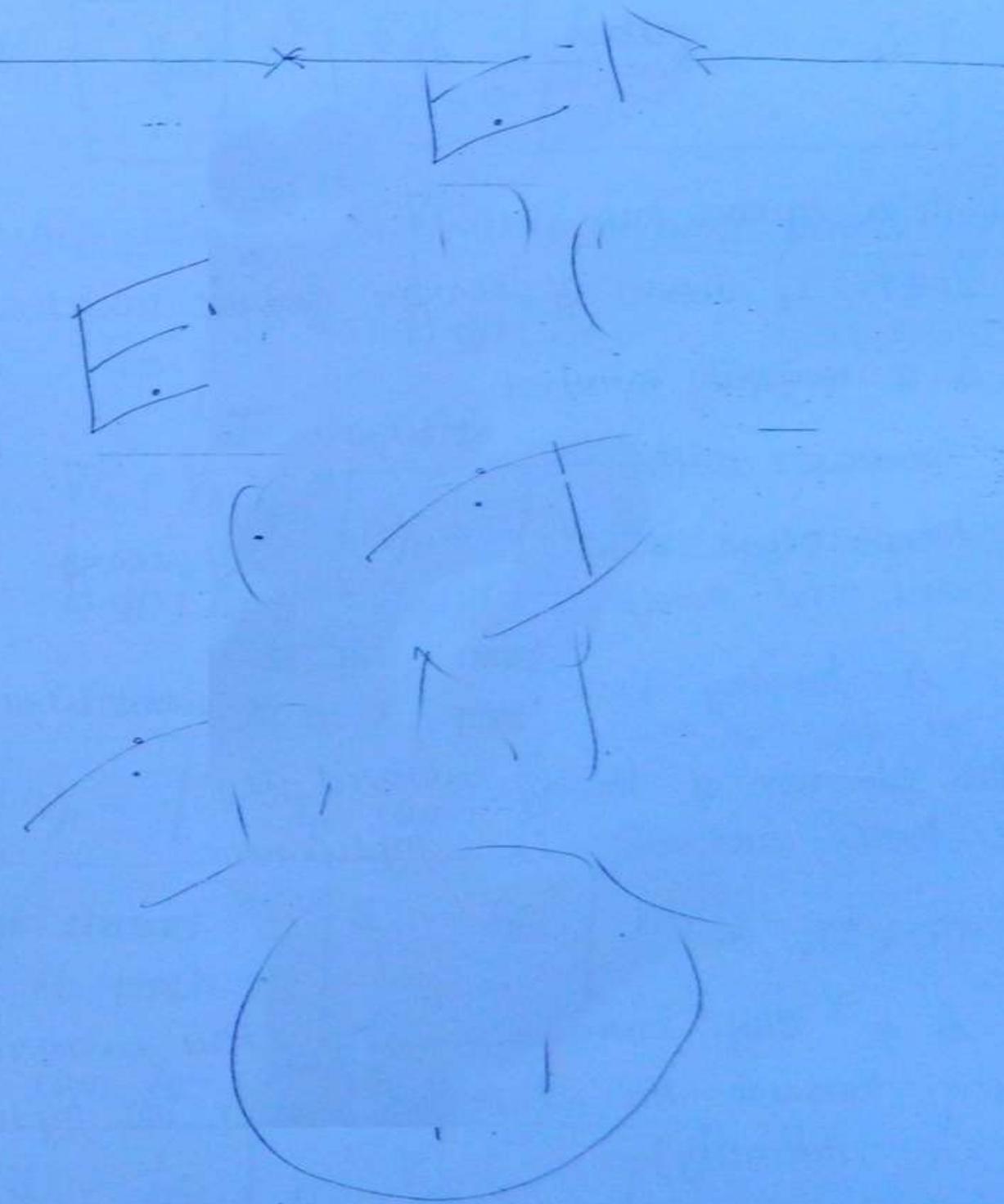
→ During pinch-off ① the two depletion layer will be coming extremely close but they will not keep touching with each other the positive ions in depletion layer of the n-channel JFET will produce a repulsive force & due to this repulsive force the two depletion layer will not being touching each other

→ ② During the pinch off as V_{ds} is increasing above V_p , the two depletion layer will be penetrating more into the channel and they will be try to touch each other but at the same time field intensity will become very large near the drain it is pointing towards the source due to field intensity the two depletion layer are unable to touch each other

During the pinch off the deplete channel width is narrow but drain voltage is very high and therefore K.E. of e- will be increasing hence drain is receiving maximum e- from channel and drain current ~~will~~ now also be increased

The e^- in the channel will now move towards
diam with high $K.E.$

The



Equation for Drain Current (I_D): -

In the saturation region of FET

$$\Rightarrow I_D = I_{DSS} \left[1 - \frac{V_{GS}}{V_P} \right]^2 \text{ Amp}$$

- FET is a square law device.
- In JFET I_D decreases as a parabolic variation with V_{GS} .
- I_D is a majority carrier current.
- I_D decreases with the temperature.
- As temperature increases mobility of charge carriers decreases and therefore I_D decreases.
- FET is having excellent thermal stability and this is due to:
 - (i) The absence of likeage current
 - (ii) As temp increases I_D decrease
- For 1°C , I_D decreases by 0.7% .
- I_D is a drift current (becoz this current is passing through the channel under the influence of EF intensity)

Equation for V_{GS} :

→ In the saturation region of FET:

$$\Rightarrow V_{GS} = V_P \left[1 - \sqrt{\frac{I_D}{I_{DSS}}} \right]$$

Relationship between V_{GS} cut-off and pinch-off voltage

$$I_D = I_{DSS} \left[1 - \frac{V_{GS}}{V_P} \right]^2$$

Let $V_{GS} \equiv V_P$, then $I_D = 0$.

↓ (condⁿ for cut-off)
 V_{GS} (cut off) [Pinch off voltage].

In n-channel JFET

$$\Rightarrow V_P = |V_{GS}(\text{cut off})|$$

→ In n-channel JFET V_{GS} cut-off is -8V .
then its pinch off voltage (V_P) is $\pm 8\text{V}$.

I_D can be written as

$$\Rightarrow I_D = I_{DSS} \left[1 - \frac{V_{GS}}{V_{GS}(\text{cut off})} \right]^2$$

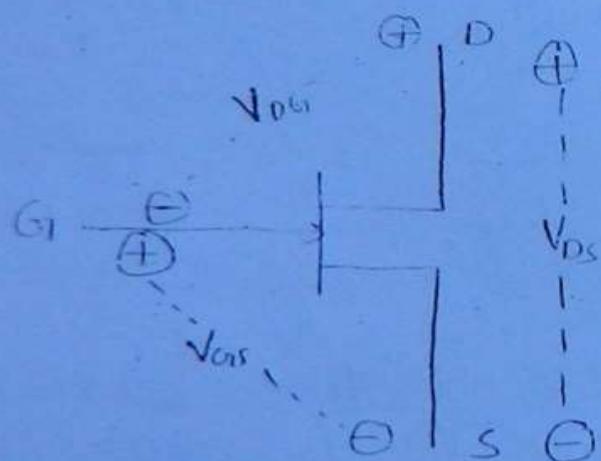
→ In the equation for I_D , the polarity of V_{GS} and V_P must have the same sign.

→ Pinch-off voltage is also define as the minimum V_{GS} where I_D is reduced to zero.

→ Pinch off voltage is defined as

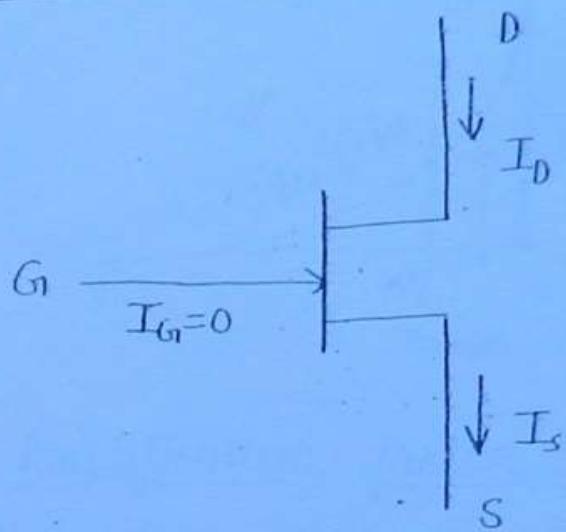
- (a) Minimum V_{GS} where I_D is zero. ✓
- (b) Minimum V_{GS} where I_D is max.
- (c) Maximum V_{GS} where I_D is max. ✓
- (d) Min. V_{GS} where I_D is zero.

Relationship between terminal Voltages of FET.



$$\Rightarrow V_{DS} = V_{DG_1} + V_{G_1S}$$

Source Current (I_s) \rightarrow



$$I_s \equiv I_D \quad \text{In magnitude}$$

FET Parameters \rightarrow

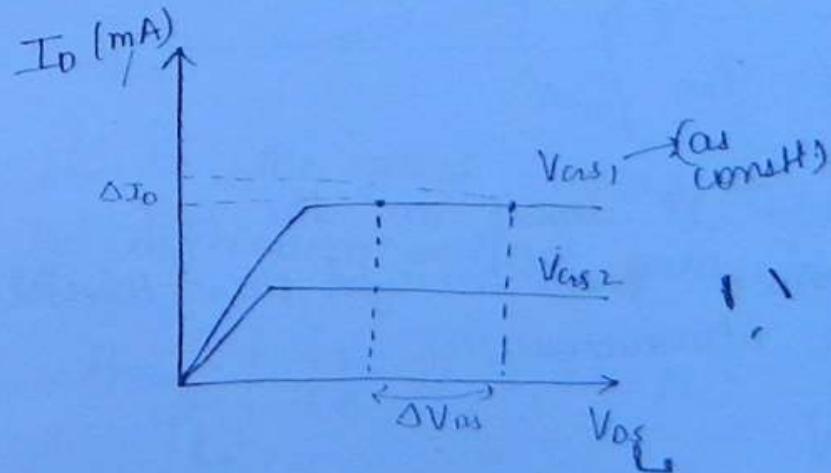
I_D is a f (V_{GS} and V_{DS}).

i) Drain Resistance $\rightarrow R_d$: \Rightarrow

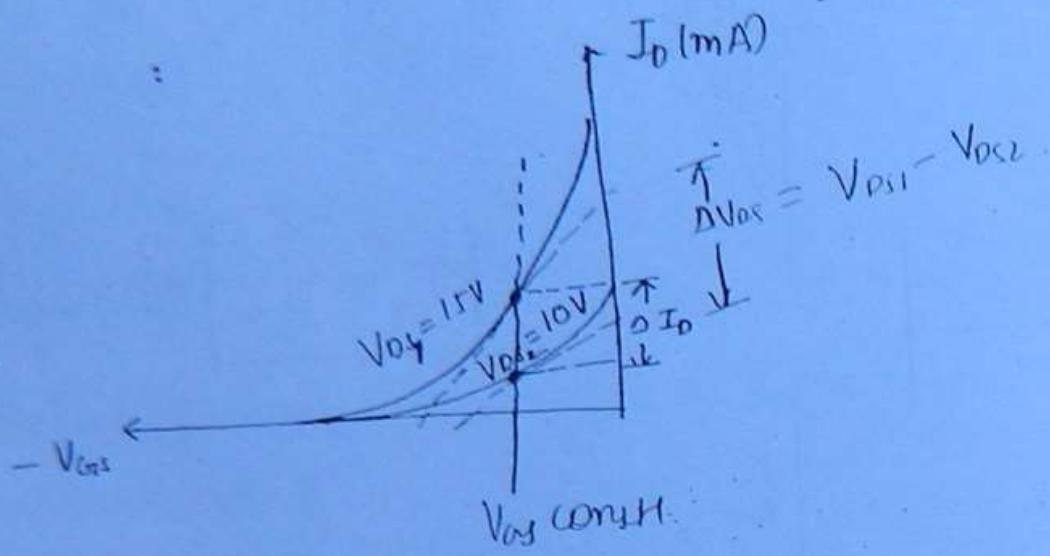
$$R_d = \frac{\Delta V_{DS}}{\Delta I_D} \quad |_{V_{GS} = \text{const}}$$

$R_d \rightarrow 10\text{k}\Omega$ to $600\text{k}\Omega$
 $T_{typ} \rightarrow 500\text{k}\Omega$

ii) R_d is graphically obtained from drain characteristics and transfer characteristic



[For conventional]



→ (b) Trans-conductance $\rightarrow g_m$ or mutual conductance

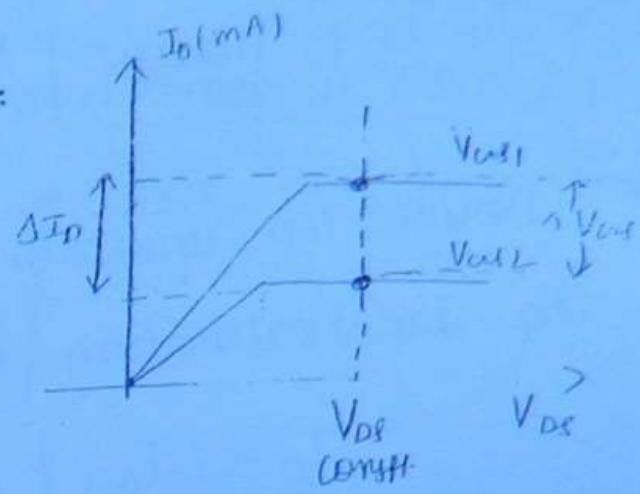
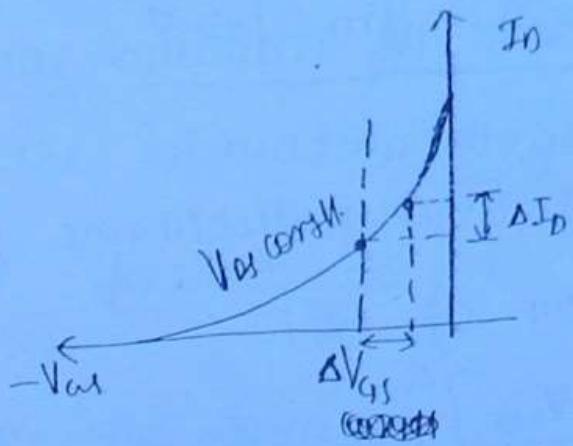
$$\Rightarrow \left| g = \frac{\partial I_D}{\partial V_{GS}} \right|_{V_{DS}} = \left| \frac{\Delta I_D}{\Delta V_{GS}} \right|_{V_{DS}}$$

	JFET	MOSFET	BJT	<u>Not</u> <u>imp</u> <u>only</u> <u>for</u> <u>ref.</u>
$g_m =$	0.1 ms to 10 ms	0.1 ms to 20 ms	50 ms to 600 ms	

In any device

$$\Rightarrow |Gain| A \propto g_m$$

- Since g_m is small, gain is small in the FET
- g_m is graphically obtained from transfer characteristics and also from drain characteristics



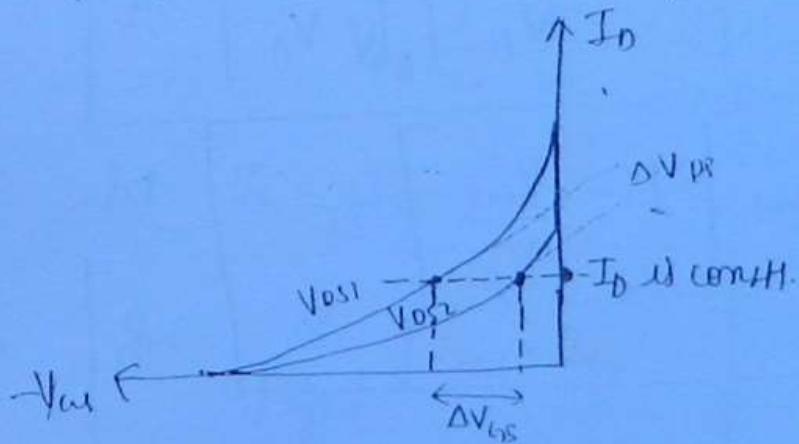
(c) Amplification factor $\Rightarrow (\mu)$

Also called voltage amplification factor.

$$\Rightarrow \boxed{\mu = -\left(\frac{\Delta V_{DS}}{\Delta V_{GS}}\right) \Big|_{I_D = \text{const.}}} \quad \mu \rightarrow 2.5 \text{ to } 150$$

μ is always positive value

μ is graphically obtained only from transfer characteristic



$\rightarrow \mu$ is the most important specification of the FET

\rightarrow The maximum voltage gain in the FET is given by

$$\rightarrow \mu = -\left(\frac{\partial V_{DS}}{\partial V_{GS}}\right) \Big|_{I_D} \quad \text{or} \quad \mu = -\frac{V_{DS}}{V_{GS}} \Big|_{I_D=0}$$

$$\rightarrow \text{In FET always } |u = \mathcal{H}_d \times g_m| \Rightarrow \star$$

Derive an equation for transconductance g_m

In the saturation region of FET

$$I_D = I_{DSS} \left[1 - \frac{V_{GS}}{V_P} \right]^2$$

By definition

$$g_m = \left. \frac{\partial I_D}{\partial V_{GS}} \right|_{V_{DS}}$$

Differentiating the above eqn w.r.t V_{GS} and keeping V_{DS} const.

$$\frac{\partial I_D}{\partial V_{GS}} = 2 I_{DSS} \left[1 - \frac{V_{GS}}{V_P} \right] \left[-\frac{1}{V_P} \right]$$

$$\Rightarrow \boxed{g_m = -\frac{2 I_{DSS}}{V_P} \left[1 - \frac{V_{GS}}{V_P} \right] \text{ or}}$$

General equation for transconductance in FET

In the saturation region of FET

$$g_m = -\frac{2 I_{DSS}}{V_P} \left[1 - \frac{V_{GS}}{V_P} \right] \quad \text{--- (1)}$$

From the equation of I_D .

$$1 - \frac{V_{GS}}{V_P} = \sqrt{\frac{I_D}{I_{DSS}}}$$

Substitute the value in eq (1).

$$g_m = -\frac{2 I_{DSS}}{V_P} \sqrt{\frac{I_D}{I_{DSS}}}$$

$$\Rightarrow \boxed{g_m = -\frac{2}{V_P} \sqrt{I_{DSS} \cdot I_D}}$$

Let $I_D = I_{DS}$

$$\Rightarrow \boxed{g_m = \frac{2}{|V_P|} \sqrt{I_{DSS} \cdot I_{DS}}}$$

If V_{GS} is kept zero in eq (1).

$$\Rightarrow \boxed{g_{m0} = -\frac{2 I_{DSS}}{V_P}} \rightarrow \frac{g_{m0}}{g_m} \text{ is the maximum value}$$

$\therefore g_{m0}$ occurs when $V_{GS} = 0$

$$\text{value of } g_m \text{ when } V_{GS} = 0 \Rightarrow \boxed{g_{m0} = -\frac{2 I_{DSS}}{V_P}}$$

when $V_{GS} = 0$ then $V_P \rightarrow V_{P0}$

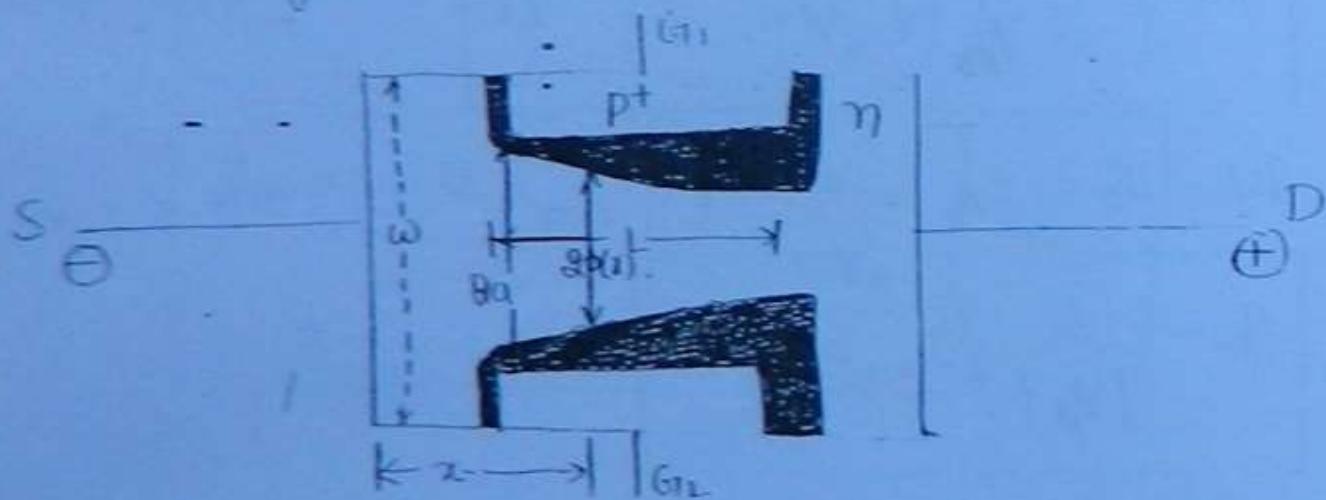
$$\Rightarrow V_{P0} = -\frac{2I_{DSS}}{g_m} \text{ Volts}$$

$$\Rightarrow g_m = g_{mo} \left[1 - \frac{V_{GS}}{V_P} \right] 25$$

$$\Rightarrow g_m = g_{mo} \sqrt{\frac{I_D}{I_{DSS}}} 25$$

General equation for JFET \rightarrow

Considering N-channel JFET



- L is the length of channel
- w is the width of sc bar.
- x is distance measured from source end
- $2a$ is channel width before the penetration of depletion layer.
- a is the half channel width before the penetration of depletion layer.
- $2b(x)$ is the channel width after the penetration of depletion layer measured at the distance x .
- In n-channel JFET
- The internal pinch-off voltage is given by :-

IES

$$V_P = \frac{q N_D a^2}{2\epsilon} \text{ volts}$$

→ Drain current

$$I_D = \beta b \cdot q N_D u_n \left[\frac{V_{DS}}{L/w} \right]$$

$\Rightarrow I_D \propto N_D$

$\Rightarrow I_D \propto V_{DS}$

$\Rightarrow I_D \propto \frac{w}{L}$

Drain to source resistance R_{ds}

$$\Rightarrow \boxed{R_{ds} = \frac{V_{DS}}{I_D}}$$

\downarrow
 $R_{d(ON)}$ (channel Resistance)

* $\boxed{R_{ds} = \frac{L}{2bq\mu_n N_D w}}$

* $\boxed{R_{d(ON)} \propto \frac{L}{w}}$ $R_{d(ON)} \rightarrow$ look to look

$$\boxed{V_{PO} = V_{bi} + V_p}$$

$$? V_{bi} = V_T \log_{10} \frac{N_A N_D}{n_i^2} \text{ volt}$$

[for gate exam]

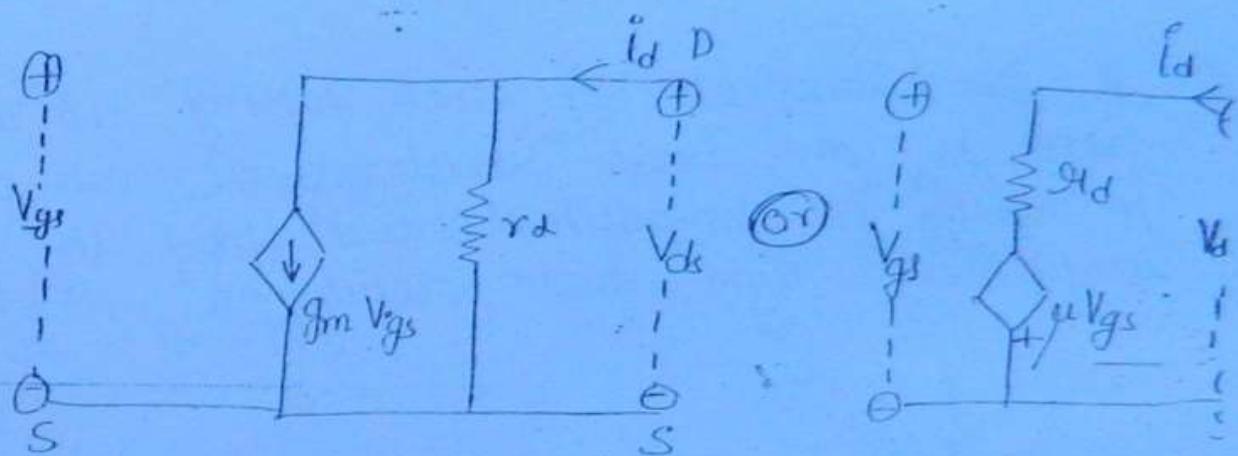
$R_{d(ON)}$ is important parameter in the switching application of FET.

Input resistance of BJT is less than $R_{d(ON)}$

$$\Rightarrow \boxed{R_i \text{ of BJT} < R_{d(ON)}}$$

Equivalent Circuit of FET (JFET & MOSFET) :-

- It is also called low frequency and small signal equivalent circuit of the FET.
- It is also called AC equivalent circuit.



- The above circuit is used to calculate voltage gain and output resistance of the FET amp.

Ques what is the maximum voltage gain obtain from FET having $g_m = 5 \text{ ms}$ & $R_d = 10 \text{ k}\Omega$. The max.

Soln $\mu = R_d \times g_m = 50$

Ques what is the maximum g_m of JFET having $I_{DS} = 2 \text{ mA}$ $V_P = -4 \text{ V}$

Soln $g_{m\max} = - \frac{2I_{DS}}{V_P} = - \frac{2 \times 2 \times 10^{-3}}{-4} = 4 \text{ mS}$

Ques Calculate the g_m of FET having $I_{DS} = 2 \text{ mA}$, $V_P = -4 \text{ V}$ and it is biased to operate at $V_{GS} = -1.8 \text{ V}$.

$$g_m = - \frac{2I_{DS}}{V_P} \left[1 + \frac{V_{GS}}{V_P} \right] = - \frac{2 \times 2 \times 10^{-3}}{-4} \left[1 + \frac{-1.8}{-4} \right]$$

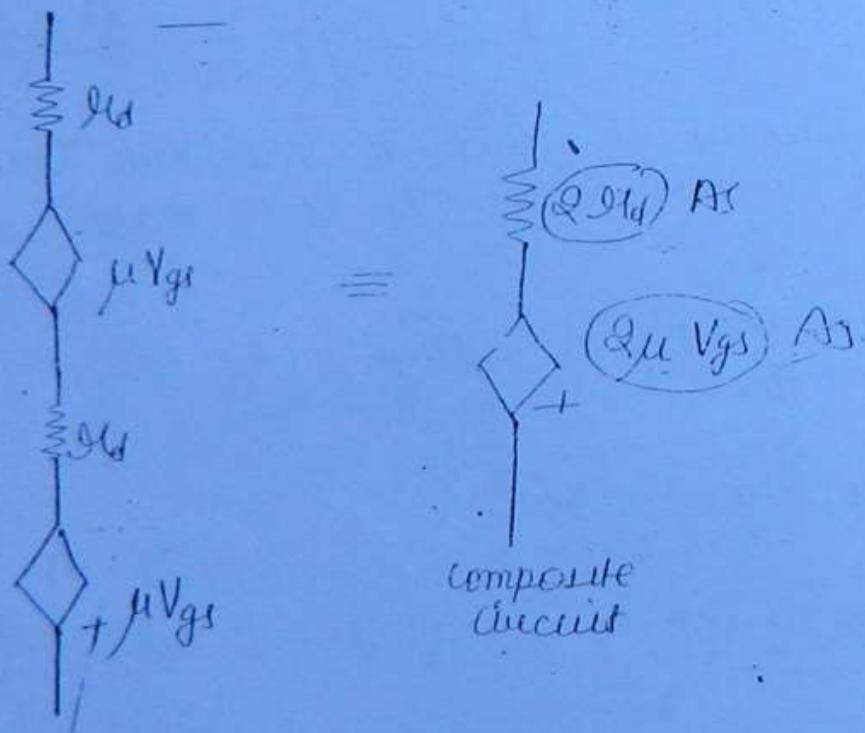
$| g_m = 3.2 \text{ mS} |$

Prob When gate source voltage of FET changes from -3V to -3.1V and I_D changes from 1.3mA to 1mA assuming other parameters to be constt. find g_m

$$g_m = \frac{\Delta I_D}{\Delta V_{GS}} = \frac{1.3 - 1}{-3.1 + 3} = 3 \text{ ms}$$

Prob If two identical FET each having an amplification factor μ and drain resistance R_d are connected in series for composite circuit find its amplification and drain resistance

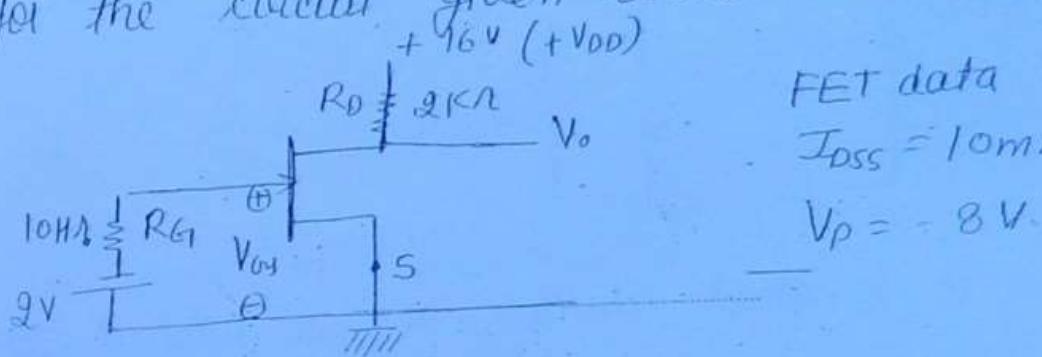
Soln



Prob if two identical FET each having a transconductance g_m and drain resistance r_d are connected in parallel for the composite circuit find there new values.

Ans $\frac{I_d}{2}$ and $2g_m$.

Prob for the circuit given below calculate V_{ds} , I_D & V_o



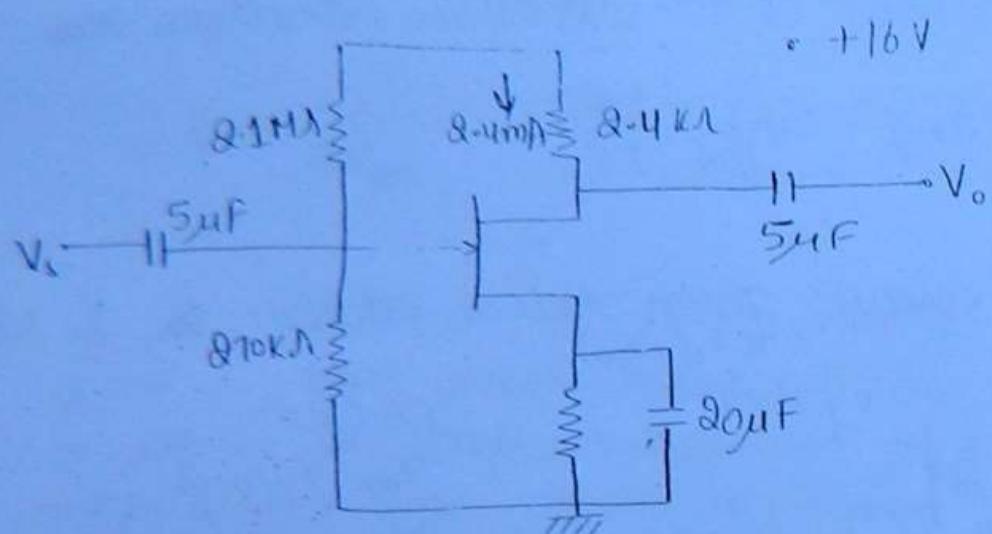
since $I_{G1} = 0$

$$V_{GS} = -2\text{V}$$

$$\begin{aligned} \therefore I_D &= I_{DSS} \left[1 - \frac{V_{GS}}{V_p} \right]^2 \\ &= 10 \times 10^{-3} \left[1 - \left[\frac{-2}{-8} \right] \right]^2 = 5.625\text{mA} \end{aligned}$$

$$\begin{aligned} V_{DS} &= V_o = V_{DD} - I_D R_D \\ &= 16 - [5.625 \times 2^k] \\ &= 4.75\text{V} \end{aligned}$$

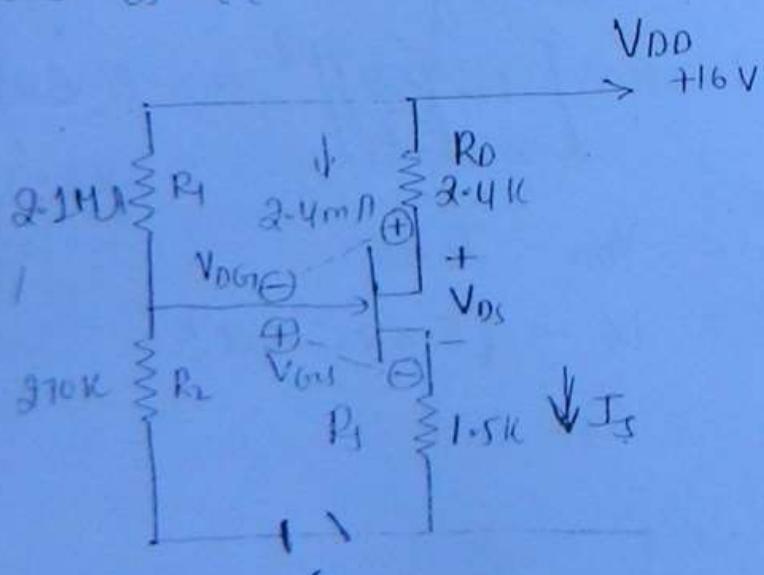
Ques Calculate V_{ou} , V_{D_s} & V_{D_G} :



→ It is a potential divider or self biased ckt.

V_s = Signal voltage

→ Terminal voltages are calculated under DC analysis or under biasing cond'n i.e. with zero AC signal supply and therefore all capacitors in the ckt will be treated as OC.



→ By using approximate analysis i.e. by O.C. the gate

$$\begin{aligned} V_{R2} &= \frac{V_{DD} R_2}{R_1 + R_2} \\ &= \frac{16 \times 270K}{2.1M + 270K} \end{aligned}$$

$$V_{R2} = 1.82 \text{ VDC}$$

$$V_{R2} = V_{GDS} + I_s R_S$$

$$1.82 = V_{GDS} + 2.4 \text{ m} \times 1.5 \text{ k}$$

$$\Rightarrow \boxed{V_{GDS} = -1.78 \text{ V}}$$

$$V_{DS} = V_{DD} - I_D (R_D + R_S)$$

$$V_{DS} = 16 - 2.4 \text{ m} [2.4 \text{ k} + 1.5 \text{ k}]$$

$$\boxed{V_{DS} = 6.64 \text{ V}} \quad \text{Ans}$$

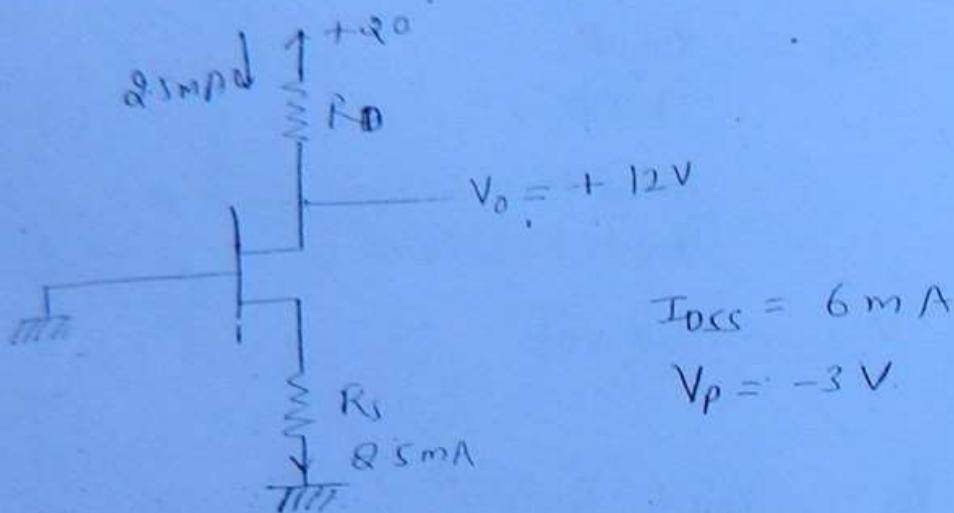
$$V_{DS} = V_{DD} + V_{GDS}$$

$$6.64 = V_{DD} + (-1.78)$$

$$\boxed{V_{DD} = 8.42 \text{ V}} \quad \text{Ans}$$

18

Ques find R_D & R_S \rightarrow



Soln

$$R_D = \frac{(20 - 12)}{25} = \frac{80}{25 \times 10^3} = \frac{80 \times 1000}{25}$$
$$= 3200 \Omega = 3.2 k\Omega$$

$$V_{GS} = V_P \left[1 - \sqrt{\frac{I_P}{I_{DSS}}} \right]$$

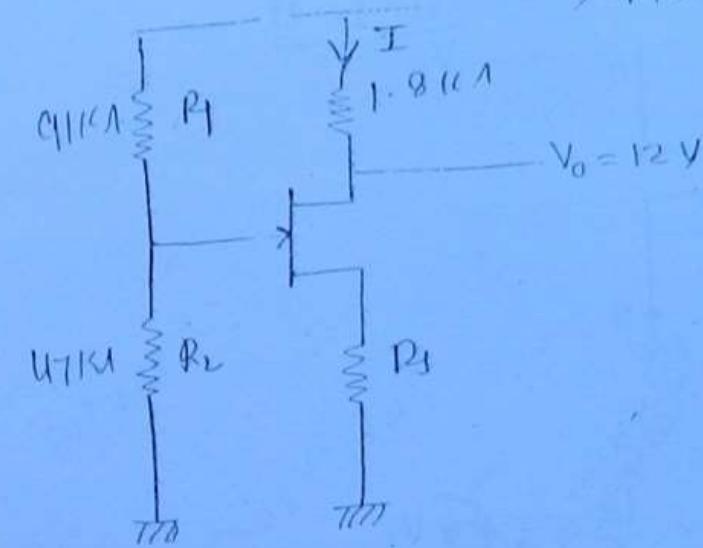
$$V_{GS} = -1.06V$$

$$V_{DS} = V_{GS} + I_S R_S$$

$$0 = -1.06 + (2.5m) (R_S)$$

$$\left| \frac{1.06}{2.5m} \right| = R_S$$
$$\boxed{R_S = 424 \Omega}$$

Prob if $V_{GS} = -2V$, find R_s > +16V



$$I = \frac{16 - 12}{1.8} = \frac{40}{1.8 \times 10^3}$$

$$I = 2.22 \text{ mA}$$

$\approx 10\text{m}$

$$V_{R2} = \frac{47 \times 10^3 \times 16}{91 + 47}$$

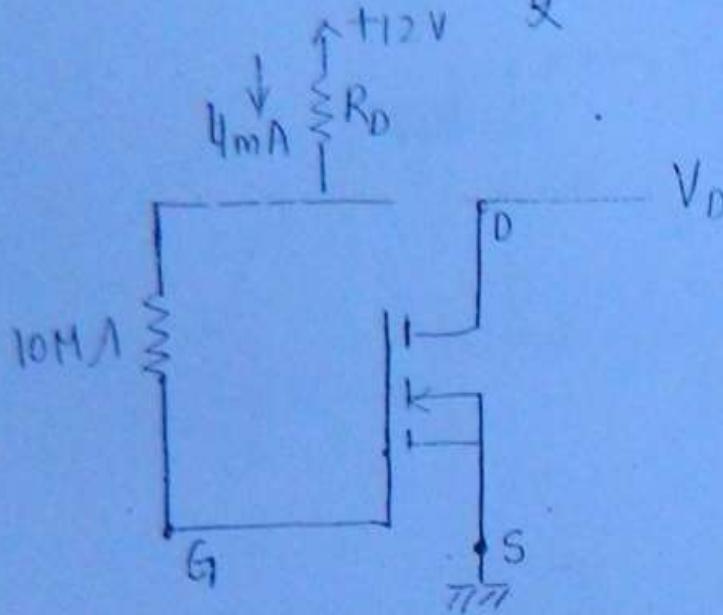
$$V_{R2} = \frac{47 \times 16 \times 10^3}{13.8 \times 10^3} = 5.44 \text{ V}$$

$$V_g = V_{GS} + I_s R_s$$

$$5.44 = -2V + 2.22 \text{ m A} (R_s)$$

$$\Rightarrow R_s = 3.35 \text{ k}\Omega$$

Prob Given that $i_D = \frac{V_{DD}}{R}$, find R_D ..



$$V_D = \frac{V_{DD}}{2} = \frac{12}{2} = 6V$$

$$R_D = \frac{12 - 6}{I_m} = 1.5 k\Omega$$

END
OF
DAY

B·J·T

BIPOLAR
JUNCTION
TRANSISTER

BJT (Bipolar junction transistor) :-

Emitter	E	Highly doped	medium space
Base	B	lightly	smaller
Collector	C	med.	largest

A bipolar device having both majority and minority carriers.

Invented by William Shockley (1947)
Bardeen
Brattain

Current Control device (CCD)

low input res. device

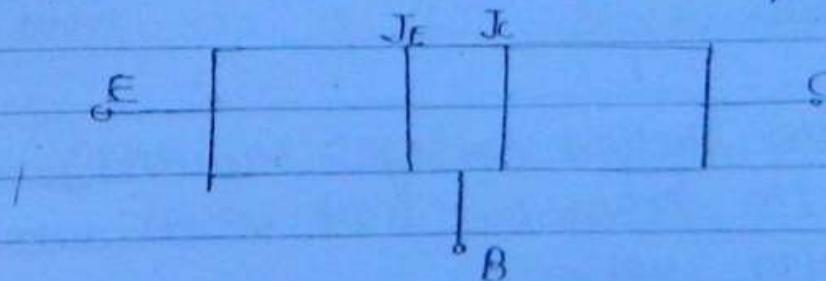
when compare to FET power consumption is more.

Noisy device, due to the presence of minority carrier.

Leakage Current - are existing due to the presence of minority carrier.

Temp. Sensitive device

- * Emitter is lightly doped to inject the majority carrier into the base.
- * Emitter is provided with medium area.
- * Base is lightly doped to reduce the recombination.
- * Transistor action take place in the base
- * Base is provided with smallest area to reduce the transit time
transit time - time taken by charge carriers to move from E to C
- * Collector is moderately doped
- * Collector is provided with largest area to overcome heat dissipation.



$J_E \rightarrow E + B$

$J_C \rightarrow C + B$

J_E	J_C		
1 RB	RB	Cutoff Region or OFF	<p>$I_C = 0$</p> <p>OC switch</p> <p>OFF State</p>
2 FB	FB	Saturation Region or (SAT)	<p>$I_C = \text{max}$</p> <p>SC switch</p> <p>ON state</p>

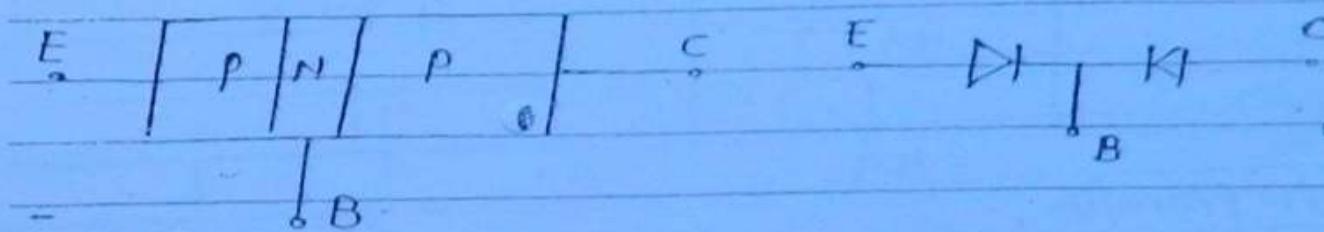
NOTE :- \rightarrow If emitter junction Voltage $>$ Collector Junction Voltage the transistor is under forward saturation region.

\rightarrow If collector Junction Voltage $>$ emitter Junction Voltage the transistor is in under reverse saturation region.

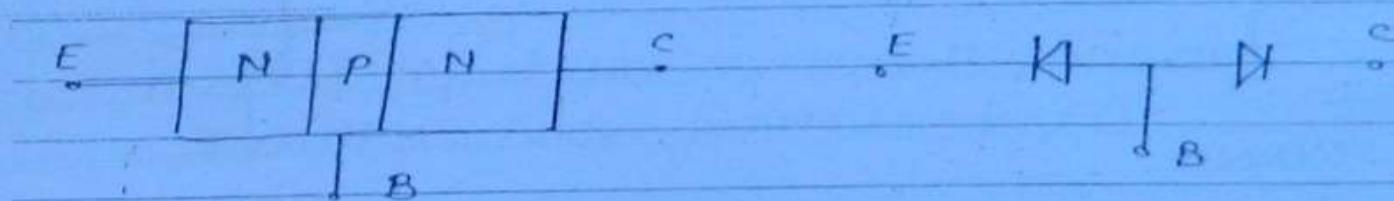
3	FB	RB	Active Region (forward active Region) (Working as amplifier) gain is negligible (never operation in this region)
4	RB	FB	

Diode equivalent circuit of BJT :-

PNP transistor :-



NPN transistor :-

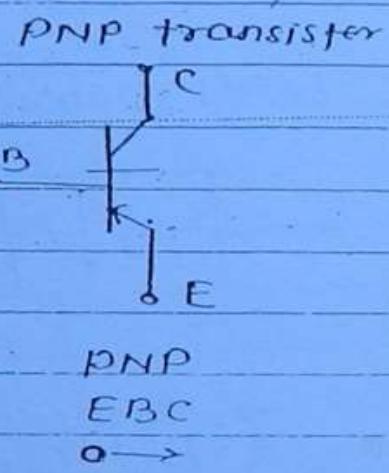
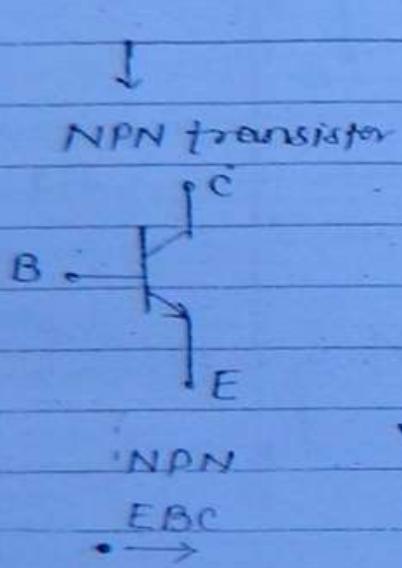


- * A BJT can be represented by two diodes are connected back to back.
- * When two diodes are connected as shown in the equivalent ckt, it will not work as a BJT because.
 - i) There is no bonding force in bet' the two diodes
 - ii) The base width will become very large so that no charge carrier will be reaching the collector.

Ques 10

NOTE - The transistor can work as a switch when operated both in the Cutoff and Saturation Region.

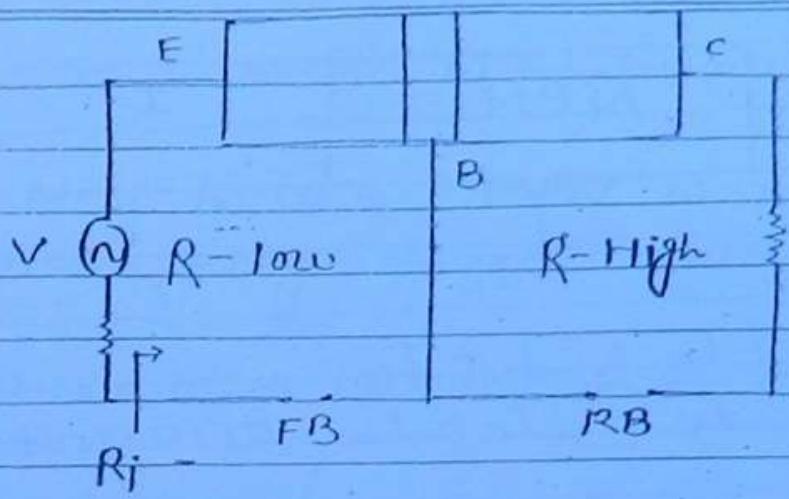
BJT



- * In NPN transistor Current is predominantly (mainly) by the flow of e^-
- * In PNP transistor Current is mainly due to both
- * NPN transistor is superior to PNP transistor because $l_{n2} > l_{p1}$

Q. In a transistor, arranging the doping level of E, B, C in ascending order to the current sequence is B, C, E

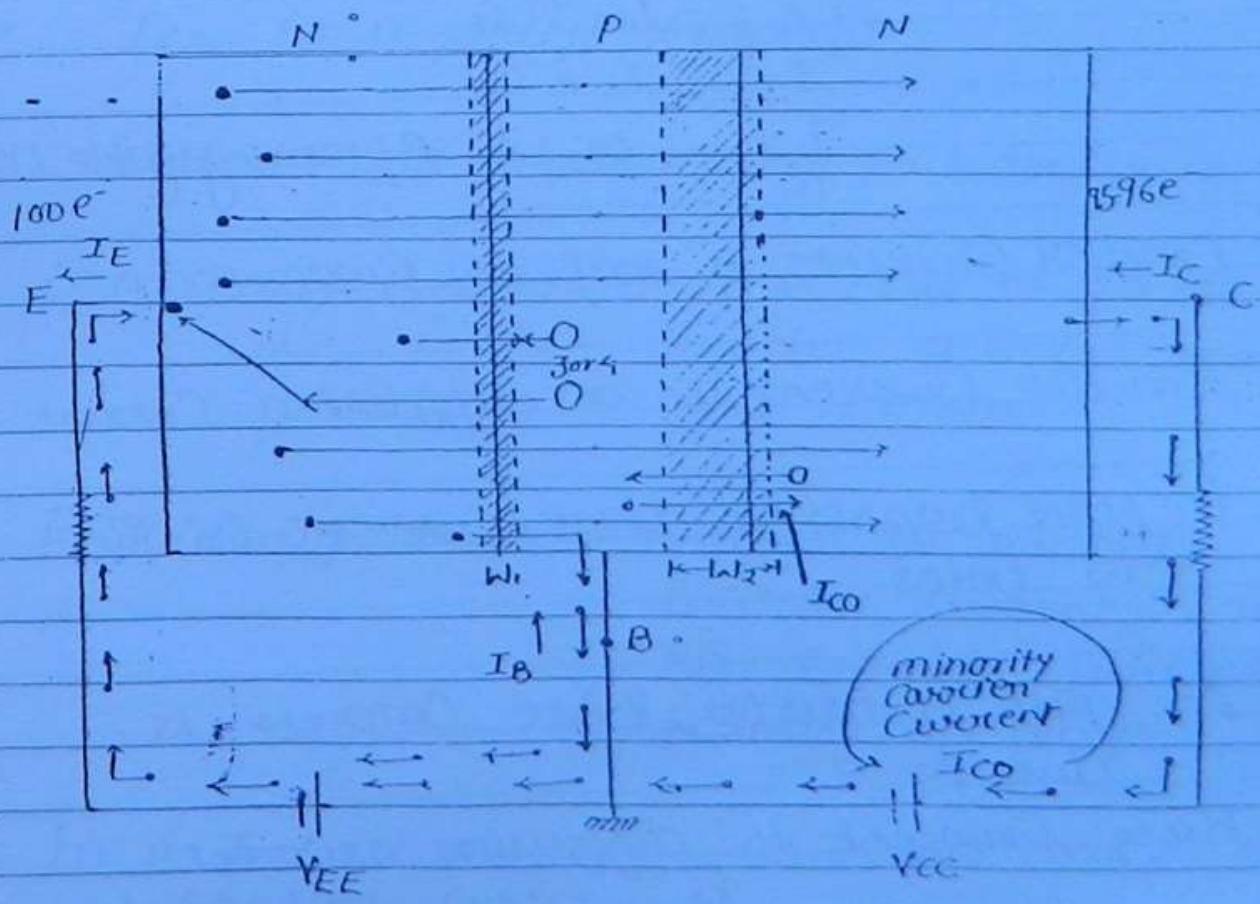
Q. In Ti transistor arranging the physical dimension of E, B, C in the descending order or decreasing order the current seq. is C, E, B

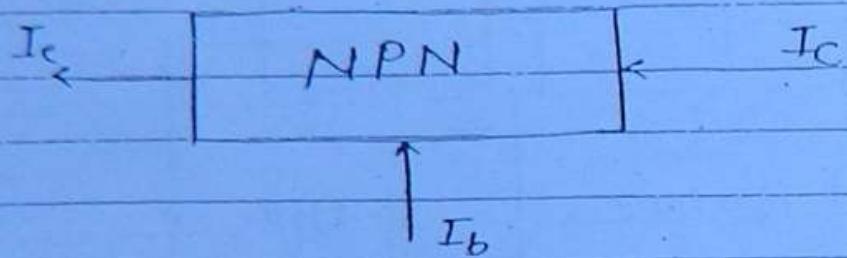


TRANSFER + RESISTOR = TRANSISTOR

In BJT input res. is small because
emitter base junction is FB

Operation of NPN transistor under active Region



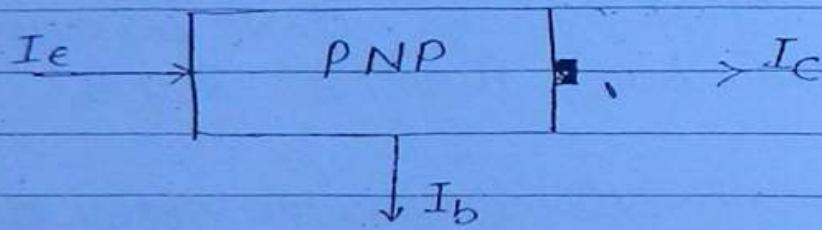


$$-I_E = I_C + I_B$$

$I_E = I_C + I_B$ in magnitude

I_B is very small, negligible (μA)

$$[I \approx I_E]$$



$$I_E = -I_C + I_B$$

$$I_E = I_C + I_B$$

$$[I_C \approx |I_E|] \text{ After negligible } I_B$$

- * Emitter Current is majority Current.
- * Emitter Current is a diffusion Current.
- * In NPN transistor, base Current is due to holes.
- * In PNP transistor, base Current is due to e^- .
- * Base Current is diffusion Current.

- * Base Current is a recombination current.
- * In NPN Tr base Current is due to the no holes getting recombine with the incoming e.
- * Recombination Current flow only in BJT
- * Tr action take place in the base region.
- * The movement or flow of charge carrier betⁿ base and collector in the Tr is due to diffusion of minority carrier.
- * Collector Current is a diffusion current
- * I_{CO} is a drift current
- * Collector is made up of few components.
 - i) majority Current \rightarrow It is due to 95-96 emitter electrons reaching the collector
 - ii) Minority Current \rightarrow It is the minority carrier current in the RB Colleter Junction because of temp.
- * In a Tr all the major currents are diffusion currents.

In a Tr there are three Current Components

- i) diffusion Current
- ii) drift Current
- iii) recombination Current

- Q) In a Tr recombination occurs
- a only into the emitter
 - b in the emitter and base
 - c only in the base
 - d In emitter base and collector Jn.

I_{CO} :-

Collector reverse saturation Current
or Collector leakage Current
or minority carrier Current
or thermally generated Current

GeTr SiTr

I_{CO} mA mA

- * I_{CO} is highly sensitive to temp.
- * I_{CO} is double for every 10°C
- * for 1°C I_{CO} approx increases by 7%
- * I_{CO} is independent of collector junction Voltage
- * I_{CO} is a drift Current.

$$I_{CO(T_2)} = I_{CO(T_1)} \left[2^{\frac{T_2 - T_1}{10}} \right]$$

General eqⁿ for Collector Current (I_C) :-

In the active region of Tr

$$I_C = \beta I_B + (1+\beta) I_{CO}$$

↓ ↓
 majority minority carrier
 carrier current current

$$I_C \approx \beta I_B$$

Base width of a Tr :-

- * In a Tr always the base width must be less than diffusion length of the Charge Carrier (minority carrier moving from base to collector)

$$[W_B < L]$$

| In the NPN Tr

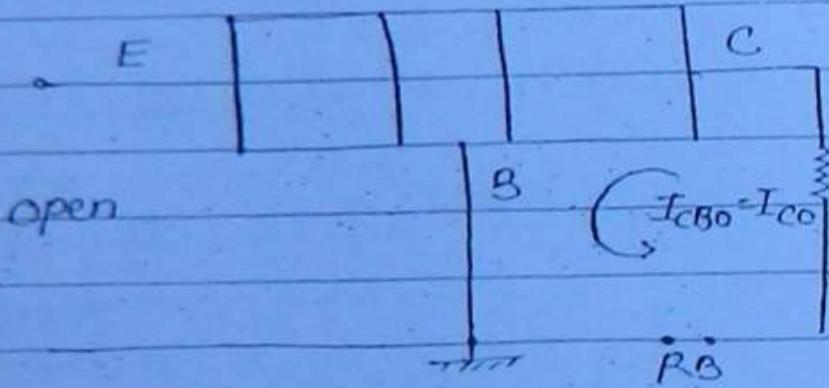
$$[W_B < L_n]$$

$$[W_B < \sqrt{D_n t_n}]$$

- * If the above condition is satisfied the Tr action will take place in the transistor.

I_{CBO} :-

It is the leakage current passing from collector to base with a emitter open circuited.



$I_{CBO} = I_{CO}$ Collector Reverse Saturation Current

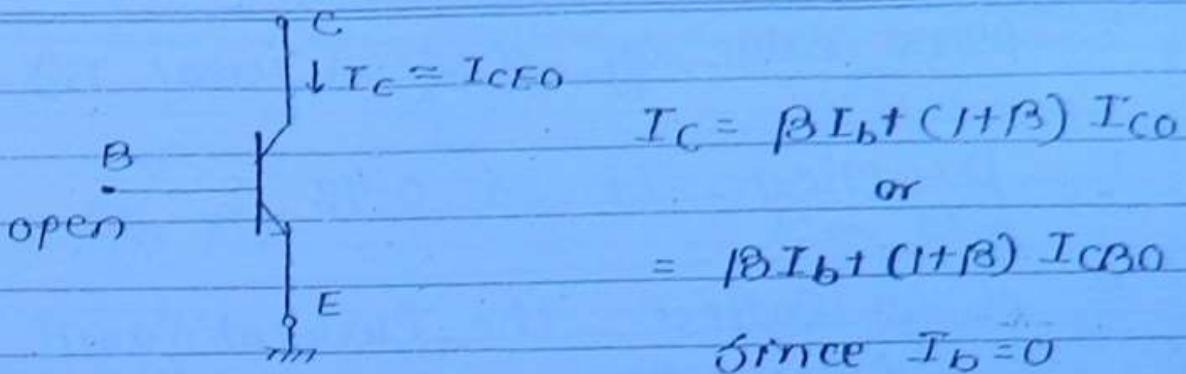
* I_{CBO} is also called emitter cutoff current.

I_{CEO} :-

It is the leakage current passing from collector to emitter with base open circuited.

Also called base cutoff current

If a Tr working under active region and if base terminal is suddenly open. The current in the Tr is I_{CEO}

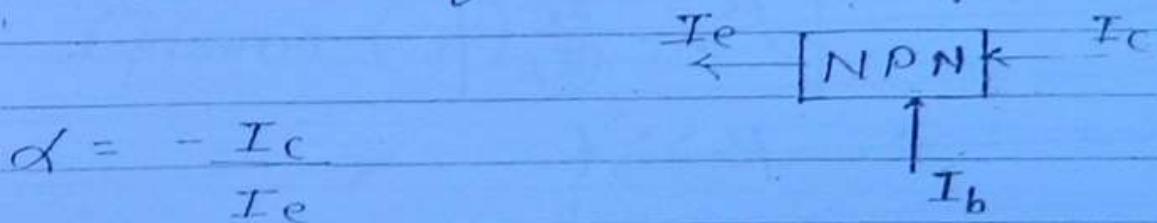


$$I_C \approx I_{CEO}$$

Imp

$$\boxed{I_{CEO} = (1+\beta) I_{CBO}}$$

Alpha (α) of the Tr :-



Since I_C & I_E have opp. sign

α is negative

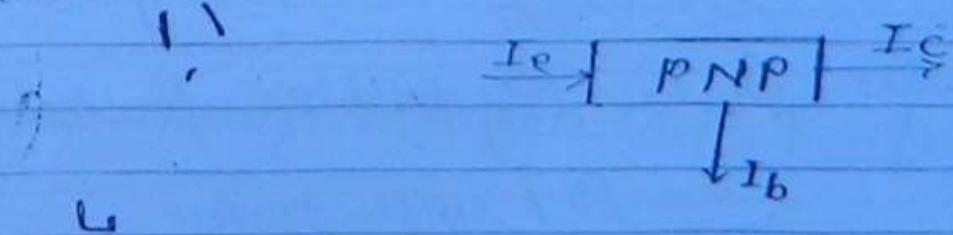
$$\left| \alpha = \left| \frac{I_C}{I_E} \right| \right|$$

∴ emitter current is slightly greater than collector current

$$\alpha \approx 1$$

α is slightly < 1

Typical value = 0.98



* Max value of $\alpha = 1$ (ideal T_r)

* practical T_r $\alpha = 0.98$

* α is called the current gain of common base T_r

$$\Rightarrow \alpha = \frac{\beta}{\beta + 1}$$

Beta [β] of the T_r :-

$$\beta = \frac{I_c}{I_b}$$

• $\beta \gg 1$

• $\beta_{typ} = 49$

β in terms of α is :-

$$\beta = \frac{\alpha}{1-\alpha}$$

* β is the most important specification of the T_r

* In Ge T_r β doubles for every $50^\circ C$

* In Si T_r β doubles for every $75^\circ C$

$\beta \uparrow$ with temp.

* β is the current gain of common emitter

$$\beta \downarrow$$

$\beta_{\text{or } \beta_{\text{dc}}}$	$\beta_{\text{or } \beta_{\text{ac}}}$
or h_{FE}	or h_{FE}
$= \frac{I_C}{I_B}$	$= \frac{\partial I_C}{\partial I_B}$
	$= \frac{\Delta I_C}{\Delta I_B}$

$$\beta_{\text{dc}} > \beta_{\text{ac}}$$

or $h_{FE} > h_{FE}$

Gamma (γ) of the Tr :-

$$\gamma = -\frac{I_e}{I_b}$$

Since I_e & I_b have opp sign; γ is

$$\boxed{\gamma = \left| \frac{I_e}{I_b} \right|}$$

$$\boxed{\gamma = \beta + 1}$$

\Rightarrow Typical value - 50

* γ is for the current gain of Common Collector Tr (CC Tr)

Relationship between α, β, γ of the Tr

$$\boxed{\gamma = 1 + \beta = \frac{1}{1 - \alpha}}$$

In a BJT various current gain are α , β & γ and arranged in the ascending order in the seqⁿ of α, β, γ .

Emitter Current in terms of base current:-

$$I_e = I_c + I_b$$

$$\text{but } I_c \approx \beta I_b$$

$$I_e \approx (1 + \beta) I_b$$

$$\text{or } I_e \approx \frac{I_b}{1 - \alpha}$$

Effect of temp on Collector Current (I_c) :-

$$I_c = \beta I_b + (1 + \beta) I_{co}$$

As $T \uparrow$, $I_{co} \uparrow$

& $\beta \uparrow$

$$I_c \uparrow \text{ with } T$$

psu

* Collector Current increases with temp. BJT has +ve temp. coefficient (PTC)

Standard eqn for I_E :-

$$I_E \approx I_{C0} e^{\frac{V_{BE}}{nV_T}}$$

$$\left. \begin{array}{l} \\ + \\ V_{BE} \end{array} \right\}$$

$$\left[\because I_f \approx I_0 e^{\frac{V_{BE}}{nV_T}} \right]$$

In a Tr emitter Current is the forward current of emitter diode.

Base emitter voltage of the Tr :-

$$V_{BE} < 1V$$

for Ge Tr $V_{BE} = 0.1V$ to $0.5V$ typ $0.2V$

for Si Tr $V_{BE} = 0.6V$ to $0.9V$ typ $0.7V$

$$\left[\downarrow V_{BE} \approx nV_T \log \left(\frac{I_E}{I_{C0}} \right) \right]$$

$\therefore V_{BE} \downarrow$ with T

Imp

for $1^\circ C$ $V_{BE} \downarrow$ by $2.3mV$

At room temp

In NPN Tr

	Ge Tr	Si Tr
V_{BE} (cutin)	0.1V	0.6V
V_{BE} (active)	0.2V	0.7V
V_{BE} (sat)	0.3V	0.8V

Drift Tr and diffusion Tr :-

In a diffusion Tr base current is made only with diffusion current.

A normal Tr is a diffusion Tr.

In a drift Tr base current is made of both drift current & diffusion current.

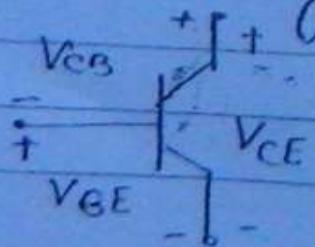
Recombination Agent :-

The best recombination agent is hole.

Recombination agent use to increase the recombination in the base region.

In a Speeral Tr a small quantity of hole is introduced into the base region. They will formed in local center. They will be working as TRAP the e- so that the recombination will be increased in the base region.

Terminal Voltage of Tr :-

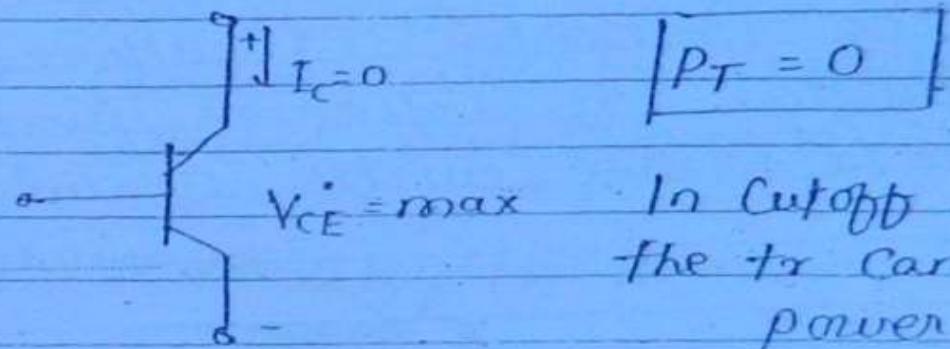


$$V_{CE} = V_{CB} + V_{BE}$$

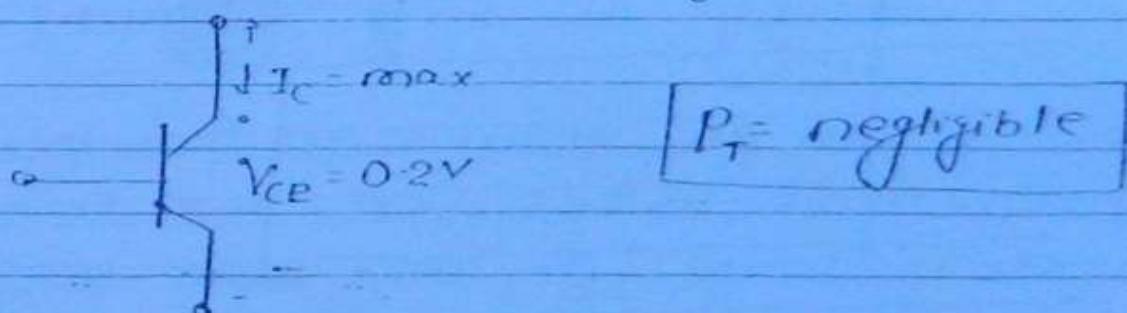
Power classification of a T_r (P_T):-

$$P_T = |I_C| V_{CE} \quad \text{watts}$$

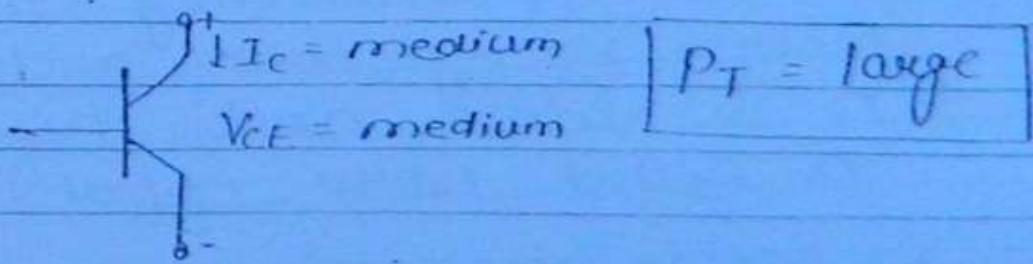
In the cutoff region:-



In the Saturation Region :- .



In the active Region:-



- * The tr will consuming max power when operated in the active region.
- * The tr cannot consume any power when operated in cutoff region.

IMP

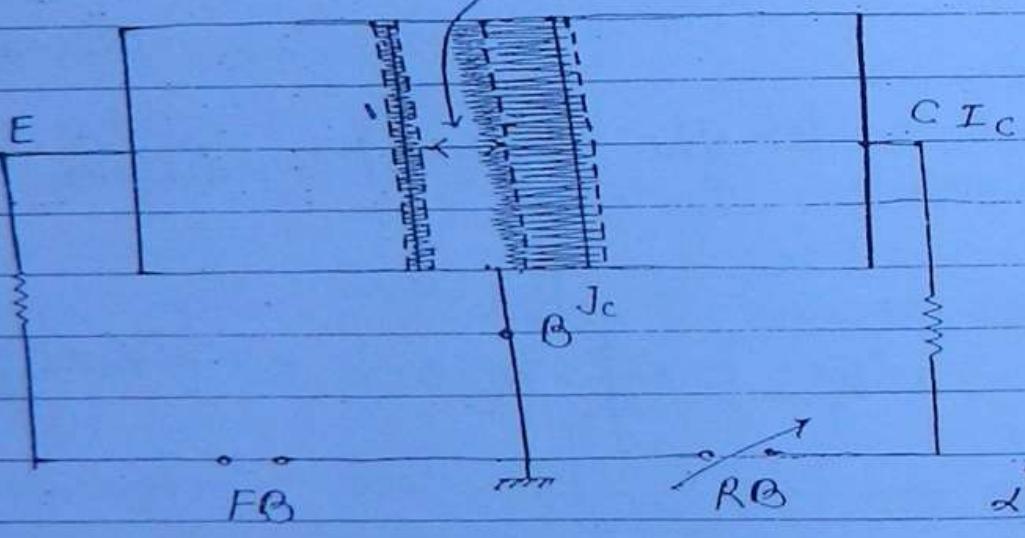
Base Width Modulation :-

(small change
or small variation)

Also Called "EARLY Effect"

- * The process where the effective base width of the transistor is altered by changing the collector junction is called base width modulation.

Effective base width of a Tr



- * In a Tr by increasing Collector junction Voltage, base width of the Tr is reduce and this property is called early effect.

$$\beta^2 = \frac{I_C}{I_E}$$

- * If Collector to base junction (C-B J_n) is more R_B the base width of the Tr reduce.

* Base Narrowing = early effect

* Due to the early effect.

i) The chances of recombination in the base is reduced so that more charge carriers will be reaching the collector and therefore I_c increases.

ii) α_{io} slightly increases (0.9 to 0.99)

iii) β increases by larger value.

iv) Transit time is reduced.

* The effective base width of the Tr will offer a res. rbb called base spread loss to the flow of signal current at high freq. and this res. will reduce the performance of device.

* At low freq. the effect of rbb is neglected.

* The process where the effective base width of the Tr is reduced to 0 by applying larger collector junction voltage is called punch through or Rees through.

Breakdown Voltage of Tr :-
 $(V_{Br}) \propto (Br)$

$$V_{Br} \propto \frac{1}{\text{doping}}$$

In a Tr collector junction breakdown voltage is always greater than emitter junction breakdown voltage.

$$BV_{C-B} > BV_{E-B}$$

In a Tr emitter junction breakdown is due to Zener effect and collector junction breakdown is due to avalanche effect.

Problems:-

Q. A Tr has $\alpha = 0.98$ $\beta = ?$

$$\beta = \frac{\alpha}{1-\alpha}$$

$$= \frac{0.98}{1-0.98}$$

$$[\beta = 49]$$

Q. If Tr has $\alpha = 0.99$ $\beta = ?$

$$\beta = \frac{\alpha}{1-\alpha} = \frac{0.99}{1-0.99} = 99$$

U [$\alpha = 0.98$ to 0.99 small variation
 $\beta = 49$ to 99 large variation]

Q. A Tr having $\beta = 49$

$$I_B = 5mA$$

$$\begin{aligned} I_E &= (1 + \beta) I_B \\ &= (1 + 49) 5 \times 10^{-3} \\ &= 250mA \\ &\boxed{I_E = 0.25mA} \end{aligned}$$

Q. A Tr has $\beta = 59$.

$$I_B = 10mA$$

$$I_{CO} = 10mA$$

$$I_C = ?$$

$$\begin{aligned} I_C &= \beta I_B + (1 + \beta) I_{CO} \\ &= 59 \times 10 \times 10^{-3} + (1 + 59) 10 \times 10^{-3} \end{aligned}$$

$$\boxed{I_C = 590mA}$$

Q. A Tr has $I_O = -10mA$

$$I_C = 9.95mA$$

find I_B , α , β

$$I_E = I_C + I_B \quad \text{in magnitude}$$

$$\begin{aligned} I_B &= I_E - I_C \\ &= 10mA - 9.95mA \\ &= 0.05mA \\ &\boxed{I_B = 50mA} \end{aligned}$$

$$\begin{aligned} \beta &= \frac{I_C}{I_B} \\ &= \frac{9.95mA}{0.05mA} \end{aligned}$$

$$\boxed{\beta = 199}$$

$$\alpha = \frac{\beta}{\beta + 1} = \frac{199}{200} = 0.995$$

Ans.

Q. 9 Tr has a leakage current of 5mA when emitter is OC. If base is OC the leakage current are 20mA find α & β of the Tr.

Sol. $I_{CBO} = 5\text{mA}$,

$$I_{CEO} = 20\text{mA}$$

$$I_{CEO} = (1+\beta) I_{CBO}$$

$$1+\beta = \frac{I_{CEO}}{I_{CBO}} = 40$$

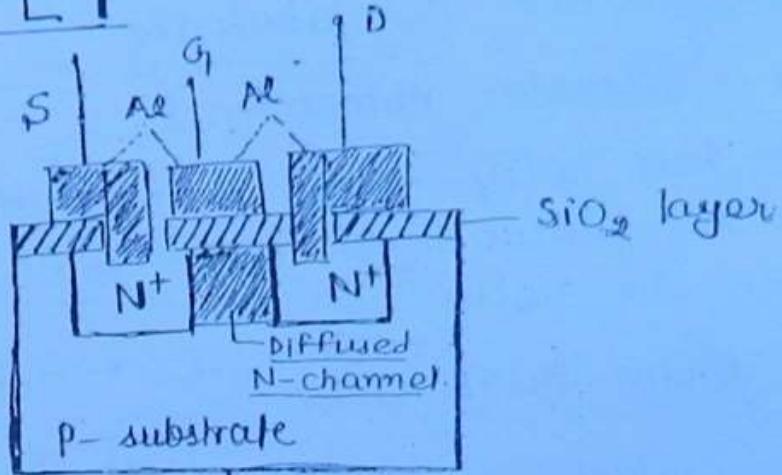
$$\boxed{\beta = 39} \quad \text{Ans.}$$

$$\alpha = \frac{\beta}{\beta + 1}$$

$$= \frac{39}{40}$$

$$\boxed{\alpha = 0.975} \quad \text{Ans.}$$

MOSFET



N-channel MOSFET. (Depletion)

- An integrated circuit or semiconductor chip
- Fabricated by VLSI by using planar technology.
- The thickness of Si wafer is $0.5\ \mu\text{m}$.
- For N-channel MOSFET substrate is p-type
- For P-channel MOSFET substrate is N-type
- The thickness of SiO_2 is 1000 \AA to 2000 \AA .
- The large input resistance of MOSFET is due to SiO_2 layer.
- Voltage control device
- Symmetrical device
- A capacitance (parallel) is formed at the gate section with Al plate and SC channel as the two plate of capacitor and SiO_2 as the dielectric material
- MOSFET is a capacitor
- MOSFET is voltage control capacitor (VCC)
- Channel is also called inversion layer
- Envelope area of MOSFET is less than 5% of area required for BJT.

when compared to JFET MOSFET is smaller in size and easier to fabricate
JFET is a discrete component.

MOSFET is less noisy than compared to JFET it is due to grounding the substrate so that it will filter the noise.

MOSFET is faster than JFET

MOSFET are widely used as switches in digital circuits.

MOSFET is very sensitive static electrical noise and static electrical disturbance.

In the Depletion MOSFET there will be a preexisting channel

In the Depletion mosfet the channel is diffused channel

In BJT is a discrete component

In BJT there will be a minority carrier storage time

In MOSFET minority carrier storage time is zero (due to absence of minority carrier).

In MOSFET turn-off time is very small typ value 75ns

When compared to BJT MOSFET is relatively more suitable for high frequency application and thus it due to absence of minority carrier storage time.

BJT is faster than MOSFET

Depletion Mode :-

max $I_D \rightarrow I_{DSS}$

$$\Rightarrow \boxed{I_D \leq I_{DSS}}$$

Enhancement mode :-

min $I_D \rightarrow I_{DSS}$

$$\Rightarrow \boxed{I_D \geq I_{DSS}}$$

- JFET is always operated under depletion mode.
- N-channel depletion mosfet is sometimes called dual mosfet becoz it is suitable to operate both in the depletion mode and enhancement mode.
- P-channel depletion mosfet is more popular for enhancement operation.
- N-mos is faster than p-mos (becoz $\mu_n > \mu_p$)
- Pmos is easier to fabricate.
- Pmos is bulky.
- Nmos suffer from ion contamination problem during the fabrication.
- To get equal performance between nmos and pmos pmos require twice the area require for n-mos.
- The main advantage of nmos is higher package density (it can store more information in the smaller area).

ICmos

- CMOS consist of PMOS and NMOS.
- Input resistance $R_i = 10^{15} \Omega$.
- It will not consume any power or power dissipation is zero.
- Major application as a inverter (NOT gate).
- In the CMOS inverter, whatever the input signal apply one transistor is ON and other is OFF.



VMOS

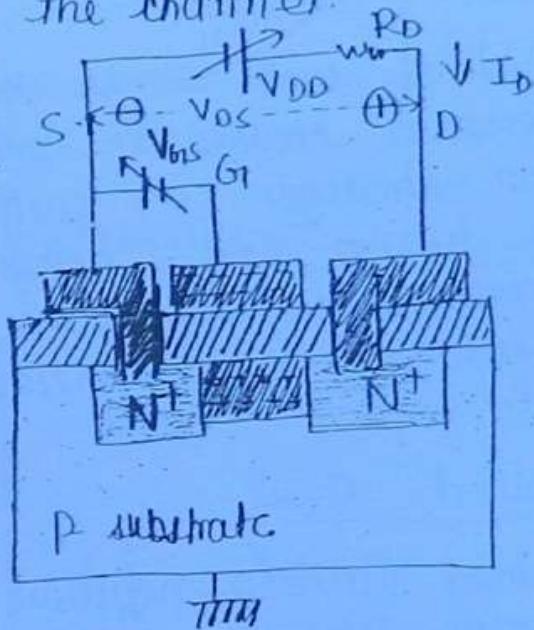
- Vertically grooved MOSFET
- It is a asymmetrical MOSFET
- Voltage controlled Device.
- VMOS is a power MOSFET (it can handle large amount of power when compare to normal MOSFET)
- V_{DS} is faster than normal MOSFET
- Response time is very small (Typ value 75 ns)

(only for conventional MOSFET)

Operation of N-channel Depletion MOSFET

in Depletion mode

→ The principle of depletion mode the applied gate to source voltage must reduce the majority carrier of the channel.



Operation of N-channel depletion mode

→ if $V_{GS} = 0$

∴ $\Rightarrow \max I_D \rightarrow I_{DSS}$

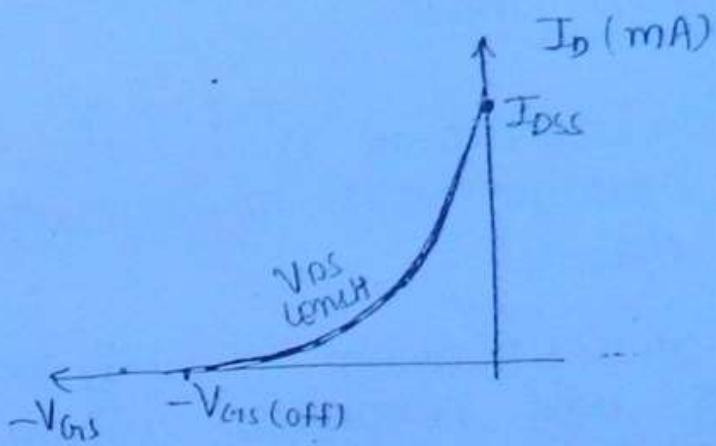
if V_{GS} is applied

-2V	$I_D \downarrow$
-4V	$I_D \downarrow$
-6V	$I_D \downarrow$
+8V	$I_D = 0$

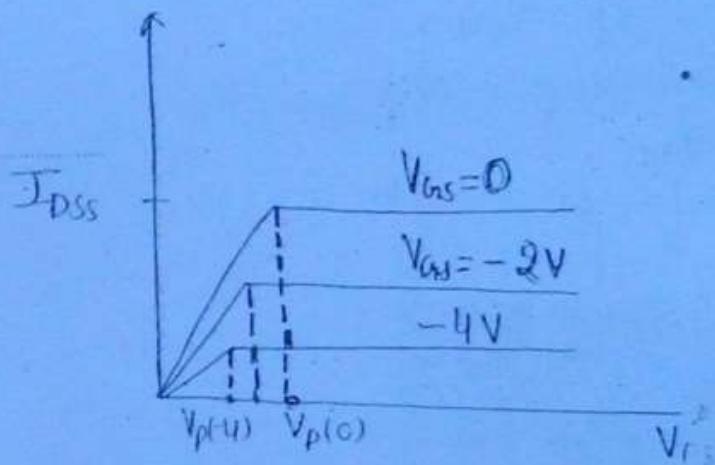
→ For N-channel MOSFET drain is positively biased with respect to source and to operate under depletion mode the gate is very biased w.r.t. source

- In n-channel depletion mosFET :-
- ① channel potential increases from S to D.
 - ② Inversion charge increases from S to D.
- If V_{GS} is kept '0' ($V_{GS}=0$) :-
- The gate is provided with zero voltage and therefore the inversion charge is zero and the maximum negative charges (e^-) will be moving from source to drain and therefore the drain current is maximum and is given by I_{DSs} (Drain to source safe current or saturation current)
- When V_{GS} is applied
- The gate is provided with a negative voltage and therefore the charges are created in the channel and due to the recombination less negative charges will be reaching the drain and drain current is reduced
- To further decrease As gate is given with more negative voltage.
- When gate is given sufficiently more negative voltage, a large no of +ve charges will be created in the channel and this will result a total recombination. So that no negative charges will be reaching the drain and I_D reduces to zero ($I_D=0$) Now channel is cut-off.
- { The transfer and drain characteristic for N-channel Depletion mosFET under depletion mode }

Transfer characteristic \rightarrow



Drain characteristic



\rightarrow The equation for drain current in depletion mode is

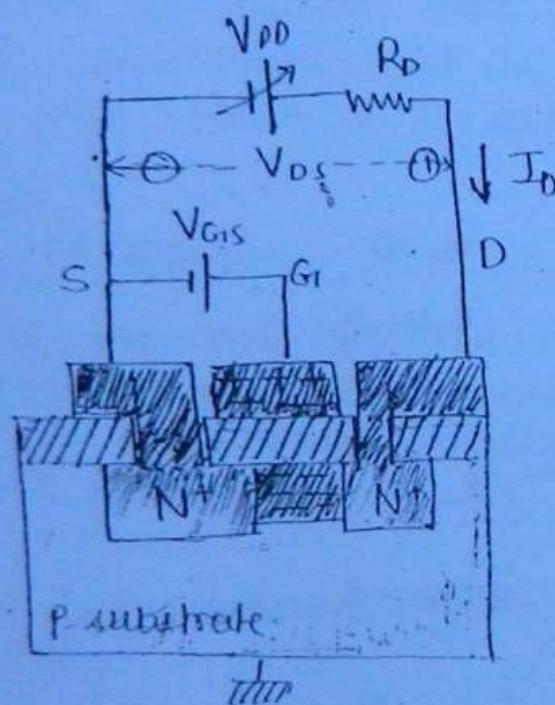
$$I_D = I_{DSS} \left[1 - \frac{V_{GS}}{V_P} \right]^2 \text{ Amp}$$

\rightarrow The polarity of V_{GS} and V_P are same.

\rightarrow The above equation indicate In a depletion mosFET under depletion mode, the drain current decreases in a parabolic variation with V_{GS} .

Operation of N-channel depletion MOSFET under enhancement mode.

- The principle of enhancement mode is the applied gate to source voltage must increase the majority carriers of the channel.
- For N-channel MOSFET drain is fully biased w.r.t the source and to operate under enhancement mode. gate is fully biased w.r.t source.



→ When $V_{GDS} = 0$ →

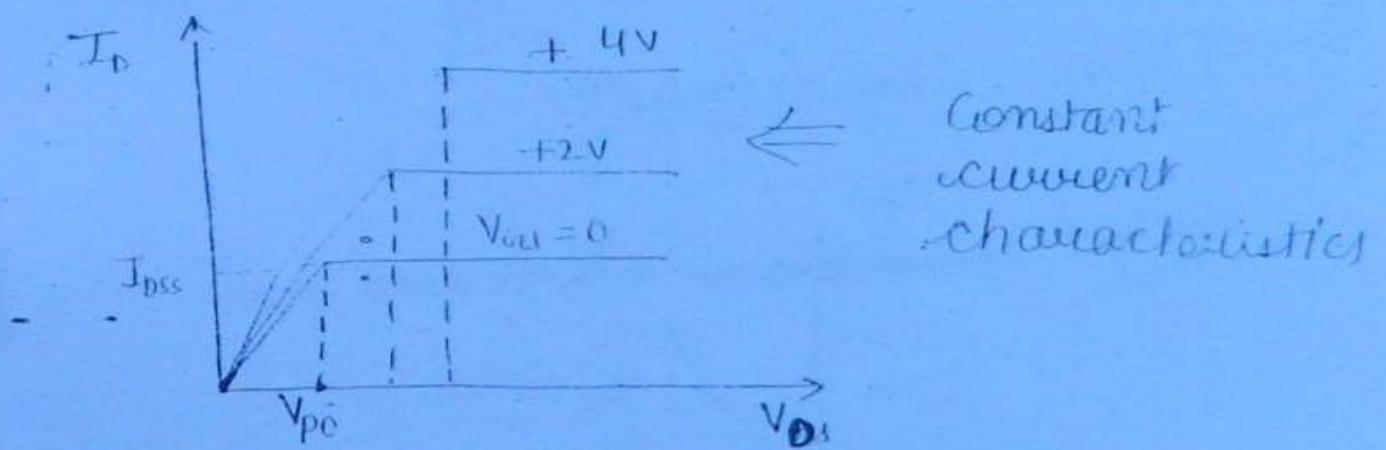
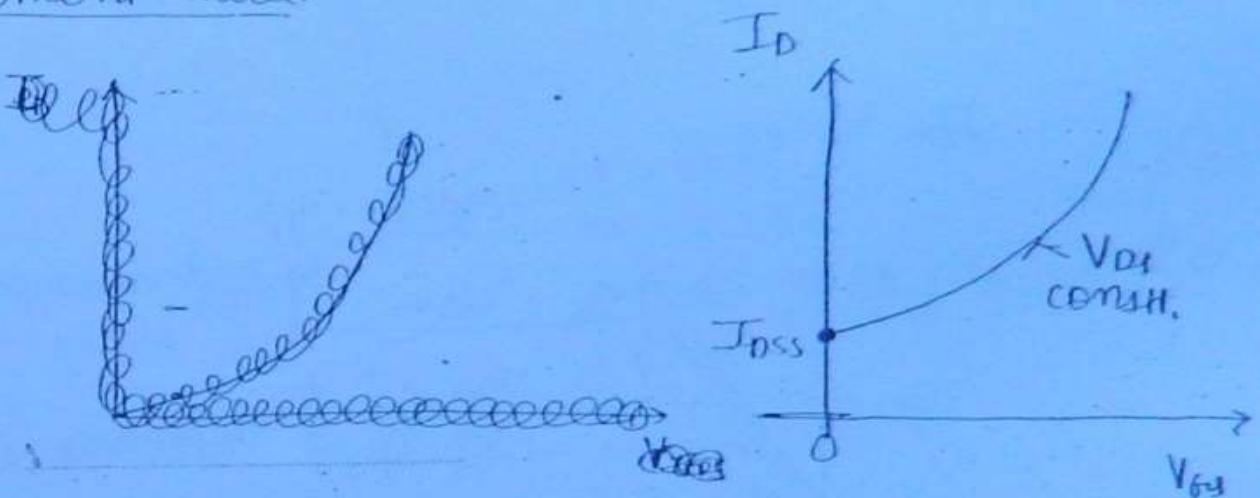
The gate voltage is zero and therefore inversion charge is zero and therefore minimum no. of -ve charges will be moving from source to drain & drain current is minimum and is denoted by I_{DS0} (drain to source safe current).

→ When V_{GDS} is applied.

The gate is provided with a +ve voltage and therefore -ve charges are created in the channel and this will increase no. of -ve charges to drain & I_D increases if it is greater than I_{DS0} .

I_D further increases if gate is given small +ve voltage

Transfer characteristics & drain characteristics for N-channel depletion MOSFET under enhancement mode.



Constant current characteristics

- V_{PO} is the minimum pinch-off voltage
- MOSFET is now working under pinch-off mode.
- Under pinch-off condⁿ : →

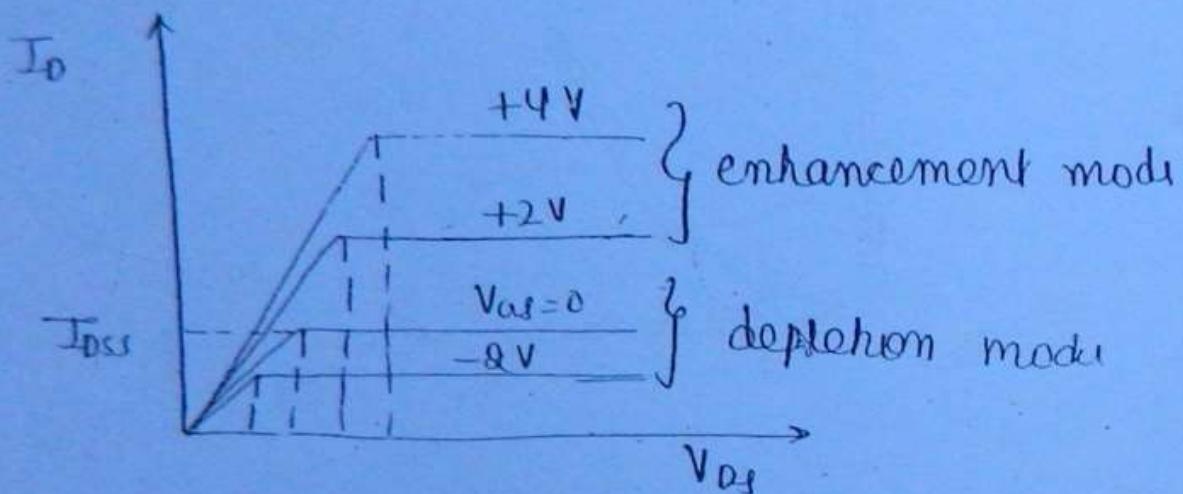
$$\Rightarrow \left[\min V_{DS} = V_{GS} + V_p \right]$$

$$I_D = I_{DSS} \left[1 - \frac{V_{GS}}{V_p} \right]^2$$

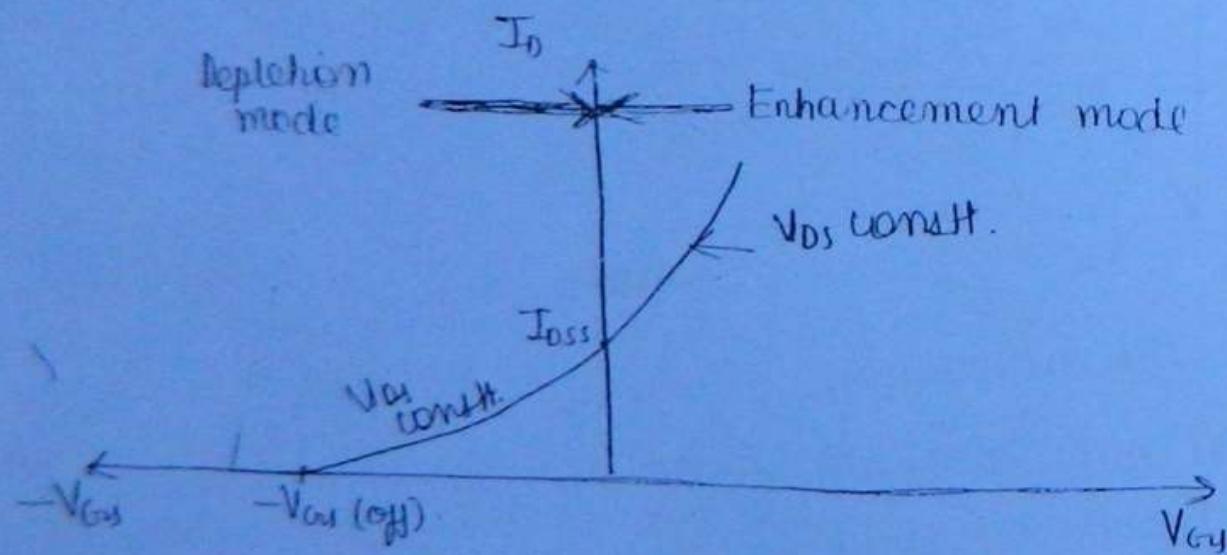
V_{GS} & V_p must have opposite sign.

→ The eqn for I_D indicates that I_D increases as a parabolic variation with V_{GS} .

Characteristics curve for N-channel depletion MOSFET.

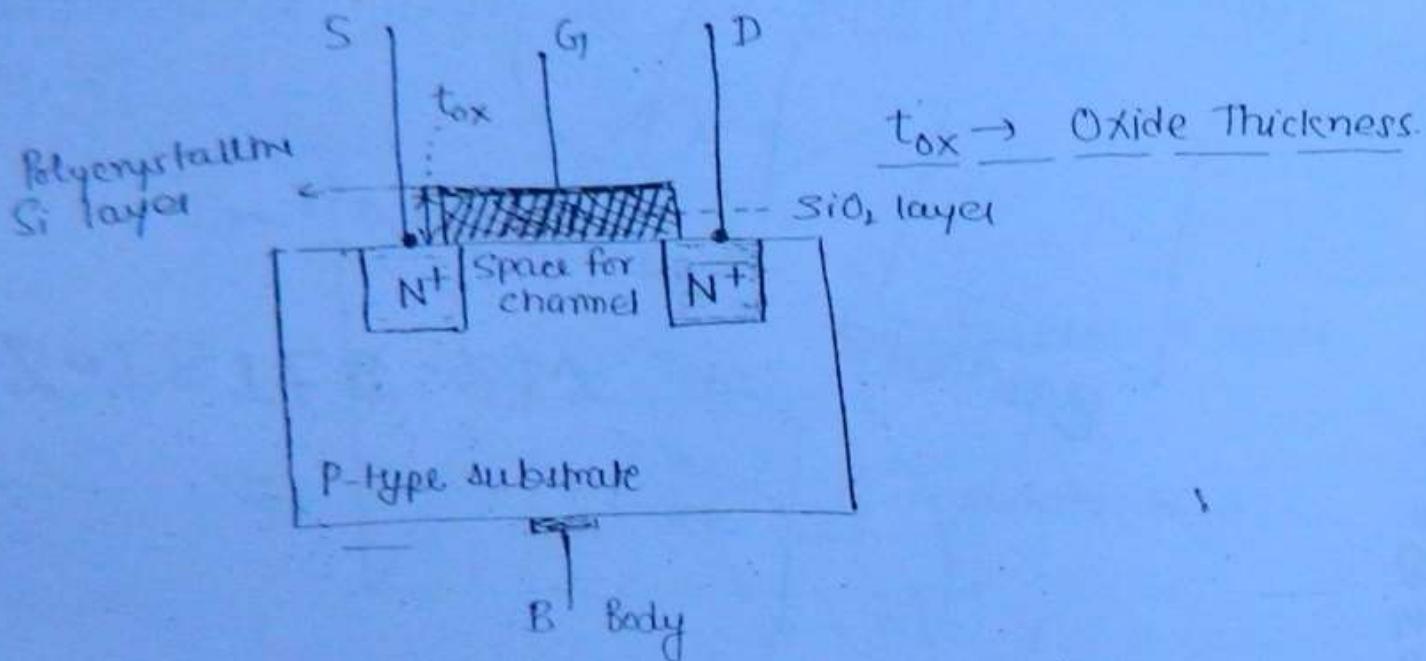


Drain Characteristics



- In the depletion MOSFET channel is diffused channel
- In de MOSFET if V_{GS} is kept zero then $I_D = I_{DSS}$.

Enhancement MosFET → or E-only MOSFET

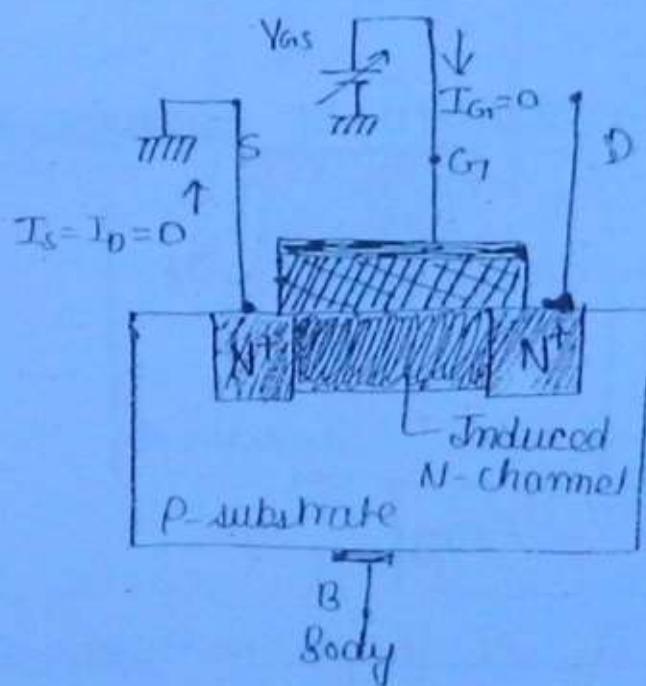


- E-only mosFET is a modern mosFET in which the Al plate are replaced with polycrystalline Si material.
- E-only mosFET is smaller in size, economical and also provide better performance then Depletion mosFET
- In E-only mosFET the source and drain will be kept apart so that there is no channel existing in between source and drain regions
- In E-only mosFET there is no preexisting channel and the channel has to be created by applying proper gate to source voltage

When proper gate to source voltage is applied and then body is grounded the gate to source voltage is also appearing between gate and body of MOSFET. Due to electric field intensity produced channel is induced in between the two N⁺ region

In the E-only MOSFET the channel is induced channel.

The channel is a flat channel of length 'L' as given below :-



Since drain terminal is kept floating, no current will be passing through the channel i.e. $I_D = 0$

A parallel plate capacitor is created at the gate region with polycrystalline silicon plate and induced N-channel as the two plates of capacitor and SiO₂ as the dielectric.

The MOSFET now working as a capacitor.

for mos capacitor \rightarrow

The oxide capacitance per unit cross sectional Area is (C_{ox})

$$\Rightarrow C_{ox} = \frac{\epsilon_{ox}}{t_{ox}} F/m^2$$

ϵ_{ox} = permittivity in F/m .

$$\epsilon_{ox} = \epsilon_0 \epsilon_r (\text{SiO}_2)$$

ϵ_0 = Absolute permittivity of ~~paramagnetic~~ free space

$$\epsilon_0 = 8.854 \times 10^{-12}$$

ϵ_r = Relative permittivity of SiO_2 .

$$\epsilon_r = 3.9$$

$$\epsilon_0 \epsilon_r = 8.854 \times 3.9 \times 10^{-12}$$

$$\boxed{\epsilon_0 \epsilon_r = 3.45 \times 10^{-11} F/m}$$

$$\Rightarrow C_{ox} = \frac{3.45 \times 10^{-11}}{t_{ox}} F/m^2$$

gate capacitance (C_{gate})

$$\Rightarrow C_{gate} = C_{ox} \cdot w \cdot l \quad \text{Farad.}$$

$\Rightarrow [w > L]$ in width of gate plate or channel length of gate plate or channel
in MOSFET.

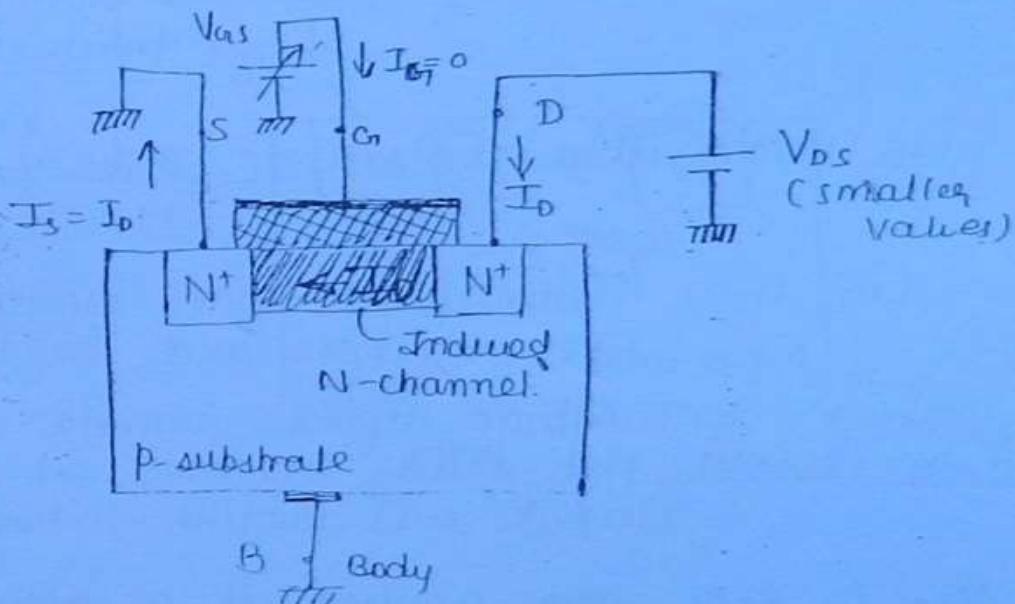
$$W > L$$

OR

$$\frac{W}{L} > 1 \Rightarrow \text{Aspect Ratio.}$$

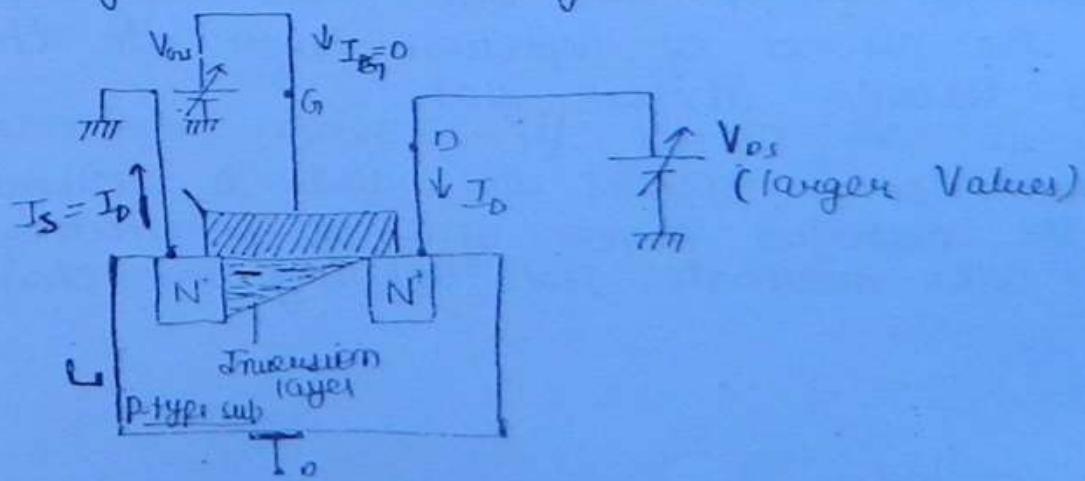
→ Length of the gate plate is equal to the length of the channel.

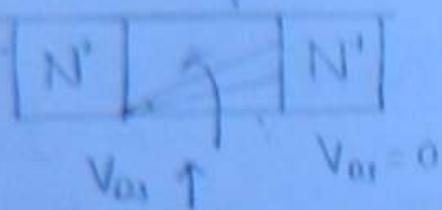
→ The drain current can pass through the MOSFET only when V_{DS} is applied.



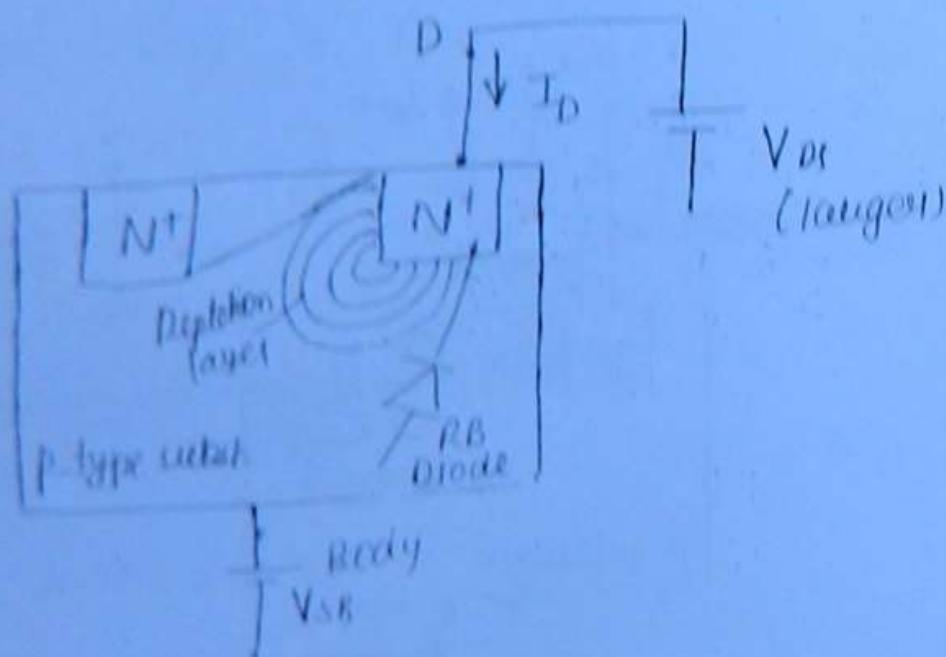
→ When smaller values of V_{DS} is applied the channel will remain almost flat as given in the above and drain current will pass into the channel.

→ When larger values of V_{DS} is applied, the channel gets tapered as given in the diagram below.





- when V_{DS} is kept zero the channel remains flat
- when V_{DS} is applied the increasing the channel got happened.



- when V_{DS} is kept zero applied it is appearing between drain and source and also between drain and body of the MOSFET.
The drain and body of mosfet as a reverse biased diode.
- when V_{DS} is kept zero the diode is unbiased and in the absence of depletion layer the channel will remain almost flat
- when V_{DS} is applied the diode is reverse biased to the depletion layer will be penetrating more into the substrate and happens the channel

When largest V_{DS} is applied there is a discontinuity in the channel and the channel will be broken but due to the largest $E-F$ intensity the drain current will remain almost constant.

The discontinuity of the channel can be avoided by connecting substrate voltage V_{SB} or body voltage when V_{DS} is increasing the channel length decreases and this process where the length of the channel can be altered by varying V_{DS} is called channel length modulation.

* Channel length modulation will occur only in E-only MOSFET.

The channel length modulation will not exist in depletion MOSFET and JFET.

* Due to channel length modulation E-only MOSFET cannot be operated with self biased arrangement or potential divider bias circuit.

In N-channel enhancement MOSFET:-

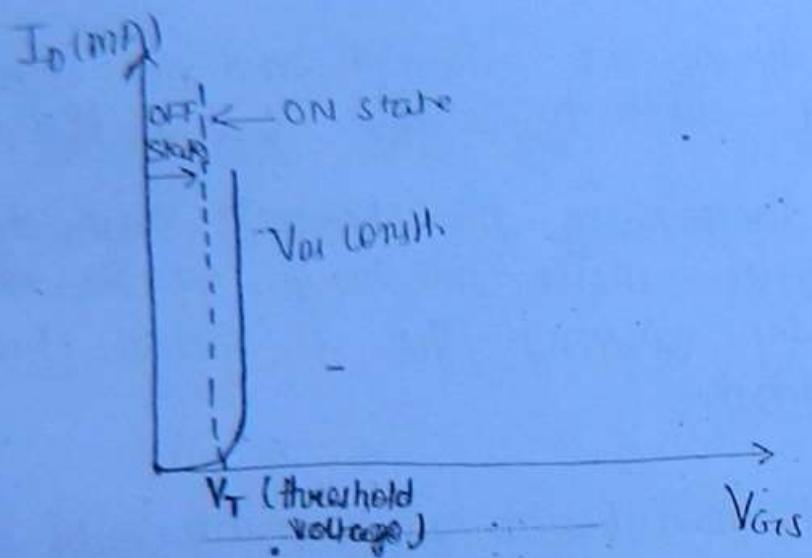
(1) channel potential increases from source to drain
(2) inversion charge decreases from source to drain

In enhancement MOSFET when V_{GS} is kept zero and V_{DS} is existing then channel will disappear
 $\therefore I_D = 0$

In enhancement MOSFET if $V_{GS} = 0$ then $I_D = 0$.



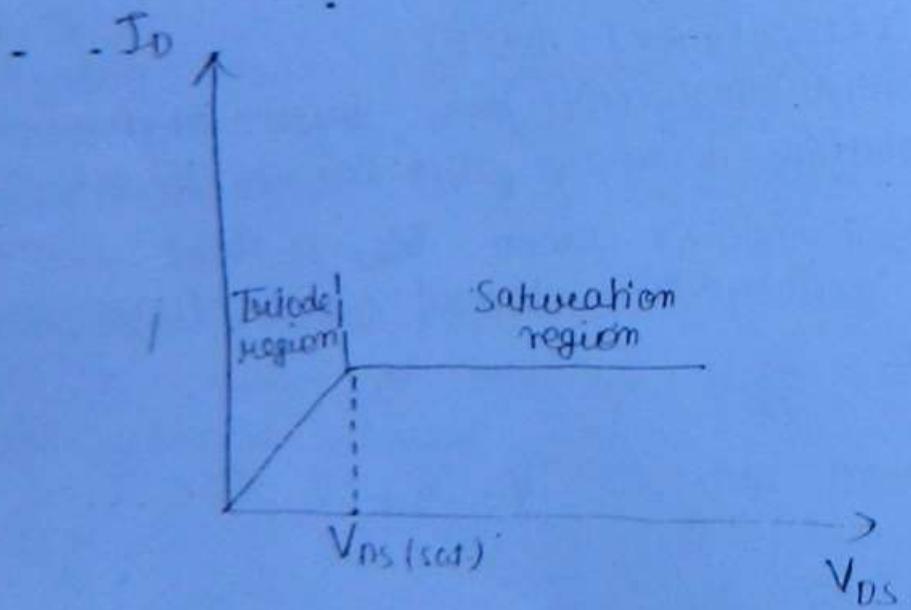
Transfer characteristics for n-channel E-only MOSFET



if $V_{GS} \leq V_T$, MOSFET is OFF state

if $V_{GS} \geq V_T$, MOSFET is ON i.e. SC

Drain characteristics of N-channel E-only MOSFET



$$\Rightarrow V_{DS(sat)} = (V_{GS} - V_T) :$$

Tetode Region

Also called ohmic region or linear region or non-saturation region.

$$\therefore \nexists \left\{ \begin{array}{l} V_{DS} < V_{DS(sat)} \\ \text{or} \\ V_{DS} < (V_{GS} - V_T) \end{array} \right\}$$

Saturation Region (Pentode Region) :- or pinch-off region

$$\nexists \left\{ \begin{array}{l} V_{DS} \geq V_{DS(sat)} \\ \text{or} \\ V_{DS} \geq (V_{GS} - V_T) \end{array} \right\} :$$

Equation for drain current in the saturation region of E-only MOSFET.

$$I_D = I_{DSS} \left[1 - \frac{V_{GS}}{V_T} \right]^2 \text{Amp}$$

$$\left[\because V_{GS} \gg V_T \right]$$

→ The above equation indicates in the F-only most I_D increases as a parabolic variation with V_{DS} .

Comparison between Depletion mosFET & E-only mosf.

Depletion mosfet

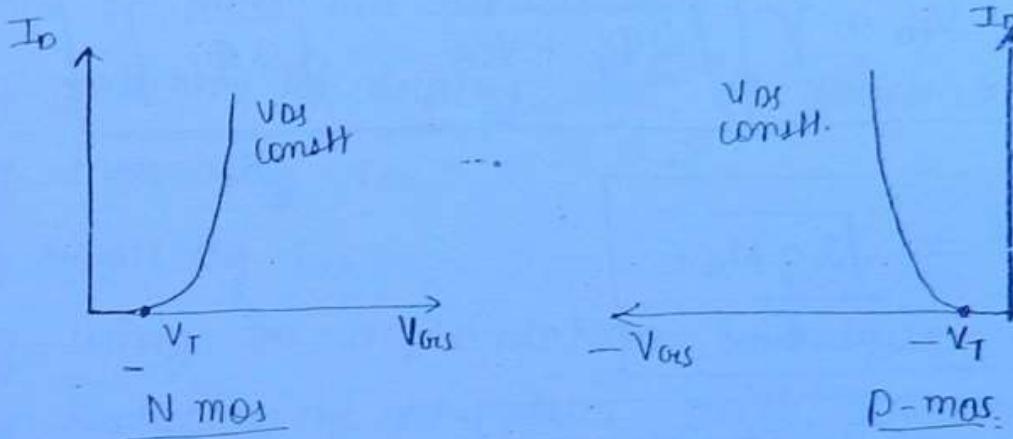
- ① Existing channel is available.
- ② Diffused channel
- ③ Suitable to operate in Depletion and enhancement mode.
- ④ When $V_{GS} = 0$, $I_D = I_{DSS}$
- ⑤ No channel length modulation
- ⑥ Continuous channel
- ⑦ comparatively larger in size and expensive due to provision of Al plate.
- ⑧ Can be designed in self biased arrangement

Enhancement mos

- ① No preexisting channel and channel has to be created by applying proper V_{GS} .
- ② Induced channel.
- ③ Suitable only for enhancement mode
- ④ When $V_{GS} = 0$, $I_D = 0$.
- ⑤ Channel length modulation exists
- ⑥ Channel is discontinuous.
- ⑦ comparatively smaller in size, economical and better performance due to replacement of Al plates by polycrystalline Si material
- ⑧ Cannot be designed in self biased arrangement

THRESHOLD VOLTAGE (V_T or V_t or V_{th}) :-

→ It is also called gate to source threshold voltage denoted by V_{GSt} .



- Threshold voltage is defined as the minimum V_{GSt} where the mosfet enters into ON state.
- For N-mos threshold voltage is +ve.
- For pmos V_{th} is -ve.
- $V_T \rightarrow 0.5V$ to $3V$ [typ value $1V$]
- For better performance of mosfet V_T must be smaller
- V_T can be graphically obtained from the transfer characteristics of mosfet.
- V_{th} will appear only in E-only mosfet.
- Advantages of V_{th} smaller :-
 - ① It enables the device to operate with smaller supply voltage
 - ② It increases the compatibility of device
 - ③ Reduces switching time of device so that mosfet becomes faster in operation

Equation for V_{th} :-

N channel enhancement mosfet V_{th} is given by :-

$$\Rightarrow V_{th} = V_{to} + \gamma \left[\sqrt{2\varphi_f + V_{SB}} - \sqrt{2\varphi_f} \right]$$

$$\Rightarrow \gamma = \frac{\sqrt{2qN_A\epsilon}}{C_{ox}}$$

$$\Rightarrow \gamma = \frac{t_{ox}\sqrt{2qN_A\epsilon}}{3.45 \times 10^{-11}}$$

- γ is called fabrication process parameter
- φ_f physical parameter or fermi voltage
- V_{SB} substrate voltage or body voltage
- N_A acceptor concⁿ or doping concⁿ of p-type sub in N channel mosf.
- V_{to} is threshold voltage of mosf when substrate voltage is kept zero ($V_{SB}=0$)
- V_{th} of mosf can be increased by increasing V_{SB} .
- Suppose if there is a small variation in substrate voltage, this will cause small variation in V_t , in this result a small variation in I_D . It follows that V_{SB} controls the gate current. Hence body will be acting as the 2nd gate in the mosfet. This property is called Body effect.

Procedure to Reduce V_f :-

- The V_{th} of mosfet can be reduced by using anyone of the following methods (it should be done only at time of fabricating the device)
 - By reducing the doping conc' of substrate material.
 - By increasing C_{ox}
 - By reducing t_{ox} .
 - By using ion implantation technique.
 - By replacing the Al. plates with polycrystalline Si material (Al is a metal with larger contact potential while polycrystalline Si is oxide material with very low contact potential becoz of smaller contact potential the V_{th} of mosfet can be reduced)
 - Polycrystalline Si is also called poly Si.
 - Alternative material for polycrystalline Si material is Si Nitride.
 - In modern most gate material polycrystalline Si

APPARAT

Equations For Nmos Transistor :-

(1) Over drive voltage :- V_{ov} .

$$\Rightarrow \boxed{V_{ov} = V_{DS(sat)} \\ \text{or} \\ V_{ov} = (V_{GS} - V_T)}$$

(2) Operation in Triode Region :-

Condition :- $\boxed{V_{DS} < V_{DS(sat)}} \\ \Rightarrow \boxed{V_{DS} < (V_{GS} - V_T)}$

$$i_d = \mu_n C_{ox} \frac{W}{L} \left\{ (V_{GS} - V_T) V_{ds} - \frac{V_{ds}^2}{2} \right\}$$

Triode region occurs for smaller value of V_{ds}
 \therefore neglecting $V_{ds}^2/2$

$$i_d = \mu_n C_{ox} \frac{W}{L} \left\{ (V_{GS} - V_T) V_{ds} \right\}$$

$$\Rightarrow \boxed{i_d = \mu_n C_{ox} \frac{W}{L} [(V_{GS} - V_T) V_{ds}]}$$

Let $\mu_n C_{ox} = K_n \rightarrow$ process Transconductance parameter

$$\Rightarrow \boxed{i_d = K_n \frac{W}{L} [(V_{GS} - V_T) V_{ds}]} \quad \text{in } A/V^2$$

$$\Rightarrow k_n \frac{w}{L} = k'_n \rightarrow \text{constant in } A/V^2$$

$$\Rightarrow \boxed{i_d = k'_n [(V_{gs} - V_T) V_{ds}]}$$

The equation is a 1st order equation and the curve represent a linear variation.

Drain to source resistance given by

$$\Rightarrow \boxed{R_{ds} = \frac{V_{ds}}{i_d}}$$

$$\Rightarrow \boxed{R_{ds} = \frac{1}{k'_n [V_{gs} - V_T]}} \Omega$$

$$\Rightarrow \boxed{R_{ds} = \frac{1}{\mu_n C_o x \frac{w}{L} [(V_{gs} - V_T)]}} \Omega$$

This indicates that in the ohmic region or triode region FET will be working as voltage controllable resistor by varying V_{ds} .

In the triode region, the transconductance of FET

$$g_m = \frac{\partial i_d}{\partial V_{gs}} \Big|_{V_{ds}}$$

$$i_d = k'_m [V_{gs} - V_T] V_{ds}$$

$$\frac{\partial i_d}{\partial V_{gs}} = k'_m V_{ds}$$

$$\Rightarrow \boxed{g_m = k'_m V_{ds}} \quad 25$$

$$\Rightarrow \boxed{g_m = \mu_n C_{ox} \frac{w}{L} V_{ds}} \quad 25$$

(iii) Operation In Saturation region :-

cond'n

$$\Rightarrow \boxed{\begin{aligned} V_{DS} &\geq V_{DS(\text{sat.})} \\ V_{DS} &\geq (V_{GS} - V_T) \end{aligned}}$$

$$i_d = \frac{1}{2} \mu_n C_{ox} \frac{w}{L} (V_{gs} - V_T)^2$$

$$i_d = \frac{1}{2} k_m \frac{w}{L} (V_{gs} - V_T)^2$$

$$\Rightarrow \boxed{i_d = K (V_{gs} - V_T)^2}$$

Let $\frac{1}{2} k_m \frac{w}{L} = K$

A/V^2

IInd order equation and this indicates that it increases as a parabolic variation with V_{ds} .

→ The transconductance in saturation region

$$g_m = \frac{\partial i_d}{\partial V_{Gs}} \Big|_{V_{ds}}$$

$$i_d = K_s (V_{gs} - V_T)^2$$

$$\frac{\partial i_d}{\partial V_{Gs}} = 2K [V_{gs} - V_T]$$

$$\Rightarrow \boxed{g_m = 2K [V_{gs} - V_T]} \quad \text{Ans}$$

$$\rightarrow \boxed{g_m = \mu_n C_{ox} \frac{w}{L} [V_{gs} - V_T]} \quad \text{Ans}$$

$$I_{ds} = \frac{1}{k_p} [V_{gs} - V_T]$$

$$\Rightarrow I_m = k_p V_{ds}$$

(iii) Operation In Saturation Region \Rightarrow

cond^b $\left\{ \begin{array}{l} V_{DS} \leq V_{DS}(\text{sat}) \\ V_{DS} \leq (V_{GS} - V_T) \end{array} \right\}$

$$i_d = \frac{1}{2} \mu_p C_{ox} \frac{\omega}{L} \{ V_{gs} - V_T \}^2$$

$$= \frac{1}{2} k_p \frac{\omega}{L} (V_{gs} - V_T)^2$$

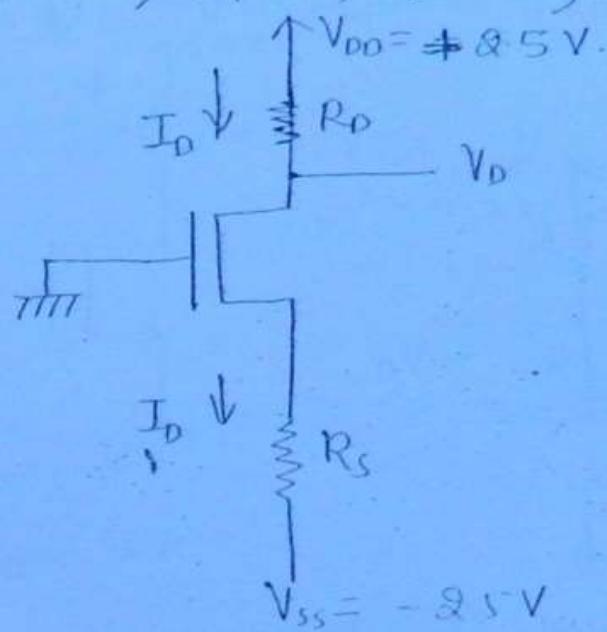
$$\frac{1}{2} k_p \frac{\omega}{L} = K \Rightarrow \text{constt. in } A/V^2$$

$$\Rightarrow i_d = K (V_{gs} - V_T)^2$$

$$\Rightarrow g_m = 2K [V_{gs} - V_T]$$

Prob

Design the circuit shown below so that
 Tr. operate at $I_d = 0.4 \text{ mA}$ and $V_{dd} = 0.5 \text{ V}$
 the nmos transistor has $V_t = 0.7 \text{ V}$
 $\mu n C_{ox} = 100 \mu \text{A/V}^2$, $L = 1 \mu\text{m}$, $W = 32 \mu\text{m}$



Ans since gate is grounded $V_g = 0$
 $V_D > V_a$ the mos in sat. Region

$$I_d = \frac{1}{2} \mu n C_{ox} \frac{W}{L} (V_{gs} - V_t)^2$$

$$0.4 \times 10^{-3} = \frac{1}{2} \times 100 \times 10^{-6} \times \frac{32}{1} (V_{gs} - 0.7)^2$$

$$0.4 \times 10^{-3} = 10^{-4} \times 16 (V_{gs} - 0.7)^2$$

$$P_p = \frac{V_{DD} - V_D}{I_D} \quad 4 \times 10^{-4} = \frac{1}{16} \times 10^{-4} (V_{gs} - 0.7)^2$$

$$P_p = \frac{V_{DD} - V_D}{I_D} \quad 2 = 4 (V_{gs} - 0.7)$$

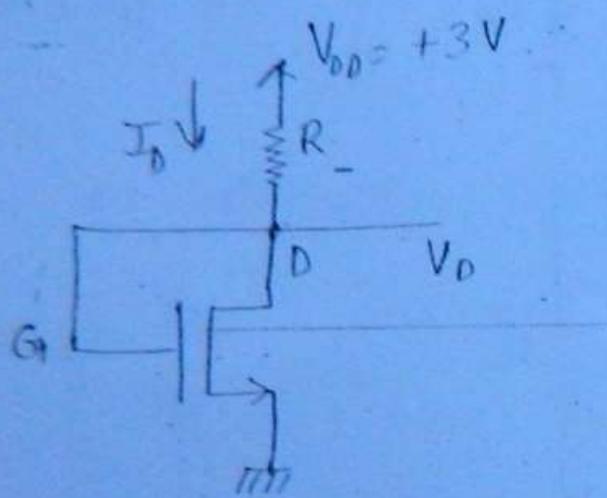
(5 k Ω)

$$2 = 4 V_{gs} - 0.7$$

$$4 V_{gs} = 1.3 \Rightarrow V_{gs} = \frac{1.3}{4} = 0.325$$

$$V_{in} = V_{out} + I_D R_S + V_{ss} = 1.3 + 0.4 \times 10^{-3} (R_S) - 2.5 = 1.2$$

Ques Design the circuit given to obtain a current $I_D = 80 \mu A$ find the value required for R_S . D.C voltage V_D . The mos Tr. has $V_T = 0.6 V$, $\mu n C_{ox} = 800 \mu A/V^2$, $W = 0.8 \mu m$, $L = 4 \mu m$?



Since G & D are SC

$$V_{GS} = V_{DS}$$

It is work on switch.

$$I_D = \frac{1}{2} \mu n C_{ox} \frac{W}{L} (V_{GS} - V_T)^2$$

$$80 \times 10^{-6} = \frac{1}{2} \times 800 \mu A \times \frac{4}{0.8} (V_{GS} - 0.6)^2$$

$$8 = \frac{10 \times 40}{0.128} (V_{GS} - 0.6)^2 \quad \left\{ \begin{array}{l} R = \frac{3 - 1}{80 \times 10^{-6}} \\ R = 25 k\Omega \end{array} \right.$$

$$40 = 25 (V_{GS} - 0.6)^2$$

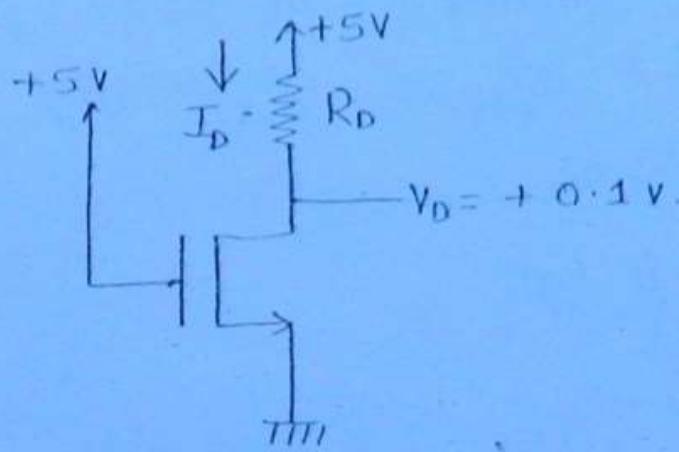
$$2 = 5 (V_{GS} - 0.6)$$

$$2 = 5V_{GS} - 3 \Rightarrow 5V_{GS} = 5$$

$$(V_{GS} = 1 V)$$

Ques Design the circuit given to establish a drain voltage $V_D = 0.1V$ what is the effective resistance between drain & source at this operating point.

$$V_T = 1V, \quad K_m \frac{w}{L} = 1mA/V^2$$



$$V_{GS} = 5V$$

$$V_{DS} = V_D = 0.1V$$

$V_{GS} > V_D$ most μ in Triode

$$I_d = \mu_n C_{ox} \frac{w}{L} \left[(V_{GS} - V_T) \frac{V_{DS}}{2} - \frac{V_{DS}^2}{2} \right]$$

$$I_d = 1m \left[(5 - 1) \frac{V}{2} - \frac{(0.1)^2}{2} \right]$$

$$I_d = 0.395mA$$

$$R_D = \frac{5 - 0.1}{0.395} = (12.4k\Omega)$$

$$R_{ds} = \frac{V_{DS}}{I_d} = \frac{0.1}{0.395 \times 10^{-3}} = (253\Omega)$$

Ans Consider a p-channel enhancement mode mosfet with $k_p = 10 \mu A/V^2$ the device has following observations :-

$$I_D = 0.825 \text{ mA} \quad \text{at} \quad V_{SD1} = V_{SD1} = 3 \text{ V}$$

$$I_{DS} = 1.4 \text{ mA} \quad \text{at} \quad V_{SD2} = V_{SD2} = 4 \text{ V}$$

find V_{TP} & Aspect Ratio.

$V_{SD} \equiv V_{SD}$ most is sat.

$$i_d = K [V_{SD} - V_T]^2$$

$$i_d = K [V_{SD} - |V_{TP}|]^2$$

$$\frac{I_{D1}}{I_{D2}} = \frac{(V_{SD1} - |V_{TP}|)^2}{(V_{SD2} - |V_{TP}|)^2}$$

$$\frac{0.825}{1.4} = \frac{(3 - |V_{TP}|)^2}{(4 - |V_{TP}|)^2}$$

$$|V_{TP}| = 2.33 \text{ V} \Rightarrow (V_{TP} = -2.33 \text{ V})$$

Aspect Ratio

$$I_{D1} = \frac{W}{L} K_P [V_{SD1} - |V_{TP}|]^2$$

$$\frac{W}{L} = 85$$

18

Prob An ideal n-channel MOSFET has the following specification:

$w = 30\ \mu m$, $L = 8\ \mu m$, $\mu_n = 450\ cm^2/Vsec$
 $t_{ox} = 350\ \text{\AA}$, $V_{TN} = 0.8\ V$ if Tr. is operating
in sat. region if $V_{GS} = 4\ V$

defn $g_m = K' V_{ds}$

$$g_m = J_{ln} t_{ox} \frac{w}{L} (V_{GS} - V_T)^{25}$$

$$= \mu_n \left[\frac{3.45 \times 10^{-11}}{350 \times 10^{-10}} \right] \frac{w}{L} (V_{GS} - V_T)$$

$$= 0.045 \left[\frac{3.45 \times 10^{-11}}{350 \times 10^{-10}} \right] \left(\frac{30}{2} \right) [4 - 0.8]$$

$g_m = 2.13\ mS$